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Author and Subject Index
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The Computer-Derived 1974 Journal Index

The Publication Committee of the Society recommended the use of a computer-derived index in 1968, and this practice is planned to be continued. This index is published two months earlier than the usual index and makes possible indexing more information than before. These indices refer only to *Journal* articles, reviews, brief communications, and discussions. They do not include meeting papers and items in the news and reviews section. These indices were prepared for the *Journal* by the Institute for Scientific Information, Philadelphia, Pennsylvania.

Using the Index

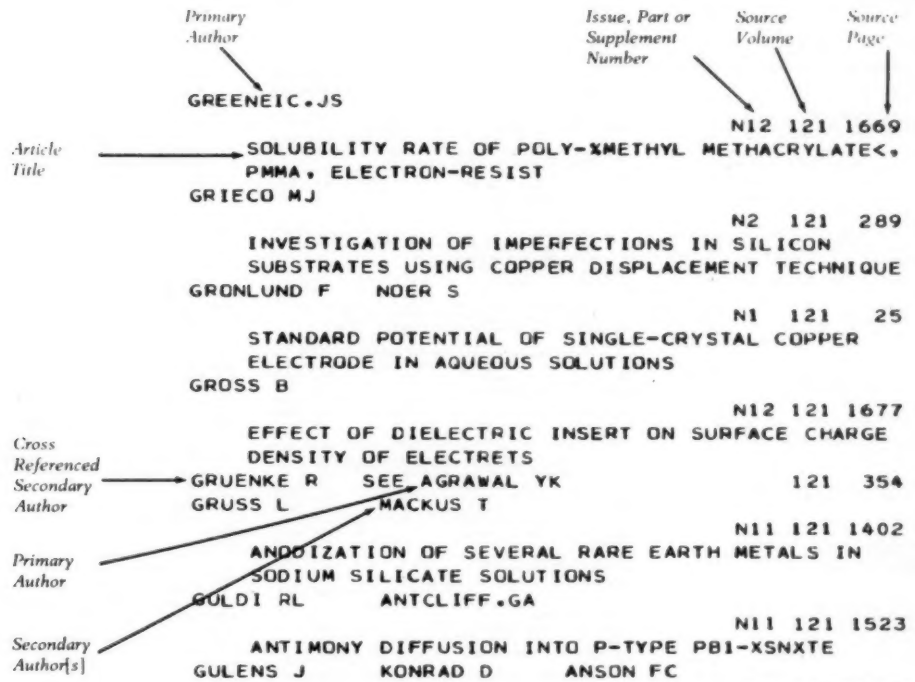
1. Given any author, go directly to his name in the author and title index to find the full paper title with a page citation or, if he is a secondary author, to find a cross-reference to a primary author.
2. Given any topic, go to the subject index and search for the key word itself.
3. For a detailed explanation of symbols and abbreviations, see the sample pages before the individual author and title index and the subject index.
4. Chemical formulae cannot be reproduced directly because the conventional computer printout appears in capital letters only. For example, B13 could be three atoms of bismuth or boron triiodide. To avoid this ambiguity, an attempt has been made to write out chemical formulae.
5. In the author index, an author is always listed with all available initials, which for lack of space sometimes can mean omission of one or two letters from the end of his last name. This truncation is indicated by a period at the end of the last name.

The Publication Committee will appreciate comments on the usefulness and accuracy of this index.

NEWTON SCHWARTZ
Chairman
Publication Committee

JOURNAL ARTICLE AUTHOR AND TITLE INDEX

To locate a full description of a source item, look up the primary author. Under a given name, journal articles of primary authorship are described first. Items of secondary authorship follow. These are cross-referenced to the primary author whose name follows the word SEE.




```
                                                        N12 121 1669
    SOLUBILITY RATE OF POLY-%METHYL METHACRYLATE<,
    PMMA, ELECTRON-RESIST
GRIECO MJ
                                                        N2  121  289
    INVESTIGATION OF IMPERFECTIONS IN SILICON
    SUBSTRATES USING COPPER DISPLACEMENT TECHNIQUE
GRONLUND F    NOER S
                                                        N1  121   25
    STANDARD POTENTIAL OF SINGLE-CRYSTAL COPPER
    ELECTRODE IN AQUEOUS SOLUTIONS
GROSS B
                                                        N12 121 1677
    EFFECT OF DIELECTRIC INSERT ON SURFACE CHARGE
    DENSITY OF ELECTRETS
GRUENKE R     SEE AGRAWAL YK                              121  354
GRUSS L       MACKUS T
                                                        N11 121 1402
    ANODIZATION OF SEVERAL RARE EARTH METALS IN
    SODIUM SILICATE SOLUTIONS
GULDI RL      ANTCLIFF.GA
                                                        N11 121 1523
    ANTIMONY DIFFUSION INTO P-TYPE PB1-XSNXTE
GULENS J      KONRAD D      ANSON FC
                                                        N11 121 1421
    CYCLIC VOLTAMMETRY AND CHRONOCOULCMETRY WITH
    TRANS-RH%EN<2CL2& AT MERCURY ELECTRODES
GUPTA K       MARTON JP     SHEWCHUN J
                                                        N1  121  118
    OXIDATION CHARACTERISTICS OF SOME NICKEL ALLOY
    FILMS IN AIR AND WATER VAPOR
GURLUSKY PJ SEE SIMON AC                                121  463
GUTHRIE JW
                                                        N12 121 1617
    IDENTIFICATION OF AGCL AS A SURFACE
    CONTAMINANT ON HYBRID MICROCIRCUIT CAPACITORS
    USING ION MICROPROBE TECHNIQUES
```

ABE Y SEE IMAI K 121 1674
ABRAHAMS MS SEE OLSEN GH 121 1650
ADAMS AA BARGER MJ
NB 121 987
NEW ELECTROLYTE FOR HYDROCARBON AIR FUEL CELLS
ADAMS AC SEE MELLIARS.CM 121 298
ADAMS JE SEE HAAS WE 121 1667
ADAMS LG SEE UHRACH MB 121 233
ADZIC R YEAGER E CAHAN BD
N4 121 474
OPTICAL AND ELECTROCHEMICAL STUDIES OF UNDERPOTENTIAL DEPOSITION OF LEAD ON GOLD EVAPORATED AND SINGLE-CRYSTAL ELECTRODES
ADZIC R SEE SCHMIDT E 121 1510
AGRAWAL YK SHORT DW GRUENKE R RAPP RA
N3 121 384
CONTROL OF OXYGEN ACTIVITES IN ARGON-OXYGEN MIXTURES BY COULOMETRIC TITRATION
ALBERS W VANHOOF LAH
N10 121 1341
ENHANCED CONVERSION OF X-RAYS INTO VISIBLE LIGHT IN THIN COMPOSITE LAYERS %COMPOSITE ANTHRACENE-PBCL2 SCREENS%
ALESSAND.EI CAMPBELL DR
NB 121 1115
CATALYZED CRYSTALLIZATION IN SIO2 THIN FILMS
ALESSAND.EI SEE CAMPBELL DR 121 1001
ALKIRE R NG PK
N1 121 98
2-DIMENSIONAL CURRENT DISTRIBUTION WITHIN A PACKED-BED ELECTROCHEMICAL FLOW REACTOR
ALKIRE R NICOLAID.G
N2 121 183
DIFFERENTIAL AERATION CORROSION OF A PASSIVATING METAL UNDER A MOIST FILM OF LOCALLY VARIABLE THICKNESS
ALKIRE R VARJIAN R
N5 121 622
RESISTIVE WIRE ELECTRODES
ALLENSWO.R ROGERS JW RIDGE G BARD AJ
N11 121 1412
VOLTAMMETRY OF %E(-)-PHENYL-2-NITRO-1-PROPENE IN N,N-DIMETHYLFORMAMIDE SOLUTIONS
ALWITT RS BERNARD WJ
NB 121 1019
INVESTIGATION OF COMPOSITE ALUMINUM OXIDE FILMS BY RADIOTRACER AND GRAVIMETRIC METHODS
ALWITT RS
N10 121 1322
GROWTH OF HYDROUS OXIDE FILMS ON ALUMINUM
AMBROSE JR KRUGER J
N5 121 599
TRIBO-ELLIPSOMETRIC STUDY OF REPASSIVATION KINETICS OF A TI 8AL-1MO-1V ALLOY
ANDERSEN TN SEE CLARK GJ 121 618
ANDERSON LJ SEE MARUSKA HP 121 1202
ANDERSON RB SEE DOUGIALL.EJ 121 1134
ANDERSON WJ HANSEN WN
N12 121 1570
ELECTRODE SURFACE CONDUCTANCE MEASUREMENTS IN AN ELECTROCHEMICAL CELL
ANGERSTE.H SEE CAPON A 121 780
ANGERSTE.H SEE CONWAY BE 121 1596
ANSON FC SEE GULENS J 121 1421
ANTCLIFF.GA SEE GULDI RL 121 1523
ANTYPAS GA HOON RL
N3 121 416
GROWTH AND CHARACTERIZATION OF GAASSB-GAALASSB LATTICE-MATCHED HETEROJUNCTIONS
APPERT JR SEE ENSTROM RE 121 1516
ARAI E TERUNUMA Y
N5 121 676
WATER ADSORPTION IN CHEMICALLY VAPOR-DEPOSITED BOROSILICATE GLASS FILMS
ARMSTRON.RE TOLLIVER DL
N2 121 307
SCANNING ELECTRON MICROSCOPE INVESTIGATION OF GLASS FLOW IN MOS INTEGRATED CIRCUIT FABRICATION
ASAKURA S LU CC NOBE K
N5 121 608
ELECTRODISSOLUTION KINETICS OF IRON IN CHLORIDE SOLUTIONS .4% ALKALINE SOLUTIONS CONTAINING BENZOTRIAZOLE
ASAKURA S LU CC NOBE K
N10 121 1276
ELECTRODISSOLUTION KINETICS OF IRON IN CHLORIDE SOLUTIONS .5% NEUTRAL SOLUTIONS CONTAINING BENZOTRIAZOLE
AUBORN J SEE FRENCH K 121 1048
AVIGAL Y BEINGLAS.I SCHIEBER M
N5 121 1103
NEW METHOD FOR CHEMICAL VAPOR DEPOSITION OF SILICON DIOXIDE
AYABE M SEE KANEKO K 121 586
BACHMANN KJ BUEHLER E
N6 121 838
PHASE EQUILIBRIA AND VAPOR PRESSURES OF PURE PHOSPHORUS AND INDIUM/PHOSPHORUS SYSTEM AND THEIR IMPLICATIONS REGARDING CRYSTAL GROWTH OF INP
BACHMANN KJ VITANOV T POPOV A BUDEVSKI E
N12 121 1699
MECHANISM OF ELECTROCRYSTALLIZATION
BAKER IN SEE BEYNON JDE 121 1124
BAKER JA SEE MINZE JW 121 1328
BARAONA CR SEE WANG EY 121 973
BARBER MD SEE OSHAUGHN.TA 121 1380
BARD AJ SEE ALLENSWO.R 121 1412
BARGER MJ SEE ADAMS AA 121 987
BARILE CA DOCKERTY RC NAGARAJA.A
N7 121 907
INSULATOR CHARGE AND VFB STABILITY OF SNOS CAPACITORS
BARNA G SEE JASINSKI R 121 1575
BASHTAVE.E SEE PAVLOV D 121 884
BATES FL HEE YT
N1 121 79
STANDARD ELECTRODE POTENTIAL MEASUREMENTS OF PB/PBCL2/HCL AND TL/TLCL/HCL HALF CELLS IN DIMETHYLFORMAMIDE AT 30 DEGREES C
BAUER HH SEE VENKATAD.AS 121 249
BAYLIS SKW SEE SCHLESIN.H 121 1461
BEARD RB CAPIN HM DUBIN SE DEROSA JF
MILLER AS
N9 121 1129
CORROSION AND HISTOPATHOLOGICAL STUDIES ON ANODE MATERIALS FOR IMPLANTABLE POWER SOURCES
BECK AF BROCK AJ PRYOR MJ
N5 121 718
OXIDATION OF 2-PHASE ALUMINUM-COPPER ALLOYS
BEER EA SEE OBRIEN RN 121 370
BEHL WK
N7 121 959
THERMODYNAMIC PROPERTIES, TRANSFERENCE NUMBERS, AND IONIC MOBILITIES IN MOLTEN LITHIUM CHLORIDE-CADMIUM CHLORIDE MIXTURES FROM EMF MEASUREMENTS
BEHL WK
N8 121 991
TRANSFERENCE NUMBERS IN MOLTEN MIXTURES OF ALKALI CHLORIDE-CERIUM CHLORIDE FROM EMF MEASUREMENTS
BEINGLAS.I SEE AVIGAL Y 121 1103
BELANGER A VIJH AK
N2 121 225
HYDROGEN EVOLUTION REACTION ON VANADIUM, CHROMIUM, MANGANESE, COBALT
BELL RO
N10 121 1386
AN ANALYSIS OF TEMPERATURE DISTRIBUTION DURING CRYSTAL GROWTH BY THM
BENNION DN SEE KATAN T 121 757
BENZ KW SEE MESS K 121 1208
BERNARD WJ SEE ALWITT RS 121 1019
BETTY KR SEE KRATOCHVI.B 121 851
BEYNON JDE HAKEN RA BAKER IN
NB 121 1124
SELF-ALIGNED GAPS - ALTERNATIVE TECHNIQUE FOR CLOSELY SPACED METALLIZATION PATTERNS
BHAGAT S SEE RASTOGI RP 121 1063
BHALLA AS
N1 121 170
CRYSTALLOGRAPHIC ASSIGNMENT OF DOMAINS IN SINGLE CRYSTALS OF GADOLINIUM MOLYBDATE SGMOC
BIERLEIN JD SEE DONOHUE PC 121 829
BIERSTED.PE SEE DONOHUE PC 121 327
BLOEM J GILING LJ GRAEF MWM
N10 121 1354
INCORPORATION OF PHOSPHORUS IN SILICON EPITAXIAL LAYER GROWTH
BLUMENTH.RN HOFMAIER AL
N1 121 126
TEMPERATURE AND COMPOSITIONAL DEPENDENCE OF ELECTRICAL CONDUCTIVITY OF NONSTOICHIOMETRIC CEO2-X
BLUMENTH.PN SEE VANHANDE.GJ 121 1198
BLURTON KF SEOLAK JM
N10 121 1315
ELECTRO-OXIDATION OF CARBON MONOXIDE ON PLATINUM
BOWDEN MJ THOMPSON LF
N12 121 1620
POLYSTYRENE SULFONE%-A SENSITIVE ION-MILLABLE POSITIVE ELECTRON BEAM RESIST
BOWDEN MJ SEE THOMPSON LF 121 1900
BOXALL LG JONES HL OSTERYOU.RA
N2 121 212
ELECTROCHEMICAL STUDIES ON AG, PT, AND CU SPECIES IN ALCL3-NACL MELTS
BRANDHOR.HW SEE WANG EY 121 973
BRAUNSTE.J SEE SODD DD 121 247
BRAUNSTE.J SEE VALLET CE 121 1429
BREDRICK RF PANLENER RJ
N7 121 932
SYSTEMATIC INVESTIGATION OF QUANTITATIVE FITS TO III-V PSEUDOBINARIES USING QUASIREGULAR MODEL AND ITS SPECIAL CASES
BRESSAN DJ SEE DAY M 121 798
BRIGHAM RJ TOZER EW
N9 121 1192
PITTING RESISTANCE OF 18 PERCENT CR FERRITIC STAINLESS STEELS CONTAINING MOLYBDENUM
BRISKA M KIOPSKY A
N7 121 972
ANALYTICAL DETERMINATION OF BORON IN CHEMICALLY DEPOSITED POLYCRYSTALLINE SILICON
BRO P SEE SELIN R 121 1497
BROCK AJ SEE BECK AF 121 718
BROCKWAY LO SEE FAN PL 121 1534
BRONSTEI.HR SEE VALLET CE 121 1429
BROTHERT.DL SEE GILBERT B 121 773
BROWN DM
N12 121 1677
ANOMALOUS BORON DIFFUSION IN SILICON FROM PLANAR-BORON NITRIDE SOURCES
BROWN F SEE MACINTO.WD 121 1281
BRUCKENS.S SEE MILLER B 121 1598
BRUCKENS.S SEE SHABRANG M 121 1439
BRUCKENS.S SEE UNTEREKE.OF 121 360
BUDEVSKI E SEE BACHMANN KJ 121 1606
BUDEVSKI E SEE VITANOV T 121 207
BUEHLER E SEE BACHMANN KJ 121 835
BUTLER SR SEE OTA Y 121 1107
CADLE SH
N5 121 645
RING-DISK ELECTRODE STUDY OF PALLADIUM DISSOLUTION
CAHAN BD SEE ADZIC R 121 474
CAHAN BD SEE SCHMIDT E 121 1610
CAMPBELL DR ALESSAND.EI YU KN LEWIS JE
N5 121 1081
PHOSPHORUS DIFFUSION IN PARTIALLY CRYSTALLIZED FILMS OF SIO2
CAMPBELL DR SEE ALESSAND.EI 121 1115
CAPON A PARSONS R ANGERSTE.H MACDOUGA.B
CONWAY BE
N6 121 780
ORIGIN OF ACTIVATION EFFECTS OF ACETONITRILE AND MERCURY IN ELECTROCATALYTIC OXIDATION OF FORMIC ACID
CAPSIMAL.GP SEE COTE PJ 121 776
CARIN RW SEE BEARD RB 121 1129
CARLSTEN RW SEE NISSEN DA 121 950
CARUSO R VONNEIDA AR
N10 121 1332
EFFECT OF HEAT-TREATMENT ON PHOTOLUMINESCENCE EFFICIENCY AND MINORITY CARRIER LIFETIME IN LEC-GAP%ZN,O%
CARUSO R SEE JORDAN AS 121 183
CASTEEL JF SEE REDAGAY TV 121 977
CAULDER SH SIMON AC
N12 121 1546
THERMAL DECOMPOSITION MECHANISM OF FORMED AND CYCLED LEAD DIOXIDE ELECTRODES AND ITS RELATIONSHIP TO CAPACITY LOSS AND BATTERY FAILURE
CAULDER SH SEE SIMON AC 121 463
CAULDER SH SEE SIMON AC 121 531
CAVES RM SEE LEVINE SR 121 1051
CERISIER P SEE SABOUNGI ML 121 1258
CEZNER V SEE RAJASEKA.S 121 340
CEZNER V SEE ROUSAR I 121 336
CEZNER V SEE ROUSAR I 121 343
CEZNER V SEE ROUSAR I 121 648
CHAN JC SEE JACOB KT 121 934
CHANG IF
N6 121 815
SYNTHESIS OF PHOTOCHROMIC AND CATHODOCHROMIC SODALITE
CHAPMAN TW SEE DUMESIC J 121 1405
CHIN DT
N4 121 827
CHARACTERIZATION OF DEPOSITION OF IRON OXIDES ON A PLATINUM RING ELECTRODE
CHIN DT
N12 121 1892
DISSOLUTION OF MILD STEEL WITH A ROTATING RING HEMISPHERICAL ELECTRODE
CHIN DT SEE MAO KW 121 191
CHOUDHUR.NS SEE STERTEN A 121 1603
CHOW SL SEE FELDSTEI.N 121 736
CHRISTOU A DAY MM
NB 121 1076
RELIABILITY OF GOLD/STABILIZED TANTALUM METALLIZATIONS FOR MICROWAVE POWER TRANSISTORS
CHRISTOU A SEE DAY M 121 798
CHU SSC SEE CHU TL 121 159
CHU TL ITO K SMELTZER RK CHU SSC
N1 121 159
CRYSTAL GROWTH AND CHARACTERIZATION OF GALLIUM NITRIDE
CHU TL WYSLOP AE
N3 121 412
PREPARATION AND PROPERTIES OF BORON ARSENIDE FILMS
CLARK GJ ANDERSEN TN VALENTIN.RS EYRING H
N6 121 610
COMPARISON OF IMMERSION AND OPEN-CIRCUIT SCRAPE METHODS FOR DETERMINING POTENTIAL OF ZERO CHARGE OF METAL ELECTRODES
CLAUDEL B
N12 121 1676
TEMPERATURE AND COMPOSITIONAL DEPENDENCE OF ELECTRICAL CONDUCTIVITY OF NON-STOICHIOMETRIC CEO2-X
CLAYTON PR MANANTOV G MANNING DL
N1 121 88
ELECTROCHEMICAL STUDIES OF URANIUM AND THORIUM IN MOLTEN LIF-NAF-KF AT 500 DEGREES C
COCKS FH STORMONT RW
N4 121 596
HIGH PRESSURE CRYSTAL GROWTH OF SODIUM BETA-ALUMINA
COHEN M MASHINOT.K
N1 121 42
CATHODIC REDUCTION OF GAMMA-FEOOH, GAMMA-FE2O3, AND OXIDE FILMS ON IRON
COHEN M SEE MASHINOT.K 121 37
COHEN M SEE MACDOUGA.B 121 1152
CONTRERA.CH ROCK PA
N9 121 1048
ELECTROCHEMISTRY IN NORMAL-HEXANOL %1.H2NG.PT(/MCL3NEXC/TLCLRSC/TLRHGC CELL
CONWAY BE SEE CAPON A 121 780
CONWAY BE ANGERSTE.H LALIBERT.LH
N12 121 1596
REFLECTANCE CHANGES DURING FORMATION AND REDUCTION OF OXIDE FILMS ON GOLD AND PLATINUM - CORRECTIONS FOR DOUBLE-LAYER EFFECTS
CORBOY JF SEE CULLEN GW 121 1345
COTE PJ CAPSIMAL.GP GRECO VP
N6 121 776
ELECTRODEPOSITION OF AN AMORPHOUS COBALT RHENIUM ALLOY
COX CD SEE RAMACHAN.KN 121 673
CRAFT WH SEE OKIMAKA Y 121 86
CREVECOE.C WIT HJD
N11 121 1465
GROWTH OF ANODIC ALUMINUM OXIDE LAYERS AFTER A HEAT-TREATMENT
CUKOR P SEE FRENCH K 121 1048
CULLEN GW CORBOY JF
N10 121 1345
COMPARISON OF SEMICONDUCTING PROPERTIES OF THIN FILMS OF SILICON ON SAPPHIRE AND SPINEL
CURIE D SEE GARANDER.MP 121 1676
DALVI AD SMELTZER WW
N3 121 386
DIFFUSION MODEL FOR OXIDATION OF NICKEL-IRON ALLOYS AT 1000 DEGREES C
DANJANOV.A WARD AT GJEA M
N9 121 1186
EFFECT OF THICKNESS OF ANODIC OXIDE FILMS ON RATE OF OXYGEN EVOLUTION REACTION AT PT IN H2SO4 SOLUTION .1. GROWTH AT CONSTANT CURRENT
DAPNIER FW
N9 121 656
CATHODIC BEHAVIOR OF CUS, NIO3, AND NIO2 IN LITHIUM CELLS
DANNA PA
N10 121 1286
EFFECT OF BRINE LEVEL ON VOLTAGE OF MERCURY-TYPE CHLOR-ALKALI CELLS
DAPO RF
N2 121 253
VARIABLE COMPOSITION OF BASIC LEAD SULFATES
DARWISH N TAUBENES.R
NB 121 1119
C-MOS AND COMPLEMENTARY ISOLATED BIPOLAR TRANSISTOR MONOLITHIC INTEGRATION PROCESS
DAVIES H SMELTZER WW
N4 121 843
OXYGEN AND METAL ACTIVITIES OF CHROMIUM-NICKEL-OXYGEN SYSTEM BETWEEN 900 DEGREES AND 1100 DEGREES C
DAY M CHRISTOU A BRESSAN DJ
NB 121 798
RETENTION OF FLUORINE BY SILICON SURFACES - INTERACTION WITH GOLD-REFRACTORY TRANSISTOR METALLIZATIONS
DAY MM SEE CHRISTOU A 121 1076
DECOSTER.JP SEE FONTANA PV 121 148
DEGERBEC.J SEE GRASSIAN.M 121 778
DEROSA JF SEE BEARD RB 121 1129
DESPIC AR PURENOVI.MM
N3 121 329
CRITICAL OVERPOTENTIAL AND INDUCTION TIME OF DENDRITIC GROWTH
DESPIC AR SEE VORKAPIC LZ 121 1368
DEVEREUX OF SEE LIBSCH TA 121 400
DEY AN RUDD EJ
N10 121 1294
ELECTROINITIATED POLYMERIZATION OF TETRAHYDROFURAN
DHAEMENS LJ SEE KIEWIT DA 121 310
DIEGLE RB
N4 121 583
MICROSEGREGATION OF IRON IN ELECTROLYTIC CAPACITOR GRADE ALUMINUM
DIETZE W HUNT LP SAWYER DH
NB 121 1112
PREPARATION AND PROPERTIES OF CVD-SILICON TUBES AND BOATS FOR SEMICONDUCTOR DEVICE TECHNOLOGY
DIGGES TG YAWS CL
N9 121 1222
PREPARATION OF HIGH-RESISTIVITY SILICON BY VACUUM FLOAT ZONING
DIGIACOM.G
N3 121 419
MICROPROBE TECHNIQUE FOR DETERMINATION OF THICKNESS AND PHOSPHOROUS CONCENTRATION OF GATE OXIDE PHOSPHOSILICATE GLASS IN FET DEVICES
DILORENZ.JV SEE ROZGONYI GA 121 426
DIMARIN.CR SEE MYERS M 121 1526
DIN GA SEE HAAS WE 121 1667
DOCKERTY RC SEE BARILE CA 121 907
DONAGHEY LF PONG R

N4 121 806
OXYGEN TRANSFER KINETICS BETWEEN GA-GA203 ELECTRODES AND SOLID ELECTROLYTE CALCIA-STABILIZED ZIRCONIA
DONAHUE FW
N7 121 887
COMPUTATION OF STANDARD SPECIFIC RATE CONSTANTS OF PARTIAL PROCESSES IN MIXED POTENTIAL SYSTEMS
DONOHUE PC HANLON JE
N1 121 137
SYNTHESIS AND PHOTOLUMINESCENCE OF MIIIEIIIS5.5EGA
DONOHUE PC BIERSTEDT.PE
N3 121 327
CELL DIMENSIONS AND ELECTRICAL PROPERTIES OF SOLID SOLUTIONS - 1-XZNS-XCUALS2 AND 1-XZNSE-XCUALSE2 WHERE X # 0 TO 0.33
DONOHUE PC BIERLEIN JD HANLON JE JARRETT HS
N6 121 829
SYNTHESES, ELECTRICAL AND OPTICAL PROPERTIES OF DOPED AND UNDOPED CUALS2
DOSEN H SEE KANEKO K 121 956
DOUGHERT.FC SEE WANG CC 121 971
DOUGLASS DL SEE NASRALLA.MM 121 265
DOWGIALL.EJ OSULLIVA.JB SMELLING.IR ANDERSON RB
N9 121 1134
HIGH POWER FACILITY FOR TESTING ELECTROCHEMICAL POWER SOURCES
DRAZIC DM SEE VORKAPIC LZ 121 1385
DUBIN SE SEE GEARD RG 121 1129
DUMESIC J KOUTSKY JA CHAPMAN TW
N11 121 1405
RATE OF ELECTROLESS COPPER DEPOSITION BY FORMALDEHYDE REDUCTION
EFREMOV N SEE SMITH MI 121 1803
EHMAN MF
N9 121 1240
SURFACE PREPARATION OF CERAMIC OXIDE CRYSTALS - WORK DAMAGE AND MICROHARDNESS
EKLUND GS
N4 121 467
INITIATION OF PITTING AT SULFIDE INCLUSIONS IN STAINLESS STEEL
ELDER JP
N2 121 175
COMPUTER-CONTROLLED BATTERY PULSE CHARGING
ELMORE GV HERSHBER.RF
N1 121 107
MOLTEN ALKALI TREATMENT OF ALUMINA SURFACES FOR BONDING TO ELECTROLESS COPPER
ELVING PJ SEE SCHWAKEL CO 121 345
ELVING PJ SEE SCHWAKEL CO 121 1033
ENSTROM RE NUESE CJ APPERT JR GANNON JJ
N11 121 1516
INFLUENCE OF GAS-PHASE STOICHIOMETRY ON DEFECT MORPHOLOGY, IMPURITY DOPING, AND ELECTROLUMINESCENCE EFFICIENCY OF VAPOR-GROWN GAAS P-N JUNCTIONS
EPELBOIN I FROMENT M GARREAU M
N12 121 1694
POLARIZATION CHARACTERISTICS AND ANODIC DISINTEGRATION OF BERYLLIUM IN NONAQUEOUS SOLUTIONS
ERDMANN PM SEE MANASEVI.MM 121 967
ERMANIS F SCHWARTZ B
N12 121 1665
ANODIC OXIDATION OF GALLIUM PHOSPHIDE IN AQUEOUS HYDROGEN PEROXIDE
ETTEL VA TILAK BV GENDRON AS
N7 121 867
MEASUREMENT OF CATHODE MASS TRANSFER COEFFICIENTS IN ELECTROWINNING CELLS
EVANS DH SEE NIFKIN SC 121 769
EVANS DH SEE RYAN MD 121 881
EYRING H SEE CLARK GJ 121 618
FAHRNER W
N6 121 784
CONTRIBUTIONS OF OXYGEN, SILICON, AND HYDROGEN TO INTERFACE STATES OF AN SI-SIO2 INTERFACE
FAN PL BROCKWAY LO
N11 121 1534
OXIDATION OF THIN SINGLE CRYSTALS OF IRON
FARIA S MEHALCHI.EJ
N2 121 305
YVO4-EU,TB - EFFICIENT HIGH PRESSURE MERCURY VAPOR LAMP PHOSPHOR
FARRINGT.GC
N10 121 1314
MEASUREMENT OF BETA-ALUMINA IMPEDANCE WITH CONSTANT CURRENT PULSES
FARROW RFC
N7 121 899
KINETICS OF SILICON DEPOSITION ON SILICON BY PYROLYSIS OF SILANE - MASS SPECTROMETRIC INVESTIGATION BY MOLECULAR BEAM SAMPLING
FEIT ED SEE THOMPSON LF 121 1800
FELDMAN C PLACHY R
N5 121 685
VACUUM DEPOSITED SILICON DEVICES ON FUSED SILICA SUBSTRATES
FELDMAN DW SEE RYAN FM 121 1475
FELDSTEI.M SCHLESIN.M HEDGECOC.NE CHOW SL
N6 121 738
ELECTRON MICROSCOPE INVESTIGATION OF MIXED STANNOUS CHLORIDE/PALLADIUM CHLORIDE CATALYSTS FOR PLATING DIELECTRIC SUBSTRATES
FERNANDE.CG SEE KEENAN AG 121 885
FLENGAS BN SEE KUCHARSK.AS 121 1298
FONTANA PV DECOSTER.JP MEGHANN L
N1 121 146
INVESTIGATIONS OF CARBON RESIDUES ON SURFACES OF SILICON INTEGRATED CIRCUITS
FOSTER LM
N12 121 1662
LATTICE PARAMETER CRITERION FOR MISCIBILITY GAPS IN III-V AND II-VI PSEUDOBINARY SOLID SOLUTIONS
FRASER HR SEE TURETZKY MN 121 1098
FRENCH K CUKOR P PERSIANI C AUBORN J
N8 121 1045
DETERMINATION OF WATER CONTAMINATION IN LIQUID INORGANIC OXYHALIDE ELECTROLYTES
FRIESER RG
N5 121 669
CHARACTERIZATION OF THERMALLY GROWN SIO2 SURFACES BY CONTACT ANGLE MEASUREMENTS
FRITZSCH.C SEE ROTHEMUN.W 121 586
FROMENT M SEE EPELBOIN I 121 1404
FRYBURG GC KOHL PJ STEARNS CA
N7 121 952
ENHANCED OXIDATIVE VAPORIZATION OF CR2O3 AND CHROMIUM BY OXYGEN ATOMS
FRYBURG GC SEE STEARNS CA 121 945
FUJITA I SEE IKEZAKI K 121 901
FULLENWI.MA
N2 121 313
FLUX STEP BOUNDARY CONDITION SOLUTION TO DIFFUSION EQUATION CORRESPONDING TO ERROR FUNCTION COMPLEMENT PROFILE
FULLENWI.MA
N12 121 1589
CONTRIBUTIONS OF DISSOLVED HYDROGEN TO POTENTIAL AND IRREVERSIBLE BEHAVIOR OF HYDROGEN ELECTRODE
GAGNON EG
N4 121 912
TRIANGULAR VOLTAGE SWEEP METHOD FOR DETERMINING DOUBLE-LAYER CAPACITY OF POROUS ELECTRODES .3. POROUS NICKEL IN POTASSIUM HYDROXIDE
GAGNON EG
N11 121 1444
TRIANGULAR SWEEP VOLTAMMETRY STUDIES ON POROUS SILVER IN KOH - EFFECT OF TEMPERATURE AND SWEEP RATE ON DOUBLE-LAYER CAPACITANCE
GALE RJ OSTRYOU.RA
N8 121 983
INVESTIGATION OF SUBVALENT ION EFFECTS DURING ALUMINUM ANODIZATION IN MOLTEN NACL-ALCL3 SOLVENTS
GALLOP LD SEE VALERIOT.EM 121 1345
GALVELE JR SEE WEXLER SRO 121 1271
GANNON JJ NUESE CJ
N9 121 1215
CHEMICAL ETCHANT FOR SELECTIVE REMOVAL OF GAAS THROUGH SIO2 MASKS
GANNON JJ SEE ENSTROM RE 121 1516
GARANDER.MP CURIE D PAPPALAR.R
N12 121 1676
ON THEORY OF THERMAL QUENCHING OF LUMINESCENCE
GARREAU M SEE EPELBOIN I 121 1404
GATOS HC SEE KIM KN 121 449
GATOS HC SEE SINGH R 121 380
GATOS HC SEE WITT AF 121 787
GENDRON AS SEE ETTEL VA 121 867
GHANDHI SK SEE JAYANTBA.B 121 1642
GHANDI SK SEE JAYANTBA.B 121 1646
GIANI E KELLY R
N3 121 394
STUDY OF SNO2 THIN FILMS FORMED BY SPUTTERING AND BY ANODIZING
GIBBON CF SEE MEEK RL 121 444
GIBBONS EF SEE LAUD KR 121 303
GIDDINGS RA GORDON RS
N6 121 793
SOLID-STATE COULOMETRIC TITRATION - CRITICAL ANALYSIS AND APPLICATION TO WUSVITE
GILBERT AG SULZMANN KG
N6 121 832
VAPOR PRESSURE OF IRON PENTACARBONYL
GILBERT B BROTHERT.DL HAMANTOV G
N6 121 773
CHRONOPOTENTIOMETRIC INVESTIGATION OF OXIDATION OF ALUMINUM IN CHLOROALUMINATE MELTS
GILING LJ SEE BLOEM J 121 1354
GNADINGE.AP ROSENZWE.W
N5 121 700
POLARIZATION AND CHARGE MOTION IN METAL-AL2O3-SIO2-SI STRUCTURES
GOLDMAN J WAGNER JB
N10 121 1316
STUDY OF LOW TEMPERATURE DIFFUSION OF COPPER IN SINGLE CRYSTALLINE GOLD USING A CUCL SOLID ELECTROLYTE
GOLDSTEI.JI SEE LANGER PH 121 963
GONZALEZ OD JOSEPHIC PH ORIANI RA
N1 121 29
UNDERCUTTING OF ORGANIC LACQUERS ON STEEL
GORDON RS SEE GIDDINGS RA 121 793
GRAEF WJH SEE BLOEM J 121 1354
GRANDOV L VIELSTIC.W
N6 121 779
DIFFUSION COEFFICIENTS AND KINETIC PARAMETERS IN COPPER SULFATE ELECTROLYTES AND IN COPPER FLUOROBORATE ELECTROLYTES CONTAINING ORGANIC ADDITION AGENTS
GRASSIAN.H GEGERGEC.J
N6 121 778
ACCELERATED PITTING AND CREVICE CORROSION TESTS
GRECO VP SEE COTE PJ 121 776
GREENEIC.JS
N12 121 1669
SOLUBILITY RATE OF POLY-METHYL METHACRYLATEC. PMMA, ELECTRON-RESIST
GRIECO MJ
N2 121 289
INVESTIGATION OF IMPERFECTIONS IN SILICON SUBSTRATES USING COPPER DISPLACEMENT TECHNIQUE
GRONLUND F NOER S
N1 121 25
STANDARD POTENTIAL OF SINGLE-CRYSTAL COPPER ELECTRODE IN AQUEOUS SOLUTIONS
GROSS B
N12 121 1677
EFFECT OF DIELECTRIC INSERT ON SURFACE CHARGE DENSITY OF ELECTRETS
GRUENKE R SEE AGRAWAL YK 121 384
GRUSS L MACKUS T
N11 121 1402
ANODIZATION OF SEVERAL RARE EARTH METALS IN SODIUM SILICATE SOLUTIONS
GULDI RL ANTCLIFF.GA
N11 121 1523
ANTIMONY DIFFUSION INTO P-TYPE PBS-KSNXTE
GULENS J KONRAD D ANSON FC
N11 121 1421
CYCLIC VOLTAMMETRY AND CHRONOCOULOMETRY WITH TRANS-RHXEN(CEC)2 AT MERCURY ELECTRODES
GUPTA K NARTON JP SHEWCHUN J
N1 121 118
OXIDATION CHARACTERISTICS OF SOME NICKEL ALLOY FILMS IN AIR AND WATER VAPOR
GURLUSKY PJ SEE SIMON AC 121 463
GUTHRIE JW
N12 121 1617
IDENTIFICATION OF AGCL AS A SURFACE CONTAMINANT ON HYBRID MICROCIRCUIT CAPACITORS USING ION MICROPROBE TECHNIQUES
HAAS WE NELSON KF ADAMS JE DIP GA
N12 121 1667
UV IMAGING WITH NEMATIC CHLOROSTILBENES
HACKERMAN SEE OGURA K 121 1013
HAKEN RA SEE BEYNON JDE 121 1124
HAMBY DC HOMINER AR
N1 121 104
THERMODYNAMIC PROPERTIES OF MOLTEN MIXTURES OF NICKEL CHLORIDE WITH CESIUM CHLORIDE AT 700 DEGREES AND 800 DEGREES C
HANLON JE SEE DONOHUE PC 121 137
HANLON JE SEE DONOHUE PC 121 829
HANSEN WN SEE ANDERSON WJ 121 1870
HARRIS WS SEE MILES MH 121 459
HASHIMOT.K COHEN M
N1 121 37
ANODIC DEPOSITION OF FERRIC OXY-HYDROXIDE FILMS ON PLATINUM FROM PERCHLORATE SOLUTIONS
HASHIMOT.K SEE COHEN M 121 42
HASZKO SE SEE MARCUS RB 121 692
HEASELL EL SEE OSHAUGHN.YA 121 1380
HEDGECOC.NE SEE FELDSTEI.N 121 738
HEILMANN SM SEE WANZONEK S 121 376
HEILMANN SM SEE WANZONEK S 121 816
HEINLEIN E SEE MCGONTY GA 121 428
HELDT LA SEE JOHNSEN WC 121 34
HERMANN HD SEE LORENZ WJ 121 1167
HERSH MN SEE OZAWA L 121 894
HERSHBER.RP SEE ELMORE GV 121 107
HESS JW SWEET JR WHITE WB
N1 121 142
CANDOLUMINESCENCE IN TRANSITION-ION-ACTIVATED OXIDE PHOSPHORS
HESS R STATH N BENZ KW
N9 121 1200
LIQUID PHASE EPITAXY OF INP
HILBERT F SEE LORENZ WJ 121 1167
HILLS GJ SEE INMAN D 121 778
HINE F YASUDA H SUGIURA I YODA T
N2 121 220
EFFECTS OF ACTIVE CHLORINE AND PH ON CONSUMPTION OF GRAPHITE ANODE IN CHLOR-ALKALI CELLS
HINE F YASUDA H IWATA H
N6 121 749
CHLORINE AND OXYGEN ELECTRODE PROCESSES ON GLASSLIKE CARBON, PYROLYTIC GRAPHITE, AND CONVENTIONAL GRAPHITE ANODES
HINE F YASUDA H
N10 121 1289
STUDIES ON MECHANISM OF CHLORINE ELECTRODE PROCESS
HINZE JW BAKER JA PATTERSO.JW
N10 121 1328
INTERFACE STABILITY IN ELECTROLYTIC DECOMPOSITION OF SILICON DIOXIDE FILMS AT ELEVATED TEMPERATURES
HOARE JP WIESE CR
N1 121 83
TRANSFERENCE NUMBER FOR LIS ION IN PROPYLENE CARBONATE SOLUTIONS FROM EMF MEASUREMENTS
HOARE JP
N7 121 872
EFFECT OF OXYGEN DISSOLVED IN PT ON POTENTIAL OF A PT-O2 ELECTRODE AT REST
HOBBS BS SEE VERTES G 121 782
HOFNAIER PL SEE BLUMENTH.RN 121 126
HOHIMER AR SEE HANBY DC 121 104
HOLLEMAN J SEE MIDDELHO.J 121 132
HOLLIDAY TB SEE SEITZ MA 121 122
HOLONYAK N SEE YONENIN VA 121 1657
HONMA Y SEE SUGAWARA K 121 1835
HONSY RV NEWMAN J
N4 121 521
ASYMPTOTIC SOLUTION FOR WARBURG IMPEDANCE OF A ROTATING DISK ELECTRODE
HONSY RV NEWMAN J
N11 121 1448
CURRENT DISTRIBUTION ON A PLANE BELOW A ROTATING DISK
HORANYI G SEE VERTES G 121 782
HUNT LP SEE DIETZE W 121 1112
HUNT LP SEE SIRTL E 121 919
HURET TM MALOY JT
N9 121 1178
ANALYTICAL ASPECTS OF ENERGY-DEFICIENT ELECTROGENERATED CHEMILUMINESCENCE
HYSLOP AE SEE CHU TL 121 412
IKEZAKI K FUJITA I WADA K NAKAMURA J
N4 121 901
EFFECT OF DIELECTRIC INSERT ON SURFACE CHARGE DENSITY OF ELECTRETS
ILIEV V SEE PAVLOV D 121 884
IMAI K SATO M ABE Y
N12 121 1674
CONFIRMATION OF EXISTENCE OF PHASE TRANSITIONS IN INSE BY SPECIFIC HEAT MEASUREMENT AND X-RAY ANALYSIS
INMAN D LOVERING DG HILLS GJ SCHIFFRI.DJ THOMPSON J
N6 121 775
MONOLAYER FORMATION IN REDUCTION OF NICKEL AND SILVER IONS FROM LICL-KCL EUTECTIC
IRENE EA
N12 121 1613
EFFECTS OF TRACE AMOUNTS OF WATER ON THERMAL OXIDATION OF SILICON IN OXYGEN
IRVIN JC SEE MARCUS RB 121 692
ITO K SEE CHU TL 121 159
IVES MB SEE ZANIN M 121 1141
IWATA M SEE HINE F 121 749
JACOB KT CHAN JC
N4 121 534
ELECTROCHEMICAL DETERMINATION OF STABILITY OF MONOCALCIUM AND DICALCIUM STANNATES
JAKSIC MM
N1 121 70
MUTUAL EFFECT OF CURRENT DENSITY, PH, TEMPERATURE, AND HYDRODYNAMIC FACTORS ON CURRENT EFFICIENCY IN CHLORATE CELL PROCESS
JAMES GAA SEE KULKARNI MV 121 880
JAMES WJ SEE VAIDYANA.H 121 7
JAMES WJ SEE VAIDYANA.H 121 876
JARRETT HS SEE DONOHUE PC 121 829
JASINSKI R TRACHTEN.I RICE G
N3 121 363
CHALCOGENIDE GLASS ELECTRODE SENSITIVE TO CUPRIC IONS
JASINSKI R BARNA G TRACHTEN.I
N12 121 1675
STUDIES OF A NITROGEN DIOXIDE SENSITIVE, CHALCOGENIDE GLASS ELECTRODE
JASINSKI R
N12 121 1679
PALLADIUM HYDRIDE PH ELECTRODE FOR USE IN BUFFERED FLUORIDE ETCH SOLUTIONS
JAYANTBA.S GHANDHI SK
N12 121 1642
HETEROEPITAXIAL INAS GROWN ON GAAS FROM TRIETHYLINDIUM AND ARSINE .1. GROWTH CHARACTERIZATION
JAYANTBA.S GHANDI SK
N12 121 1646
HETEROEPITAXIAL INAS GROWN ON GAAS FROM TRIETHYLINDIUM AND ARSINE .2. ELECTRICAL PROPERTIES
JENKINS JD SEE TURETZKY MN 121 1098
JOHNSON JW SEE VAIDYANA.H 121 876
JOHNSON WC HELDT LA
N1 121 34
COMPOSITION OF PT ANODE SURFACES BY AUGER SPECTROSCOPY
JONES ML SEE GOXALL LG 121 212
JORDAN AS VONNEIDA AR CARUSO R KIM CK
N1 121 103
DETERMINATION OF SOLIDUS AND GALLIUM AND PHOSPHORUS VACANCY CONCENTRATIONS IN GAP
JORDAN AS WEINER ME
N12 121 1634

CALCULATION OF LIQUIDUS ISOTHERMS AND COMPONENT ACTIVITIES IN GA-AS-SI AND GA-P-SI TERNARY SYSTEMS
JORNE J TOBIAS C® N8 121 904

ELECTRODE KINETICS OF ALKALI METALS IN ALCL3-PROPYLENE CARBONATE SOLUTION
JOSEPHIC PH SEE GONZALEZ OD 121 29
KAISER RH SEE MELLIARS.CH 121 298
KAMINS TI N2 121 286

DIFFUSION IN THIN SILICON FILMS FORMED BY ELECTROCHEMICAL ETCHING
KAMINS TI N5 121 681

DEFORMATION OCCURRING DURING DEPOSITION OF POLYCRYSTALLINE-SILICON FILMS
KAMMLOTT GW SINCLAIR WR N7 121 929

FE2O3 - INORGANIC ELECTRON RESIST MATERIAL
KANEKO K AYABE M DOSEN M MORIZANE K
USUI S WATANABE N N4 121 556

DIFFUSION OF PHOSPHORUS IN GALLIUM MELT
KAO YC SEE RAICHOUD.P 121 1509
KATAN T SZPAK S BENNION DN N6 121 757

SILVER/SILVER CHLORIDE ELECTRODES - SURFACE MORPHOLOGY ON CHARGING AND DISCHARGING
KATODA T SUGANO T N8 121 1066

HALL EFFECT. SCHOTTKY BARRIER CAPACITANCE, AND PHOTOLUMINESCENCE SPECTRA MEASUREMENTS FOR GAAS EPITAXIAL LAYER AND THEIR CORRELATION
KATZ LE N7 121 969

RELATIONSHIP BETWEEN PROCESS-INDUCED DEFECTS AND SOFT P-N JUNCTIONS IN SILICON DEVICES
KEATING KB SEE WOLFE WR 121 1125
KEENAN AG FERNANDE.. WILLIAMS.TR N7 121 885

STABILITY OF CARBONATE ION IN FUSED NITRATE
KELLEY PL SEE SMITH HI 121 1503
KELLY R SEE GIANI E 121 394
KENNEDY JH SAMMELLS AF N1 121 1

GALVANIC CELLS CONTAINING CATHODES OF IRON-DOPED BETA-ALUMINA
KETCHOW OR N9 121 1237

GERMANIUM-DOPED GAAS FOR P-TYPE OHMIC CONTACTS
KHAN IH RAJAPAKS.Y N6 121 848

CHLORINE ADSORPTION AT A TITANIUM SURFACE
KIDOKORO N SEE UENO Y 121 202
KIEWIT DA OHAENENS EJ ROTH JA N2 121 310

GERMANIUM SURFACE CLEANING - AUGER ANALYSIS
KIM CK SEE JORDAN AS 121 153
KIM JJ SEE RIECHEL TL 121 1462
KIM KN WITT AF GATOS HC N3 121 448

SEGREGATION BEHAVIOR IN A STATIONARY VERTICAL ZONE WITH CONVERGING INTERFACES - PRESSURE-INDUCED SEGREGATION EFFECTS
KINOSHIT.J SEE ROSZTOCZ.PE 121 439
KIOFSKY A SEE BRISKA M 121 972
KNORR K LESLIE JD N6 121 805

ELLIPSOMETRIC MEASUREMENTS OF PLASMA OXIDATION OF NB AND TA AND THEIR INTERPRETATION
KNORR K SEE LESLIE JD 121 263
KOCH FB MEEK RL MCCAUGHA.DV N4 121 558

IMPLANTATION OF ARGON INTO SIO2 FILMS DUE TO BACKSPUTTER CLEANING
KODYNOVA.J LASKA L KREJCI V N7 121 943

THERMAL NITRIDATION OF MAGNESIUM AT LOWER TEMPERATURES AND PRESSURES OF NITROGEN ATMOSPHERE
KOHL PJ SEE FRYBURG GC 121 952
KOHL PJ SEE STEARNS CA 121 945
KOIZUMI T UHLIG HH N9 121 1137

PASSIVITY AND PITTING OF NI-CU ALLOYS IN NACL SOLUTIONS
KOLARIK K SEE ROUSAR I 121 343
KONRAD O SEE GULENS J 121 1421
KOUTSKY JA SEE DUMESIC J 121 1405
KRAJCA M SEE ROUSAR I 121 343
KRAMBECK RH N4 121 588

NUMERICAL CALCULATION OF IMPURITY REDISTRIBUTION DURING THERMAL OXIDATION OF SEMICONDUCTORS
KRATOCHV.B BETTY KR N7 121 851

SECONDARY BATTERY BASED ON COPPERNII<~5IC AND NI<~80C COUPLES IN ACETONITRILE
KREJCI V SEE KODYNOVA.J 121 943
KRONEMBE.ML N3 121 378

USE OF D-C RESISTANCE AND A-C IMPEDANCE MEASUREMENTS ON DISCHARGED AND UNDISCHARGED CATHODES AS A MEASURE OF RELATIVE ELECTRONIC AND IONIC CONDUCTANCE
KRUGER J SEE AMBROSE JR 121 599
KUCHARSK.AS FLENGAS SN N10 121 1298

ELECTRICAL CONDUCTIVITIES AND MOLAR VOLUMES IN BINARY SYSTEMS MNCL2-LICL, MNCL2-NACL, MNCL2-KCL, MNCL2-RBCL, MNCL2-CSCL
KUHL C SCHWIDEF.F N11 121 1496

OPTICAL INVESTIGATION OF DIFFERENT SILICON FILMS
KULKARNI NV SMITH PJ JAMES GAA TROUTMAN HA N2 121 280

STRUCTURE OF ANODICALLY DECORATED NPN BIPOLAR TRANSISTORS
KUNG JK SPITZER WG N11 121 1482

INFRARED REFLECTIVITY AND FREE CARRIER ABSORPTION OF SI-DOPED, N-TYPE GAAS
KUSHNER RA SEE MCCAUGHA.DV 121 724
KUSHNER RA SEE MELLIARS.CH 121 298
LAIRD EC SEE MAHATO BK 121 13
LALIBERT.LH SEE CONWAY BE 121 1596
LANGER PH GOLOSTEI.JI N4 121 563

IMPURITY REDISTRIBUTION DURING SILICON EPITAXIAL GROWTH AND SEMICONDUCTOR DEVICE PROCESSING
LARSON WL NARUSKA HP STEVENSO.DA N12 121 1673

SYNTHESIS AND PROPERTIES OF ZNGEN2
LASKA L SEE KODYNOVA.J 121 943
LAU SS SIGURD D N11 121 1538

INVESTIGATION OF STRUCTURE OF PD2SI FORMED ON SI
LAUD KR TIEN TY GIBBONS EF STADLER HL N2 121 303

LUMINESCENCE OF MN2S IN ALPHA-LIALSIO4
LEHMANN W SEE RYAN FM 121 1475
LEJA J SEE OBRIEN RN 121 370
LENZO PV SEE THOMPSON LF 121 1500
LESLIE JD KNORR K N2 121 263

ELLIPSOMETRIC STUDY OF PLASMA OXIDATION OF TANTALUM
LESLIE JD SEE KNORR K 121 805
LEVINE SN CAVES RW N8 121 1051

THERMODYNAMICS AND KINETICS OF PACK ALUMINIDE COATING FORMATION ON LN-100
LEVY DJ SEE MONYER WR 121 484
LEWIS JE SEE CAMPBELL DR 121 1081
LIEBSCH TA DEVEREUX OF N3 121 400

RELATION BETWEEN ENVIRONMENTAL PH, POROSITY, AND IMPEDANCE OF ANODIC ALUMINUM OXIDE FILMS
LICHTENS.M SEE WITT AF 121 787
LIEBERMA.R SEE MOLINE RA 121 1362
LIEBLICH N SEE REISFELD R 121 1338
LIEN SY SEE PRUETT HD 121 822
LIGHTOWL.EC SEE NORTH JC 121 993
LIZUKA T N8 121 1085

ETCHING STUDIES OF ANOMALOUS DEFECTS IN P-TYPE GAP CRYSTALS
LORENZ MJ HERMANN HD WUTHRICH N HILBERT F N9 121 1167

FORMATION OF MONOLAYER METAL FILMS ON ELECTRODES
LORIMOR OG SEE ROCCASEC.DD 121 962
LOVERING DG SEE INMAN D 121 778
LOWELL CE SEE SMIALEK JL 121 800
LU CC SEE ASAKURA S 121 605
LU CC SEE ASAKURA S 121 1276
MACDONAL.DD N5 121 651

CYCLIC VOLTAMMETRY OF COPPER METAL IN LITHIUM HYDROXIDE SOLUTION AT ELEVATED TEMPERATURES
MACDOUGA.B COHEN M N9 121 1152

ANODIC OXIDATION OF NICKEL IN NEUTRAL SULFATE SOLUTION
MACDOUGA.B SEE CAPON A 121 780
MACKINTO.WD BROWN F PLATTNER HH N10 121 1281

MOBILITY OF METALLIC FOREIGN ATOMS DURING ANODIC OXIDATION OF ALUMINUM
MACKSEY HM SEE VORONIN VA 121 1657
MACKUS Y SEE GRUSS L 121 1402
MACRAE AU SEE MOLINE RA 121 1362
MAHATO BK WEISSMAN EY LAIRD EC N1 121 13

SOME ASPECTS OF GAS RECOMBINATION IN LEAD-ACID SYSTEMS
MAIER MA SEE SOULES TF 121 407
MALOY JT SEE MURET TM 121 1178
MAMANTOV G SEE CLAYTON FR 121 86
MAMANTOV G SEE GILBERT B 121 773
MANASEVI.HM N2 121 293

GAS-PHASE ETCHING OF SAPPHIRE .3. CHLOROTRIFLUOROMETHANE
MANASEVI.HM SIMPSON WI ERDMANN FM N7 121 967

TRIMETHYLSTIBINE AS A SOURCE OF SB FOR DOPING EPITAXIAL SI LAYERS
MANNING DL SEE CLAYTON FR 121 86
MAO KW CHIN OT N2 121 191

ANODIC BEHAVIOR OF MILD STEEL IN NACLO3 AT HIGH CURRENT DENSITIES
MARCUS RB HASZKO SE MURARKA SP IRVIN JC N5 121 692

SCANNING ELECTRON MICROSCOPE STUDIES OF PREMATURE BREAKDOWN SITES IN GAAS IMPATT TESTERS
MARGALIT N N11 121 1460

DISCHARGE BEHAVIOR OF LI-MOO3 CELLS
MARSHALL GW SEE VORONIN VA 121 1657
MARTON JP SEE GUPTA K 121 110
MARUSKA HP ANDERSON LJ STEVENSO.DA N9 121 1202

MICROSTRUCTURAL OBSERVATIONS ON GALLIUM NITRIDE LIGHT-EMITTING DIODES
MARUSKA HP SEE LARSON WL 121 1673
MATSUYAN.K SEE TABEI H 121 67
MAYER P SMELTZER WW N4 121 538

DIFFUSIONAL GROWTH OF COBALTOUS-FERROUS OXIDE SCALES ON COBALT-IRON ALLOYS
MAYER P SEE YOUNG DJ 121 689
MAZANDAR.PN PEMLKE RD N5 121 711

STANDARD FREE ENERGY OF FORMATION OF CR2O3
MCCAFFER.E N8 121 1007

ELECTROCHEMICAL BEHAVIOR OF IRON WITHIN CREVICES IN NEARLY NEUTRAL CHLORIDE SOLUTIONS
MCCARTY LV REITH WE SIMON MT N10 121 1372

DIFFUSION AS RATE CONTROLLING STEP IN REACTION OF TUNGSTEN HEXAFLUORIDE WITH TUNGSTEN AND ROLE OF TUNGSTEN PENTAFLUORIDE
MCCAUGHA.DV KUSHNER RA WAGNER S N5 121 724

COMPLETE REMOVAL OF SODIUM FROM SILICON DIOXIDE FILMS BY FORMATION OF PHOSPHOSILICATE GLASS
MCCAUGHA.DV SEE KOCH FB 121 558
MCCRIGHT RD STAEHLE RW N5 121 689

EFFECT OF ARSENIC UPON ENTRY OF HYDROGEN INTO M1.0 STEEL AS DETERMINED AT CONSTANT ELECTROCHEMICAL POTENTIAL
MCFARLAN.BH SEE WANG CC 121 671
MEEK RL N1 121 172

HIGH SENSITIVITY DETECTION OF SOLUTION CONTAMINANTS BY MEV ION SCATTERING
MEEK RL GIBSON CF N3 121 444

PRELIMINARY RESULTS OF AN ION SCATTERING STUDY OF PHOSPHOSILICATE GLASS GETTERING
MEEK RL SEE KOCH FB 121 558
MEHALCHI.EJ SEE FARIA S 121 305
MEISUHR SG N10 121 1264

SURFACE-CATALYZED ANODES FOR HYDRAZINE FUEL CELLS .1. PREPARATION OF SUBSTRATE
MELLIARS.CH ADAMS AC KAISER RH KUSHNER RA N2 121 298

CHEMICALLY VAPOR DEPOSITED TUNGSTEN FOR SEMICONDUCTOR METALLIZATIONS
MELNGAIL.I SEE WOLFE CH 121 1506
MEMMING R SEE MOLLERS F 121 1160
METZGER M SEE ZAMAVI J 121 268
MIDDELHO.J HOLLEMAN J N1 121 132

LOW PHOSPHORUS CONCENTRATIONS IN SI BY DIFFUSION FROM DOPED OXIDE LAYERS
MILES MH YATES CA N2 121 230

HYDROGEN AND NITROGEN EVOLUTION REACTIONS IN ACID LIQUID AMMONIA
MILES MH HARRIS WS N4 121 459

DECOMPOSITION REACTION OF CONCENTRATED LITHIUM-AMMONIA SOLUTIONS
MILES MH SEE TRASATTI S 121 1609
MILLER AS SEE BEARD RB 121 1129
MILLER B BRUCKENS.S N12 121 1958

THEORETICAL AND EXPERIMENTAL STUDY OF HYDRODYNAMICALLY MODULATED CURRENT-POTENTIAL CURVES AT ROTATING DISK ELECTRODES UNDER CONDITIONS OF MIXED ELECTRON AND MASS TRANSFER CONTROL
MISHRA AK TANDON KN N1 121 91

CONDUCTANCES OF PROTONIC AND LEWIS ACIDS IN N,N-DIMETHYLFORMAMIDE XDMF<
MOLINE RA LIEBERMA.R SIMPSON J MACRAE AU N10 121 1362

GROWTH OF HIGH QUALITY EPITAXIAL SILICON OVER ION IMPLANTED BURIED ARSENIC LAYERS
MOLLERS F TOLLE HJ MEMMING R N9 121 1160

ON ORIGIN OF PHOTOCATALYTIC DEPOSITION OF NOBLE METALS ON TIO2
MONYER WR LEVY DJ N4 121 484

ELECTRICAL RESISTIVITY OF SILVER DEPOSITED BY AEROSOL SPRAY
MOON RL SEE ANTYPAS GA 121 416
MORCOS I N11 121 1417

ELECTROCAPILLARY PHENOMENA AT LEAD ELECTRODE
MORI Y SEE SUGANO T 121 113
MORIMOTO Y N10 121 1383

FEW CHARACTERISTICS OF EPITAXIAL GAN-ETCHING AND THERMAL DECOMPOSITION
MORIZANE K SEE KANEKO K 121 556
MORRIS BL N3 121 422

SOME DEVICE APPLICATIONS OF SPREADING RESISTANCE MEASUREMENTS ON EPITAXIAL SILICON
MURARKA SP SEE MARCUS RB 121 692
MURPHY J SEE RYAN FM 121 1475
MYERS M VANHANDL.HR DIMARTIN.CR N11 121 1526

EFFECTS OF CALCIUM, TIN, AND BISMUTH ON EARLY STRENGTH OF CALCIUM-LEAD ALLOYS
NAGARAJA.A SEE BARILE CA 121 907
NAGASIMA N SUZUKI M TANAKA K NISHIDA S N3 121 434

INTERACTION BETWEEN PHOSPHOSILICATE GLASS FILMS AND WATER
NAKAMURA H OHYAMA S TADACHI C N10 121 1377

BORON DIFFUSION COEFFICIENT INCREASED BY PHOSPHORUS DIFFUSION
NAKAMURA J SEE IKEZAKI K 121 591
NARA S SEE TABEI M 121 67
NARASAGO.RA SEE VAIDYANA.M 121 876
NASRALLA.MM DOUGLASS DL N2 121 255

IONIC AND ELECTRONIC CONDUCTIVITY IN Y2O3-DOPED MONOCLINIC ZRO2
NEE YT SEE BATES FL 121 79
NELSON KF SEE HAAS WE 121 1467
NEUBERT G PRATER KB N6 121 745

ELECTRO-OXIDATIVE COUPLING OF N,N-DIMETHYLANILINE - ROTATING RING-DISK ELECTRODE STUDY
NEWMAN J SEE MONSY RV 121 521
NEWMAN J SEE MONSY RV 121 1448
NEWMAN J SEE NISANCIO.K 121 241
NEWMAN J SEE NISANCIO.K 121 523
NEWMAN J SEE SNYRL WH 121 1000
NG PK SEE ALKIRE R 121 95
NICHOLSO.MM N6 121 734

LITHIUM-MAGNESIUM ELECTRODES IN PROPYLENE CARBONATE
NICOLAID.G SEE ALKIRE R 121 183
NISANCIO.K NEWMAN J N2 121 241

CURRENT DISTRIBUTION ON A ROTATING SPHERE BELOW LIMITING CURRENT
NISANCIO.K NEWMAN J N4 121 523

SHORT-TIME RESPONSE OF A DISK ELECTRODE
NISHIDA S SEE NAGASIMA N 121 434
NIESSEN DA CARLSTEN RW N4 121 500

SURFACE TENSION OF MOLTEN BINARY SYSTEM LICL-KCL
NOBE K SEE ASAKURA S 121 605
NOBE K SEE ASAKURA S 121 1276
NODA T SEE MINE F 121 220
NOER S SEE GROMLUND P 121 25
NORTH JC LIGHTOWL.EC N4 121 503

DETERMINATION OF BORON AND OXYGEN SURFACE CONTAMINATION DUE TO COMMON SOLVENTS BY NUCLEAR NEUTRON ACTIVATION ANALYSIS
NUESE CJ SEE ENSTROM RE 121 1516
NUESE CJ SEE GANNON JJ 121 1215
OBRIEN RN LEJA J BEER EA N3 121 370

INTERFEROMETRIC STUDY OF ZN-ZNSO4-ZN SYSTEM .2. CONCENTRATION GRADIENTS UNDER CONVECTIONLESS TRANSPORT
OGURA K HACKERMA.N N8 121 1013

EFFECT OF CHELATING AGENTS ON TRANSIENT BEHAVIOR OF PASSIVATED IRON UNDER CATHODIC POTENTIAL PULSING
OHYAMA S SEE NAKAMURA H 121 1377
OJEA M SEE GANJANOV.A 121 1186
OKEEFE TJ SEE VAIDYANA.M 121 876
OKINAKA Y SARD R WOLMODI.C CRAFT WH RETAJCZY.TF N1 121 86

SOME PRACTICAL ASPECTS OF ELECTROLESS GOLD PLATING
OKINAKA Y SEE SARD R 121 62
OKTAY S SCHMECKE.AF N7 121 912

PREPARATION AND PERFORMANCE OF DENDRITIC HEAT

SINKS
OKUYAMA H SEE SUGAWARA K 121 1233
OKUYAMA H SEE SUGAWARA K 121 1235
OLSEN GH ABRAHAMS MS ZAMEROWS.TJ
NI2 121 1650
ASYMMETRIC CRACKING IN III-V COMPOUNDS
ORIANI RA SEE GONZALEZ OD 121 29
ORMOND DW SEE OSBURN CM 121 1195
ORMOND DW SEE OSBURN CM 121 1229
OSBURN CM
N6 121 809
DIELECTRIC BREAKDOWN PROPERTIES OF SIO2 FILMS GROWN IN HALOGEN AND HYDROGEN-CONTAINING ENVIRONMENTS
OSBURN CM ORMOND DW
N9 121 1195
SODIUM-INDUCED BARRIER-HEIGHT LOWERING AND DIELECTRIC BREAKDOWN ON SIO2 FILMS ON SILICON
OSBURN CM ORMOND DW
N9 121 1229
EFFECT OF SILICON WAFER IMPERFECTIONS ON MINORITY CARRIER GENERATION AND DIELECTRIC BREAKDOWN IN MOS STRUCTURES
OSBURN CM SEE ZECHNALL W 121 849
OSHAUGHN.TA BARBER HD THOMPSON DA MEASEL EL
N10 121 1350
SOLID SOLUBILITY OF GOLD IN DOPED SILICON BY OXIDE ENCAPSULATION
OSTERYOU.RA SEE BOXALL LG 121 212
OSTERYOU.RA SEE GALE RJ 121 583
OSULLIVA.JB SEE DOWGIALL.EJ 121 1134
OTA Y BUILER SR
N8 121 1107
REEXAMINATION OF SOME ASPECTS OF THERMAL OXIDATION OF SILICON
OZAWA L HERSH HN
N7 121 894
OPTIMUM ARRANGEMENT OF PHOSPHOR PARTICLES IN CATHODE-RAY PICTURE TUBE SCREENS
PADOVANI FA SEE RUIZ HJ 121 689
PAHLENER RJ SEE BREBRICK RF 121 932
PAPAZOV G SEE PAVLOV D 121 854
PAPPALAR.R
N2 121 312
THEORY OF THERMAL QUENCHING OF LUMINESCENCE
PAPPALAR.R SEE GARANDER.NP 121 1676
PARSONS R SEE CAPON A 121 780
PATTERSO.JW SEE MINZE JW 121 1328
PAVLOV D ILIEV V PAPAZOV G BASHTAVE.E
N7 121 854
FORMATION PROCESSES OF LEAD-ACID BATTERY NEGATIVE PLATES
PEARLSTE.F WEIGHTMA.RF
N8 121 1023
ELECTROLESS COBALT DEPOSITION FROM ACID BATHS
PEHLKE RD SEE MAZANDAR.FN 121 711
PERSIANI C SEE FRENCH K 121 1045
PFEIFFER H SEE PREIER H 121 595
PICKHARD.VY SMITH DL
N8 121 1064
CHEMOMECHANICAL POLISHING OF CDS
PIERSON JP SEE SIMON AC 121 463
PIGGOTT MR SEE PRABRIPU.K 121 430
PLACHY R SEE FELDMAN C 121 685
PLATTNER HH SEE MACKINTO.WD 121 1281
PLAUGER LR
N3 121 455
CONTROLLED CHEMICAL ETCHING OF GAP
PLOOG K
N6 121 846
CRYSTAL CHEMICAL RELATIONS BETWEEN NONMETAL OXIDES B4B02C2 AND B4B02N2 AND HYPOTHETICAL I-TETRAGONAL BORON
PONG R SEE DONAGHEY LF 121 506
PONJEE JJ SEE VANDAM HT 121 1655
POPOV A SEE BACHMANN KJ 121 1606
POPOV A SEE VITANOV T 121 207
PCVILONI.EI SEE WAGNER S 121 1487
PRABRIPU.K PIGGOTT MR
N3 121 430
REACTION BETWEEN SILICA AND ALUMINUM
PRATER KB SEE NEUBERT G 121 745
PREIER H PFEIFFER H
N4 121 895
ETCHING SOLUTION FOR REVEALING P-N JUNCTIONS IN PBS AND PBSI-KSEX
PRINCE JL SCHWETTN.FN
N5 121 705
DIFFUSION OF BORON FROM IMPLANTED SOURCES UNDER OXIDIZING CONDITIONS
PRINGLE JPS
N1 121 45
RANGE PROFILES FOR IONS IMPLANTED INTO ANODIC TANTALUM OXIDE
PRINGLE JPS
N2 121 195
EFFECT OF ION IMPLANTATION UPON DISSOLUTION OF ANODIC TANTALUM OXIDE IN BUFFERED HYDROGEN FLUORIDE
PRINGLE JPS
N7 121 860
IMPURITY EFFECTS IN DISSOLUTION OF ANODIC TANTALUM OXIDE
PRINGLE JPS
N7 121 865
FURTHER OBSERVATIONS ON MARKER BEHAVIOR OF NOBLE GASES DURING ANODIC OXIDATION OF TANTALUM
PRUETT HD LIEN SY
N6 121 822
X-RAY IMAGING TECHNIQUE FOR OBSERVING LIQUID ENCAPSULATION CZOCHRALSKI CRYSTAL GROWTH
PRYOR WJ SEE BECK AP 121 710
PURENOVI.MN SEE DESPIC AR 121 329
RADIELOV.D SEE VERSTEGE.JN 121 1627
RAICHOUD.P TAKEI WJ
N9 121 1228
FORMATION OF SILICON WHISKERS BY ALUMINUM-QUARTZ INTERACTION
RAICHOUD.P KAB VC SWEENEY GG
N11 121 1509
COMPATIBILITY OF OXIDE PASSIVATION AND PLANAR JUNCTIONS WITH AL, GA, AND P DIFFUSIONS
RAJAPAKS.Y SE. KHAN IH 121 848
RAJASEKA.S ROUSAR I CEZNER V
N3 121 340
AMALGAM DECOMPOSITION .2. MEASUREMENT OF AMALGAM DECOMPOSITION RATE IN TOWER DECOMPOSER
RAJASEKA.S SEE ROUSAR I 121 336
RALEIGH DO
N5 121 632
ELECTRODE CAPACITANCE IN SILVER-HALIDE SOLID ELECTROLYTE CELLS .1. ROOM TEMPERATURE GRAPHITE AND PLATINUM ELECTRODES
RALEIGH DO
N5 121 639
ELECTRODE CAPACITANCE IN SILVER-HALIDE SOLID ELECTROLYTE CELLS .2. TEMPERATURE-DEPENDENT BEHAVIOR OF AGBR-GRAPHITE POWDER INTERFACE
RAMACHAN.KN COX GD
N5 121 673
INVESTIGATION OF SURFACE OXIDE LAYERS BY X-RAY APPEARANCE POTENTIAL SPECTROSCOPY
RAMANARA.TA WORRELL WL
N11 121 1830
THERMODYNAMIC INVESTIGATION OF CUBIC SODIUM TUNGSTEN BRONZE, NAXWO3
RANDIN JP
N8 121 1029
ELECTROREDUCTION OF OXYGEN AND HYDROGEN PEROXIDE ON SODIUM-TUNGSTEN BRONZES
RAPP RA SEE AGRAWAL YK 121 354
RASTOGI RP SHUKLA RD BHAGAT S
N12 121 1963
PRECIPITATION AND DISSOLUTION POTENTIALS OF ELECTROLYTES IN D2O. ACETONE, AND FORMAMIDE
RAVI KV
N8 121 1000
HETEROGENEOUS PRECIPITATION OF SILICON OXIDES IN SILICON
REARDON JD
N5 121 720
METHOD FOR DETERMINING OPTIMUM THICKNESS OF GRAPHITIC COATINGS USED IN ELECTRON DEVICES
REBAGAY TV CASTEEL JF SEARS PG
N8 121 977
CONDUCTANCE-VISCOSITY STUDIES ON SOME MODERATELY CONCENTRATED NONAQUEOUS ELECTROLYTE SOLUTIONS FROM -50 DEGREES C TO 125 DEGREES C .1. SOLUTIONS OF BUANL, KSCN, AND NH4BR IN N,N-DIMETHYLFORMAMIDE
REINHEIM.HA
N4 121 490
CARBON IN GOLD ELECTRODEPOSITS
REISFELD R LIEBLICH N
N10 121 1338
ENERGY TRANSFER BETWEEN PB2+ AND EU3+ IN GERMANATE GLASS
REITH ME SEE MCCARTY LV 121 1372
RETAJCZY.TF SEE OKINAKA Y 121 56
RHODES CSL SALAMA CAT
N9 121 1219
SIMPLIFIED METHOD OF MEASURING LIFETIME USING STEADY-STATE BACK ILLUMINATION OF AN MOS CAPACITOR
RICE G SEE JASINSKI R 121 363
RIDGE G SEE ALLENSWO.G 121 1412
RIECHEL TL KIM JJ ROCK PA
N11 121 1462
DIRECT ELECTROCHEMICAL DETERMINATION OF HAMMETT SUBSTITUENT CONSTANTS
RIFKIN SC EVANS DH
N6 121 769
APPLICATION OF CURRENT-REVERSAL CHRONOPOTENTIOMETRY TO STUDY OF ELECTROLYTIC REDUCTIVE COUPLING
RITCHIE K SEE SMITH JN 121 827
ROCCASEC.DO SAUL RM LORIMOR OG
N7 121 962
NITROGEN DOPING BEHAVIOR IN GAP USING NH3 AS DOPANT SOURCE
ROCK PA SEE CONTRERA.CH 121 1048
ROCK PA SEE RIECHEL TL 121 1462
ROCK PA SEE SILVESTE.LF 121 251
ROCK PA SEE SILVESTE.LF 121 518
RODEANU IT
N10 121 1311
INFLUENCE OF ELECTROLYTE IMPURITIES ON MERCURY LOSSES IN ELECTROLYSIS OF AQUEOUS NACL SOLUTIONS
ROGERS JW SEE ALLENSWO.P 121 1412
ROSENZWE.W SEE GNADINGE.AP 121 700
ROSZTOCZ.FE KINOSHIT.J
N3 121 439
GROWTH AND EVALUATION OF EPITAXIAL GAAS FOR MICROWAVE DEVICES
ROTH JA SEE KIEWIT DA 121 310
ROTHEMUN.W FRITZSCH.CR
N4 121 586
OPTICAL ABSORPTION AND ELECTRICAL CONDUCTIVITY OF SIC FILMS PRODUCED BY ION IMPLANTATION
ROUSAR I RAJASEKA.S CEZNER V
N3 121 336
AMALGAM DECOMPOSITION .1. THEORETICAL RELATIONS FOR DECOMPOSITION KINETICS OF SODIUM AMALGAM IN TOWER DECOMPOSER
ROUSAR I CEZNER V KRAJCA M KOLARIK K
N3 121 343
AMALGAM DECOMPOSITION .3. COMPARISON OF DIFFERENT SORTS OF GRAPHITE BED FOR DECOMPOSITION OF AMALGAM IN TOWER DECONPOSER
ROUSAR I CEZNER V
N5 121 648
EXPERIMENTAL DETERMINATION AND CALCULATION OF PARASITIC CURRENTS IN BIPOLAR ELECTROLYZERS WITH APPLICATION TO CHLORATE ELECTROLYZER
ROUSAR I SEE RAJASEKA.S 121 340
ROUSSEAU DL SEE SINCLAIR MR 121 925
ROZGONYI GA DILORENZ.JV HEINLEIN E
N3 121 426
FABRICATION OF GAAS IMPATT DEVICES USING ELECTROPLATED HEAT SINKS .2. CONTROL OF WAFER CURVATURE
RUDD EJ SEE DEY AN 121 1294
RUIZ HJ WILLIAMS CS PADOVANI FA
N5 121 689
SILICON SLICE ANALYZER USING A HE-NE LASER
RYAN FM LEHMANN W FELDMAN DW MURPHY J
N11 121 1475
FINE STRUCTURE IN OPTICAL SPECTRA OF DIVALENT EUROPIUM IN ALKALINE EARTH SULFATES
RYAN MD EVANS DH
N7 121 881
EFFECT OF SODIUM IONS ON ELECTROCHEMICAL REDUCTION OF DIETHYL FUMARATE IN DIMETHYLSULFOXIDE AND ACETONITRILE
SABOUNGI ML CERISIER P
N10 121 1298
ADDITIVE TERNARY MOLTEN SALT SYSTEMS-CALCULATION OF PHASE DIAGRAMS FROM THERMODYNAMIC DATA OF LOWER ORDER SYSTEMS
SALAMA CAT SEE RHODES CSL 121 1219
SALOMON M
N7 121 884
ELECTROCHEMICAL MEASUREMENTS OF DILUTE THALLIUM AMALGAMS
SALOMON M
N12 121 1584
COMPLEX SOLUBILITIES OF SILVER HALIDES IN ACETONE-WATER MIXTURES
SALZBERG HW
N11 121 1451
ELECTROCHEMICAL OXIDATION OF NITRITE IONS AT PLATINUM, GOLD, AND GLASSY CARBON ANODES IN ACETONITRILE
SAMMELLS AF SEE KENNEDY JH 121 1
SANDLER YL
N6 121 764
ELECTROCHEMICAL SURFACE AREA METER
SANTHANA.KS SEE SCHWAKEL CD 121 345
SANTHANA.KS SEE SCHWAKEL CD 121 1033
SARD R OKINAKA Y WAGGENER HA
N1 121 62
ELECTROLESS GOLD BEAM LEAD PLATING
SARD R SEE OKINAKA Y 121 56
SATO M SEE IMAI K 121 1674
SAUL RH SEE ROCCASEC.DO 121 962
SAWYER DM SEE DIETZE W 121 1112
SAWYER DM SEE SIRTL E 121 919
SCHIEBER M SEE AVIGAL Y 121 1103
SCHIFFRI.DJ SEE INMAN D 121 770
SCHLESIN.M
N8 121 887
ULTRAVIOLET INHIBITION OF ELECTROLESS PLATING ON GLASS
SCHLESIN.M BAYLIS BKN
N11 121 1481
ULTRAVIOLET INHIBITION OF ELECTROLESS PLATING ON PLASTICS
SCHLESIN.M SEE FELDSTEI.N 121 738
SCHWAKEL CD SANTHANA.KS ELVING PJ
N3 121 349
NICOTINAMIDE AND N8-METHYLNICOTINAMIDE - ELECTROCHEMICAL REDOX PATTERN - BEHAVIOR OF FREE RADICAL, DIMERIC, AND DIHYDROPYRIDINE SPECIES
SCHWAKEL CD SANTHANA.KS ELVING PJ
N6 121 1033
ELECTROCHEMICAL REDOX PATTERNS FOR PYRIDINIUM SPECIES - 1-METHYLNICOTINAMIDE AND NICOTINAMIDE MONONUCLEOTIDE
SCHWECKE.AF SEE OKTAY S 121 912
SCHWIDT K WUTHRICH M ADZIC R YEAGER E CAHAN BD
N12 121 1610
OPTICAL AND ELECTROCHEMICAL STUDIES OF UNDERPOTENTIAL DEPOSITION OF LEAD ON GOLD EVAPORATED AND SINGLE-CRYSTAL ELECTRODES
SCHWARTZ B SEE EMMANIS F 121 1605
SCHWARTZ B SEE SPITZER SM 121 820
SCHWARTZ N SEE SILVERMA.PJ 121 550
SCHWETTN.FN SEE PRINCE JL 121 705
SCHWIDEF.F SEE KUHL C 121 1496
SEARS PG SEE REBAGAY TV 121 977
SECOR FW SEE WEININGE.JL 121 315
SECOR FW SEE WEININGE.JL 121 1541
SEDGWICK TO
N3 121 482
FIELD EFFECT MODULATED PHOTOLUMINESCENCE IN ZNO
SEDLAK JM SEE BLURTON KF 121 1315
SEITZ MA HOLLIDAY TB
N1 121 122
HIGH-TEMPERATURE DIELECTRIC BEHAVIOR OF CA-DOPED ZRO2
SEITZ MA SOKOLY TO
N1 121 163
HIGH-TEMPERATURE DIELECTRIC BEHAVIOR OF POLYCRYSTALLINE ZNO
SELIN R GRC P
N11 121 1457
SOME OBSERVATIONS ON RECHARGEABLE LITHIUM ELECTRODES IN A PROPYLENE CARBONATE ELECTROLYTE
SEVERIN PJ
N1 121 150
INFLUENCE OF PHASE SHIFT ON THICKNESS MEASUREMENTS OF SILICON EPITAXIAL LAYERS WITH A FOURIER TRANSFORM SPECTROMETER
SHABRANG M BRUCKENS.S
N11 121 1439
EQUIVALENT CIRCUIT FOR UNCOMPENSATED RESISTANCES OCCURING AT RING-DISK ELECTRODES
SHEMCHUN J SEE GUPTA K 121 110
SHIRASU Y SEE SUGAWARA K 121 1233
SHORT DW SEE AGRAWAL YK 121 354
SHUKLA RD SEE RASTOGI RP 121 1963
SIGURD D SEE LAU SS 121 1638
SILVERMA.PJ SCHWARTZ N
N4 121 550
RUTHERFORD SCATTERING ANALYSIS OF ANODIC TANTALUM-SILICON OXIDES
SILVESTE.LF ROCK PA
N2 121 251
AUTOMATIC, SPARKLESS GAS PUMP FOR GAS ELECTRODES
SILVESTE.LF ROCK PA
N4 121 510
ELECTROCHEMISTRY IN N,N-DIMETHYLFORMAMIDE .1. H2RU.PT</HCLIDMF</TLCL3S</TLXHG< CELL
SIMON AC CAULDER SM GURLUSKY PJ PIERSON JR
N4 121 463
EFFECT OF ADDITIVES ON REACTION MECHANISM OF PB-PBSO4 ELECTRODE
SIMON AC CAULDER SM
N4 121 531
INFLUENCE OF ACTIVE MATERIAL THICKNESS ON POSITIVE GRID CORROSION IN PB-ACID BATTERY
SIMON AC SEE CAULDER SM 121 1346
SIMON MT SEE MCCARTY LV 121 1372
SIMPSON J SEE MOLINE RA 121 1362
SIMPSON WI SEE MANASEVI.MN 121 967
SINCLAIR MR ROUSSEAU DL STANCAVI.JJ
N7 121 925
IRON OXIDE - INORGANIC PHOTORESIST AND MASK -TATERIAL
SINCLAIR WR SEE KANNLOTT GW 121 929
SINGH R WITT AF GATOS HC
N3 121 380
OSCILLATORY INTERFACE INSTABILITY DURING CZOCHRALSKI GROWTH OF HEAVILY DOPED GERMANIUM
SIRTL E HUNT LP SAWYER DH
N7 121 919
HIGH TEMPERATURE REACTIONS IN SILICON-HYDROGEN-CHLORINE SYSTEM
SMELTZER RK SEE CHU TL 121 159
SMELTZER WW SEE DALVI AD 121 386
SMELTZER WW SEE DAVIES M 121 543
SMELTZER WW SEE MAYER P 121 538
SMELTZER WW SEE YOUNG DJ 121 889
SMIALEK JL LOWELL CE
N8 121 800
EFFECTS OF DIFFUSION ON ALUMINUM DEPLETION AND DEGRADATION OF NIAL COATINGS
SMITH GL SEE PICKHARD.VY 121 1064
SMITH HI EFREMOW N KELLEY PL
N11 121 1503
PHOTOLITHOGRAPHIC CONTACT PRINTING OF 4000A LINEWIDTH PATTERNS
SMITH JN THOMAS S RITCHIE K
N6 121 827
AUGER ELECTRON SPECTROSCOPY DETERMINATION OF OXYGEN-SILICON RATIO IN SPIN-ON GLASS FILMS
SMITH PJ SEE KULKARNI MV 121 290
SMITH RE SEE URBACH HB 121 233
SMYRL WH NEWMAN J
N8 121 1000
MASS TRANSFER OF MINOR COMPONENTS IN A PROPAGATING CRACK
SMELLING.IR SEE DOWGIALL.EJ 121 1134

SOKOLY TO SEE SEITZ MA 121 163
SOOD DD BRAUNSTE.J
N2 121 247
LITHIUM-BISMUTH ALLOY ELECTRODES FOR THERMODYNAMIC INVESTIGATION OF MOLTEN LIF-BEF2 MIXTURES
SOULES TF MAIER MA
N3 121 407
OPTIMIZED SPECTRAL POWER DISTRIBUTIONS FOR MERCURY VAPOR LAMPS
SPENCER EG SEE THOMPSON LF 121 1500
SPINK DR VIJAYAN CP
N7 121 879
HAFNIUM ELECTROWINNING STUDIES
SPITZER SM SCHWARTZ B WEIGLE GD
N6 121 820
NATIVE OXIDE MASK FOR ZINC DIFFUSION IN GALLIUM ARSENIDE
SPITZER WG SEE KUNG JK 121 1482
STACH J TURLEY A
N5 121 722
ANOMALOUS BORON DIFFUSION IN SILICON FROM PLANAR BORON NITRIDE SOURCES
STADLER HL SEE LAUD KR 121 303
STAEHLE RW SEE MCCRIGHT RD 141 609
STAEHLE RW SEE SZKLARSK.Z 121 1146
STAEHLE RW SEE SZKLARSK.Z 121 1393
STANCAVI.JJ SEE SINCLAIR WR 121 925
STATH N SEE MESS K 121 1208
STEARNS CA KOHL PJ FRYBURG GC
N7 121 945
OXIDATIVE VAPORIZATION KINETICS OF CR2O3 IN OXYGEN FROM 1000 DEGREES TO 1300 DEGREES C
STEARNS CA SEE FRYBURG GC 121 952
STEIN HJ
N8 121 1073
GE-NITRIDE, GE-OXIDE, AND GE-OXYNITRIDE FORMATION BY ION IMPLANTATION
STERTEN A CHOUDHUR.NS
N12 121 1603
ELECTROMOTIVE FORCE MEASUREMENTS ON CELLS INVOLVING BETA-ALUMINA SOLID ELECTROLYTE
STEVENS.RK SEE VISSERS DR 121 665
STEVENSO.DA SEE LARSON WL 121 1673
STEVENSO.DA SEE MARUSKA HP 121 1202
STEWART WD SEE VORONIN VA 121 1657
STILLMAN GE SEE WOLFE CM 121 1506
STOPKO EJ SEE YIM WM 121 985
STONEHAM EB
N10 121 1382
NONAQUEOUS ELECTROLYTE FOR ANODIZING GAAS AND GAAS0.6P0.4
STORMONT RW SEE COCKS FH 121 996
STRAUMAN.ME SEE VAIDYANA.M 121 7
SUGANO T MORI Y
N1 121 113
OXIDATION OF GAAS1-XPX SURFACE BY OXYGEN PLASMA AND PROPERTIES OF OXIDE FILM
SUGANO T SEE KATODA T 121 1006
SUGAWARA K YOSHIMI T OKUYAMA M SHIMASU T
N9 121 1233
IN-SITU MONITORING OF FILM DEPOSITION USING HE-NE LASER SYSTEM .1. MEASUREMENTS OF CVD INSULATING FILM AT 6328A
SUGAWARA K YOSHIMI T OKUYAMA M HONMA Y
N9 121 1235
IN-SITU MONITORING OF FILM DEPOSITION USING HE-NE LASER SYSTEM .2. MEASUREMENTS OF POLYCRYSTALLINE SILICON FILM IN INFRARED
SUGIURA I SET MINE F 121 220
SUGIYAMA K SEE TAKAHASH.T 121 714
SULZMANN KG
N9 121 1239
VAPOR PRESSURE OF SOLID ALUMINUM BROMIDE
SULZMANN KG SEE GILBERT AG 121 632
SUZUKI M SEE NAGASIMA N 121 434
SWANSON AW UNLIG MH
N12 121 1551
EFFECT OF GASEOUS PRETREATMENT ON OXIDATION OF IRON
SWEENEY GG SEE RAICHOUD.P 121 1509
SWEET JM SEE MESS JM 121 142
SZKLARSK.Z STAEHLE RW
N9 121 1146
ELLIPSOMETRIC STUDY OF FORMATION OF FILMS ON IRON IN CHROMATE SOLUTIONS
SZKLARSK.Z STAEHLE RW
N11 121 1393
ELLIPSOMETRIC STUDY OF FORMATION OF FILMS ON IRON IN ORTHOPHOSPHATE SOLUTIONS
SZPAK S SEE KATAN T 121 787
TABEI M NARA S MATSUYAM.K
N1 121 67
METHOD FOR FORMING A PRINTED CIRCUIT BY PHOTOLYSIS OF SILVER SALT OF ORGANIC ACID
TADACHI C SEE NAKAMURA H 121 1377
TAKAHASH.T SUGIYAMA K
N5 121 714
FIBROUS GROWTH OF TANTALUM CARBIDE BY A-C DISCHARGE METHOD
TAKEI WJ SEE RAICHOUD.P 121 1228
TANAKA K SEE NAGASIMA N 121 434
TANDON KN SEE MISHRA AK 121 91
TAUBENES.R SEE DARWISH N 121 1119
TENCH DM YEAGER E
N3 121 318
REDOX COUPLE BEHAVIOR ON LITHIATED NICKEL OXIDE ELECTRODES
TERUNUMA Y SEE ARAI E 121 676
TESSEUNG ACC SEE VERTES G 121 782
THOMAS S SEE SMITH JH 121 827
THOMPSON DA SEE OSHAUGHN.TA 121 1350
THOMPSON J SEE INMAN D 121 778
THOMPSON LF FEIT ED BOWDEN MJ LENZO PV SPENCER EG
N11 121 1800
POLYMERIC RESISTS FOR X-RAY LITHOGRAPHY
THOMPSON LF SEE BOWDEN MJ 121 1620
TIEDEMAN.W
N10 121 1388
ELECTROCHEMICAL BEHAVIOR OF FLUOROGRAPHITE FLECTRODE IN NONAQUEOUS MEDIA
TIEN TY SEE LAUD KR 121 303
TILAK BV SEE ETTEL VA 121 867
TOBIAS CW SEE JORNE J 121 994
TOLLE MJ SEE MOLLERS F 121 1180
TOLLIVER DL SEE ARMSTRON.WE 121 307
TONCZUK Z SEE VISSERS DR 121 665
TOZER EW SEE BRIGHAM RJ 121 1192
TRACHTEN.I SEE JASINSKI R 121 363
TRACHTEN.I SEE JASINSKI R 121 1675
TRASATTI S MILES MH YATES CA
N12 121 1609
HYDROGEN AND NITROGEN EVOLUTION REACTIONS IN ACID LIQUID AMMONIA
TROUTMAN MA SEE KULKARNI MV 121 280
TSUIKI M SEE UENO Y 121 202
TU KN SEE CAMPBELL DR 121 1081
TURETZKY MN JENKINS JB FRASER HR
N8 121 1098
VICKERS MICROHARDNESS CHARACTERIZATION OF SINTERED BOROSILICATE FILMS
TURLEY A SEE STACH J 121 722
TVARUSKO A
N5 121 661
MEASUREMENT OF CURRENT DISTRIBUTION ON WIRE
UENO Y KIDOKORO H TSUIKI M
N2 121 202
NUCLEATION OF COPPER ELECTRODEPOSITS ON THIN NICKEL FILMS OF EVAPORATED COPPER
UHLIG MM SEE KOIZUMI T 121 1137
UHLIG MM SEE SWANSON AW 121 1551
UNTERBERG.OF BRUCKENS.S
N3 121 360
DISSOLUTION-REDEPOSITION MECHANISM FOR ROUGHENING OF PLATINUM ELECTRODES BY CYCLIC POTENTIAL PROGRAMS
URBACH HB ADAMS LG SMITH RE
N2 121 233
RADIOMETRIC STUDY OF CARBON DIOXIDE ADSORPTION ON PLATINUM
USUI S SEE KANEKO K 121 556
VAIDYANA.M STRAUMAN.ME JAMES WJ
N1 121 7
POLARIZATION CHARACTERISTICS AND ANODIC DISINTEGRATION OF BERYLLIUM IN NONAQUEOUS SOLUTIONS
VAIDYANA.M NARASAGO.RA OKEEFE TJ JAMES WJ JOHNSON JB
N7 121 876
FILM FORMATION ON ANODICALLY POLARIZED LEAD
VALENTIN.RS SEE CLARK GJ 121 618
VALERIOT.ER GALLOP LD
N10 121 1245
HIGH PRESSURE EFFECTS ON EMF OF SEAWATER BATTERY ELECTRODES IN CHLORIDE ELECTROLYTE
VALLET CE BRONSTEI.HR BRAUNSTE.J
N11 121 1429
ELECTROMIGRATIONAL DEPLETION SEDC CHRONOPOTENTIOMETRY TEMPERATURE DEPENDENCE OF DIFFUSION IN MOLTEN BEF2-LIF
VANDAM HT PONJEE JJ
N12 121 1555
ELECTROCHEMICALLY GENERATED COLORED FILMS OF INSOLUBLE VIOLOGEN RADICAL COMPOUNDS
VANHANDE.GJ BLUMENTH.RN
N9 121 1198
TEMPERATURE AND OXYGEN PRESSURE DEPENDENCE OF IONIC TRANSFERENCE NUMBER OF NONSTOICHIOMETRIC CEO2-X
VANHANDL.HR SEE MYERS H 121 1526
VANHOOF LAH SEE ALBERS W 121 1341
VARJIAN R SEE ALKIRE R 121 622
VECHT A SEE WAITE MS 121 109
VENKATAD.AS BAUER HH WAGNER WF
N2 121 249
POTENTIOSTATIC ANODIC SYNTHESIS OF PERRAZEVIC
VERMILYE.DA
N9 121 1190
MORPHOLOGY OF TRANSGRANULAR STRESS CORROSION CRACK IN TYPE 304 STAINLESS STEEL TESTED IN PH 2.8, H2S84 AT 289 DEGREES C
VERSTEGE.JM
N12 121 1623
SURVEY OF A GROUP OF PHOSPHORS, BASED ON HEXAGONAL ALUMINATE AND GALLATE HOST LATTICES
VERSTEGE.JM RADIELOV.O VRENKEN LE
N12 121 1627
NEW GENERATION OF DELUXE FLUORESCENT LAMPS, COMBINING AN EFFICACY OF 80 LUMENS/W OR MORE WITH A COLOR RENDERING INDEX OF APPROXIMATELY 85
VERSTEGE.JM
N12 121 1631
LUMINESCENCE OF TB3+ IN BORATES OF COMPOSITION R2ZEB3O3Z RX # BA, SR, CA-Z # CA, MGX
VERTES G HORANYI G HOBBS DS TESEUNG ACC
N6 121 782
ANODIC OXIDATION OF HYDROGEN ON PLATINIZED TUNGSTEN OXIDES .2. MECHANISM OF H2 OXIDATION ON PLATINIZED WO3 ELECTRODES
VIELSTIC.W SEE GRANBOW L 121 770
VIJAYAN CP SEE SPINK DR 121 879
VIJH AK SEE BELANGER A 121 225
VISSERS DR TONCZUK Z STEUNENB.RK
N5 121 665
PRELIMINARY INVESTIGATION OF HIGH TEMPERATURE LITHIUM-IRON SULFIDE SECONDARY CELLS
VITANOV T POPOV A SUDEVSKI E
N2 121 287
MECHANISM OF ELECTROCRYSTALLIZATION
VITANOV T SEE BACHMANN KJ 121 1606
VOGT H
N12 121 1606
MUTUAL EFFECT OF CURRENT DENSITY, PH, TEMPERATURE, AND HYDRODYNAMIC FACTORS ON CURRENT EFFICIENCY IN CHLORATE CELL PROCESS
VONNEIDA AR SEE CARUSO R 121 1332
VONNEIDA AR SEE JORDAN AS 121 153
VORKAPIC LZ DRAZIC DM DESPIC AR
N11 121 1305
CORROSION OF PURE AND AMALGAMATED ZINC IN CONCENTRATED ALKALI HYDROXIDE SOLUTIONS
VORONIN VA STEWART WD MARSHALL GW WAGNER JB HACKSEY HM HOLONYAK N
N12 121 1657
SCANNING ELECTRON MICROSCOPE STUDY OF INI-XGAXP
VRENKEN LE SEE VERSTEGE.JM 121 1627
WADA K SEE IKEZAKI K 121 991
WAGGENER HA SEE SARO R 121 62
WAGNER JB SEE GOLDMAN J 121 1310
WAGNER JB SEE VORONIN VA 121 1657
WAGNER S PCVILONI.EI
N11 121 1487
DIFFUSION OF GALLIUM THROUGH SILICON DIOXIDE FILMS INTO SILICON
WAGNER S SEE MCCAUGHA.DV 121 724
WAGNER WF SEE VENKATAD.AS 121 249
WAITE MS VECHT A
N1 121 109
GREEN DIRECT CURRENT ELECTROLUMINESCENCE FROM LEAD-DOPED ZINC SULFIDE POWDER PHOSPHORS
WAITE MS
N9 121 1122
LUMINESCENCE OF ALKALI-ALKALINE EARTH-PHOSPHATES ACTIVATED WITH EU2S
WALES CP
N1 121 17
OXIDATION OF SILVER ELECTRODES IN CSOH SOLUTIONS
WALES CP
N6 121 727
REDUCTION OF SILVER OXIDE ELECTRODE IN CSOH SOLUTIONS
WANG CC DOUGHERT.FC ZANZUCCH.PJ MCFARLAN.SH
N6 121 871
EPITAXIAL GROWTH AND PROPERTIES OF GAAS ON MAGNESIUM ALUMINATE SPINEL
WANG EY BARAONA CR BRANDHOR.HW

JOURNAL ARTICLE SUBJECT INDEX

TO FIND ARTICLES ON A SPECIFIC TOPIC:

1. Locate any one of the words (Primary Terms) that describes the topic. If you want every title that includes that primary term, select only the articles marked with an arrow (>). This eliminates unnecessary lookups.
2. To narrow selection, use any of the other words (Co-Terms) listed below that Primary Term. When using co-terms always disregard arrows.
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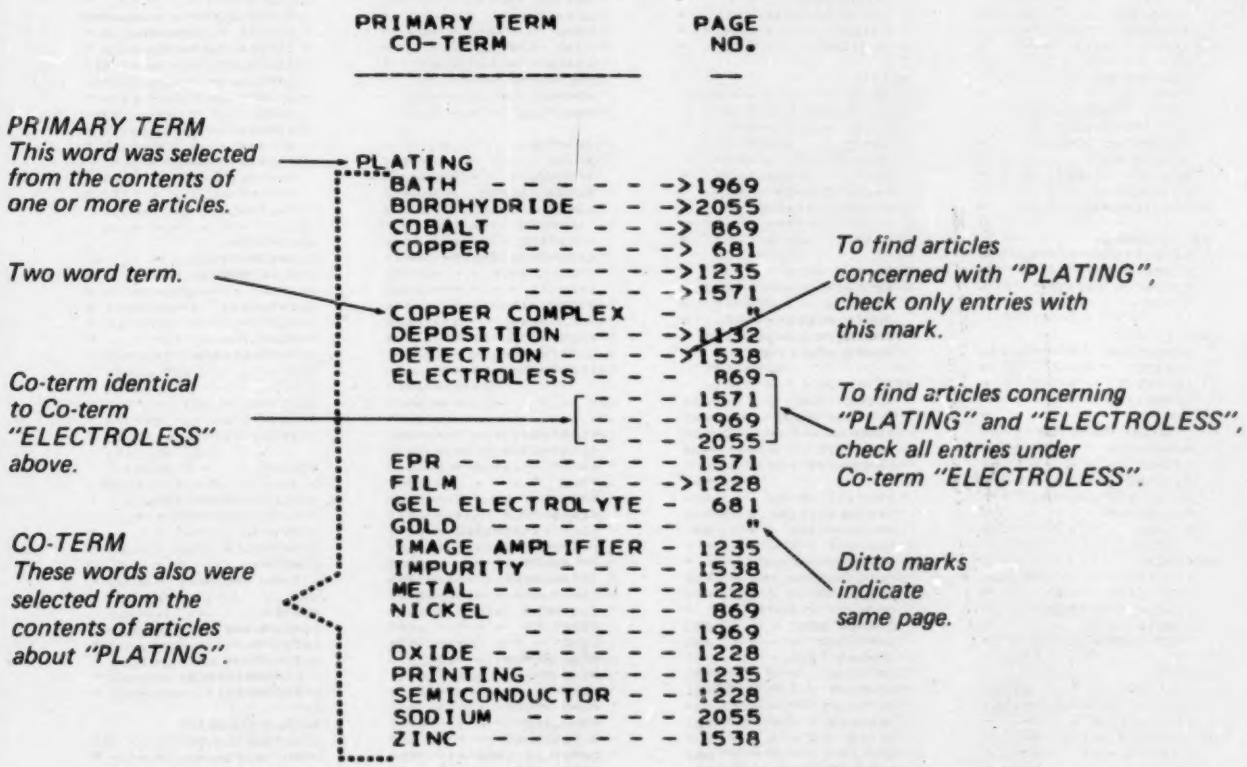
4. The PAGE NO. refers to the beginning page in the Journal on which the article containing the keyword appears.


PRIMARY TERM
CO-TERM
PAGE NO.
PRIMARY TERM
This word was selected from the contents of one or more articles.
Two word term.
Co-term identical to Co-term "ELECTROLESS" above.
CO-TERM
These words also were selected from the contents of articles about "PLATING".
PLATING
BATH - - - - - - ->1969
BOROHYDRIDE - - ->2055
COBALT - - - - - -> 869
COPPER - - - - - -> 681
- - - - - ->1235
- - - - - ->1571
COPPER COMPLEX - "
DEPOSITION - - ->1132
DETECTION - - - ->1538
ELECTROLESS - - - 869
- - - 1571
- - - 1969
- - - 2055
EPR - - - - - - - - 1571
FILM - - - - - - ->1228
GEL ELECTROLYTE - 681
GOLD - - - - - - - "
IMAGE AMPLIFIER - 1235
IMPURITY - - - - 1538
METAL - - - - - - 1228
NICKEL - - - - - 869
- - - - - 1969
OXIDE - - - - - - 1228
PRINTING - - - - 1235
SEMICONDUCTOR - - 1228
SODIUM - - - - - 2055
ZINC - - - - - - 1538
To find articles concerned with "PLATING", check only entries with this mark.
To find articles concerning "PLATING" and "ELECTROLESS", check all entries under Co-term "ELECTROLESS".
Ditto marks indicate same page.

PRIMARY TERM / CO-TERM	PAGE NO.
ABSORPTION	
ACTIVATION	-> 434
ANALYSIS	"
ANNEALING	->1073
CARRIER	->1482
COMPOUND	-> 586
CONCENTRATION	434
	1482
CONDUCTIVITY	586
CRYSTAL QUALITY	->1496
DRUDE ZENER	1482
ELECTRIC	586
FORMATION	"
GAAS	1482
GERMANIUM NITRIDE	1073
GERMANIUM OXIDE	"
GERMANIUM OXYNIT.	"
IMPLANTATION	"
INFRARED	434
	1073
	1482
INTERACTION	434
ION	1073
ION IMPLANTATION	586
KRAMERS KRONIG	1496
MOISTURE	434
OPTICAL	586
OPTICAL INTERFER.	1496
PHOSPHORUS	434
PSG FILM	"
REFLECTIVITY	1482
REFRACTIVE INDEX	1496
RESISTANCE	434
SEMICONDUCTOR	1482
SILICON CARBIDE	586
SILICON DOPED	1482
SILICON FILM	1496
THIN FILM	"
WATER	434
AC	
ALKALINE	-> 375
CATHODE	"
CONDUCTIVITY	"
DC	"
DISCHARGED	"
IMPEDANCE	"
IONIC CONDUCTANC.	"
LECLANCHE CELL	"
MANGANESE DIOXIDE	"
MEASUREMENT	"
MERCURY OXIDE	"
RESISTANCE	"
UNDISCHARGED	"
AC DISCHARGE	
DEPOSITION	-> 714
FIBER GROWTH	"
TANTALUM CARBIDE	"
VAPOR	"
ACCELERATE	
CORROSION	-> 778
CREVICE	"
EUTECTIC	"
FORMATION	"
ION	"
LITHIUM CHLORIDE	"
MONOLAYER	"
NICKEL	"
PITTING	"
POTASSIUM CHLORI.	"
REDUCTION	"
SILVER	"
ACCEPTOR	
EPITAXY	->1208
HALL DATA	"
INDIUM PHOSPHIDE	"
LIQUID PHASE	"
PHOTOLUMINESCENCE	"
ACETONE	
CONSTANT	->1584
CRYSTAL GROWTH	->1563
DISSOLUTION	"
DUTERIUM OXIDE	"
ELECTROLYTES	"
FORMAMIDE	"
FORMATION	-> 1584
MIXTURE	"
POTENTIAL	1563
PRECIPITATION	"
PRODUCT	1584
SILVER HALIDES	"
SOLUBILITY	"
TRANSIENT	1563
ACETONE (CONTD)	
WATER	1584
ACETONITRILE	
ACTIVATION	-> 780
CARBON	->1451
DIETHYLFUMARATE	-> 681
DMSO	"
ELECTRO OXIDATION	1451
ELECTROCATALYST	780
ELECTROHYDRODIME.	681
FORMIC ACID	780
GOLD	1451
ION PAIRS	681
MERCURY	780
NITRITE IONS	1451
OXIDATION	780
PLATINUM	1451
REDUCTION	681
SODIUM ION	"
VOLTAMMETRY	"
ACETONITRILE	
BATTERY	-> 851
COPPER	"
SECONDARY BATTERY	"
ACID	
AMMONIA	->1609
EVOLUTION	"
HYDROGEN	"
LIQUID	"
NITROGEN	"
REACTION	"
ACID BATH	
AMINE	->1023
BORANE	"
COBALT	"
DEPOSITION	"
ELECTROLESS	"
HYPOPHOSPHITE	"
NICKEL	"
PLATING	"
ACIDIC	
ANODE	->1141
CHLORIDE	"
COLD	"
GRAIN	"
MICROSCOPY	"
NICKEL	"
POLARIZATION	"
POTENTIOSTATIC	"
SIZE	"
WORK	"
ACOUSTIC WAVE	
CONTACT PRINT	->1503
MASK	"
PHOTO RESIST	"
PHOTOLITHOGRAPHY	"
SUBMICRON LINE	"
ACTIVATION	
ABSORPTION	-> 434
ACETONITRILE	-> 780
AMMONIA	-> 459
ANALYSIS	434
CONCENTRATION	"
	459
CONTAMINATION	-> 681
DECOMPOSITION	459
DEFORMATION	681
DEPOSIT	"
DICHLOROSILANE	"
ELECTROCATALYST	780
ELECTRON	459
ENTROPY	"
FORMIC ACID	780
INFRARED	434
INTERACTION	"
LITHIUM	459
MERCURY	780
MOISTURE	434
NEUTRON	681
OXIDATION	780
OXYGEN	681
PHOSPHORUS	434
POLYCRYSTALLINE	681
PSG FILM	434
RESISTANCE	"
SILICON FILM	681
SOLVATED	459
VAPOR	681
WATER	434
ACTIVE	
BATTERY	-> 531
CHLORALKALI CELL	> 220
CHLORINE	"
CONSUMPTION	"
CORROSION	"
	531
GRAPHITE ANODE	220
GRID	531
LEAD ACID	"
LEAD ANTIMONY	"
MATERIAL	"
PH	220
PROTECTION	531
THICKNESS	"
ACTIVITY	
AMALGAMS	-> 884
ARGON OXYGEN	-> 354
CHROMIUM	-> 543
COEFFICIENT	884
CONTROL	354
COULOMETRY	"
DILUTE	884
ELECTRODE	354
METAL	543
MIXTURE	354
NICKEL	543
OXYGEN	354
	543
PLATINUM	354
POTENTIAL	884
POTENTIOSTAT	354
STANDARD	884
SYSTEN	543
THALLIUM	884
TITRATION	354
ZIRCONIA	"
ADDITIVE	
BARIUM SULFATE	-> 463
ELECTRODE	"
LEAD	"
LEAD SULFATE	"
LIGNIN	"
MECHANISM	"
MORPHOLOGY	"
REACTION	"
ADSORPTION	
ANION	-> 987
ARSENIC	-> 609
BUROSILICATE	-> 676
CARBON DIOXIDE	-> 233
CARBONYL	"
CHLORINE	-> 848
CHRONOCOULOMETRY	>1421
CONDUCTANCE	->1570
DEPOSIT	676
DEPOSITION	-> 474
DIFFUSION	676
ELECTROCHEMISTRY	> 764
ELECTROCRYSTALLI.	>1167
ELECTRODE	474
	1167
	1421
	1570
ELECTROLYTE	987
ELECTROSORPTION	233
ENTRY	609
FILM	1167
GALVANIC CELL	764
GLASS FILM	676
GOLD EVAPORATED	474
HYDROCARBON	987
HYDROGEN	609
INSTRUMENT	764
ION	1167
ISOTHERM	474
KINETICS	1167
LEAD	474
MEASUREMENT	1570
MERCURY	1421
METAL	1167
MONOHYDRATE	987
MONOLAYER	1167
OXIDATION	987
PARTICLE SIZE	764
PERMEATION	609
PLATINUM	233
POTENTIAL	609
PROPANE	987
RADIOMETRY	233
REDUCED	"
REFLECTANCE	474
RHODIUM	1421
SILANOL	676
ABSORPTION (CONTD)	
SINGLE CRYSTAL	474
SPECTROSCOPY	"
	676
STEEL	609
STRUCTURE	1167
SURFACE	848
	1570
SURFACE AREA	764
THERMODYNAMICS	1167
THIN FILM	1570
TITANIUM	848
TRIFLUOROMETHANE.	987
UNDERPOTENTIAL	474
VAPOR	676
VOLTAMMETRY	1421
WATER	676
AERATION	
CORROSION	-> 183
DIFFERENTIAL	"
FILM	"
METAL	"
MOISTNESS	"
PASSIVATING	"
THICKNESS	"
VARIABLE	"
AEROSOL	
DEPOSIT	-> 484
ELECTRICAL	"
FORMALDEHYDE	"
HYDRAZINE	"
PLATING	"
RESISTIVITY	"
SILVER	"
SPRAY	"
AGENT	
CATHODE	->1013
CHELATING	"
COEFFICIENT	-> 779
COPPER FLUOROBOR.	"
COPPER SULFATE	"
COVERAGE	1013
DIFFUSION	779
ELECTROLYTE	"
IRON	1013
KINETIC	779
ORGANIC	"
PARAMETER	"
PASSIVATED	1013
POTENTIAL	"
PULSING	"
AGITATION	
BOROHYDRIDE	-> 56
ELECTROLESS	"
GOLD	"
IMPURITY	"
PLATING	"
PROCEDURE	"
THICKNESS	"
AIR	
NICKEL ALLOY	-> 118
OXIDATION	"
WATER VAPOR	"
ALCOHOLS	
CELL	->1048
ELECTROCHEMISTRY	"
ELECTRODE	"
HEXANOL	"
HYDROGEN	"
NORMAL	"
THALLIUM	"
ALKALI	
ALKALINE	->1122
EARTH	"
EUROPIUM	"
LUMINESCENCE	"
PHOSPHATES	"
ALKALI CHLORIDE	
CERIUM CHLORIDE	-> 991
EMF	"
MEASUREMENT	"
MIXTURE	"
MOLTEN SALT	"
NUMBERS	"
TRANSFERENCE	"
ALKALI HYDROXIDE	
AMALGAMATE	->1385
CONCENTRATE	"

PRIMARY TERM
CO-TERM — PAGE NO.

ALKALI HYDROXIDE (CONTD)
CORROSION - - - - 1385
ZINC - - - - - - "
ZINC OXIDE - - - "

ALKALI METAL
ALUMINUM CHLORIDE> 994
CARBONATE - - - - "
CHLORIDE - - - - "
COEFFICIENT - - - "
CURRENT DENSITY - "
ELECTRODE - - - - "
EXCHANGE - - - - "
KINETICS - - - - "
PROPYLENE - - - - "
TRANSFER - - - - "

ALKALINE
AC - - - - - - -> 375
ALKALI - - - - ->1122
ANODE DISSOLUTION> 605
BENZOTRIAZOLE - - "
CATHODE - - - - - 375
CHLORIDE - - - - 605
CONDUCTIVITY - - 375
CORROSION - - - - 605
CRYSTAL - - - - ->1475
DC - - - - - - - 375
DISCHARGED - - - "
DIVALENT - - - - 1475
EARTH - - - - - - 1122
- - - - - - 1475
EUROPIUM - - - - 1122
- - - - 1475
IMPEDANCE - - - - 375
INHIBITION - - - 605
IONIC CONDUCTANCE 375
IRON - - - - - - 605
LECLANCHE CELL - 375
LUMINESCENCE - - 1122
- - 1475
MANGANESE DIOXIDE 375
MEASUREMENT - - - "
MERCURY OXIDE - - "
OPTICAL SPECTRA - 1475
PHOSPHATES - - - 1122
RESISTANCE - - - 375
SOLUTION - - - - 605
STRUCTURE - - - - 1475
SULFATES - - - - "
UNDISCHARGED - - 375

ALLOY
ALUMINIDE - - - ->1051
ALUMINUM - - - -> 800
- - - ->1129
- - - ->1245
ALUMINUM COPPER -> 718
AMORPHOUS - - - -> 776
ATMOSPHERE - - -> 889
BATTERY - - - - - 1245
- - - - ->1526
BATTERY ANODE - -> 734
BERYLLIUM - - - -> 247
BISMUTH - - - - - "
- - - - - 1526
BUFFER - - - - - 1245
CALCIUM - - - - - 1526
CALCIUM LEAD - - "
CARBONATE - - - - 734
CHARACTERIZATION > 416
CHLORIDE - - - - 1245
COATING - - - - - 800
- - - - - 1051
COBALT IRON - - -> 538
- - - 889
COBALT RHENIUM - 776
COBALTOUS IRON - 538
COPPER - - - - ->1137
CORROSION - - - - 1129
CURVE - - - - - - 1137
DEGRADATION - - - 800
DEPLETION - - - - "
DIFFUSION - - - - 538
- - - - 734
- - - - 800
- - - - 1051
DIFFUSION MODEL -> 386
ELECTRODE - - - - 247
- - - - 734
ELECTRODEPOSITION 776
EMF - - - - - - - 1245
FLUORIDE - - - - 247
GAAS - - - - - - 416
GRID - - - - - - - 1526
GROWTH - - - - - 416
- - - - - 538

ALLOY (CONTD)
HETEROJUNCTION - 416
HIGH PRESSURE - - 1245
HISTOPATHOLOGY - 1129
HYDROGEN SULFIDE 889
IMPLANTABLE - - - 1129
INTERMETALLIC - - 734
INVITRO - - - - - 1129
INVIVO - - - - - "
KINETICS - - - - 889
- - - - 1051
LATTICE MATCH - - 416
LITHIUM - - - - - 247
LITHIUM MAGNESIUM 734
LPE - - - - - - - 416
MAGNESIUM - - - - 1129
- - - - 1245
MICROSTRUCTURE - 718
MOLTEN SALT - - - 247
NICKEL - - - - - 800
- - - - - 1051
- - - - - 1137
NICKEL IRON - - - 386
NICKEL OXIDE - - "
OXIDATION - - - - "
- - - - 718
- - - - 800
OXIDE - - - - - - 538
PACK - - - - - - 1051
PARABOLIC - - - - 889
PASSIVITY - - - - 1137
PITTING - - - - - "
POLARIZATION - - "
POTENTIAL - - - - "
POTENTIOSTATIC - "
POWER - - - - - - 1129
PROPYLENE - - - - 734
PROTECTIVE - - - 1051
SEAWATER - - - - 1245
SODIUM CHLORIDE - 1137
SOURCE - - - - - 1129
SPALLING - - - - 800
SULFIDATION - - - 889
SUPERALLOY - - - 800
THERMODYNAMICS - 1051
TIN - - - - - - - 1526
TWO PHASE - - - - 718
ZINC - - - - - - 1129

ALUMINA
BOND - - - - - -> 107
BONDING - - - - - "
COPPER - - - - - "
ELECTROLESS - - - "
METALLIZATION - - "
MOLTEN ALKALI - - "
SURFACE - - - - - "

ALUMINATE
CANDOLUMINESCENCE> 142
EPITAXY - - - - -> 571
GALLIUM ARSENIDE "
GROWTH - - - - - "
LANTHANUM - - - - 142
MAGNESIUM - - - - 571
PHOSPHORS - - - - 142
SPINEL - - - - - 571
TRANSITION ION - 142
WILLEMITE - - - - "
ZINC PHOSPHATE - , "

ALUMINATES
GALLATE - - - - ->1623
HEXAGONAL - - - - "
HOST LATTICE - - "
LAMP - - - - - - "
NEW - - - - - - - "
PHOSPHORS - - - - "
RARE EARTH - - - "

ALUMINIDE
ALLOY - - - - - ->1051
COATING - - - - - "
DIFFUSION - - - - "
KINETICS - - - - "
NICKEL - - - - - "
PACK - - - - - - "
PROTECTIVE - - - "
THERMODYNAMICS - "

ALUMINUM
ALLOY - - - - - -> 800
- - - - - ->1129
- - - - - ->1245
ALUMINUM CHLORIDE> 983
ALUMINUM SELINIDE> 327
ANODE - - - - - ->1271

ALUMINUM (CONTD)
ANODE - - - - - ->1281
ANODE FILM - - -> 268
ANODIZATION - - - 983
ANTIMONIDE - - ->1662
ARSENIDE - - - - "
BARIUM - - - - -> 137
BATTERY - - - - - 1245
BAYERITE - - - ->1322
BROMIDE - - - - ->1239
BUFFER - - - - - 1245
CALCIUM - - - - - 137
CAPACITOR - - - -> 583
CHLORIDE - - - - 268
- - - - 1245
- - - - 1271
CHLORDALUMINATE -> 773
CHRONOPOTENTIOME. "
COATING - - - - - 800
COPPER - - - - - 327
- - - - -> 829
CORROSION - - - - 583
- - - - 1129
CRYSTALLIZATION ->1509
DEGRADATION - - - 800
DEPLETION - - - - "
DIFFRACTION - - -> 430
DIFFUSION - - - - 800
DOPING - - - - - 829
- - - - - 1509
ELECTRICAL - - - 829
ELECTRODE - - - - 983
ELECTROLYTE - - - 583
ELECTRON - - - - 268
EMF - - - - - - - 1245
ETCHABILITY - - - 583
EUROPIUM - - - - 137
FUSED - - - - - - 983
GALLIUM - - - - - 137
- - - - - 1509
- - - - - 1662
GROUP II-VI - - - "
GROUP III-V - - - "
GROWTH - - - - - 268
- - - - ->1228
- - - - - 1322
HALIDES - - - - - 773
HIGH PRESSURE - - 1245
HISTOPATHOLOGY - 1129
HYDROLYSIS - - - 1322
HYDROTHERMAL - -> 303
IMPLANTABLE - - - 1129
INDIUM - - - - - 1662
INVITRO - - - - - 1129
INVIVO - - - - - "
ION - - - - - - - 983
ION IMPLANT - - - 1281
IRON - - - - - - 583
LATTICE - - - - - 1662
LITHIUM - - - - - 303
LUMINESCENCE - - "
MAGNESIUM - - - - 1129
- - - - 1245
MANGANOUS - - - - 303
MASKING - - - - - 1509
MELT - - - - - - 773
METAL ATOMS - - - 1281
MICROSEGREGATION 583
MISCIBILITY GAP - 1662
MOBILITY - - - - 1281
MOLTEN - - - - - 773
- - - - - 983
NICKEL - - - - - 800
NITRATE - - - - - 1271
NUCLEATION - - - 1322
OPACITY - - - - - 268
OPTICAL - - - - - 829
ORTHOSILICATE - - 303
OXIDATION - - - - 773
- - - - 800
- - - - 1281
- - - - 1509
OXIDE FILM - - - 1322
PARAMETER - - - - 1662
PASSIVATION - - - 1509
PHOSPHIDE - - - - 1662
PHOSPHOR - - - - 303
PHOSPHORUS - - - 1509
PHOTOLUMINESCENCE 137
PITTING - - - - - 268
- - - - - 1271
PLANAR JUNCTION - 1509
POWER - - - - - - 1129
PRECIPITATION - - 583
PROPERTIES - - - 829
PSEUDOBINARY - - 1662
PSEUDOBOEHMITE - 1322

ALUMINUM (CONTD)
QUARTZ - - - - - 1228
REACTION - - - - 430
RUTHERFORD - - - 1281
SALT - - - - - - 983
SEAWATER - - - - 1245
SEGREGATION - - - 1509
SEMICONDUCTOR - - 137
- - - 1662
SILICA - - - - - 430
SILICON - - - - - 1228
SODIUM CHLORIDE - 983
SOLID - - - - - - 1239
SOLID SOLUTION - 327
- 1662
SOLUTION - - - - 1271
SOURCE - - - - - 1129
SPALLING - - - - 800
STRAINING - - - - 1271
STRONTIUM - - - - 137
SUBSTRATE - - - - 430
SUBVALENT - - - - 983
SULFIDE - - - - - 829
SUPERALLOY - - - 800
SYNTHESIS - - - - 137
THERMODYNAMICS - 1228
TRANSPORT - - - - "
TUNNEL - - - - - 583
VAPOR PRESSURE - 1239
WHISKER - - - - - 1228
X RAY - - - - - - "
YTTERBIUM - - - - 137
ZINC - - - - - - 1129
ZINC SELINIDE - - 327
ZINC SULFIDE - - "

ALUMINUM CHLORIDE
ALKALI METAL - -> 994
ALUMINUM - - - -> 983
ANODIZATION - - - "
CARBONATE - - - - 994
CHLORIDE - - - - "
COEFFICIENT - - - "
COPPER - - - - -> 212
CURRENT DENSITY - 994
ELECTRODE - - - - 983
- - - - 994
EXCHANGE - - - - "
FUSED - - - - - - 983
FUSED SALT - - - 212
ION - - - - - - - 983
IRON - - - - - - 212
KINETICS - - - - 994
MELT - - - - - - 212
METAL ION - - - - "
MOLTEN - - - - - "
POLAROGRAPHY - - 212
PROPYLENE - - - - 994
SALT - - - - - - 983
SILVER - - - - - 212
SODIUM CHLORIDE - "
- 983
SUBVALENT - - - - "
SYSTEM - - - - - 212
TRANSFER - - - - 994
VOLTAMMETRY - - - 212

ALUMINUM COPPER
ALLOY - - - - - -> 718
MICROSTRUCTURE - "
OXIDATION - - - - "
TWO PHASE - - - - "

ALUMINUM FILM
ANODE OXIDATION -> 400
ENVIRONMENT - - - "
IMPEDANCE - - - - "
PH - - - - - - - "
POROSITY - - - - "

ALUMINUM OXIDE
ANNEALING - - - ->1465
ANODE FILM - - - "
ANODE OXIDE - - ->1019
CHARGE MOTION - -> 700
COMPOSITE - - - - 1019
CONTAMINATION - - 700
ELECTROETCH - - - 1465
FILM - - - - - - 1019
GRAVIMETRY - - - "
HYDROUS - - - - - "
POLARIZATION - - 700
PSEUDOBOEHMITE - 1019
RADIOTRACER - - - "
SILICON DIOXIDE - 700
SODIUM - - - - - "
SURFACE GAIN - - 1465

PRIMARY TERM / CO-TERM	PAGE NO.
ALUMINUM OXIDE (CONTD)	
TRANSFORMATION - 1465	
ALUMINUM SELINIDE	
ALUMINUM - - - -> 327	
COPPER - - - - - "	
SOLID SOLUTION - "	
ZINC SELINIDE - - "	
ZINC SULFIDE - - "	
AMALGAN	
COMPARISON - - -> 343	
CRUSHED - - - - - "	
DECOMPOSITION - -> 337	
- -> 340	
- - 343	
GRAPHITE BED - - "	
RATE - - - - - - 340	
SODIUM - - - - - 337	
SODIUM HYDROXIDE 340	
343	
TOWER - - - - - - 337	
- - - - - - 340	
- - - - - - 343	
AMALGAMATE	
ALKALI HYDROXIDE >1385	
CONCENTRATE - - - "	
CORROSION - - - - "	
ZINC - - - - - - "	
ZINC OXIDE - - - "	
AMALGAMS	
ACTIVITY - - - -> 884	
COEFFICIENT - - - "	
DILUTE - - - - - "	
POTENTIAL - - - - "	
STANDARD - - - - "	
THALLIUM - - - - "	
AMINE	
ACID BATH - - - ->1023	
BORANE - - - - - "	
COBALT - - - - - "	
DEPOSITION - - - "	
ELECTROLESS - - - "	
HYPOPHOSPHITE - - "	
NICKEL - - - - - "	
PLATING - - - - - "	
AMINES	
CATION RADICAL -> 378	
HOFMANN LOEFFLER "	
OXIDATION - - - - "	
SECONDARY - - - - "	
AMMONIA	
ACID - - - - - ->1609	
ACTIVATION - - -> 459	
BEHAVIOR - - - -> 962	
COEFFICIENT - - -> 230	
CONCENTRATION - - 459	
DECOMPOSITION - - "	
DIODES - - - - - 962	
ELECTRON - - - - 459	
EMITING - - - - - 962	
ENTROPY - - - - - 459	
EPITAXY - - - - - 962	
EVOLUTION - - - - 230	
- - - - 1609	
EXCHANGE CURRENT 230	
GAP - - - - - - - 962	
HYDROGEN - - - - 230	
- - - - 1609	
IMPURITY - - - - 962	
LIGHT - - - - - - "	
LIQUID - - - - - 230	
- - - - - 1609	
LIQUID PHASE - - 962	
LITHIUM - - - - - 459	
NITROGEN - - - - 230	
- - - - 1609	
NITROGEN DOPING - 962	
OVERVOLTAGE - - - 230	
REACTION - - - - 1609	
SOLVATED - - - - 459	
SOURCE - - - - - 962	
TAFEL SLOPE - - - 230	
TRANSFER - - - - "	
AMMONIUM	
BIPOLAR - - - - ->1215	
BROMIDE - - - - -> 977	
CHEMICAL - - - - 1215	
CONDUCTANCE - - - 977	
DIMETHYLFORMAMIDE "	
ELECTROLYTE - - - "	
AMMONIUM (CONTD)	
ETCHANT - - - - - 1215	
GALLIUM ARSENIDE "	
HYDROGEN PEROXIDE "	
HYDROXIDE - - - - "	
ISOTHIOCYANATE - 977	
NICKEL - - - - - "	
NONAQUEOUS - - - "	
POTASSIUM - - - - "	
REMOVAL - - - - - 1215	
SELECTIVE - - - - "	
SILICON DIOXIDE - "	
SOLUTION - - - - 977	
TETRABUTYL - - - "	
TRANSISTOR - - - 1215	
VISCOSITY - - - - 977	
AMMONOLYSIS	
CHARACTERIZATION > 159	
CRYSTAL GROWTH - "	
GALLIUM - - - - - "	
GALLIUM NITRIDE - "	
SAPPHIRE - - - - "	
SEMICONDUCTOR - - "	
AMORPHOUS	
ALLOY - - - - - -> 776	
COBALT RHENIUM - "	
ELECTRODEPOSITION "	
AMORPHOUSNESS	
ANODIZATION - - -> 394	
SPUTTERING - - - "	
THIN FILM - - - - "	
TIN - - - - - - - "	
ANALYSIS	
ABSORPTION - - -> 434	
ACTIVATION - - - "	
CADMIUM - - - - ->1366	
CONCENTRATION - - 434	
CRYSTAL - - - - ->1671	
CRYSTAL GROWTH - 1366	
DISTRIBUTION - - "	
GROWING - - - - - 1671	
INFRARED - - - - 434	
INTERACTION - - - "	
MOISTURE - - - - "	
PHOSPHORUS - - - "	
PSG FILM - - - - "	
RESISTANCE - - - "	
TELLURIDE - - - - 1366	
TEMPERATURE - - - "	
TRAVELING HEATER "	
WATER - - - - - - 434	
ZONE LEVELING - - 1671	
ZONE MELTING - - "	
ANALYTICAL	
BORON - - - - - -> 972	
DETERMINATION - - "	
POLYCRYSTALLINE - "	
SHEET RESISTIVITY "	
SILICON FILM - - "	
ANALYZER	
DEFECT - - - - -> 689	
HELIUM - - - - - "	
LASER - - - - - - "	
NITROGEN - - - - "	
SILICON - - - - - "	
SLICE - - - - - - "	
SURFACE - - - - - "	
ANION	
ADSORPTION - - -> 987	
ELECTROLYTE - - - "	
HYDROCARBON - - - "	
MONOHYDRATE - - - "	
OXIDATION - - - - "	
PROPANE - - - - - "	
TRIFLUOROMETHANE. "	
ANION VACANCY	
ANTI FRENKEL - -> 255	
CONDUCTIVITY - - "	
DEFECT STRUCTURE "	
ELECTRON - - - - "	
ION - - - - - - - "	
YTTRIA DOPED - - "	
ZIRCONIUM OXIDE - "	
ANNEALING	
ABSORPTION - - ->1073	
ALUMINUM OXIDE ->1465	
ANODE FILM - - - "	
ELECTROETCH - - - "	
ANNEALING (CONTD)	
GERMANIUM NITRIDE 1073	
GERMANIUM OXIDE - "	
GERMANIUM OXYNIT. "	
IMPLANTATION - - "	
INFRARED - - - - "	
ION - - - - - - - "	
SURFACE GAIN - - 1465	
TRANSFORMATION - "	
ANODE	
ACIDIC - - - - ->1141	
ALUMINUM - - - ->1271	
- - - ->1281	
BACKSCATTERING -> 550	
BENZOTRIAZOLE - ->1276	
BIPOLAR - - - - -> 280	
CARBON - - - - -> 749	
CATALYST - - - ->1264	
CHLORIDE - - - - 1141	
- - - - 1271	
CHLORIDE SOLUTION 1276	
CHLORINE ELECTRO. 749	
CHROMATE - - - ->1146	
COLD - - - - - - 1141	
CORROSION - - - - 1146	
- - - - 1276	
CRYSTAL DEFECT - 280	
DECORATION - - - "	
ELECTRODISSOLUTI. 1276	
ELECTROLYTE - - ->1382	
ELECTRON - - - -> 876	
ELLIPSOMETRY - - 1146	
FILM - - - - - - "	
FUEL CELL - - - - 1264	
GAAS - - - - - - 1382	
GAASP - - - - - - "	
GLASSLIKE - - - - 749	
GRAIN - - - - - - 1141	
GRAPHITE - - - - 749	
HYDRAZINE - - - - 1264	
IMPLANT - - - - -> 45	
INHIBITION - - - 1276	
INHIBITOR - - - - 1146	
ION - - - - - - - 45	
- - - - - - - 550	
ION IMPLANT - - - 1281	
IRON - - - - - - 1146	
- - - - - - 1276	
JUNCTION - - - - 280	
LEAD - - - - - - 876	
LEAKAGE - - - - - 280	
METAL ATOMS - - - 1281	
MICROSCOPY - - - 876	
- - - 1141	
MOBILITY - - - - 1281	
NEUTRAL SOLUTION 1276	
NICKEL - - - - - 1141	
NICKEL BORIDE - - 1264	
NITRATE - - - - - 1271	
NONAQUEOUS - - - 1382	
NPN - - - - - - - 280	
OPEN CIRCUIT - - 1146	
OXIDATION - - - - 1281	
- - - - 1382	
OXIDE - - - - - - 550	
OXYGEN ELECTRODE 749	
PASSIVITY - - - - 1146	
PITTING - - - - - 1271	
POLARIZATION - - 1141	
POLARIZED - - - - 876	
POTENTIAL - - - - 1146	
POTENTIOSTATIC - 1141	
PYROLYSIS - - - - 749	
RANGE PROFILE - - 45	
RUTHERFORD - - - 550	
- - - 1281	
SCATTERING - - - 550	
SILICON - - - - - "	
SIZE - - - - - - 1141	
SOLUTION - - - - 1271	
STRAINING - - - - "	
SUBSTRATE - - - - 1264	
SURFACE OXIDE - - 749	
TANTALUM - - - - 550	
TANTALUM OXIDE - 45	
THIN FILM - - - - 550	
TRANSISTOR - - - 280	
VOLTAMMETRY - - - 876	
WORK - - - - - - 1141	
ANODE BEHAVIOR	
DENSITY - - - - -> 191	
ELECTROCHEMICAL - "	
HIGH CURRENT - - "	
NILO - - - - - - "	
POLISHING - - - - "	
ANODE BEHAVIOR (CONTD)	
SODIUM CHLORATE - 191	
STEEL - - - - - - "	
ANODE DEPOSITION	
IRON OXIDE - - -> 37	
IRON OXYHYDROXIDE "	
PASSIVITY - - - - "	
PERCHLORATE - - - "	
PLATINUM - - - - "	
ANODE DISINTEGRA.	
BERYLLIUM - - - ->1604	
CHARACTERISTICS - "	
NONAQUEOUS - - - "	
POLARIZATION - - "	
SOLUTION - - - - "	
ANODE DISINTERGR.	
ANODE DISSOLUTION> 7	
ANOMALOUS VALENCY "	
BERYLLIUM - - - - "	
CHARACTERISTIC - "	
ELECTRON - - - - "	
MICROSCOPE - - - "	
NONAQUEOUS - - - "	
POLARIZATION - - "	
SCANNING - - - - "	
SOLUTION - - - - "	
ANODE DISSOLUTION	
ALKALINE - - - -> 605	
ANODE DISINTERGR.> 7	
ANOMALOUS VALENCY "	
BENZOTRIAZOLE - - 605	
BERYLLIUM - - - - 7	
CHARACTERISTIC - "	
CHLORIDE - - - - 605	
CORROSION - - - - "	
ELECTROCHEMICAL -> 249	
ELECTRON - - - - 7	
FERRATE - - - - - 249	
INHIBITION - - - 605	
IRON - - - - - - "	
IRON (VI) - - - - 249	
MICROSCOPE - - - 7	
NONAQUEOUS - - - "	
POLARIZATION - - "	
POTENTIOSTATIC - 249	
SCANNING - - - - 7	
SOLUTION - - - - "	
- - - - 605	
SYNTHESIS - - - - 249	
ANODE FILM	
ALUMINUM - - - -> 268	
ALUMINUM OXIDE ->1465	
ANNEALING - - - - "	
CATALYSIS - - - ->1186	
CHLORIDE - - - - 268	
ELECTROETCH - - - 1465	
ELECTRON - - - - 268	
ELLIPSOMETRY - - 1186	
EVOLUTION - - - - "	
GALVANOSTATIC - - "	
GROWTH - - - - - 268	
OPACITY - - - - - "	
OXYGEN - - - - - 1186	
PITTING - - - - - 268	
PLATINUM - - - - 1186	
REACTION - - - - "	
SULFURIC ACID - - "	
SURFACE GAIN - - 1465	
THICKNESS - - - - 1186	
TRANSFORMATION - 1465	
ANODE OXIDATION	
ALUMINUM FILM - -> 400	
AQUEOUS - - - - ->1665	
BEHAVIOR - - - -> 865	
BUFFERED - - - -> 195	
CHARGING - - - -> 757	
COMPOUND - - - -> 820	
- - - - 1665	
CONCENTRATION - - 195	
DEVICE - - - - - 820	
DIFFUSION - - - - "	
DIMETHYLANILINE - 757	
DISCHARGING - - - "	
DISSOLUTION - - -> 860	
ELECTRODE - - - - 757	
ELECTROOPTICAL - 820	
ENVIRONMENT - - - 400	
FILM - - - - - - ->1152	
GALLIUM ARSENIDE 820	
GALLIUM PHOSPHIDE 1665	
HYDROGEN - - - -> 782	

PRIMARY TERM / CO-TERM — PAGE NO.

ANODE OXIDATION (CONTD)
HYDROGEN FLUORIDE 195
HYDROGEN PEROXIDE 1665
IMPEDANCE - - - - 400
IMPURITY - - - - 860
ION IMPLANT - - - "
- - - 865
ION IMPLANTATION 195
MARKER - - - - - 865
MORPHOLOGY - - - 757
NATIVE OXIDE - - 1665
NEUTRAL - - - - - 1152
NICKEL - - - - - "
NICKEL OXIDE - - "
NOBEL GASES - - - 865
OXIDE DISSOLUTION 195
PASSIVITY - - - - 1152
PH - - - - - - - 400
PLATINIZED - - - 782
POROSITY - - - - 400
PROFILE - - - - - 195
SEMICONDUCTOR - - 820
SEMICONDUCTORS - 1665
SILVER - - - - - 757
SILVER CHLORIDE - "
SULFATE - - - - - 1152
SURFACE - - - - - 757
TANTALUM - - - - 195
- - - - 865
TANTALUM OXIDE - 860
TUNGSTEN OXIDE - 782
TUNGSTEN TRIOXIDE "
ZINC - - - - - - 820

ANODE OXIDE
ALUMINUM OXIDE ->1019
COMPOSITE - - - - "
FILM - - - - - - "
GRAVIMETRY - - - "
HYDROUS - - - - - "
PSEUDOBOEHMITE - "
RADIOTRACER - - - "

ANODE SPARK
DYSPROSIUM - - ->1402
ERBIUM - - - - - "
GADOLINIUM - - - "
HOLMIUM - - - - - "
SAMARIUM - - - - "
SCDIUM SILICATE - "
YTTERBIUM - - - - "
YTTRIUM - - - - - "

ANODIZATION
ALUMINUM - - - -> 983
ALUMINUM CHLORIDE "
AMORPHOUSNESS - -> 394
ELECTRODE - - - - 983
FUSED - - - - - - "
ION - - - - - - - "
MOLTEN - - - - - "
SALT - - - - - - "
SODIUM CHLORIDE - "
SPUTTERING - - - 394
SUBVALENT - - - - 983
THIN FILM - - - - 394
TIN - - - - - - - "

ANOMALOUS
BORON - - - - - ->1677
CARRIER MOBILITY >1212
DENSITY - - - - - 1677
DIELECTRIC - - - "
DIFFUSION - - - - "
DISTRIBUTION - - 1212
EFFECT - - - - - 1677
ELECTRETS - - - - "
GERMANIUM - - - - 1212
HALL - - - - - - "
IMPURITY - - - - "
INHOMOGENEITY - - "
INSERT - - - - - 1677
METHOD - - - - - 1212
MOBILITY - - - - "
NITRIDE - - - - - 1677
PLANAR - - - - - "
RADIAL - - - - - 1212
SEMICONDUCTOR - - "
SILICON - - - - - 1677
SURFACE CHARGE - "
VANDERPAUW - - - 1212

ANOMALOUS VALENCY
ANODE DISINTERGR.> 7
ANODE DISSOLUTION "
BERYLLIUM - - - - "
CHARACTERISTIC - "

ANOMALOUS VALENCY (CONTD)
ELECTRON - - - - 7
MICROSCOPE - - - "
NONAQUEOUS - - - "
POLARIZATION - - "
SCANNING - - - - "
SOLUTION - - - - "

ANOMALUS
BORON DIFFUSION -> 722
BORON NITRIDE - - "
PLANAR SOURCE - - "
SILICON - - - - - "

ANTHRACENE
COMPOSITE - - - ->1341
CONVERSION - - - "
LEAD CHLORIDE - - "
LIGHT - - - - - - "
LUMINESCENCE - - "
VISIBLE - - - - - "
X RAY - - - - - - "

ANTI FRENKEL
ANION VACANCY - -> 255
CONDUCTIVITY - - "
DEFECT STRUCTURE "
ELECTRON - - - - "
ION - - - - - - - "
YTTRIA DOPED - - "
ZIRCONIUM OXIDE - "

ANTIMONIDE
ALUMINUM - - - ->1662
ARSENIDE - - - - "
GALLIUM - - - - - "
GROUP II-VI - - - "
GROUP III-V - - - "
INDIUM - - - - - "
LATTICE - - - - - "
MISCIBILITY GAP - "
PARAMETER - - - - "
PHOSPHIDE - - - - "
PSEUDOBINARY - - "
SEMICONDUCTOR - - "
SOLID SOLUTION - "

ANTIMONY
CHALCOGENIDES - ->1523
DOPING - - - - -> 967
- - - - - 1523
EPITAXY - - - - - 967
INFRARED DEVICE - 1523
JUNCTION - - - - "
LEAD - - - - - - "
METALORGANICS - - 967
SAPPHIRE - - - - "
SILICON - - - - - "
SOURCE - - - - - "
TELLURIDE - - - - 1523
TERNARIES - - - - "
TIN - - - - - - - "
TRIMETHYLSTIBINE 967

APPLICATION
CIRCUIT - - - - -> 422
DEVICE - - - - - "
EPITAXIAL - - - - "
INTEGRATED - - - "
MEASUREMENT - - - "
RESISTANCE - - - "
RESISTIVITY - - - "
SILICON - - - - - "
SPREADING - - - - "

APROTIC
DIMETHYLFORMAMIDE> 518
ELECTHOCHEMISTRY "
ELECTRODE - - - - "
HYDROGEN - - - - "
REVERSIBLE CELL - "
SOLVENT - - - - - "
THALLIUM - - - - "

AQUEOUS
ANODE OXIDATION ->1665
COMPOUND - - - - "
GALLIUM PHOSPHIDE "
HYDROGEN PEROXIDE "
NATIVE OXIDE - - "
SEMICONDUCTORS - "

AQUEOUS SOLUTION
ELECTROLYSIS - ->1311
IMPURITIES - - - "
MERCURY - - - - - "
SODIUM CHLORIDE - "

ARGON
BACKSPUTTERING -> 558
CONTROL - - - - ->1372
DIFFUSING - - - - "
EQUILIBRIA - - - "
ETCHING - - - - - "
FILM - - - - - - 558
HELIUM - - - - - 1372
HEXAFLUORIDE - - "
IMPLANTATION - - 558
ION - - - - - - - "
LANGMUIR SHEATH - 1372
METALLIZATION - - 558
NITROGEN - - - - 1372
PENTA FLUORIDE - "
RATE - - - - - - "
REACTION - - - - "
SILICON DIOXIDE - 558
SPUTTERING - - - "
TRAPPING - - - - "
TUNGSTEN - - - - 1372

ARGON OXYGEN
ACTIVITY - - - -> 354
CONTROL - - - - - "
COULOMETRY - - - "
ELECTRODE - - - - "
MIXTURE - - - - - "
OXYGEN - - - - - "
PLATINUM - - - - "
POTENTIOSTAT - - "
TITRATION - - - - "
ZIRCONIA - - - - "

ARRANGEMENT
CATHODOLUMINESCE.> 894
CRT - - - - - - - "
DISTRIBUTION - - "
PARTICLE - - - - "
PHOSPHOR - - - - "
SIZE - - - - - - "
TELEVISION - - - "

ARSENIC
ADSORPTION - - -> 609
ARSENIDE - - - ->1650
ASYMMETRIC - - - "
ASYMMETRY - - - - "
CHALCOGENIDE - -> 363
COMPOUND - - - ->1634
COMPOUNDS - - - - 1650
COPPER SULFIDE - 363
CRACKING - - - - 1650
CROSS MATCH - - - "
DOPING - - - - - 1634
ENTRY - - - - - - 609
EPITAXY - - - - ->1362
ETCH - - - - - - 1650
GALLIUM - - - - - 1634
- - - - - 1650
GLASS ELECTRODE - 363
GROUP III-V - - - 1650
GROWTH - - - - - 1362
HYDROGEN - - - - 609
INDIUM - - - - - 1650
ION IMPLANT - - - 1362
ISOTHERMS - - - - 1634
LIQUIDUS - - - - "
PERMEATION - - - 609
PHOSPHIDE - - - - 1650
PHOSPHORUS - - - 1634
POTENTIAL - - - - 609
SEMICONDUCTOR - - 1634
SILICON - - - - - 1362
- - - - - 1634
SINNERITE - - - - 363
SIRTL - - - - - - 1650
STEEL - - - - - - 609
SYSTEM - - - - - 1634
TERNARY - - - - - "

ARSENIDE
ALUMINUM - - - ->1662
ANTIMONIDE - - - "
ARSENIC - - - - ->1650
ASYMMETRIC - - - "
ASYMMETRY - - - - "
COMPOUNDS - - - - "
CRACKING - - - - "
CROSS MATCH - - - "
ETCH - - - - - - "
GALLIUM - - - - - "
- - - - - 1662
GROUP II-VI - - - "
GROUP III-V - - - 1650
- - - 1662
INDIUM - - - - - 1650
INDIUM - - - - - 1662
INTERFACE - - - - 1650
LATTICE - - - - - "
MISCIBILITY GAP - "
PARAMETER - - - - "
PHOSPHIDE - - - - 1650
- - - - 1662
PSEUDOBINARY - - "
SEMICONDUCTOR - - "
SIRTL - - - - - - 1650
SOLID SOLUTION - 1662

ARSINE
CHARACTERIZATION >1642
CHEMICAL - - - - "
- - - ->1646
ELECTRICAL - - - "
GALLIUM ARSENIDE 1642
1646
GROWTH - - - - - 1642
HETEROEPITAXY - - "
- - 1646
INDIUM ARSENIDE - 1642
- 1646
PROPERTIES - - - "
TRIETHYLINDIUM - 1642
- 1646
VAPOR DEPOSITION 1642
1646

ASSIGNMENT
CRYSTAL DEFECTS -> 170
CRYSTALLOGRAPHY - "
DOMAIN - - - - - "
ETCHING - - - - - "
FERROELECTRIC - - "
GMO - - - - - - - "
SINGLE CRYSTAL - "

ASYMMETRIC
ARSENIC - - - - ->1650
ARSENIDE - - - - "
ASYMMETRY - - - - "
COMPOUNDS - - - - "
CRACKING - - - - "
CROSS MATCH - - - "
ETCH - - - - - - "
GALLIUM - - - - - "
GROUP III-V - - - "
INDIUM - - - - - "
PHOSPHIDE - - - - "
SIRTL - - - - - - "

ASYMMETRY
ARSENIC - - - - ->1650
ARSENIDE - - - - "
ASYMMETRIC - - - "
COMPOUNDS - - - - "
CRACKING - - - - "
CROSS MATCH - - - "
ETCH - - - - - - "
GALLIUM - - - - - "
GROUP III-V - - - "
INDIUM - - - - - "
PHOSPHIDE - - - - "
SIRTL - - - - - - "

ASYMPTOTIC
ELECTRODE - - - -> 521
IMPEDANCE - - - - "
ROTATING DISK - - "
SOLUTION - - - - "
WARBURG - - - - - "

ATMOSPHERE
ALLOY - - - - - -> 889
COBALT IRON - - - "
HYDROGEN SULFIDE "
KINETICS - - - - "
LOW PRESSURE - -> 943
LOW TEMPERATURE - "
MAGNESIUM - - - - "
NITROGEN - - - - "
PARABOLIC - - - - 889
SULFIDATION - - - "
THERMAL NITRIDAT. 943

AUGER
CHLORINE - - - -> 34
CLEANING - - - -> 310
COMPOSITION - - - 34
DENSIFICATION - -> 827
ELECTRON SPECTRO. 310
827
GERMANIUM - - - - 310
GLASS FILM - - - 827
OXYGEN - - - - - 34

PRIMARY TERM / CO-TERM	PAGE NO.
AUGER	(CONTD)
OXYGEN	827
PLATINUM ANODE	34
RATIO	827
SILICON	"
SILICON DIOXIDE	"
SPECTROSCOPY	34
SPIN ON	827
STOICHIOMETRY	"
SURFACE	34
	310
AUTOMATIC	
ELECTRODE ->	251
GAS	"
HYDROGEN	"
PUMP	"
SPARKLESS	"
BACKSCATTERING	
ANODE ->	550
ION	"
OXIDE	"
RUTHERFORD	"
SCATTERING	"
SILICON	"
TANTALUM	"
THIN FILM	"
BACKSPUTTERING	
ARGON ->	558
FILM	"
IMPLANTATION	"
ION	"
METALLIZATION	"
SILICON DIOXIDE	"
SPUTTERING	"
TRAPPING	"
BANDGAP	
CHEMICAL ->1673	
COMPOUND	"
CRYSTAL	"
GERMANIUM	"
NITRIDE	"
PROPERTIES	"
STRUCTURE	"
SYNTHESIS	"
TERNARY	"
VAPOR DEPOSITION	"
ZINC	"
BARIUM	
ALUMINUM ->	137
CALCIUM	"
EUROPIUM	"
GALLIUM	"
PHOTOLUMINESCENCE	"
SEMICONDUCTOR	"
STRONTIUM	"
SYNTHESIS	"
YTTERBIUM	"
BARIUM CALCIUM	
BARIUM MAGNESIUM	>1631
BORATES	"
CALCIUM	"
CALCIUM MAGNESIUM	"
CALCIUM STRONTIUM	"
LUMINESCENCE	"
MAGNESIUM STRONT.	"
TERBIUM	"
BARIUM MAGNESIUM	
BARIUM CALCIUM	>1631
BORATES	"
CALCIUM	"
CALCIUM MAGNESIUM	"
CALCIUM STRONTIUM	"
LUMINESCENCE	"
MAGNESIUM STRONT.	"
TERBIUM	"
BARIUM SULFATE	
ADDITIVE ->	463
ELECTRODE	"
LEAD	"
LEAD SULFATE	"
LIGNIN	"
MECHANISM	"
MORPHOLOGY	"
REACTION	"
BARRIER	
CAPACITANCE ->1066	
EPITAXY	"
GAAS	"
BARRIER	(CONTD)
HALL EFFECT	1066
LAYER	"
MEASUREMENT	"
MOBILITY	"
PHOTOLUMINESCENCE	"
SCHOTTKY	"
SPECTRA	"
BARRIER HEIGHT	
BREAKDOWN ->1195	
CONTAMINATION	"
DIELECTRIC	"
FILM	"
LOWERING	"
SILICON	"
SILICON DIOXIDE	"
SODIUM	"
SODIUM INDUCED	"
BASIC	
COMPOSITION ->	253
LEAD CARBONATE	"
LEAD OXIDE	"
LEAD SULFATE	"
VARIABLE	"
BATTERY	
ACETONITRILE ->	851
ACTIVE ->	531
ALLOY ->1245	
->1526	
ALUMINUM	1245
BEHAVIOR ->	656
BISMUTH	1526
BUFFER	1245
CADMIUM ->	175
CALCIUM	1526
CALCIUM LEAD	"
CARBONATE ->	315
	656
->1457	
CATHODE	656
CELL	175
CHARGE ACCEPTANCE	"
CHLORIDE	1245
COMPUTER	175
CONTAMINATION ->1045	
CONTROLLED	175
COPPER	656
	851
CORROSION	531
ELECTRODEPOSITION	1457
ELECTROINITIATE ->1294	
ELECTROLYTE	1045
	1457
ELECTRON ->1541	
EMF	1245
FORMATION ->	854
GALVANIC CELL	315
GRID	531
	1526
HIGH ENERGY	1294
HIGH PRESSURE	1245
INFRARED	1045
INORGANIC	"
LEAD ACID	531
	854
	1541
LEAD ANTIMONY	531
LEAD CALCIUM	1541
LEAD ELECTRODE	854
	1541
LIQUID	1045
LITHIUM	"
	1294
LITHIUM ANODE	315
LITHIUM BROMINE	"
LITHIUM CELLS	656
LITHIUM ELECTRODE	1457
MAGNESIUM	1245
MANGANESE	656
MATERIAL	531
MERCURY	175
MICROSCOPY	1541
MOLYBDENUM	656
NEGATIVE	1541
NEGATIVE PLATE	854
NICKEL	175
NONAQUEOUS	315
OXYHALIDE	1045
PERCHLORATE	1294
POLYMER BONDING	1541
POLYMERIZATION	1294
PROPYLENE	315
	656
	1457
BATTERY	(CONTD)
PROTECTION	531
PULSE CHARGING	175
RECHARGABLE	1457
SCANNING	1541
SEAWATER	1245
SECONDARY	315
SECONDARY BATTERY	851
SOLVENT	315
TETRAHYDROFURAN	656
	1294
THICKNESS	531
TIN	1526
TRACE ANALYSIS	1045
WATER	"
BATTERY ANODE	
ALLOY ->	734
CARBONATE	"
DIFFUSION	"
ELECTRODE	"
INTERMETALLIC	"
LITHIUM MAGNESIUM	"
PROPYLENE	"
BATTERY CELL	
BETA ALUMINA ->	1
CATHODE	"
GALVANIC CELL	"
IRON DOPED	"
IRON SPINEL	"
MOSS BAUER	"
SPECTROSCOPY	"
BATTERY FAILURE	
CAPACITY ->1546	
CYCLE	"
DECOMPOSITION	"
ELECTRODE	"
FORM	"
LEAD DIOXIDE	"
MECHANISM	"
THERMAL ANALYSIS	"
BAYERITE	
ALUMINUM ->1322	
GROWTH	"
HYDROLYSIS	"
NUCLEATION	"
OXIDE FILM	"
PSEUDOBUEHMITE	"
BEAM	
CIRCUIT ->	62
DEPOSITION ->	899
ELECTROLESS	62
GOLD	"
LEAD	"
MOLECULE	899
PLATING	62
PYROLYSIS	899
SAMPLE	"
SILANE	"
SILICON	62
	899
SPECTROMETRY	"
BEHAVIOR	
AMMONIA ->	962
ANODE OXIDATION ->	865
BATTERY ->	656
CALCIUM COPED ->	122
CARBONATE	656
CATHODE	"
CERIUM DIOXIDE	122
CHEMISORPTION ->	163
CONVERGING ->	448
COPPER	656
DIELECTRIC	122
	163
DIFFUSION	"
DIHYDROPYRIDINES >	345
DIMERIZATION	"
DIODES	962
DISCHARGE ->1460	
DOPING	163
DOUBLE LAYER ->1308	
ELECTROLYTE ->1460	
EMBRITTLEMENT ->1589	
EMITING	962
EPITAXY	"
FLUOROGRAPHITE	1308
FREE RADICAL	345
GAP	962
HIGH TEMPERATURE	122
	163
HYDROGEN	1589
BEHAVIOR	(CONTD)
HYDROGEN ELECTRO.	1589
IMPURITY	962
INDIUM ANTIMONIDE	448
INTERFACE	"
ION IMPLANT	865
IRREVERSIBLE	1589
LIGHT	962
LIQUID PHASE	"
LITHIUM	163
LITHIUM CELL	1460
LITHIUM CELLS	656
MANGANESE	"
MARKER	865
METHYLNICOTINAMI.	345
MOLYBDENUM	656
	1460
NICKEL OXIDE ->	318
NICOTINAMIDE	345
NITROGEN DOPING	962
NOBEL GASES	865
NONAQUEOUS	1308
	1460
OXIDATION	345
POLYCRYSTALLINE	163
POROUS ELECTRODE	1308
POTENTIAL	"
PRESSURE INDUCED	448
PROPYLENE	656
REDOX COUPLE	318
REDOX PATTERN	345
	"
REDUCTION	"
SEGREGATION	448
SEMICONDUCTOR	318
SODIUM	163
SOLIDIFICATION	448
SOLUTION	1460
SOURCE	962
STATIONARY	448
TANTALUM	865
TETRAHYDROFURAN	656
VERTICAL ZONE	448
ZINC OXIDE	163
BENZENES	
COMPOUND ->	516
PARA DIHALOSUBST.	"
POLAROGRAPHY	"
RELATED	"
BENZOTRIAZOLE	
ALKALINE ->	605
ANODE ->1276	
ANODE DISSOLUTION	605
CHLORIDE	"
CHLORIDE SOLUTION	1276
CORROSION	605
	1276
ELECTRODISSOLUTI.	"
INHIBITION	605
	1276
IRON	605
	1276
NEUTRAL SOLUTION	"
SOLUTION	605
BERYLLIA	
CERAMIC OXIDE ->1240	
CRYSTAL	"
DAMAGE	"
GARNET	"
HARDNESS	"
POLISHING	"
PREPARATION	"
SAPPHIRE	"
SPINEL	"
SURFACE	"
BERYLLIUM	
ALLOY ->	247
ANODE DISINTEGRA.>1604	
ANODE DISINTEGR.>	7
ANODE DISSOLUTION	"
ANOMALOUS VALENCY	"
BISMUTH	247
CHARACTERISTIC	7
CHARACTERISTICS	1604
CHRONOPOTENTIOME.>1429	
DEPENDENCE	"
DEPLETION	"
ELECTRODE	247
ELECTROMIGRATION	1429
ELECTRON	7
FLOURIDES	1429
FLUORIDE	247
GLASSES	1429

PRIMARY TERM
CO-TERM — PAGE NO.

BERYLLIUM (CONTD)
LITHIUM - - - - - 247
- - - - - 1429
MICROSCOPE - - - 7
MOLTEN HALIDES - 1429
MOLTEN SALT - - - 247
NONAQUEOUS - - - 7
- - - 1604
POLARIZATION - - 7
- - 1604
SCANNING - - - - 7
SOLUTION - - - - "
- - - - 1604
TEMPERATURE - - - 1429

BETA ALUMINA
BATTERY CELL - -> 1
CATHODE - - - - - "
CONDUCTANCE - - ->1314
CRYSTAL GROWTH -> 596
CURRENT - - - - - 1314
EMF - - - - - - ->1603
GALVANIC CELL - - 1
HIGH PRESSURE - - 596
IMPEDANCE - - - - 1314
IRON DOPED - - - 1
IRON SPINEL - - - "
MEMBRANE - - - - 596
MOSS BAUER - - - 1
PULSE - - - - - - 1314
SODIUM - - - - - 596
SOLID ELECTROLYTE 1603
SPECTROSCOPY - - 1

BINARY
COULOMBIC - - - -> 500
INTERACTION - - - "
LITHIUM CHLORIDE "
MOLTEN SALT - - - "
POSTASSIUM CHLOR. "
SURFACE TENSION - "

BIPOLAR
AMMONIUM - - - ->1215
ANODE - - - - - -> 280
CHEMICAL - - - - 1215
CHLORATE - - - -> 648
COMPLEMENTARY - ->1119
CRYSTAL DEFECT - 280
DECORATION - - - "
DEVICE - - - - - 1119
ELECTROLYSIS - - 646
ELECTROLYZER - - "
ETCHANT - - - - - 1215
GALLIUM ARSENIDE "
HYDROGEN PEROXIDE "
HYDROXIDE - - - - "
INTEGRATION - - - 1119
ISOLATED - - - - "
JUNCTION - - - - 280
LEAKAGE - - - - - "
MONOLITHIC - - - 1119
MOS - - - - - - - "
NPN - - - - - - - 280
PARASITE CURRENT 648
REMOVAL - - - - - 1215
SELECTIVE - - - - "
SEMICONDUCTOR - - 1119
SILICON DIOXIDE - 1215
TRANSISTOR - - - 280
- - - 1119
- - - 1215

BIPOLAR ELECTRODE
CURRENT - - - - -> 622
DISTRIBUTION - - "
ELECTRODE - - - - "
POTENTIAL - - - - "
RESISTIVE - - - - "
WIRE ELECTRODE - "

BISMUTH
ALLOY - - - - - -> 247
- - - - - ->1526
BATTERY - - - - - "
BERYLLIUM - - - - 247
CALCIUM - - - - - 1526
CALCIUM LEAD - - "
ELECTRODE - - - - 247
FLUORIDE - - - - "
GRID - - - - - - 1526
LITHIUM - - - - - 247
MOLTEN SALT - - - "
TIN - - - - - - - 1526

BOAT
CVD - - - - - - ->1112

BOAT (CONTD)
PREPARATION - - - 1112
PROPERTY - - - - "
QUARTZ - - - - - "
REDUCTION - - - - "
SEMICONDUCTOR - - "
SILICON - - - - - "
TRICHLOROSILANE - "
TUBE - - - - - - "

BOND
ALUMINA - - - - -> 107
BONDING - - - - - "
COPPER - - - - - "
ELECTROLESS - - - "
METALLIZATION - - "
MOLTEN ALKALI - - "
SURFACE - - - - - "

BONDING
ALUMINA - - - - -> 107
BOND - - - - - - "
COPPER - - - - - "
ELECTROLESS - - - "
METALLIZATION - - "
MOLTEN ALKALI - - "
SURFACE - - - - - "

BORANE
ACID BATH - - - - ->1023
AMINE - - - - - - "
COBALT - - - - - "
DEPOSITION - - - "
ELECTROLESS - - - "
HYPOPHOSPHITE - - "
NICKEL - - - - - "
PLATING - - - - - "

BORATES
BARIUM CALCIUM ->1631
BARIUM MAGNESIUM "
CALCIUM - - - - - "
CALCIUM MAGNESIUM "
CALCIUM STRONTIUM "
LUMINESCENCE - - "
MAGNESIUM STRONT. "
TERBIUM - - - - - "

BORIDES
BORON - - - - - -> 846
CHEMICAL - - - - "
ELEMENTAL - - - - "
MODIFICATION - - "
NONMETAL - - - - "
STRUCTURE - - - - "
TETRAGONAL - - - "
VAPOR DEPOSITION "

BOROHYDRIDE
AGITATION - - - -> 56
ELECTROLESS - - - "
GOLD - - - - - - "
IMPURITY - - - - "
PLATING - - - - - "
PROCEDURE - - - - "
THICKNESS - - - - "

BORON
ANALYTICAL - - -> 972
ANOMALOUS - - - ->1677
BORIDES - - - - -> 846
CHEMICAL - - - - "
CONTAMINATION - -> 593
DENSITY - - - - - 1677
DETERMINATION - - 972
DIELECTRIC - - - 1677
DIFFUSION - - - -> 705
- - - ->1377
- - - - 1677
EFFECT - - - - - "
ELECTRETS - - - - "
ELEMENTAL - - - - 846
EMITTER DIP - - - 1377
INSERT - - - - - 1677
ION IMPLANT - - - 705
MICROANALYSIS - - 593
MODIFICATION - - 846
NITRIDE - - - - - 1677
NONMETAL - - - - 846
NUCLEAR - - - - - 593
OXIDATION - - - - 705
OXYGEN - - - - - 593
PHOSPHORUS - - - 1377
PLANAR - - - - - 1677
POLYCRYSTALLINE - 972
SEGREGATION - - - 705
SHEET RESISTIVITY 972

BORON (CONTD)
SILICON - - - - - 1677
SILICON FILM - - 972
SOLVENTS - - - - 593
STRUCTURE - - - - 846
SURFACE - - - - - 593
SURFACE CHARGE - 1677
TETRAGONAL - - - 846
VAPOR DEPOSITION "

BORON ARSENIDE
CONDUCTION - - -> 412
DECOMPOSITION - - "
PREPARATION - - - "
PROPERTY - - - - "
SEMICONDUCTOR - - "
SUBSTRATE - - - - "

BORON DIFFUSION
ANOMALUS - - - -> 722
BORON NITRIDE - - "
PLANAR SOURCE - - "
SILICON - - - - - "

BORON NITRIDE
ANOMALUS - - - -> 722
BORON DIFFUSION - "
PLANAR SOURCE - - "
SILICON - - - - - "

BOROSILICATE
ADSORPTION - - -> 676
DEPOSIT - - - - - "
DIFFUSION - - - - "
GLASS FILM - - - "
- - ->1098
GLASS METAL - - - "
HARDNESS - - - - "
SILANOL - - - - - 676
SINTERING - - - - 1098
SPECTROSCOPY - - 676
STRESS - - - - - 1098
VAPOR - - - - - - 676
VICKERS - - - - - 1098
WATER - - - - - - 676

BOUNDARY
COMPLEMENT - - -> 313
CONDITION - - - - "
DIFFUSION - - - - "
EQUATION - - - - "
ERROR - - - - - - "
FLUX STEP - - - - "
FUNCTION - - - - "
PROFILE - - - - - "
SEMICONDUCTOR - - "

BREAKDOWN
BARRIER HEIGHT ->1195
CARRIER - - - - ->1229
CONTAMINATION - - 1195
DIELECTRIC - - -> 809
- - - 1195
- - - 1229
DIODE - - - - - -> 692
ELECTRON - - - - "
ETCHING - - - - - 1229
FILM - - - - - - 809
- - - - - - 1195
GAAS - - - - - - 692
GENERATION - - - 1229
HALOGEN - - - - - 809
HYDROGEN CHLORIDE "
IMPATT - - - - - 692
IMPERFECTION - - 1229
LOWERING - - - - 1195
MICROSCOPE - - - 692
MINORITY - - - - 1229
OXIDATION - - - - 809
PREMATURE - - - - 692
RELIABILITY - - - 809
SCANNING - - - - 692
SCHOTTKY - - - - "
SILICON - - - - - 1195
- - - - - 1229
SILICON DIOXIDE - 809
- 1195
SITES - - - - - - 692
SODIUM - - - - - 1195
SODIUM INDUCED - "
WAFER - - - - - - 1229

BRINE LEVEL
CHLORALKALI CELL >1286
GAS LIFT - - - - "
MERCURY TYPE - - "
PUMP - - - - - - "

BRINE LEVEL (CONTD)
SCALE UP - - - - 1286
VOLTAGE - - - - - "

BROMIDE
ALUMINUM - - - ->1239
AMMONIUM - - - -> 977
CONDUCTANCE - - - "
DIMETHYLFORMAMIDE "
ELECTROLYTE - - - "
ISOTHIOCYANATE - "
NICKEL - - - - - "
NONAQUEOUS - - - "
POTASSIUM - - - - "
SOLID - - - - - - 1239
SOLUTION - - - - 977
TETRABUTYL - - - "
VAPOR PRESSURE - 1239
VISCOSITY - - - - 977

BRONZE
CONDUCTIVITY - ->1530
ELECTROREDUCTION >1029
HYDROGEN - - - - "
HYDROGEN PEROXIDE "
OXYGEN - - - - - "
PLATINUM - - - - "
SODIUM - - - - - "
- - - - - 1530
SODIUM ION - - - "
TRACES - - - - - 1029
TUNGSTEN - - - - "
- - - - 1530

BUFFER
ALLOY - - - - - ->1245
ALUMINUM - - - - "
BATTERY - - - - - "
CHLORIDE - - - - "
EMF - - - - - - - "
ETCH SULUTION - ->1579
FLUORIDE - - - - "
HIGH PRESSURE - - 1245
MAGNESIUM - - - - "
PALLADIUM HYDRIDE 1579
PH ELECTRODE - - "
SEAWATER - - - - 1245

BUFFERED
ANODE OXIDATION -> 195
CONCENTRATION - - "
HYDROGEN FLUORIDE "
ION IMPLANTATION "
OXIDE DISSOLUTION "
PROFILE - - - - - "
TANTALUM - - - - "

CADMIUM
ANALYSIS - - - ->1366
BATTERY - - - - -> 175
CELL - - - - - - "
CHARGE ACCEPTANCE "
COMPUTER - - - - "
CONTROLLED - - - "
CRYSTAL GROWTH - 1366
DEPOSITION - - -> 965
DISTRIBUTION - - 1366
EPITAXY - - - - - 965
HETEROEPITAXY - - "
MERCURY - - - - - 175
NICKEL - - - - - "
PHOTOSENSITIVITY 965
PULSE CHARGING - 175
SAPPHIRE - - - - 965
SELENIDE - - - - "
SULFIDE - - - - - "
TELLURIDE - - - - 1366
TEMPERATURE - - - "
TRAVELING HEATER "
VAPOR - - - - - - 965
VAPOR PHASE - - - "

CADMIUM CHLORIDE
EMF - - - - - - -> 959
FREE ENERGY - - - "
GIBBS - - - - - - "
ION MOBILITY - - "
- - "
LITHIUM CHLORIDE "
MOLTEN MIX - - - "
TRANSFERENCE - - "

CADMIUM SULFIDE
CHEMOMECHANICAL ->1064
POLISHING - - - - "

PRIMARY TERM / CO-TERM — PAGE NO.

CALCIA STABILIZED
CONDUCTION -> 793
COULOMETRY "
ELECTRODE -> 506
ELECTROLYTE "
GALLIUM "
GALLIUM SESQUIOX. "
HOLE 793
KINETICS 506
OXYGEN "
793
PERMEATION "
SOLID 506
SOLID STATE 793
TITRATION "
TRANSFER 506
WUSTITE 793
ZIRCONIA 506
793

CALCIUM
ALLOY ->1526
ALUMINUM -> 137
BARIUM "
BARIUM CALCIUM ->1631
BARIUM MAGNESIUM "
BATTERY 1526
BISMUTH "
BORATES 1631
CALCIUM LEAD 1526
CALCIUM MAGNESIUM 1631
CALCIUM STRONTIUM "
DICALCIUM -> 534
ELECTROCHEMISTRY "
EUROPIUM 137
GALLIUM "
GALVANIC CELL 534
GRID 1526
LUMINESCENCE 1631
MAGNESIUM STRONT. "
MONOCALCIUM 534
PHOTOLUMINESCENCE 137
SEMICONDUCTOR "
STABILITY 534
STANNATE "
STRONTIUM 137
SYNTHESIS "
TERBIUM 1631
TIN 1526
VAPORIZATION 534
YTTERBIUM 137

CALCIUM DOPED
BEHAVIOR -> 122
CERIUM DIOXIDE "
DIELECTRIC "
HIGH TEMPERATURE "

CALCIUM LEAD
ALLOY ->1526
BATTERY "
BISMUTH "
CALCIUM "
GRID "
TIN "

CALCIUM MAGNESIUM
BARIUM CALCIUM ->1631
BARIUM MAGNESIUM "
BORATES "
CALCIUM "
CALCIUM STRONTIUM "
LUMINESCENCE "
MAGNESIUM STRONT. "
TERBIUM "

CALCIUM STRONTIUM
BARIUM CALCIUM ->1631
BARIUM MAGNESIUM "
BORATES "
CALCIUM "
CALCIUM MAGNESIUM "
LUMINESCENCE "
MAGNESIUM STRONT. "
TERBIUM "

CALCULATION
DEPOSITION ->1357
EPITAXY "
GAASP "
IMPURITY -> 588
LIQUIDUS TEMPERA.>1258
MOLTEN SALT "
NUMERICAL 588
OXIDATION "
PHASE DIAGRAM 1258
REDISTRIBUTION 588

CALCULATION (CONTD)
SEMICONDUCTOR 588
SILICON "
SILICON DIOXIDE "
THERMAL "
VAPOR PHASE 1357

CANDOLUMINESCENCE
ALUMINATE -> 142
LANTHANUM "
PHOSPHORS "
TRANSITION ION "
WILLEMITE "
ZINC PHOSPHATE "

CAPACITANCE
BARRIER ->1066
COPPER ->1318
COPPER CHLORIDE "
DIFFUSION "
DOUBLE LAYER -> 632
1318
ELECTRODE 632
-> 639
ELECTROLYTE CELL 632
639
EPITAXY 1066
GAAS "
GOLD 1318
GRAPHITE 632
639
HALL EFFECT 1066
INTERFACE 639
LAYER 1066
LOW TEMPERATURE 1318
MEASUREMENT 1066
MOBILITY "
PHOTOLUMINESCENCE "
PLATINUM 632
ROOM TEMPERATURE "
ROUGHENING 639
SCHOTTKY 1066
SILVER HALIDES 632
639
SINGLE CRYSTAL 1318
SOLID ELECTROLYTE 632
639
1318
SOLID STATE 639
SPECTRA 1066
WETTING 639

CAPACITATOR
CARRIER -> 849
GENERATION "
MINORITY "
MOS "
SILICON "

CAPACITOR
ALUMINUM -> 583
CARRIER ->1219
CORROSION 583
DEEP 1219
DEPLETION "
DIFFUSION "
ELECTROLYTE 583
ETCHABILITY "
IRON "
LENGTH 1219
LIFETIME "
MICROSEGREGATION 583
MINORITY 1219
MOS "
PRECIPITATION 583
SILICON 1219
STEADY STATE "
TUNNEL 583

CAPACITY
BATTERY FAILURE ->1546
CYCLE "
DECOMPOSITION "
DOUBLE LAYER -> 512
->1444
ELECTRODE 512
1546
FORM "
LEAD DIOXIDE "
MECHANISM "
NICKEL 512
POROUS "
POTASSIUM HYDROX. "
1444
SILVER "
SPECTROGRAPHY "
SWEEP 512

CAPACITY (CONTD)
SWEEP RATE 1444
TEMPERATURE "
THERMAL ANALYSIS 1546
TRIANGLE 1444
TRIANGULAR 512
VOLTAGE "
VOLTAMMETRY 1444

CARBON
ACETONITRILE ->1451
ANODE -> 749
CHLORINE ELECTRO. "
CIRCUIT -> 146
CONTAMINATION "
DEPOSITION -> 527
DOPING 146
ELECTRO OXIDATION 1451
ELECTRODEPOSIT -> 490
GLASSLIKE 749
GOLD 490
1451
GRAPHITE 749
INTEGRATED 146
IRON 527
IRON OXIDE "
NITRITE IONS 1451
OXYGEN ELECTRODE 749
PASSIVATION 527
PLATINUM "
1451
POTENTIOSTATIC 527
PYROLYSIS 749
RESIDUE 146
RING ELECTRODE 527
SILICON 146
STEELS 527
SURFACE 146
SURFACE OXIDE 749
TRANSIENT 527

CARBON DIOXIDE
ADSORPTION -> 233
CARBONYL "
ELECTROSORPTION "
PLATINUM "
RADIOMETRY "
REDUCED "

CARBON FILM
GASEOUS ->1551
IRON "
OXIDATION "
PRETREATMENT "
THIN FILM "

CARBON MONOXIDE
DIFFUSION ->1315
ELECTRODE "
GAS SENSOR "
OXIDATION "
PLATINUM "

CARBON OXIDE
CHLORINE ELECTRO.>1289
GRAPHITE ANODE "
TAFEL "

CARBONATE
ALKALI METAL -> 994
ALLOY -> 734
ALUMINUM CHLORIDE 994
BATTERY -> 315
-> 656
->1457
BATTERY ANODE 734
BEHAVIOR 656
CATHODE "
CHLORIDE 994
COEFFICIENT "
COPPER 656
CURRENT DENSITY 994
DIFFUSION 734
ELECTRODE "
994
ELECTRODEPOSITION 1457
ELECTROLYTE "
EMF -> 83
EXCHANGE 994
GALVANIC CELL 315
INTERMETALLIC 734
KINETICS 994
LITHIUM ANODE 315
LITHIUM BROMINE "
LITHIUM CELLS 656
LITHIUM ELECTRODE 1457
LITHIUM ION 83

CARBONATE (CONTD)
LITHIUM MAGNESIUM 734
MANGANESE 656
MEASUREMENT 83
MOLYBDENUM 656
NONAQUEOUS 315
NUMBER 83
PROPYLENE "
315
656
734
994
1457
RECHARGABLE "
SECONDARY 315
SOLUTION 83
SOLVENT 315
TETRAHYDROFURAN 656
TRANSFER 994
TRANSFERENCE 83

CARBONATE ION
EMF -> 885
FUSED NITRATES "
OXIDE ION "
OXYGEN ELECTRODE "
STABILITY "

CARBONYL
ADSORPTION -> 233
CARBON DIOXIDE "
ELECTROSORPTION "
PLATINUM "
RADIOMETRY "
REDUCED "

CARRIER
ABSORPTION ->1482
BREAKDOWN ->1229
CAPACITATOR -> 849
CAPACITOR ->1219
CONCENTRATION 1482
DEEP 1219
DEPLETION "
DIELECTRIC 1229
DIFFUSION -> 973
1219
DIODE ->1332
DRUDE ZENER 1482
EFFICIENCY 1332
ETCHING 1229
GAAS 1482
GALLIUM 1332
GENERATION 849
1229
HEAT 1332
IMPERFECTION 1229
INFRARED 1482
LENGTH 1219
LIFETIME "
1332
MINORITY 849
973
1219
1229
MOS 849
1219
PHOSPHORUS 1332
PHOTOLUMINESCENCE "
PHOTOVOLTAGE 973
REFLECTIVITY 1482
SEMICONDUCTOR "
SILICON 849
973
1219
1229
SILICON DOPED 1482
SOLAR CELL 973
STEADY STATE 1219
SURFACE 973
WAFER 1229
ZINC OXIDE 1332

CARRIER MOBILITY
ANOMALOUS ->1212
DISTRIBUTION "
GERMANIUM "
HALL "
IMPURITY "
INHOMOGENEITY "
METHOD "
MOBILITY "
RADIAL "
SEMICONDUCTOR "
VANDERPAUW "

PRIMARY TERM / CO-TERM — PAGE NO.

CATALYSIS
ANODE FILM - - ->1186
ELLIPSOMETRY - - "
EVOLUTION - - - - "
GALVANOSTATIC - - "
OXYGEN - - - - - "
PLATINUM - - - - "
REACTION - - - - "
SULFURIC ACID - - "
THICKNESS - - - - "

CATALYST
ANODE - - - - - ->1264
DIELECTRIC - - -> 738
ELECTROLESS - - ->1461
ELECTRON MICROSC. 738
FUEL CELL - - - - 1264
HYDRAZINE - - - - "
INHIBITION - - - 1461
MIXED - - - - - - 738
NICKEL BORIDE - - 1264
PALLADIUM CHLORI. 738
PLASTICS - - - - 1461
PLATING - - - - - 738
- - - - - 1461
STANNOUS CHLORIDE 738
SUBSTRATE - - - - "
- - - - 1264
ULTRA VIOLET - - 1461

CATALYZE
COMPOUND - - - ->1115
CRISTOBALITE - - "
CRYSTALLIZATION - "
PHOSPHOSILICATE - "
QUARTZ - - - - - "
SILICON DIOXIDE - "
THIN FILM - - - - "

CATHODE
AC - - - - - - -> 375
AGENT - - - - - ->1013
ALKALINE - - - - 375
BATTERY - - - - -> 656
BATTERY CELL - -> 1
BEHAVIOR - - - - 656
BETA ALUMINA - - 1
CARBONATE - - - - 656
CHELATING - - - - 1013
COEFFICIENT - - -> 867
CONDUCTIVITY - - 375
CONVECTION - - - 867
COPPER - - - - - 656
COVERAGE - - - - 1013
DC - - - - - - - 375
DISCHARGED - - - "
ELECTROWINNING - 867
FORCED - - - - - "
GALVANIC CELL - - 1
IMPEDANCE - - - - 375
IONIC CONDUCTANC. "
IRON - - - - - - 1013
IRON DOPED - - - 1
IRON OXIDE - - -> 42
IRON SPINEL - - - 1
LECLANCHE CELL - 375
LITHIUM CELLS - - 656
MANGANESE - - - - "
MANGANESE DIOXIDE 375
MASS - - - - - - 867
MEASUREMENT - - - 375
MERCURY OXIDE - - "
MODEL CELL - - - 867
MOLYBDENUM - - - 656
MOSS BAUER - - - 1
NATURAL - - - - - 867
PASSIVATED - - - 1013
PLATINUM - - - - 42
POTENTIAL - - - - 1013
PROPYLENE - - - - 656
PULSING - - - - - 1013
REDUCTION - - - - 42
RESISTANCE - - - 375
SPECTROSCOPY - - 1
TETRAHYDROFURAN - 656
THIN FILM - - - - 42
TRANSFER - - - - 867
UNDISCHARGED - - 375

CATHODOCHROMICS
METHOD - - - - -> 815
PHOTOCHROMICS - - "
SODALITE - - - - "
STRUCTURE CONVER. "
SYNTHESIS - - - - "

CATHODOLUMINESCE.
ARRANGEMENT - - -> 894
CRT - - - - - - - "
DISTRIBUTION - - "
PARTICLE - - - - "
PHOSPHOR - - - - "
SIZE - - - - - - "
TELEVISION - - - "

CATION RADICAL
AMINES - - - - -> 378
HOFMANN LOEFFLER "
OXIDATION - - - - "
SECONDARY - - - - "

CELL
ALCOHOLS - - - ->1048
BATTERY - - - - -> 175
CADMIUM - - - - - "
CHARGE ACCEPTANCE "
COMPUTER - - - - "
CONTROLLED - - - "
ELECTROCHEMISTRY 1048
ELECTRODE - - - - "
HEXANOL - - - - - "
HYDROGEN - - - - "
MERCURY - - - - - 175
NICKEL - - - - - "
NORMAL - - - - - 1048
PULSE CHARGING - 175
THALLIUM - - - - 1048

CERAMIC OXIDE
BERYLLIA - - - ->1240
CRYSTAL - - - - - "
DAMAGE - - - - - "
GARNET - - - - - "
HARDNESS - - - - "
POLISHING - - - - "
PREPARATION - - - "
SAPPHIRE - - - - "
SPINEL - - - - - "
SURFACE - - - - - "

CERIUM CHLORIDE
ALKALI CHLORIDE -> 991
EMF - - - - - - - "
MEASUREMENT - - - "
MIXTURE - - - - - "
MOLTEN SALT - - - "
NUMBERS - - - - - "
TRANSFERENCE - - "

CERIUM DIOXIDE
BEHAVIOR - - - -> 122
CALCIUM DOPED - - "
COMMENTS - - - ->1676
COMPOSITION - - -> 126
COMPOSITIONAL - - 1676
CONDUCTIVITY - - 126
- - ->1198
- - 1676
DEPENDENCE - - - 126
- - - 1198
- - - 1676
DIELECTRIC - - - 122
ELECTRICAL - - - 1676
ELECTRON MOBILITY 126
HIGH TEMPERATURE 122
IONIC - - - - - - 1198
LUMINESCENCE - - 1676
NONSTOICHIOMETRIC 126
1198
NUMBER - - - - - "
OXYGEN - - - - - "
PRESSURE - - - - "
QUENCHING - - - - 1676
TEMPERATURE - - - 126
- - - 1198
- - - 1676
THEORY - - - - - "
THERMAL - - - - - "
TRANSFERENCE - - 1198

CESIUM
ELECTRODE - - - -> 727
ELECTROLYTE - - - "
HYDROXIDE - - - - "
REDUCTION - - - - "
SILVER OXIDE - - "
STRUCTURE - - - - "

CESIUM CHLORIDE
FORMATION CELL -> 104
MOLTEN SALT - - - "
NICKEL CHLORIDE - "

CESIUM HYDROXIDE
MICROSCOPY - - -> 17
PARTICLE SIZE - - "
POTASSIUM HYDROX. "
SILVER OXIDE - - "
STRUCTURE - - - - "

CHALCOGENIDE
ARSENIC - - - - -> 363
COPPER SULFIDE - "
GAS SENSOR - - ->1575
GLASS ELECTRODE - 363
- 1575
NITROGEN DIOXIDE "
SINNERITE - - - - 363

CHALCOGENIDES
ANTIMONY - - - ->1523
DOPING - - - - - "
INFRARED DEVICE - "
JUNCTION - - - - "
LEAD - - - - - - "
TELLURIDE - - - - "
TERNARIES - - - - "
TIN - - - - - - - "

CHANNELING
ELECTRON MICROSC.>1657
GALLIUM - - - - - "
INDIUM - - - - - "
MICROPROBE - - - "
PATTERN - - - - - "
PHOSPHIDE - - - - "
SCANNING - - - - "

CHARACTERISTIC
ANODE DISINTEGR.> 7
ANODE DISSOLUTION "
ANOMALOUS VALENCY "
BERYLLIUM - - - - "
ELECTRON - - - - "
MICROSCOPE - - - "
NONAQUEOUS - - - "
POLARIZATION - - "
SCANNING - - - - "
SOLUTION - - - - "

CHARACTERISTICS
ANODE DISINTEGRA.>1604
BERYLLIUM - - - - "
NONAQUEOUS - - - "
POLARIZATION - - "
SOLUTION - - - - "

CHARACTERIZATION
ALLOY - - - - - -> 416
AMMONOLYSIS - - -> 159
ARSINE - - - - ->1642
CHEMICAL - - - - "
CONTACT ANGLE - -> 669
CRYSTAL GROWTH - 159
GAAS - - - - - - 416
GALLIUM - - - - - 159
GALLIUM ARSENIDE 1642
GALLIUM NITRIDE - 159
GROWTH - - - - - 416
- - - - - 1642
HETEROEPITAXY - - "
HETEROJUNCTION - 416
INDIUM ARSENIDE - 1642
LATTICE MATCH - - 416
LPE - - - - - - - "
MEASUREMENT - - - 669
SAPPHIRE - - - - 159
SEMICONDUCTOR - - "
SILICON DIOXIDE - 669
SURFACE - - - - - "
THERMAL - - - - - "
TRIETHYLINDIUM - 1642
VAPOR DEPOSITION "

CHARGE
DENSITY - - - - -> 591
DIELECTRIC - - - "
- - -> 907
ELECTRET - - - - 591
FEP - - - - - - - "
GATE - - - - - - 907
HOMOCHARGE - - - 591
INSERT - - - - - "
INSULATOR - - - - 907
NITRIDE - - - - - "
OXIDE - - - - - - "
SILICON - - - - - "
SPRAY - - - - - - 591
STABILITY - - - - 907
SURFACE - - - - - 591

CHARGE (CONTD)
TEFLON - - - - - 591
THERMOELECTRET - "

CHARGE ACCEPTANCE
BATTERY - - - - -> 175
CADMIUM - - - - - "
CELL - - - - - - "
COMPUTER - - - - "
CONTROLLED - - - "
MERCURY - - - - - "
NICKEL - - - - - "
PULSE CHARGING - "

CHARGE MOTION
ALUMINUM OXIDE -> 700
CONTAMINATION - - "
POLARIZATION - - "
SILICON DIOXIDE - "
SODIUM - - - - - "

CHARGER
CONTROLLER - - ->1134
ELECTROCHEMISTRY "
HIGH POWER - - - "
PROPULSION - - - "
SIMULATOR - - - - "
SUPPLY - - - - - "

CHARGING
ANODE OXIDATION -> 757
DIMETHYLANILINE - "
DISCHARGING - - - "
ELECTRODE - - - - "
MORPHOLOGY - - - "
SILVER - - - - - "
SILVER CHLORIDE - "
SURFACE - - - - - "

CHELATING
AGENT - - - - - ->1013
CATHODE - - - - - "
COVERAGE - - - - "
IRON - - - - - - "
PASSIVATED - - - "
POTENTIAL - - - - "
PULSING - - - - - "

CHEMICAL
AMMONIUM - - - ->1215
ARSINE - - - - ->1642
- - - - ->1646
BANDGAP - - - - ->1673
BIPOLAR - - - - - 1215
BORIDES - - - - -> 846
BORON - - - - - - "
CHARACTERIZATION 1642
COMPOUND - - - - 1673
CRYSTAL - - - - - "
DEPOSITION - - -> 298
ELECTRICAL - - - 1646
ELEMENTAL - - - - 846
ETCHANT - - - - - 1215
FET - - - - - - ->1103
GALLIUM ARSENIDE 1215
1642
1646
GERMANIUM - - - - 1673
GROWTH - - - - - 1642
HETEROEPITAXY - - "
- - - 1646
HYDROGEN PEROXIDE 1215
HYDROXIDE - - - - "
INDIUM ARSENIDE - 1642
- 1646
METALLIZATION - - 298
MODIFICATION - - 846
MOS - - - - - - - 1103
NITRIDE - - - - - 1673
NONMETAL - - - - 846
PROPERTIES - - - 1646
- - - 1673
REMOVAL - - - - - 1215
SELECTIVE - - - - "
SEMICONDUCTOR - - 298
SILICON DIOXIDE - 1103
- 1215
STRUCTURE - - - - 846
- - - - 1673
SYNTHESIS - - - - "
TERNARY - - - - - "
TETRAGONAL - - - 846
THIN FILM - - - - 1103
TRANSISTOR - - - 1215
TRIETHYLINDIUM - 1642
- 1646
TUNGSTEN - - - - 298

PRIMARY TERM / CO-TERM — PAGE NO.

CHEMICAL (CONTD)
VAPOR - - - - - - 298
VAPOR DEPOSITION 846
1103
1642
1646
1673
ZINC - - - - - - - "

CHEMILUMINESCENCE
ELECTROANALYSIS ->1178
ELECTROGENERATE - "
ENERGY DEFICIENT "
LUMINESCENCE - - "
NONAQUEOUS - - - "
SOLVENT - - - - - "
VOLTAMMETRY - - - "

CHEMISORPTION
BEHAVIOR - - - -> 163
DIELECTRIC - - - "
DIFFUSION - - - - "
DOPING - - - - - "
HIGH TEMPERATURE "
LITHIUM - - - - - "
POLYCRYSTALLINE - "
SODIUM - - - - - "
ZINC OXIDE - - - "

CHEMOMECHANICAL
CADMIUM SULFIDE ->1064
POLISHING - - - - "

CHLORALKALI CELL
ACTIVE - - - - -> 220
BRINE LEVEL - - ->1286
CHLORINE - - - - 220
CONSUMPTION - - - "
CORROSION - - - - "
GAS LIFT - - - - 1286
GRAPHITE ANODE - 220
MERCURY TYPE - - 1286
PH - - - - - - - 220
PUMP - - - - - - 1286
SCALE UP - - - - "
VOLTAGE - - - - - "

CHLORATE
BIPOLAR - - - - -> 648
ELECTROLYSIS - - "
ELECTROLYZER - - "
PARASITE CURRENT "

CHLORATE CELL
CHLORINE - - - -> 70
CURRENT - - - - - "
- - - - ->1606
CURRENT DENSITY - 70
- 1606
EFFECT - - - - - 70
- - - - - 1606
EFFICIENCY - - - 70
- - - 1606
ELECTROCRYSTALLI. "
HYDRODYNAMIC - - 70
MECHANISM - - - - 1606
MUTUAL - - - - - 70
PH - - - - - - - "
- - - - - - - 1606
PROCESS - - - - - "
SILVER ELECTRODE "
TEMPERATURE - - - 70
- - - 1606

CHLORIDE
ACIDIC - - - - ->1141
ALKALI METAL - -> 994
ALKALINE - - - -> 605
ALLOY - - - - - ->1245
ALUMINUM - - - -> 268
- - - - 1245
- - - ->1271
ALUMINUM CHLORIDE 994
ANODE - - - - - - 1141
- - - - - - 1271
ANODE DISSOLUTION 605
ANODE FILM - - - 268
BATTERY - - - - - 1245
BENZOTRIAZOLE - - 605
BUFFER - - - - - 1245
CARBONATE - - - - 994
CHROMATE - - - ->1007
COEFFICIENT - - - 994
COLD - - - - - - 1141
CONDUCTANCE - - ->1298
CORROSION - - - - 605
CREVICES - - - - 1007

CHLORIDE (CONTD)
CURRENT DENSITY - 994
DENSITY - - - - - 1298
ELECTROCHEMISTRY 1007
ELECTRODE - - - - 994
ELECTRON - - - - 268
EMF - - - - - - - 1245
EXCHANGE - - - - 994
GRAIN - - - - - - 1141
GROWTH - - - - - 268
HIGH PRESSURE - - 1245
INHIBITION - - - 605
ION - - - - - - - 1007
IRON - - - - - - 605
- - - - - - 1007
KINETICS - - - - 994
LITHIUM - - - - - 1298
MAGNESIUM - - - - 1245
MANGANESE - - - - 1298
MELT - - - - - - "
MICROSCOPY - - - 1141
NICKEL - - - - - "
NITRATE - - - - - 1271
OPACITY - - - - - 268
OXYGEN - - - - - 1007
PITTING - - - - - 268
- - - - - 1271
POLARIZATION - - 1007
- - 1141
POTASSIUM - - - - 1298
POTENTIOSTATIC - 1141
PROPYLENE - - - - 994
REDUCTION - - - - 1007
RUBIDIUM - - - - 1298
SEAWATER - - - - 1245
SIZE - - - - - - 1141
SODIUM - - - - - 1298
SOLUTION - - - - 605
- - - - 1271
STRAINING - - - - "
TRANSFER - - - - 994
WORK - - - - - - 1141

CHLORIDE SOLUTION
ANODE - - - - - ->1276
BENZOTRIAZOLE - - "
CORROSION - - - - "
ELECTRODISSOLUTI. "
INHIBITION - - - "
IRON - - - - - - "
NEUTRAL SOLUTION "

CHLORINE
ACTIVE - - - - -> 220
ADSORPTION - - -> 848
AUGER - - - - - -> 34
CHLORALKALI CELL 220
CHLORATE CELL - -> 70
COMPOSITION - - - 34
CONSUMPTION - - - 220
CORROSION - - - - "
CURRENT - - - - - 70
CURRENT DENSITY - "
DECOMPOSITION - -> 919
DEPOSITION - - - "
EFFECT - - - - - 70
EFFICIENCY - - - "
EQUILIBRIUM - - - 919
GRAPHITE ANODE - 220
HIGH TEMPERATURE 919
HYDRODYNAMIC - - 70
HYDROGEN - - - - 919
MUTUAL - - - - - 70
OXYGEN - - - - - 34
PH - - - - - - - 70
- - - - - - - 220
PLATINUM ANODE - 34
REACTION - - - - 919
REDUCTION - - - - "
SILICON - - - - - "
SPECTROSCOPY - - 34
SURFACE - - - - - "
- - - - - 848
TEMPERATURE - - - 70
TITANIUM - - - - 848

CHLORINE ELECTRO.
ANODE - - - - - -> 749
CARBON - - - - - "
CARBON OXIDE - ->1289
GLASSLIKE - - - - 749
GRAPHITE - - - - "
GRAPHITE ANODE - 1289
OXYGEN ELECTRODE 749
PYROLYSIS - - - - "
SURFACE OXIDE - - "
TAFEL - - - - - - 1289

CHLOROALUMINATE
ALUMINUM - - - -> 773
CHRONOPOTENTIOME. "
HALIDES - - - - - "
MELT - - - - - - "
MOLTEN - - - - - "
OXIDATION - - - - "

CHLOROSTILBENES
IMAGING - - - - ->1667
IRRADIATION - - - "
LIQUID CRYSTAL - "
NEMATIC - - - - - "
STILBENES - - - - "
ULTRAVIOLET - - - "

CHROMATE
ANODE - - - - - ->1146
CHLORIDE - - - ->1007
CORROSION - - - - 1146
CREVICES - - - - 1007
ELECTROCHEMISTRY "
ELLIPSOMETRY - - 1146
FILM - - - - - - "
INHIBITOR - - - - "
ION - - - - - - - 1007
IRON - - - - - - "
- - - - - - 1146
OPEN CIRCUIT - - "
OXYGEN - - - - - 1007
PASSIVITY - - - - 1146
POLARIZATION - - 1007
POTENTIAL - - - - 1146
REDUCTION - - - - 1007

CHROME COATING
DELAMINATION - -> 29
LACQUER FILM - - "
ORGANIC - - - - - "
STEEL - - - - - - "
UNDERCUTTING - - "

CHROMIUM
ACTIVITY - - - -> 543
CHROMIUM OXIDE -> 952
COBALT - - - - -> 225
CORROSION - - - - "
- - - ->1192
EVOLUTION - - - - 225
HYDROGEN - - - - "
IRON - - - - - - 1192
MANGANESE - - - - 225
METAL - - - - - - 543
MOLYBDENUM - - - 1192
NICKEL - - - - - 543
OXIDATION - - - - 952
OXYGEN - - - - - 543
OXYGEN ATOMS - - 952
PITTING - - - - - 1192
RESISTANCE - - - "
STAINLESS STEEL - "
SYSTEM - - - - - 543
TEMPERATURE - - - 1192
VANADIUM - - - - 225
VAPORIZATION - - 952

CHROMIUM OXIDE
CHROMIUM - - - -> 952
FORMATION - - - -> 711
FREE ENERGY - - - "
OXIDATION - - - -> 945
- - - - 952
OXYGEN - - - - - 945
OXYGEN ATOMS - - 952
SOLID ELECTROLYTE 711
VAPORIZATION - - 945
- - 952

CHRONOCOULOMETRY
ADSORPTION - - ->1421
ELECTRODE - - - - "
MERCURY - - - - - "
RHODIUM - - - - - "
VOLTAMMETRY - - - "

CHRONOPOTENTIOME.
ALUMINUM - - - -> 773
BERYLLIUM - - - ->1429
CHLOROALUMINATE - 773
COUPLING - - - -> 769
CURRENT REVERSAL "
DEPENDENCE - - - 1429
DEPLETION - - - - "
ELECTROHYDRODIME. 769
ELECTROLYTE - - - "
ELECTROMIGRATION 1429
FLOURIDES - - - - "

CHRONOPOTENTIOME. (CONTD)
GLASSES - - - - - 1429
HALIDES - - - - - 773
KETONES - - - - - 769
LITHIUM - - - - - 1429
MELT - - - - - - 773
MOLTEN - - - - - "
MOLTEN HALIDES - 1429
OXIDATION - - - - 773
REDUCTIVE - - - - 769
TEMPERATURE - - - 1429
UNSATURATED - - - 769

CIRCUIT
APPLICATION - - -> 422
BEAM - - - - - -> 62
CARBON - - - - -> 146
CONTAMINATION - - "
DEVICE - - - - - 422
DOPING - - - - - 146
ELECTRODE - - - ->1439
ELECTROLESS - - - 62
EPITAXIAL - - - - 422
EQUIVALENT - - - 1439
GOLD - - - - - - 62
INTEGRATED - - - 146
- - - 422
LEAD - - - - - - 62
MEASUREMENT - - - 422
OHMIC COUPLING - 1439
PLATING - - - - - 62
PSEUDOCOLLECTION 1439
RESIDUE - - - - - 146
RESISTANCE - - - 422
- - - 1439
RESISTIVITY - - - 422
RING DISK - - - - 1439
SILICON - - - - - 62
- - - - - 146
- - - - - 422
SPREADING - - - - "
SURFACE - - - - - 146

CLEANING
AUGER - - - - - -> 310
ELECTRON SPECTRO. "
GERMANIUM - - - - "
SURFACE - - - - - "

CLOSELY
GAP - - - - - - - ->1124
METALLIZATION - - "
PATTERN - - - - - "
SELF ALIGNED - - "
SPACED - - - - - "

CLUSTER
CRISTOBALITE - ->1090
HETEROGENEOUS - - "
OXYGEN - - - - - "
PRECIPITATION - - "
SILICON - - - - - "
SILICON OXIDES - "
VACANCY - - - - - "

COATING
ALLOY - - - - - -> 800
- - - - - ->1051
ALUMINIDE - - - - "
ALUMINUM - - - - 800
CRT - - - - - - - -> 720
DEGRADATION - - - 800
DEPLETION - - - - "
DEVICE - - - - - 720
DIFFUSION - - - - 800
- - - - 1051
ELECTRON - - - - 720
GRAPHITE SILICATE "
KINETICS - - - - 1051
NICKEL - - - - - 800
- - - - - 1051
OXIDATION - - - - 800
PACK - - - - - - 1051
PENETRATION - - - 720
PROTECTIVE - - - 1051
SPALLING - - - - 800
SUPERALLOY - - - "
THERMODYNAMICS - 1051
THICKNESS - - - - 720

COBALT
ACID BATH - - - ->1023
AMINE - - - - - - "
BORANE - - - - - "
CHROMIUM - - - -> 225
CORROSION - - - - "
DEPOSITION - - - 1023

PRIMARY TERM / CO-TERM — PAGE NO.

COBALT (CONTD)
ELECTROLESS - - - 1023
EVOLUTION - - - - 225
HYDROGEN - - - - "
HYPOPHOSPHITE - - 1023
MANGANESE - - - - 225
NICKEL - - - - - 1023
PLATING - - - - - "
VANADIUM - - - - 225

COBALT IRON
ALLOY - - - - - -> 538
- - - - - -> 889
ATMOSPHERE - - - "
COBALTOUS IRON - 538
DIFFUSION - - - - "
GROWTH - - - - - "
HYDROGEN SULFIDE 889
KINETICS - - - - "
OXIDE - - - - - - 538
PARABOLIC - - - - 889
SULFIDATION - - - "

COBALT RHENIUM
ALLOY - - - - - -> 776
AMORPHOUS - - - - "
ELECTRODEPOSITION "

COBALTOUS IRON
ALLOY - - - - - -> 538
COBALT IRON - - - "
DIFFUSION - - - - "
GROWTH - - - - - "
OXIDE - - - - - - "

COEFFICIENT
ACTIVITY - - - -> 884
AGENT - - - - - -> 779
ALKALI METAL - -> 994
ALUMINUM CHLORIDE "
AMALGAMS - - - - 884
AMMONIA - - - - -> 230
CARBONATE - - - - 994
CATHODE - - - - -> 867
CHLORIDE - - - - 994
CONVECTION - - - 867
COPPER FLUOROBOR. 779
COPPER SULFATE - "
CRYSTAL GROWTH -> 556
CURRENT DENSITY - 994
DIFFUSION - - - - 556
- - - - 779
DILUTE - - - - - 884
ELECTRODE - - - - 994
ELECTROLYTE - - - 779
ELECTROWINNING - 867
EVOLUTION - - - - 230
EXCHANGE - - - - 994
EXCHANGE CURRENT 230
FORCED - - - - - 867
GALLIUM - - - - - 556
HYDROGEN - - - - 230
KINETIC - - - - - 779
KINETICS - - - - 994
LIQUID - - - - - 230
MASS - - - - - - 867
MELT - - - - - - 556
MODEL CELL - - - 867
NATURAL - - - - - "
NITROGEN - - - - 230
ORGANIC - - - - - 779
OVERVOLTAGE - - - 230
PARAMETER - - - - 779
PHOSPHIDE - - - - 556
PHOSPHORUS - - - "
POTENTIAL - - - - 884
PROPYLENE - - - - 994
STANDARD - - - - 884
TAFEL SLOPE - - - 230
THALLIUM - - - - 884
TRANSFER - - - - 230
- - - - 867
- - - - 994

COLD
ACIDIC - - - - ->1141
ANODE - - - - - - "
CHLORIDE - - - - "
GRAIN - - - - - - "
MICROSCOPY - - - "
NICKEL - - - - - "
POLARIZATION - - "
POTENTIOSTATIC - "
SIZE - - - - - - "
WORK - - - - - - "

COLOR RENDITION
DISTRIBUTION - -> 407
LAMPS - - - - - - "
MERCURY VAPOR - - "
OPTIMIZED - - - - "
PHOSPHORS - - - - "
POWER - - - - - - "
SPECTRAL - - - - - "

COLORED FILMS
COMPOUND - - - ->1555
INSOLUBLE - - - - "
RADICAL - - - - - "
VIOLOGEN - - - - "

COMMENTS
CERIUM DIOXIDE ->1676
COMPOSITIONAL - - "
CONDUCTIVITY - - "
DEPENDENCE - - - "
ELECTRICAL - - - "
LUMINESCENCE - - "
QUENCHING - - - - "
TEMPERATURE - - - "
THEORY - - - - - "
THERMAL - - - - - "

COMPARISON
AMALGAM - - - - -> 343
CRUSHED - - - - - "
DECOMPOSITION - - "
GRAPHITE BED - - "
SODIUM HYDROXIDE "
TOWER - - - - - - "

COMPLEMENT
BOUNDARY - - - -> 313
CONDITION - - - - "
DIFFUSION - - - - "
EQUATION - - - - "
ERROR - - - - - - "
FLUX STEP - - - - "
FUNCTION - - - - "
PROFILE - - - - - "
SEMICONDUCTOR - - "

COMPLEMENTARY
BIPOLAR - - - - ->1119
DEVICE - - - - - "
INTEGRATION - - - "
ISOLATED - - - - "
MONOLITHIC - - - "
MOS - - - - - - - "
SEMICONDUCTOR - - "
TRANSISTOR - - - "

COMPONENT
CONVECTIVE - - ->1000
CORROSION - - - - "
CRACK - - - - - - "
DIFFUSION - - - - "
MASS TRANSFER - - "
MINOR - - - - - - "
MOLTEN SALT - - - "
PROPAGATING - - - "

COMPOSITE
ALUMINUM OXIDE ->1019
ANODE OXIDE - - - "
ANTHRACENE - - ->1341
CONVERSION - - - "
FILM - - - - - - 1019
GRAVIMETRY - - - "
HYDROUS - - - - - "
LEAD CHLORIDE - - 1341
LIGHT - - - - - - "
LUMINESCENCE - - "
PSEUDOBOEHMITE - 1019
RADIOTRACER - - - "
VISIBLE - - - - - 1341
X RAY - - - - - - "

COMPOSITION
AUGER - - - - - -> 34
BASIC - - - - - -> 253
CERIUM DIOXIDE -> 126
CHLORINE - - - - 34
CONDUCTIVITY - - 126
DEPENDENCE - - - "
ELECTRON MOBILITY "
LEAD CARBONATE - 253
LEAD OXIDE - - - "
LEAD SULFATE - - "
NONSTOICHIOMETRIC 126
OXYGEN - - - - - 34
PLATINUM ANODE - "
SPECTROSCOPY - - "

COMPOSITION (CONTD)
SURFACE - - - - - 34
TEMPERATURE - - - 126
VARIABLE - - - - 253

COMPOSITIONAL
CERIUM DIOXIDE ->1676
COMMENTS - - - - "
CONDUCTIVITY - - "
DEPENDENCE - - - "
ELECTRICAL - - - "
LUMINESCENCE - - "
QUENCHING - - - - "
TEMPERATURE - - - "
THEORY - - - - - "
THERMAL - - - - - "

COMPOUND
ABSORPTION - - -> 586
ANODE OXIDATION -> 820
->1665
AQUEOUS - - - - - "
ARSENIC - - - - ->1634
BANDGAP - - - - ->1673
BENZENES - - - -> 516
CATALYZE - - - ->1115
CHEMICAL - - - - 1673
COLORED FILMS - ->1555
CONDUCTIVITY - - 586
CRISTOBALITE - - 1115
CRYSTAL - - - - - 1673
CRYSTALLIZATION - 1115
DEVICE - - - - - 820
DIFFUSION - - - - "
DOPING - - - - - 1634
ELECTRIC - - - - 586
ELECTROOPTICAL - 820
FORMATION - - - - 586
GALLIUM - - - - - 1634
GALLIUM ARSENIDE 820
GALLIUM PHOSPHIDE 1665
GERMANIUM - - - - 1673
HYDROGEN PEROXIDE 1665
INSOLUBLE - - - - 1555
ION IMPLANTATION 586
ISOTHERMS - - - - 1634
LIQUIDUS - - - - "
NATIVE OXIDE - - 1665
NITRIDE - - - - - 1673
OPTICAL - - - - - 586
PARA DIHALOSUBST. 516
PHOSPHORUS - - - 1634
PHOSPHOSILICATE - 1115
POLAROGRAPHY - - 516
PROPERTIES - - - 1673
QUARTZ - - - - - 1115
RADICAL - - - - - 1555
RELATED - - - - - 516
SEMICONDUCTOR - - 820
- - 1634
SEMICONDUCTORS - 1665
SILICON - - - - - 1634
SILICON CARBIDE - 586
SILICON DIOXIDE - 1115
STRUCTURE - - - - 1673
SYNTHESIS - - - - "
SYSTEM - - - - - 1634
TERNARY - - - - - "
- - - - - 1673
THIN FILM - - - - 1115
VAPOR DEPOSITION 1673
VIOLOGEN - - - - 1555
ZINC - - - - - - 820
- - - - - - 1673

COMPOUNDS
ARSENIC - - - - ->1650
ARSENIDE - - - - "
ASYMMETRIC - - - "
ASYMMETRY - - - - "
CRACKING - - - - "
CROSS HATCH - - - "
ETCH - - - - - - "
GALLIUM - - - - - "
GROUP III-V - - - "
INDIUM - - - - - "
PHOSPHIDE - - - - "
SIRTL - - - - - - "

COMPUTER
BATTERY - - - - -> 175
CADMIUM - - - - - "
CELL - - - - - - "
CHARGE ACCEPTANCE "
CONTROLLED - - - "
MERCURY - - - - - "
NICKEL - - - - - "

COMPUTER (CONTD)
PULSE CHARGING - 175

CONCENTRATE
ALKALI HYDROXIDE >1385
AMALGAMATE - - - "
CORROSION - - - - "
ZINC - - - - - - "
ZINC OXIDE - - - "

CONCENTRATION
ABSORPTION - - -> 434
- - ->1482
ACTIVATION - - - 434
- - -> 459
AMMONIA - - - - - "
ANALYSIS - - - - 434
ANODE OXIDATION -> 195
BUFFERED - - - - "
CARRIER - - - - - 1482
CONVECTIONLESS -> 370
CRYSTAL GROWTH -> 153
DECOMPOSITION - - 459
DEPENDENCE - - -> 132
DEVICE - - - - -> 419
DIFFUSION - - - - 132
DISTRIBUTION - - "
DOPED OXIDE - - - "
DRUDE ZENER - - - 1482
ELECTRON - - - - 459
ENTROPY - - - - - "
FET - - - - - - - 419
GAAS - - - - - - 1482
GALLIUM - - - - - 153
GAP - - - - - - - "
GATE - - - - - - 419
GLASS - - - - - - "
GRADIENTS - - - - 370
HYDROGEN FLUORIDE 195
IMPURITY - - - - 132
INFRARED - - - - 434
- - - - 1482
INTERACTION - - - 434
INTERFACE - - - - 419
INTERFEROMETRY - 370
ION DRIFT - - - - 419
ION IMPLANTATION 195
ION TRAPPING - - 419
LAYER - - - - - - 132
LITHIUM - - - - - 459
MOISTURE - - - - 434
OXIDE - - - - - - 419
OXIDE DISSOLUTION 195
PHOSPHORUS - - - 132
- - - 153
- - - 419
- - - 434
PHOSPHOSILICATE - 419
POLARIZATION - - "
PROFILE - - - - - 195
PSG FILM - - - - 434
REFLECTIVITY - - 1482
RESISTANCE - - - 434
SEMICONDUCTOR - - 1482
SILICON - - - - - 132
SILICON DOPED - - 1482
SILICON OXIDE - - 419
SOLIDUS - - - - - 153
SOLVATED - - - - 459
TANTALUM - - - - 195
TEMPERATURE - - - 132
THICKNESS - - - - 419
THRESHOLD - - - - "
TRANSPORT - - - - 370
VACANCY - - - - - 153
VAPOR DEPOSITION 132
VOLTAGE - - - - - 419
WATER - - - - - - 434
ZINC ANODE - - - 370
ZINC CATHODE - - "

CONDITION
BOUNDARY - - - -> 313
COMPLEMENT - - - "
DIFFUSION - - - - "
EQUATION - - - - "
ERROR - - - - - - "
FLUX STEP - - - - "
FUNCTION - - - - "
PROFILE - - - - - "
SEMICONDUCTOR - - "

CONDUCTANCE
ADSORPTION - - ->1570
AMMONIUM - - - -> 977
BETA ALUMINA - ->1314
BROMIDE - - - - - 977

PRIMARY TERM / CO-TERM	PAGE NO.
CONDUCTANCE (CONTD)	
CHLORIDE	->1298
CURRENT	1314
DENSITY	1298
DIMETHYLFORMAMIDE	977
ELECTRODE	1570
ELECTROLYTE	977
IMPEDANCE	1314
ISOTHIOCYANATE	977
LITHIUM	1298
MANGANESE	"
MEASUREMENT	1570
MELT	1298
NICKEL	977
NONAQUEOUS	"
POTASSIUM	"
	1298
PULSE	1314
RUBIDIUM	1298
SODIUM	"
SOLUTION	977
SURFACE	1570
TETRABUTYL	977
THIN FILM	1570
VISCOSITY	977
CONDUCTION	
BORON ARSENIDE	-> 412
CALCIA STABILIZED	> 793
COULOMETRY	"
DECOMPOSITION	412
HOLE	793
OXYGEN	"
PERMEATION	"
PREPARATION	412
PROPERTY	"
SEMICONDUCTOR	"
SOLID STATE	793
SUBSTRATE	412
TITRATION	793
WUSTITE	"
ZIRCONIA	"
CONDUCTIVITY	
ABSORPTION	-> 586
AC	-> 375
ALKALINE	"
ANION VACANCY	-> 255
ANTI FRENKEL	"
BRONZE	->1530
CATHODE	375
CERIUM DIOXIDE	-> 126
	->1198
	->1676
COMMENTS	"
COMPOSITION	126
COMPOSITIONAL	1676
COMPOUND	586
DC	375
DEFECT STRUCTURE	255
DEPENDENCE	126
	1198
	1676
DIMETHYLFORMAMIDE	> 91
DISCHARGED	375
DISSOCIATION	91
ELECTRIC	586
ELECTRICAL	1676
ELECTRON	255
ELECTRON MOBILITY	126
FORMATION	586
IMPEDANCE	375
ION	255
ION IMPLANTATION	586
IONIC	1198
IONIC CONDUCTANCE	375
LECLANCHE CELL	"
LEWIS ACID	91
LUMINESCENCE	1676
MANGANESE DIOXIDE	375
MEASUREMENT	"
MERCURY OXIDE	"
NONSTOICHIOMETRIC	126
	1198
NUMBER	"
OPTICAL	586
OXYGEN	1198
PRESSURE	"
PROTONIC ACID	91
QUENCHING	1676
RESISTANCE	375
SILICON CARBIDE	586
SODIUM	1530
SODIUM ION	"
TEMPERATURE	126
	1198
	1676

PRIMARY TERM / CO-TERM	PAGE NO.
CONDUCTIVITY (CONTD)	
THEORY	1676
THERMAL	"
TRANSFERENCE	1198
TUNGSTEN	1530
UNDISCHARGED	375
YTTRIA DOPED	255
ZIRCONIUM OXIDE	"
CONSTANT	
ACETONE	->1584
COPPER	-> 887
CORROSION	"
ELECTROLESS	"
FORMATION	1584
MIXED POTENTIAL	887
MIXTURE	1584
PARTIAL PROCESS	887
PLATING	"
PRODUCT	1584
RATE	887
SILVER HALIDES	1584
SOLUBILITY	"
SPECIFIC	887
STANDARD	"
WATER	1584
CONSUMPTION	
ACTIVE	-> 220
CHLORALKALI CELL	"
CHLORINE	"
CORROSION	"
GRAPHITE ANODE	"
PH	"
CONTACT ANGLE	
CHARACTERIZATION	> 669
MEASUREMENT	"
SILICON DIOXIDE	"
SURFACE	"
THERMAL	"
CONTACT PRINT	
ACOUSTIC WAVE	->1503
MASK	"
PHOTO RESIST	"
PHOTOLITHOGRAPHY	"
SUBMICRON LINE	"
CONTAMINANT	
DEPTH PROFILE	->1617
ION	"
MASS SPECTROMETRY	"
MICROCIRCUIT	"
MICROPROBE	"
SECONDARY	"
SILVER CHLORIDE	"
SPUTTERING	"
SURFACE	"
CONTAMINANTS	
DETECTION	-> 172
MEV	"
SCATTERING	"
SENSITIVITY	"
SURFACE ANALYSIS	"
CONTAMINATION	
ACTIVATION	-> 681
ALUMINUM OXIDE	-> 700
BARRIER HEIGHT	->1195
BATTERY	->1045
BORON	-> 593
BREAKDOWN	1195
CARBON	-> 146
CHARGE MOTION	700
CIRCUIT	146
DEFORMATION	681
DEPOSIT	"
DICHLOROSILANE	"
DIELECTRIC	1195
DOPING	146
ELECTROLYTE	1045
FILM	1195
FLUORINE	-> 790
GOLD REFRACTORY	"
INFRARED	1045
INORGANIC	"
INTEGRATED	146
ION	790
LIQUID	1045
LITHIUM	"
LOWERING	1195
METALLIZATION	790
MICROANALYSIS	593
NEUTRON	681
NUCLEAR	593

PRIMARY TERM / CO-TERM	PAGE NO.
CONTAMINATION (CONTD)	
OXYGEN	593
	681
OXYHALIDE	1045
POLARIZATION	700
POLYCRYSTALLINE	681
RESIDUE	146
RETENTION	790
SILICON	146
	790
	1195
SILICON DIOXIDE	700
	1195
SILICON FILM	681
SODIUM	700
	1195
SODIUM INDUCED	"
SOLVENTS	593
SURFACE	146
	593
	790
TRACE ANALYSIS	1045
TRANSISTOR	790
VAPOR	681
WATER	1045
CONTRAST	
DEVELOPER	->1669
DIODE	->1202
ELECTRON BEAM	1669
ELECTRON RESIST	"
FUNCTION	"
GALLIUM NITRIDE	1202
HETEROEXPITAXIAL	"
JUNCTION	"
LIGHT EMISSION	"
LITHOGRAPHY	1669
METHACRYLATE	"
MICROSTRUCTURE	1202
PMMA	1669
POLYMETHYL	"
PROFILE	1202
RATE	1669
SOLUBILITY	"
STRUCTURE	1202
VAPOR DEPOSITION	"
VOLTAGE	"
CONTROL	
ACTIVITY	-> 354
ARGON	->1372
ARGON OXYGEN	354
COULOMETRY	"
CURRENT	-> 523
CVD	->1233
DEPOSITION	"
	->1235
DIFFUSING	1372
DISK ELECTRODE	523
DISTRIBUTION	"
ELECTRODE	354
EQUILIBRIA	1372
ETCHING	"
FILM	1233
	1235
FILM THICKNESS	1233
	1235
GALVANOSTATIC	523
HELIUM	1233
	1372
HEXAFLUORIDE	"
LANGMUIR SHEATH	"
LASER	1233
	1235
MIXTURE	354
NEON	1233
NITRIDE	"
NITROGEN	1372
OXYGEN	354
PENTA FLUORIDE	1372
PLATINUM	354
POLYCRYSTALLINE	1235
POTENTIOSTAT	354
POTENTIOSTATIC	523
RATE	1372
REACTION	"
SHORT TIME	523
SILICON	1233
	1235
SILICON DIOXIDE	1233
TITRATION	354
TUNGSTEN	1372
ZIRCONIA	354
CONTROLLED	
BATTERY	-> 175
CADMIUM	"

PRIMARY TERM / CO-TERM	PAGE NO.
CONTROLLED (CONTD)	
CELL	175
CHARGE ACCEPTANCE	"
COMPUTER	"
MERCURY	"
NICKEL	"
PULSE CHARGING	"
CONTROLLER	
CHARGER	->1134
ELECTROCHEMISTRY	"
HIGH POWER	"
PROPULSION	"
SIMULATOR	"
SUPPLY	"
CONVECTION	
CATHODE	-> 867
COEFFICIENT	"
ELECTROWINNING	"
FORCED	"
MASS	"
MODEL CELL	"
NATURAL	"
TRANSFER	"
CONVECTIONLESS	
CONCENTRATION	-> 370
GRADIENTS	"
INTERFEROMETRY	"
TRANSPORT	"
ZINC ANODE	"
ZINC CATHODE	"
CONVECTIVE	
COMPONENT	->1000
CORROSION	"
CRACK	"
DIFFUSION	"
MASS TRANSFER	"
MINOR	"
MOLTEN SALT	"
PROPAGATING	"
CONVERGING	
BEHAVIOR	-> 448
INDIUM ANTIMONIDE	"
INTERFACE	"
PRESSURE INDUCED	"
SEGREGATION	"
SOLIDIFICATION	"
STATIONARY	"
VERTICAL ZONE	"
CONVERSION	
ANTHRACENE	->1341
COMPOSITE	"
LEAD CHLORIDE	"
LIGHT	"
LUMINESCENCE	"
VISIBLE	"
X RAY	"
COPPER	
ACETONITRILE	-> 851
ALLOY	->1137
ALUMINA	-> 107
ALUMINUM	-> 327
	-> 829
ALUMINUM CHLORIDE	> 212
ALUMINUM SELENIDE	327
BATTERY	-> 656
	851
BEHAVIOR	656
BOND	107
BONDING	"
CAPACITANCE	->1318
CARBONATE	656
CATHODE	"
CONSTANT	-> 887
COPPER CHLORIDE	1318
CORROSION	-> 651
	887
CURRENT	661
	-> "
CURVE	1137
CYCLIC	651
DIFFUSION	1318
DISPLACEMENT	-> 289
DISTRIBUTION	661
	"
DOPING	829
DOUBLE LAYER	1318
ELECTRICAL	829
ELECTRODEPOSIT	-> 202
ELECTRODEPOSITION	661
ELECTROLESS	107

PRIMARY TERM / CO-TERM	PAGE NO.
COPPER (CONTD)	
ELECTROLESS	887
	->1405
ELEVATED	651
EVAPORATION	202
FORMALDEHYDE	1405
FUSED SALT	212
GLASS	1405
GOLD	1318
IMPERFECTION	289
IRON	212
LITHIUM CELLS	656
LITHIUM HYDROXIDE	651
LOW TEMPERATURE	1318
MANGANESE	656
MEASUREMENT	661
MELT	212
METAL ION	"
METALLIZATION	107
MIXED POTENTIAL	887
MOLTEN ALKALI	107
MOLYBDENUM	656
NICKEL	1137
NUCLEATION	202
OPTICAL	829
PARTIAL PROCESS	887
PASSIVITY	1137
PITTING	"
PLATING	887
	1405
POLARIZATION	1137
POLAROGRAPHY	212
POTENTIAL	1137
POTENTIOSTATIC	"
PRINTED CIRCUIT	661
PROPERTIES	829
PROPYLENE	656
RATE	887
REDOX SYSTEM	661
SECONDARY BATTERY	851
SILICON	289
SILVER	212
SINGLE CRYSTAL	202
	1318
SODIUM CHLORIDE	212
	1137
SOLID ELECTROLYTE	1318
SOLID SOLUTION	327
SPECIFIC	887
STANDARD	"
SUBSTRATE	289
SULFIDE	829
SURFACE	107
SYSTEM	212
TEMPERATURE	651
TETRAHYDROFURAN	656
THIN FILM	202
TOPOGRAPHY	289
VOLTAMMETRY	212
	651
WIRE	661
	"
WIRE ELECTRODE	"
X RAY	289
ZINC SELENIDE	327
ZINC SULFIDE	"
COPPER CHLORIDE	
CAPACITANCE	->1318
COPPER	"
DIFFUSION	"
DOUBLE LAYER	"
GOLD	"
LOW TEMPERATURE	"
SINGLE CRYSTAL	"
SOLID ELECTROLYTE	"
COPPER ELECTRODE	
POTENTIAL	-> 18
SINGLE CRYSTAL	"
STANDARD	"
COPPER FLUOROBOR.	
AGENT	-> 779
COEFFICIENT	"
COPPER SULFATE	"
DIFFUSION	"
ELECTROLYTE	"
KINETIC	"
ORGANIC	"
PARAMETER	"
COPPER SULFATE	
AGENT	-> 779
COEFFICIENT	"
COPPER FLUOROBOR.	"
DIFFUSION	"
COPPER SULFATE (CONTD)	
ELECTROLYTE	779
KINETIC	"
ORGANIC	"
PARAMETER	"
COPPER SULFIDE	
ARSENIC	-> 363
CHALCOGENIDE	"
GLASS ELECTRODE	"
SINNERITE	"
CORONA CHARGE	
FIELD EFFECT	-> 452
INTERFACE	"
MODULATE	"
PHOTOLUMINESCENCE	"
SEMICONDUCTOR	"
TRAP	"
ZINC OXIDE	"
CORROSION	
ACCELERATE	-> 778
ACTIVE	-> 220
	-> 531
AERATION	-> 183
ALKALI HYDROXIDE	>1385
ALKALINE	-> 605
ALLOY	->1129
ALUMINUM	-> 583
	1129
AMALGAMATE	1385
ANODE	->1146
	->1276
ANODE DISSOLUTION	605
BATTERY	531
BENZOTRIAZOLE	605
	1276
CAPACITOR	583
CHLORALKALI CELL	220
CHLORIDE	605
CHLORIDE SOLUTION	1276
CHLORINE	220
CHROMATE	1146
CHROMIUM	-> 225
	->1192
COBALT	225
COMPONENT	->1000
CONCENTRATE	1385
CONSTANT	-> 887
CONSUMPTION	220
CONVECTIVE	1000
COPPER	-> 651
	887
CRACK	1000
	->1190
CRACKING	-> 599
CREVICE	778
CYCLIC	651
DIFFERENTIAL	183
DIFFUSION	1800
DISSOLUTION	-> 645
ELECTRODISSOLUTI.	1276
ELECTROLESS	887
ELECTROLYTE	583
ELEVATED	651
ELLIPSOMETRY	1146
ETCHABILITY	583
EUTECTIC	778
EVOLUTION	225
FILM	183
	1146
FORMATION	778
FRACTOGRAPHY	1190
GRAPHITE ANODE	220
GRID	531
HISTOPATHOLOGY	1129
HYDROGEN	225
IMPLANTABLE	1129
INHIBITION	605
	1276
INHIBITOR	1146
INVITRO	1129
INVIVO	"
ION	778
IRON	583
	605
	1146
	1192
	1276
LEAD ACID	531
LEAD ANTIMONY	"
LITHIUM CHLORIDE	778
LITHIUM HYDROXIDE	651
MAGNESIUM	1129
MANGANESE	225
MASS TRANSFER	1000
CORROSION (CONTD)	
MATERIAL	831
METAL	183
MICROSEGREGATION	583
MINOR	1000
MIXED POTENTIAL	887
MOISTNESS	183
MOLTEN SALT	1000
MOLYBDENUM	1192
MONOLAYER	778
MORPHOLOGY	1190
NEUTRAL SOLUTION	1276
NICKEL	778
OPEN CIRCUIT	1146
PALLADIUM	645
PARTIAL PROCESS	887
PASSIVATING	183
PASSIVITY	1146
PH	220
PITTING	778
	1192
PLATING	887
POTASSIUM CHLORI.	778
POTENTIAL	1146
POWER	1129
PRECIPITATION	583
PROPAGATING	1000
PROTECTION	531
RATE	887
REDUCTION	778
REPASSIVATION	599
RESISTANCE	1192
RING DISK	645
SILVER	778
SOLUTION	605
SOURCE	1129
SPECIFIC	887
STAINLESS STEEL	1190
	1192
STANDARD	887
STRESS	1190
STRIATION	"
SULFURIC ACID	"
TEMPERATURE	651
	1192
THICKNESS	183
	531
TITANIUM ALLOY	599
TRANSGRANULAR	1190
TRIBOELLIPSOMETRY	599
TUNNEL	583
VANADIUM	225
VARIABLE	183
VOLTAMMETRY	651
ZINC	1129
	1385
ZINC OXIDE	"
COULOMBIC	
BINARY	-> 500
INTERACTION	"
LITHIUM CHLORIDE	"
MOLTEN SALT	"
POSTASSIUM CHLOR.	"
SURFACE TENSION	"
COULOMETRY	
ACTIVITY	-> 354
ARGON OXYGEN	"
CALCIA STABILIZED>	793
CONDUCTION	"
CONTROL	354
ELECTRODE	"
HOLE	793
MIXTURE	354
OXYGEN	"
	793
PERMEATION	"
PLATINUM	354
POTENTIOSTAT	"
SOLID STATE	793
TITRATION	354
	793
WUSTITE	"
ZIRCONIA	354
	793
COUPLING	
CHRONOPOTENTIOME.>	769
CURRENT REVERSAL	"
DIGITAL	-> 745
ELECTRODE	"
ELECTROHYDRODIME.	769
ELECTROLYTE	"
ELECTROOXIDATION	745
KETONES	769
MECHANISM	745
COUPLING (CONTD)	
REDUCTIVE	769
RING DISK	745
ROTATING	"
SIMULATION	"
UNSATURATED	769
COVERAGE	
AGENT	->1013
CATHODE	"
CHELATING	"
IRON	"
PASSIVATED	"
POTENTIAL	"
PULSING	"
CRACK	
COMPONENT	->1000
CONVECTIVE	"
CORROSION	"
	->1190
DIFFUSION	1000
FRACTOGRAPHY	1190
MASS TRANSFER	1000
MINOR	"
MOLTEN SALT	"
MORPHOLOGY	1190
PROPAGATING	1000
STAINLESS STEEL	1190
STRESS	"
STRIATION	"
SULFURIC ACID	"
TRANSGRANULAR	"
CRACKING	
ARSENIC	->1650
ARSENIDE	"
ASYMMETRIC	"
ASYMMETRY	"
COMPOUNDS	"
CORROSION	-> 599
CROSS HATCH	1650
ETCH	"
GALLIUM	"
GROUP III-V	"
INDIUM	"
PHOSPHIDE	"
REPASSIVATION	599
SIATL	1650
TITANIUM ALLOY	599
TRIBOELLIPSOMETRY	"
CREVICE	
ACCELERATE	-> 778
CORROSION	"
EUTECTIC	"
FORMATION	"
ION	"
LITHIUM CHLORIDE	"
MONOLAYER	"
NICKEL	"
PITTING	"
POTASSIUM CHLORI.	"
REDUCTION	"
SILVER	"
CREVICES	
CHLORIDE	->1007
CHROMATE	"
ELECTROCHEMISTRY	"
ION	"
IRON	"
OXYGEN	"
POLARIZATION	"
REDUCTION	"
CRISTOBALITE	
CATALYZE	->1115
CLUSTER	->1090
COMPOUND	1115
CRYSTALLIZATION	->1081
	1115
DIFFUSION	1081
FILM	"
HETEROGENEOUS	1090
INTERFACE	1081
NETWORK	"
OXYGEN	1090
PHOSPHORUS	1081
PHOSPHOSILICATE	1115
PRECIPITATION	1090
QUARTZ	1115
SILICON	1090
SILICON DIOXIDE	1081
	1115
SILICON OXIDES	1090
THIN FILM	1115

PRIMARY TERM / CO-TERM	PAGE NO.
CRISTOBALITE (CONTD)	
VACANCY	1090
CRITICAL	
DENDRITE	329
GROWTH	"
INDUCTION TIME	"
OVERPOTENTIAL	"
YIELD	"
ZINC	"
CROSS HATCH	
ARSENIC	1650
ARSENIDE	"
ASYMMETRIC	"
ASYMMETRY	"
COMPOUNDS	"
CRACKING	"
ETCH	"
GALLIUM	"
GROUP III-V	"
INDIUM	"
PHOSPHIDE	"
SIRTL	"
CRT	
ARRANGEMENT	894
CATHODOLUMINESCE.	"
COATING	720
DEVICE	"
DISTRIBUTION	894
ELECTRON	720
GRAPHITE SILICATE	"
PARTICLE	894
PENETRATION	720
PHOSPHOR	894
SIZE	"
TELEVISION	"
THICKNESS	720
CRUSHED	
AMALGAM	343
COMPARISON	"
DECOMPOSITION	"
GRAPHITE BED	"
SODIUM HYDROXIDE	"
TOWER	"
CRYSTAL	
ALKALINE	1475
ANALYSIS	1671
BANDGAP	1673
BERYLLIA	1240
CERAMIC OXIDE	"
CHEMICAL	1673
COMPOUND	"
DAMAGE	1240
DEFECT	1085
DIVALENT	1475
EARTH	"
ELECTRON	1454
ETCHING	1085
EUROPIUM	1475
EXISTENCE	1674
GALLIUM	1085
GARNET	1240
GERMANIUM	1673
GROWING	1671
HARDNESS	1240
HEAT	1674
INDIUM	"
LEAD ACID	1454
LEAD SULFATE	"
LUMINESCENCE	1475
MEASUREMENT	1674
MICROSCOPY	1454
MONOSELENIDE	1674
NITRIDE	1673
OPTICAL SPECTRA	1475
PHASE TRANSITION	1674
PHOSPHIDE	1085
POLISHING	1240
PRECIPITATION	1454
PREPARATION	1240
PROPERTIES	1673
SAPPHIRE	1240
SCANNING	1454
SEMICONDUCTOR	1674
SOLUTION	1454
SPECIFIC	1674
SPINEL	1240
STRUCTURE	1454
	1475
	1673
	1674
SULFATES	1475
SURFACE	1240
CRYSTAL (CONTD)	
SYNTHESIS	1673
TERNARY	"
VAPOR DEPOSITION	"
XRAY	1674
ZINC	1673
ZONE LEVELING	1671
ZONE MELTING	"
CRYSTAL DEFECT	
ANODE	280
BIPOLAR	"
DECORATION	"
JUNCTION	"
LEAKAGE	"
NPN	"
TRANSISTOR	"
CRYSTAL DEFECTS	
ASSIGNMENT	170
CRYSTALLOGRAPHY	"
DOMAIN	"
ETCHING	"
FERROELECTRIC	"
GMO	"
SINGLE CRYSTAL	"
CRYSTAL GROWTH	
ACETONE	1563
AMMONOLYSIS	159
ANALYSIS	1366
BETA ALUMINA	596
CADMIUM	1366
CHARACTERIZATION	159
COEFFICIENT	556
CONCENTRATION	153
CZOCHRALSKI	380
	822
DIFFUSION	556
	1237
DISSOLUTION	1563
DISTRIBUTION	1366
DOPED	1237
DOPED GERMANIUM	380
DOPING	1516
DUTERIUM OXIDE	1563
ELECTROLUMINESCE.	1516
ELECTROLYTES	1563
ENCAPSULATION	822
EPITAXY	439
	1237
	1516
EVALUATION	439
FORMAMIDE	1563
GAAS	439
	1237
GALLIUM	153
	159
	556
GALLIUM NITRIDE	159
GALLIUM PHOSPHIDE	822
GAP	153
GAS PHASE	1516
GERMANIUM	1237
HIGH PRESSURE	596
IMAGING	822
INDIUM	835
INSTABILITY	380
LIQUID	439
	822
MELT	556
MEMBRANE	596
MICROWAVE DEVICE	439
MORPHOLOGY	1516
OHM	1237
OSCILLATORY	380
PHASE EQUILIBRIUM	835
PHOSPHIDE	556
	835
PHOSPHORUS	153
	556
	835
POTENTIAL	1563
PRECIPITATION	"
SAPPHIRE	159
SEMICONDUCTOR	"
	1237
SODIUM	596
SOLIDUS	153
STOICHIOMETRY	1516
SUPERCOOLING	380
TELLURIDE	1366
TEMPERATURE	"
TRANSIENT	1563
TRAVELING HEATER	1366
VACANCY	153
VAPOR PHASE	1516
CRYSTAL GROWTH (CONTD)	
VAPOR PRESSURE	835
X RAY	822
ZINC	1237
CRYSTAL QUALITY	
ABSORPTION	1496
KRAMERS KRONIG	"
OPTICAL INTERFER.	"
REFRACTIVE INDEX	"
SILICON FILM	"
THIN FILM	"
CRYSTALLIZATION	
ALUMINUM	1509
CATALYZE	1115
COMPOUND	"
CRISTOBALITE	1081
	1115
DIFFUSION	1081
DOPING	1509
FILM	1081
GALLIUM	1509
INTERFACE	1081
MASKING	1509
NETWORK	1081
OXIDATION	1509
PASSIVATION	"
PHOSPHORUS	1081
	1509
PHOSPHOSILICATE	1115
PLANAR JUNCTION	1509
QUARTZ	1115
SEGREGATION	1509
SILICON DIOXIDE	1081
	1115
THIN FILM	"
CRYSTALLOGRAPHY	
ASSIGNMENT	170
CRYSTAL DEFECTS	"
DOMAIN	"
ETCHING	"
FERROELECTRIC	"
GMO	"
SINGLE CRYSTAL	"
CURRENT	
BETA ALUMINA	1314
BIPOLAR ELECTRODE	622
CHLORATE CELL	70
	1606
CHLORINE	70
CONDUCTANCE	1314
CONTROL	523
COPPER	661
	"
CURRENT	"
	"
CURRENT DENSITY	70
	1606
DIMENSION	95
DISK ELECTRODE	523
DISTRIBUTION	95
	523
	622
	661
	"
	"
	"
	1448
EFFECT	70
	1606
EFFICIENCY	70
	1606
ELECTROCRYSTALLI.	"
ELECTRODE	622
ELECTRODEPOSITION	661
	"
FLOW REACTOR	95
GALVANOSTATIC	523
HYDRODYNAMIC	70
IMPEDANCE	1314
MASS TRANSFER	1448
MEASUREMENT	661
	"
MECHANISM	1606
MUTUAL	70
PACKED BED	95
PH	70
	1606
PLANE	1448
POTENTIAL	622
POTENTIOSTATIC	523
PRINTED CIRCUIT	661
	"
PROCESS	1606
CURRENT (CONTD)	
PULSE	1314
REDOX SYSTEM	661
	"
RESISTIVE	622
ROTATING DISK	1448
SHORT TIME	523
SILVER ELECTRODE	1606
TEMPERATURE	70
	1606
WIRE	661
	"
	"
	"
WIRE ELECTRODE	622
	661
	"
CURRENT DENSITY	
ALKALI METAL	994
ALUMINUM CHLORIDE	"
CARBONATE	"
CHLORATE CELL	70
	1606
CHLORIDE	994
CHLORINE	70
COEFFICIENT	994
CURRENT	70
	1606
EFFECT	70
	1606
EFFICIENCY	70
	1606
ELECTROCRYSTALLI.	"
ELECTRODE	994
EXCHANGE	"
HYDRODYNAMIC	70
KINETICS	994
MECHANISM	1606
MUTUAL	70
PH	"
	1606
PROCESS	"
PROPYLENE	994
SILVER ELECTRODE	1606
TEMPERATURE	70
	1606
TRANSFER	994
CURRENT DISTRIBU.	
LIMITING CURRENT	241
MASS TRANSFER	"
ROTATING	"
SPHERE	"
CURRENT POTENTIAL	
DISK	1558
ELECTRODE	"
MASS TRANSFER	"
MODULATION	"
ROTATING	"
SINUSOIDAL	"
CURRENT REVERSAL	
CHRONOPOTENTIOME.	769
COUPLING	"
ELECTROHYDRODIME.	"
ELECTROLYTE	"
KETONES	"
REDUCTIVE	"
UNSATURATED	"
CURVE	
ALLOY	1137
COPPER	"
NICKEL	"
PASSIVITY	"
PITTING	"
POLARIZATION	"
POTENTIAL	"
POTENTIOSTATIC	"
SODIUM CHLORIDE	"
CVD	
BOAT	1112
CONTROL	1233
DEPOSITION	"
FILM	"
FILM THICKNESS	"
HELIUM	"
LASER	"
NEON	"
NITRIDE	"
PREPARATION	1112
PROPERTY	"
QUARTZ	"
REDUCTION	"

PRIMARY TERM / CO-TERM — PAGE NO.

CVD (CONTD)
SEMICONDUCTOR - - 1112
SILICON - - - - - "
- - - - - 1233
SILICON DIOXIDE - "
TRICHLOROSILANE - 1112
TUBE - - - - - - "

CYCLE
BATTERY FAILURE ->1546
CAPACITY - - - - "
DECOMPOSITION - - "
ELECTRODE - - - - "
FORM - - - - - - "
LEAD DIOXIDE - - "
MECHANISM - - - - "
THERMAL ANALYSIS "

CYCLIC
COPPER - - - - -> 651
CORROSION - - - - "
DISSOLUTION - - -> 360
ELECTRODE - - - - "
ELEVATED - - - - 651
LITHIUM HYDROXIDE "
MECHANISM - - - - 360
PLATINUM - - - - "
POTENTIAL - - - - "
PROGRAM - - - - - "
REDEPOSITION - - "
RING DISK - - - - "
ROUGHENING - - - "
TEMPERATURE - - - 651
VOLTAMMETRY - - - "

CZOCHRALSKI
CRYSTAL GROWTH -> 380
-> 822
DOPED GERMANIUM - 380
ENCAPSULATION - - 822
GALLIUM PHOSPHIDE "
IMAGING - - - - - "
INSTABILITY - - - 380
LIQUID - - - - - 822
OSCILLATORY - - - 380
SUPERCOOLING - - "
X RAY - - - - - - 822

DAMAGE
BERYLLIA - - - ->1240
CERAMIC OXIDE - - "
CRYSTAL - - - - - "
GARNET - - - - - "
HARDNESS - - - - "
POLISHING - - - - "
PREPARATION - - - "
SAPPHIRE - - - - "
SPINEL - - - - - "
SURFACE - - - - - "

DC
AC - - - - - - - -> 375
ALKALINE - - - - "
CATHODE - - - - - "
CONDUCTIVITY - - "
DISCHARGED - - - "
IMPEDANCE - - - - "
IONIC CONDUCTANC. "
LECLANCHE CELL - "
MANGANESE DIOXIDE "
MEASUREMENT - - - "
MERCURY OXIDE - - "
RESISTANCE - - - "
UNDISCHARGED - - "

DECOMPOSITION
ACTIVATION - - -> 459
AMALGAM - - - - -> 337
- - - - -> 340
- - - - -> 343
AMMONIA - - - - - 459
BATTERY FAILURE ->1546
BORON ARSENIDE -> 412
CAPACITY - - - - 1546
CHLORINE - - - -> 919
COMPARISON - - - 343
CONCENTRATION - - 459
CONDUCTION - - - 412
CRUSHED - - - - - 343
CYCLE - - - - - - 1546
DEPOSITION - - - 919
ELECTRODE - - - - 1546
ELECTROLYSIS - ->1328
ELECTRON - - - - 459
ENTROPY - - - - - "
EPITAXY - - - - ->1383
EQUILIBRIUM - - - 919

DECOMPOSITION (CONTD)
ETCHING - - - - - 1383
FORM - - - - - - 1546
GAN - - - - - - - 1383
GRAPHITE BED - - 343
HIGH TEMPERATURE 919
1328
HYDROGEN - - - - 919
INTERFACE - - - - 1328
LEAD DIOXIDE - - 1546
LITHIUM - - - - - 459
MASS TRANSPORT - 1328
MECHANISM - - - - 1546
PREPARATION - - - 412
PROPERTY - - - - "
RATE - - - - - - 340
REACTION - - - - 919
REDUCTION - - - - "
SEMICONDUCTOR - - 412
SILICON - - - - - 919
SILICON DIOXIDE - 1328
SODIUM - - - - - 337
SODIUM HYDROXIDE 340
343
SOLVATED - - - - 459
STABILITY - - - - 1328
SUBSTRATE - - - - 412
THERMAL - - - - - 1383
THERMAL ANALYSIS 1546
TOWER - - - - - - 337
- - - - - - 340
- - - - - - 343

DECORATION
ANODE - - - - - - -> 280
BIPOLAR - - - - - "
CRYSTAL DEFECT - "
JUNCTION - - - - "
LEAKAGE - - - - - "
NPN - - - - - - - "
TRANSISTOR - - - "

DEEP
CAPACITOR - - - ->1219
CARRIER - - - - - "
DEPLETION - - - - "
DIFFUSION - - - - "
LENGTH - - - - - "
LIFETIME - - - - "
MINORITY - - - - "
MOS - - - - - - - "
SILICON - - - - - "
STEADY STATE - - "

DEFECT
ANALYZER - - - - -> 689
CRYSTAL - - - - ->1085
ETCHING - - - - - "
GALLIUM - - - - - "
HELIUM - - - - - 689
LASER - - - - - - "
NITROGEN - - - - "
PHOSPHIDE - - - - 1085
SILICON - - - - - 689
SLICE - - - - - - "
SURFACE - - - - - "

DEFECT STRUCTURE
ANION VACANCY - -> 255
ANTI FRENKEL - - "
CONDUCTIVITY - - "
ELECTRON - - - - "
ION - - - - - - - "
YTTRIA DOPED - - "
ZIRCONIUM OXIDE - "

DEFECTS
INDUCED - - - - -> 969
PROCESS - - - - - "
SILICON - - - - - "
SOFT JUNCTIONS - "

DEFORMATION
ACTIVATION - - -> 681
CONTAMINATION - - "
DEPOSIT - - - - - "
DICHLOROSILANE - "
NEUTRON - - - - - "
OXYGEN - - - - - "
POLYCRYSTALLINE - "
SILICON FILM - - "
VAPOR - - - - - - "

DEGRADATION
ALLOY - - - - - -> 800
ALUMINUM - - - - "
COATING - - - - - "

DEGRADATION (CONTD)
DEPLETION - - - - 880
DIFFUSION - - - - "
NICKEL - - - - - "
OXIDATION - - - - "
SPALLING - - - - "
SUPERALLOY - - - "

DEHYDROPYRIDINES
DIMERIZATION - ->1033
ELECTROCHEMISTRY "
METHYL - - - - - "
MONONUCLEOTIDE - "
NICOTINAMIDE - - "
PYRIDINIUM - - - "
REDOX - - - - - - "
SPECIES - - - - - "

DELAMINATION
CHROME COATING -> 29
LACQUER FILM - - "
ORGANIC - - - - - "
STEEL - - - - - - "
UNDERCUTTING - - "

DELUXE
FLUORESCENT - - ->1627
HIGH EFFICACY - - "
LAMPS - - - - - - "
NEW GENERATION - "

DEMARCATION
FACET GROWTH - -> 787
INTERFACE - - - - "
SEGREGATION - - - "

DENDRITE
CRITICAL - - - -> 329
ELECTROLESS - - -> 912
GROWTH - - - - - 329
HEAT SINKS - - - 912
HEAT TRANSFER - - "
INDUCTION TIME - 329
OVERPOTENTIAL - - "
PLATING - - - - - 912
PREPARATION - - - "
YIELD - - - - - - 329
ZINC - - - - - - - "

DENSIFICATION
AUGER - - - - - -> 827
ELECTRON SPECTRO. "
GLASS FILM - - - "
OXYGEN - - - - - "
RATIO - - - - - - "
SILICON - - - - - "
SILICON DIOXIDE - "
SPIN ON - - - - - "
STOICHIOMETRY - - "

DENSITY
ANODE BEHAVIOR -> 191
ANOMALOUS - - - ->1677
BORON - - - - - - "
CHARGE - - - - -> 591
CHLORIDE - - - ->1298
CONDUCTANCE - - - "
DIELECTRIC - - - 591
- - - 1677
DIFFUSION - - - - "
EFFECT - - - - - "
ELECTRET - - - - 591
ELECTRETS - - - - 1677
ELECTROCHEMICAL - 191
FEP - - - - - - - 591
HIGH CURRENT - - 191
HOMOCHARGE - - - 591
INSERT - - - - - "
- - - - - 1677
LITHIUM - - - - - 1298
MANGANESE - - - - "
MELT - - - - - - "
MILD - - - - - - 191
NITRIDE - - - - - 1677
PLANAR - - - - - "
POLISHING - - - - 191
POTASSIUM - - - - 1298
RUBIDIUM - - - - "
SILICON - - - - - 1677
SODIUM - - - - - 1298
SODIUM CHLORATE - 191
SPRAY - - - - - - 591
STEEL - - - - - - 191
SURFACE - - - - - 591
SURFACE CHARGE - 1677
TEFLON - - - - - 591
THERMOELECTRET - "

DEPENDENCE
BERYLLIUM - - - ->1429
CERIUM DIOXIDE -> 126
->1198
->1676
CHRONOPOTENTIOME. 1429
COMMENTS - - - - 1676
COMPOSITION - - - 126
COMPOSITIONAL - - 1676
CONCENTRATION - -> 132
CONDUCTIVITY - - 126
- - 1198
- - 1676
DEPLETION - - - - 1429
DIFFUSION - - - - 132
DISTRIBUTION - - "
DOPED OXIDE - - - "
ELECTRICAL - - - 1676
ELECTROMIGRATION 1429
ELECTRON MOBILITY 126
FLOURIDES - - - - 1429
GLASSES - - - - - "
IMPURITY - - - - 132
IONIC - - - - - - 1198
LAYER - - - - - - 132
LITHIUM - - - - - 1429
LUMINESCENCE - - 1676
MOLTEN HALIDES - 1429
NONSTOICHIOMETRIC 126
1198
NUMBER - - - - - "
OXYGEN - - - - - "
PHOSPHORUS - - - 132
PRESSURE - - - - 1198
QUENCHING - - - - 1676
SILICON - - - - - 132
TEMPERATURE - - - 126
- - - 132
- - - 1198
- - - 1429
- - - 1676
THEORY - - - - - "
THERMAL - - - - - "
TRANSFERENCE - - 1198
VAPOR DEPOSITION 132

DEPLETION
ALLOY - - - - - -> 800
ALUMINUM - - - - "
BERYLLIUM - - - ->1429
CAPACITOR - - - ->1219
CARRIER - - - - - "
CHRONOPOTENTIOME. 1429
COATING - - - - - 800
DEEP - - - - - - 1219
DEGRADATION - - - 800
DEPENDENCE - - - 1429
DIFFUSION - - - - 800
- - - - 1219
ELECTROMIGRATION 1429
FLOURIDES - - - - "
GLASSES - - - - - "
LENGTH - - - - - 1219
LIFETIME - - - - "
LITHIUM - - - - - 1429
MINORITY - - - - 1219
MOLTEN HALIDES - 1429
MOS - - - - - - - 1219
NICKEL - - - - - 800
OXIDATION - - - - "
SILICON - - - - - 1219
SPALLING - - - - 800
STEADY STATE - - 1219
SUPERALLOY - - - 800
TEMPERATURE - - - 1429

DEPOSIT
ACTIVATION - - -> 681
ADSORPTION - - -> 676
AEROSOL - - - - -> 484
BOROSILICATE - - 676
CONTAMINATION - - 681
DEFORMATION - - - "
DEVICE - - - - -> 685
DICHLOROSILANE - 681
DIFFUSION - - - - 676
ELECTRICAL - - - 484
FORMALDEHYDE - - "
FUSED SILICA - - 685
GLASS FILM - - - 676
HYDRAZINE - - - - 484
NEUTRON - - - - - 681
OXYGEN - - - - - "
PLATING - - - - - 484
POLYCRYSTALLINE - 681
RESISTIVITY - - - 484
SILANOL - - - - - 676

PRIMARY TERM / CO-TERM	PAGE NO.
DEPOSIT (CONTD)	
SILICON FILM	681
	685
SILVER	484
SPECTROSCOPY	676
SPRAY	484
THIN FILM	685
TRANSISTOR	"
VACUUM	"
VAPOR	676
	681
WATER	676
DEPOSITION	
AC DISCHARGE	-> 714
ACID BATH	->1023
ADSORPTION	-> 474
AMINE	1023
BEAM	-> 899
BORANE	1023
CADMIUM	-> 965
CALCULATION	->1357
CARBON	-> 527
CHEMICAL	-> 298
CHLORINE	-> 919
COBALT	1023
CONTROL	->1233
	->1235
CVD	1233
DECOMPOSITION	919
DISSOLUTION	->1592
ELECTRODE	474
	1592
	->1610
ELECTROLESS	1023
EPITAXY	965
	1357
EQUILIBRIUM	919
FIBER GROWTH	714
FILM	1233
	1235
FILM THICKNESS	1233
	1235
GAASP	1357
GOLD	1610
GOLD EVAPORATED	474
HELIUM	1233
HEMISPHERICAL	1592
HETEROEPITAXY	965
HIGH TEMPERATURE	919
HYDROGEN	"
HYPOPHOSPHITE	1023
IRON	527
IRON OXIDE	"
	1592
ISOTHERM	474
LASER	1233
	1235
LEAD	474
	1610
METAL	->1160
METALLIZATION	298
MILD	1592
MOLECULE	899
NEON	1233
NICKEL	1023
NITRIDE	1233
NOBLE	1160
OPEN CIRCUIT	"
OPTIC	1610
PALLADIUM	1160
PASSIVATION	527
PHOTOCATALYTIC	1160
PHOTOGRAPHY	"
PHOTOSENSITIVITY	965
PLATING	1023
PLATINUM	527
POLYCRYSTALLINE	1235
POTENTIOSTATIC	527
PYROLYSIS	899
REACTION	919
REDUCTION	"
REFLECTANCE	474
RING	1592
RING ELECTRODE	527
ROTATING	1592
SAMPLE	899
SAPPHIRE	965
SELENIDE	"
SEMICONDUCTOR	298
	1160
SILANE	899
SILICON	"
	919
	1233
	1235
SILICON DIOXIDE	1233

PRIMARY TERM / CO-TERM	PAGE NO.
DEPOSITION (CONTD)	
SINGLE CRYSTAL	474
	1610
SPECTROMETRY	899
SPECTROSCOPY	474
STEEL	1592
STEELS	527
SULFATE SOLUTION	1592
SULFIDE	965
TANTALUM CARBIDE	714
TITANIUM DIOXIDE	1160
TRANSIENT	527
TUNGSTEN	298
UNDER POTENTIAL	1610
UNDERPOTENTIAL	474
VAPOR	298
	714
	965
VAPOR PHASE	"
	1357
DEPTH PROFILE	
CONTAMINANT	->1617
ION	"
MASS SPECTROMETRY	"
MICROCIRCUIT	"
MICROPROBE	"
SECONDARY	"
SILVER CHLORIDE	"
SPUTTERING	"
SURFACE	"
DETECTION	
CONTAMINANTS	-> 172
HEV	"
SCATTERING	"
SENSITIVITY	"
SURFACE ANALYSIS	"
DETECTOR	
EPITAXY	->1506
GAAS	"
INGAAS	"
WAVEGUIDE	"
DETERMINATION	
ANALYTICAL	-> 972
BORON	"
ELECTRODE	->1462
HANNETT	"
HYDROGEN	"
POLYCRYSTALLINE	972
SHEET RESISTIVITY	"
SIGMA	1462
SILICON FILM	972
SUBSTITUENT	1462
DEVELOPER	
CONTRAST	->1669
ELECTRON BEAM	"
ELECTRON RESIST	"
FUNCTION	"
LITHOGRAPHY	"
METHACRYLATE	"
PMMA	"
POLYMETHYL	"
RATE	"
SOLUBILITY	"
DEVICE	
ANODE OXIDATION	-> 820
APPLICATION	-> 422
BIPOLAR	->1119
CIRCUIT	422
COATING	-> 720
COMPLEMENTARY	1119
COMPOUND	820
CONCENTRATION	-> 419
CRT	720
DEPOSIT	-> 685
DIFFUSION	820
ELECTRON	720
ELECTROOPTICAL	820
ELECTROPLATED	-> 426
EPITAXIAL	422
EPITAXY	-> 563
FABRICATION	426
FET	419
FUSED SILICA	685
GAAS	426
GALLIUM ARSENIDE	820
GATE	419
GLASS	"
GRAPHITE SILICATE	720
GROWTH	563
HEAT SINKS	426
IMPATT	"

PRIMARY TERM / CO-TERM	PAGE NO.
DEVICE (CONTD)	
IMPURITY	563
INTEGRATED	422
INTEGRATION	1119
INTERFACE	419
ION DRIFT	"
ION TRAPPING	"
ISOLATED	1119
MEASUREMENT	422
MONOLITHIC	1119
MOS	"
OXIDE	419
PENETRATION	720
PHOSPHORUS	419
PHOSPHOSILICATE	"
POLARIZATION	"
PROCESSING	563
REDISTRIBUTION	"
RESISTANCE	422
RESISTIVITY	"
SEMICONDUCTOR	563
	820
	1119
SILICON	422
	563
SILICON FILM	685
SILICON OXIDE	419
SPREADING	422
THICKNESS	419
	720
THIN FILM	685
THRESHOLD	419
TRANSISTOR	685
	1119
VACUUM	685
VOLTAGE	419
WATER CURVATURE	426
ZINC	820
DEVICE PROCESSING	
GETTERING	-> 724
GLASS	"
MOBILE CHARGE	"
PHOSPHOSILICATE	"
REMOVAL	"
SILICON DIOXIDE	"
SODIUM	"
DICALCIUM	
CALCIUM	-> 534
ELECTROCHEMISTRY	"
GALVANIC CELL	"
MONOCALCIUM	"
STABILITY	"
STANNATE	"
VAPORIZATION	"
DICHLOROSILANE	
ACTIVATION	-> 681
CONTAMINATION	"
DEFORMATION	"
DEPOSIT	"
NEUTRON	"
OXYGEN	"
POLYCRYSTALLINE	"
SILICON FILM	"
VAPOR	"
DIELECTRIC	
ANOMALOUS	->1677
BARRIER HEIGHT	->1195
BEHAVIOR	-> 122
	-> 163
BORON	1677
BREAKDOWN	-> 809
	1195
	->1229
CALCIUM DOPED	122
CARRIER	1229
CATALYST	-> 736
CERIUM DIOXIDE	122
CHARGE	-> 591
	-> 907
CHEMISORPTION	163
CONTAMINATION	1195
DENSITY	591
	1677
DIFFUSION	163
	1677
DOPING	163
EFFECT	1677
ELECTRET	591
ELECTRETS	1677
ELECTRON MICROSC.	738
ETCHING	1229
FEP	591
FILM	809

PRIMARY TERM / CO-TERM	PAGE NO.
DIELECTRIC (CONTD)	
FILM	1195
GATE	907
GENERATION	1229
HALOGEN	809
HIGH TEMPERATURE	122
	163
HOMOCHARGE	591
HYDROGEN CHLORIDE	809
IMPERFECTION	1229
INSERT	591
	1677
INSULATOR	907
LITHIUM	163
LOWERING	1195
MINORITY	1229
MIXED	738
NITRIDE	907
	1677
OXIDATION	809
OXIDE	907
PALLADIUM CHLORI.	738
PLANAR	1677
PLATING	738
POLYCRYSTALLINE	163
RELIABILITY	809
SILICON	907
	1195
	1229
	1677
SILICON DIOXIDE	809
	1195
SODIUM	163
	1195
SODIUM INDUCED	"
SPRAY	591
STABILITY	907
STANNOUS CHLORIDE	738
SUBSTRATE	"
SURFACE	591
SURFACE CHARGE	1677
TEFLON	591
THERMOELECTRET	"
WAFER	1229
ZINC OXIDE	163
DIETHYLFUMARATE	
ACETONITRILE	-> 881
DMSO	"
ELECTROHYDRODIME.	"
ION PAIRS	"
REDUCTION	"
SODIUM ION	"
VOLTAMMETRY	"
DIFFERENTIAL	
AERATION	-> 183
CORROSION	"
FILM	"
METAL	"
MOISTNESS	"
PASSIVATING	"
THICKNESS	"
VARIABLE	"
DIFFRACTION	
ALUMINUM	-> 430
REACTION	"
SILICA	"
SUBSTRATE	"
DIFFUSING	
ARGON	->1372
CONTROL	"
EQUILIBRIA	"
ETCHING	"
HELIUM	"
HEXAFLUORIDE	"
LANGMUIR SHEATH	"
NITROGEN	"
PENTA FLUORIDE	"
RATE	"
REACTION	"
TUNGSTEN	"
DIFFUSION	
ADSORPTION	-> 676
AGENT	-> 779
ALLOY	-> 538
	-> 734
	-> 800
	->1051
ALUMINIDE	"
ALUMINUM	800
ANODE OXIDATION	-> 820
ANOMALOUS	->1677
BATTERY ANODE	734

PRIMARY TERM — CO-TERM — PAGE NO.

DIFFUSION (CONTD)
BEHAVIOR - - - -> 163
BORON - - - - - -> 705
- - - - - ->1377
- - - - - - 1677
BOROSILICATE - - 676
BOUNDARY - - - -> 313
CAPACITANCE - - ->1318
CAPACITOR - - - ->1219
CARBON MONOXIDE ->1315
CARBONATE - - - - 734
CARRIER - - - - -> 973
- - - - - 1219
CHEMISORPTION - - 163
COATING - - - - - 800
- - - - - 1051
COBALT IRON - - - 538
COBALTOUS IRON - "
COEFFICIENT - - -> 556
- - - 779
COMPLEMENT - - - 313
COMPONENT - - - ->1000
COMPOUND - - - - 820
CONCENTRATION - -> 132
CONDITION - - - - 313
CONVECTIVE - - - 1000
COPPER - - - - - 1318
COPPER CHLORIDE - "
COPPER FLUOROBOR. 779
COPPER SULFATE - "
CORROSION - - - - 1000
CRACK - - - - - - "
CRISTOBALITE - ->1081
CRYSTAL GROWTH - 556
->1237
CRYSTALLIZATION - 1081
DEEP - - - - - - 1219
DEGRADATION - - - 800
DENSITY - - - - - 1677
DEPENDENCE - - - 132
DEPLETION - - - - 800
- - - - 1219
DEPOSIT - - - - - 676
DEVICE - - - - - 820
DIELECTRIC - - - 163
- - - 1677
DISTRIBUTION - - 132
DOPED - - - - - - 1237
DOPED OXIDE - - - 132
DOPING - - - - - 163
DOUBLE LAYER - - 1318
EFFECT - - - - - 1677
ELECTRETS - - - - "
ELECTROCHEMICAL -> 286
ELECTRODE - - - - 734
- - - - 1315
ELECTROLYTE - - - 779
ELECTRON - - - ->1538
ELECTROOPTICAL - 820
EMITTER DIP - - - 1377
EPITAXY - - - - - 1237
EQUATION - - - - 313
ERROR - - - - - - "
ETCHING - - - - - 286
FILM - - - - - - "
- - - - - - 1081
FLUX STEP - - - - 313
FUNCTION - - - - "
GAAS - - - - - - 1237
GALLIUM - - - - - 556
- - - - ->1487
GALLIUM ARSENIDE 820
GAS SENSOR - - - 1315
GERMANIUM - - - - 1237
GLASS FILM - - - 676
GOLD - - - - - - 1318
GROWTH - - - - - 538
HIGH TEMPERATURE 163
IMPURITY - - - - 132
INSERT - - - - - 1677
INTERFACE - - - - 1081
INTERMETALLIC - - 734
ION IMPLANT - - - 705
KINETIC - - - - - 779
KINETICS - - - - 1051
LAYER - - - - - - 132
LENGTH - - - - - 1219
LIFETIME - - - - "
LITHIUM - - - - - 163
LITHIUM MAGNESIUM 734
LOW TEMPERATURE - 1318
MASS TRANSFER - - 1000
MELT - - - - - - 556
MICROSCOPY - - - 1538
MINOR - - - - - - 1000
MINORITY - - - - 973
- - - - 1219

DIFFUSION (CONTD)
MOLTEN SALT - - - 1000
MOS - - - - - - - 1219
NETWORK - - - - - 1081
NICKEL - - - - - 800
- - - - - 1051
NITRIDE - - - - - 1677
OHM - - - - - - - 1237
ORGANIC - - - - - 779
OXIDATION - - - - 705
- - - - 800
- - - - 1315
OXIDE - - - - - - 538
PACK - - - - - - 1051
PALLADIUM - - - - 1538
PARAMETER - - - - 779
PHOSPHIDE - - - - 556
PHOSPHORUS - - - 132
- - - 556
- - - 1081
- - - 1377
PHOTOVOLTAGE - - 973
PLANAR - - - - - 1677
PLATINUM - - - - 1315
POLYCRYSTALLINE - 163
PROFILE - - - - - 313
PROPAGATING - - - 1000
PROPYLENE - - - - 734
PROTECTIVE - - - 1051
SEGREGATION - - - 705
SEMICONDUCTOR - - 313
- - 820
- - 1237
SILANOL - - - - - 676
SILICIDE - - - - 1538
SILICON - - - - - 132
- - - - - 286
- - - - - 973
- - - - - 1219
- - - - - 1487
- - - - - 1677
SILICON DIOXIDE - 1081
- 1487
SINGLE CRYSTAL - 1318
SODIUM - - - - - 163
SOLAR CELL - - - 973
SOLID ELECTROLYTE 1318
SPALLING - - - - 800
SPECTROSCOPY - - 676
STEADY STATE - - 1219
STRUCTURE - - - - 1538
SUPERALLOY - - - 800
SURFACE - - - - - 973
SURFACE CHARGE - 1677
TEMPERATURE - - - 132
THERMODYNAMICS - 1051
THIN FILM - - - - 286
VAPOR - - - - - - 676
VAPOR DEPOSITION 132
WATER - - - - - - 676
ZINC - - - - - - 820
- - - - - - 1237
ZINC OXIDE - - - 163

DIFFUSION MODEL
ALLOY - - - - - -> 386
NICKEL IRON - - - "
NICKEL OXIDE - - "
OXIDATION - - - - "

DIGITAL
COUPLING - - - -> 745
ELECTRODE - - - - "
ELECTROOXIDATION "
MECHANISM - - - - "
RING DISK - - - - "
ROTATING - - - - "
SIMULATION - - - "

DIHYDROPYRIDINES
BEHAVIOR - - - -> 345
DIMERIZATION - - "
FREE RADICAL - - "
METHYLNICOTINAMI. "
NICOTINAMIDE - - "
OXIDATION - - - - "
REDOX PATTERN - - "
- - "
REDUCTION - - - - "

DILUTE
ACTIVITY - - - -> 884
AMALGAMS - - - - "
COEFFICIENT - - - "
POTENTIAL - - - - "
STANDARD - - - - "
THALLIUM - - - - "

DIMENSION
CURRENT - - - - -> 95
DISTRIBUTION - - "
FLOW REACTOR - - "
PACKED BED - - - "

DIMERIZATION
BEHAVIOR - - - -> 345
DEHYDROPYRIDINES >1033
DIHYDROPYRIDINES 345
DIMETHYLFORMAMIDE>1412
ELECTROCHEMISTRY 1033
FREE RADICAL - - 345
METHYL - - - - - 1033
METHYLNICOTINAMI. 345
MONONUCLEOTIDE - 1033
NICOTINAMIDE - - 345
- - 1033
OXIDATION - - - - 345
PHENYLNITROPROPE. 1412
PYRIDINIUM - - - 1033
REDOX - - - - - - "
REDOX PATTERN - - 345
- - "
REDUCTION - - - - "
SPECIES - - - - - 1033
VOLTAMMETRY - - - 1412

DIMETHYLANILINE
ANODE OXIDATION -> 757
CHARGING - - - - "
DISCHARGING - - - "
ELECTRODE - - - - "
MORPHOLOGY - - - "
SILVER - - - - - "
SILVER CHLORIDE - "
SURFACE - - - - - "

DIMETHYLFORMAMIDE
AMMONIUM - - - -> 977
APROTIC - - - - -> 518
BROMIDE - - - - - 977
CONDUCTANCE - - - "
CONDUCTIVITY - -> 91
DIMERIZATION - ->1412
DISSOCIATION - - 91
ELECTROCHEMISTRY 518
ELECTRODE - - - -> 79
- - - - 518
ELECTROLYTE - - - 977
HYDROGEN - - - - 518
ISOTHIOCYANATE - 977
LEAD CHLORIDE - - 79
LEWIS ACID - - - 91
MEASUREMENT - - - 79
NICKEL - - - - - 977
NONAQUEOUS - - - "
PHENYLNITROPROPE. 1412
POTASSIUM - - - - 977
POTENTIAL - - - - 79
PROTONIC ACID - - 91
REVERSIBLE CELL - 518
SOLUTION - - - - 977
SOLVENT - - - - - 518
STANDARD - - - - 79
TETRABUTYL - - - 977
THALLIUM - - - - 518
TITANIUM CHLORIDE 79
VISCOSITY - - - - 977
VOLTAMMETRY - - - 1412

DIODE
BREAKDOWN - - - -> 692
CARRIER - - - - ->1332
CONTRAST - - - ->1202
EFFICIENCY - - - 1332
ELECTRON - - - - 692
GAAS - - - - - - "
GALLIUM - - - - - 1332
GALLIUM NITRIDE - 1202
HEAT - - - - - - 1332
HETEROEXPITAXIAL 1202
IMPATT - - - - - 692
JUNCTION - - - - 1202
LIFETIME - - - - 1332
LIGHT EMISSION - 1202
MICROSCOPE - - - 692
MICROSTRUCTURE - 1202
PHOSPHORUS - - - 1332
PHOTOLUMINESCENCE "
PREMATURE - - - - 692
PROFILE - - - - - 1202
SCANNING - - - - 692
SCHOTTKY - - - - "
SITES - - - - - - "
STRUCTURE - - - - 1202
VAPOR DEPOSITION "

DIODE (CONTD)
VOLTAGE - - - - - 1202
ZINC OXIDE - - - 1332

DIODES
AMMONIA - - - - -> 962
BEHAVIOR - - - - "
EMITING - - - - - "
EPITAXY - - - - - "
GAP - - - - - - - "
IMPURITY - - - - "
LIGHT - - - - - - "
LIQUID PHASE - - "
NITROGEN DOPING - "
SOURCE - - - - - "

DIRECT CURRENT
ELECTROLUMINESCE.> 109
GREEN - - - - - - "
LEAD DOPED - - - "
PHOSPHORS - - - - "
POWDER CELLS - - "
ZINC SULFIDE - - "

DISCHARGE
BEHAVIOR - - - ->1460
ELECTROLYTE - - - "
LITHIUM CELL - - "
MOLYBDENUM - - - "
NONAQUEOUS - - - "
SOLUTION - - - - "

DISCHARGED
AC - - - - - - - -> 375
ALKALINE - - - - "
CATHODE - - - - - "
CONDUCTIVITY - - "
DC - - - - - - - "
IMPEDANCE - - - - "
IONIC CONDUCTANC. "
LECLANCHE CELL - "
MANGANESE DIOXIDE "
MEASUREMENT - - - "
MERCURY OXIDE - - "
RESISTANCE - - - "
UNDISCHARGED - - "

DISCHARGING
ANODE OXIDATION -> 757
CHARGING - - - - "
DIMETHYLANILINE - "
ELECTRODE - - - - "
MORPHOLOGY - - - "
SILVER - - - - - "
SILVER CHLORIDE - "
SURFACE - - - - - "

DISK
CURRENT POTENTIAL>1558
ELECTRODE - - - - "
MASS TRANSFER - - "
MODULATION - - - "
ROTATING - - - - "
SINUSOIDAL - - - "

DISK ELECTRODE
CONTROL - - - - -> 523
CURRENT - - - - - "
DISTRIBUTION - - "
GALVANOSTATIC - - "
POTENTIOSTATIC - "
SHORT TIME - - - "

DISPLACEMENT
COPPER - - - - -> 289
IMPERFECTION - - "
SILICON - - - - - "
SUBSTRATE - - - - "
TOPOGRAPHY - - - "
X RAY - - - - - - "

DISSOCIATION
CONDUCTIVITY - -> 91
DIMETHYLFORMAMIDE "
LEWIS ACID - - - "
PROTONIC ACID - - "

DISSOLUTION
ACETONE - - - - ->1563
ANODE OXIDATION -> 860
CORROSION - - - -> 645
CRYSTAL GROWTH - 1563
CYCLIC - - - - -> 360
DEPOSITION - - ->1592
DUTERIUM OXIDE - 1563
ELECTRODE - - - - 360
- - - - 1892

PRIMARY TERM / CO-TERM	PAGE NO.
DISSOLUTION (CONTD)	
ELECTROLYTES	1563
FORMAMIDE	"
HEMISPHERICAL	1592
IMPURITY	860
ION IMPLANT	"
IRON OXIDE	1592
MECHANISM	360
MILD	1592
PALLADIUM	645
PLATINUM	360
POTENTIAL	"
	1563
PRECIPITATION	"
PROGRAM	360
REDEPOSITION	"
RING	1592
RING DISK	360
	645
ROTATING	1592
ROUGHENING	360
STEEL	1592
SULFATE SOLUTION	"
TANTALUM OXIDE	860
TRANSIENT	1563
DISSOLVED	
ELECTRODE ->	872
OXYGEN	"
PLATINUM	"
POTENTIAL	"
REST	"
DISTRIBUTION	
ANALYSIS	->1366
ANOMALOUS	->1212
ARRANGEMENT ->	894
BIPOLAR ELECTRODE>	622
CADMIUM	1366
CARRIER MOBILITY	1212
CATHODOLUMINESCE.	894
COLOR RENDITION ->	407
CONCENTRATION ->	132
CONTROL ->	523
COPPER ->	661
->	"
CRT	894
CRYSTAL GROWTH	1366
CURRENT ->	95
	523
	622
	661
	"
	"
	"
	->1448
DEPENDENCE	132
DIFFUSION	"
DIMENSION	95
DISK ELECTRODE	523
DISTRIBUTION	661
	"
DOPED OXIDE	132
ELECTRODE	622
ELECTRODEPOSITION	661
	"
FLOW REACTOR	95
GALVANOSTATIC	523
GERMANIUM	1212
HALL	"
IMPURITY	132
	1212
INHOMOGENEITY	"
LAMPS	407
LAYER	132
MASS TRANSFER	1446
MEASUREMENT	661
	"
MERCURY VAPOR	407
METHOD	1212
MOBILITY	"
OPTIMIZED	407
PACKED BED	95
PARTICLE	894
PHOSPHOR	"
PHOSPHORS	407
PHOSPHORUS	132
PLANE	1448
POTENTIAL	622
POTENTIOSTATIC	523
POWER	407
PRINTED CIRCUIT	661
	"
RADIAL	1212
REDOX SYSTEM	661
	"
RESISTIVE	622
DISTRIBUTION (CONTD)	
ROTATING DISK	1448
SEMICONDUCTOR	1212
SHORT TIME	523
SILICON	132
SIZE	894
SPECTRAL	407
TELEVISION	894
TELLURIDE	1366
TEMPERATURE	132
	1366
TRAVELING HEATER	"
VANDERPAUW	1212
VAPOR DEPOSITION	132
WIRE	661
	"
	"
	"
WIRE ELECTRODE	622
	661
	"
DIVALENT	
ALKALINE	->1475
CRYSTAL	"
EARTH	"
EUROPIUM	"
LUMINESCENCE	"
OPTICAL SPECTRA	"
STRUCTURE	"
SULFATES	"
DMSO	
ACETONITRILE ->	881
DIETHYLFUMARATE	"
ELECTROHYDRODIME.	"
ION PAIRS	"
REDUCTION	"
SODIUM ION	"
VOLTAMMETRY	"
DOMAIN	
ASSIGNMENT ->	170
CRYSTAL DEFECTS	"
CRYSTALLOGRAPHY	"
ETCHING	"
FERROELECTRIC	"
GMO	"
SINGLE CRYSTAL	"
DOPED	
CRYSTAL GROWTH	->1237
DIFFUSION	"
EPITAXY	"
GAAS	"
GERMANIUM	"
OHM	"
SEMICONDUCTOR	"
ZINC	"
DOPED GERMANIUM	
CRYSTAL GROWTH ->	380
CZOCHRALSKI	"
INSTABILITY	"
OSCILLATORY	"
SUPERCOOLING	"
DOPED OXIDE	
CONCENTRATION ->	132
DEPENDENCE	"
DIFFUSION	"
DISTRIBUTION	"
IMPURITY	"
LAYER	"
PHOSPHORUS	"
SILICON	"
TEMPERATURE	"
VAPOR DEPOSITION	"
DOPING	
ALUMINUM ->	829
	->1509
ANTIMONY ->	967
	->1523
ARSENIC	->1634
BEHAVIOR ->	163
CARBON ->	146
CHALCOGENIDES	1523
CHEMISORPTION	163
CIRCUIT	146
COMPOUND	1634
CONTAMINATION	146
COPPER	829
CRYSTAL GROWTH	->1516
CRYSTALLIZATION	1509
DIELECTRIC	163
DIFFUSION	"
DOPING (CONTD)	
ELECTRICAL	829
ELECTROLUMINESCE.	1516
ENCAPSULATION ->	1350
ENHANCEMENT	"
EPITAXY	967
	1516
GALLIUM	1509
	1634
GAS PHASE	1516
GOLD	1350
HIGH TEMPERATURE	163
INFRARED DEVICE	1523
INTEGRATED	146
ISOTHERMS	1634
JUNCTION	1523
LEAD	"
LIQUIDUS	1634
LITHIUM	163
MASKING	1509
METALORGANICS	967
MORPHOLOGY	1516
OPTICAL	829
OXIDATION	1509
PASSIVATION	"
PHOSPHORUS	"
	1634
PLANAR JUNCTION	1509
POLYCRYSTALLINE	163
PROPERTIES	829
RESIDUE	146
SAPPHIRE	967
SEGREGATION	1509
SEMICONDUCTOR	1634
SILICON	146
	967
	1350
	1634
SODIUM	163
SOLUBILITY	1350
SOURCE	967
STOICHIOMETRY	1516
SULFIDE	829
SURFACE	146
SYSTEM	1634
TELLURIDE	1523
TERNARIES	"
TERNARY	1634
TIN	1523
TRIMETHYLSTIBINE	967
VAPOR PHASE	1516
ZINC OXIDE	163
DOUBLE LAYER	
BEHAVIOR	->1308
CAPACITANCE ->	632
	->1318
CAPACITY ->	512
	->1444
COPPER	1318
COPPER CHLORIDE	"
DIFFUSION	"
ELECTRODE	512
	632
ELECTROLYTE CELL	"
ELLIPSOMETRY	->1596
FLUOROGRAPHITE	1308
FORMATION	1596
GOLD	1318
	1596
GRAPHITE	632
HYSTERESIS	1596
LOW TEMPERATURE	1318
NICKEL	512
NONAQUEOUS	1308
OXIDE FILM	1596
PLATINUM	632
	1596
POROUS	512
POROUS ELECTRODE	1308
POTASSIUM HYDROX.	512
	1444
POTENTIAL	1308
REDUCTION	1596
REFLECTANCE	"
ROOM TEMPERATURE	632
SILVER	1444
SILVER HALIDES	632
SINGLE CRYSTAL	1318
SOLID ELECTROLYTE	632
	1318
SPECTROGRAPHY	1444
SURFACE PROCESS	1596
SWEEP	512
SWEEP RATE	1444
TEMPERATURE	"
TRIANGLE	"
DOUBLE LAYER (CONTD)	
TRIANGULAR	512
VOLTAGE	"
VOLTAMMETRY	1444
DRUDE ZENER	
ABSORPTION ->	1482
CARRIER	"
CONCENTRATION	"
GAAS	"
INFRARED	"
REFLECTIVITY	"
SEMICONDUCTOR	"
SILICON DOPED	"
DUTERIUM OXIDE	
ACETONE ->	1563
CRYSTAL GROWTH	"
DISSOLUTION	"
ELECTROLYTES	"
FORMAMIDE	"
POTENTIAL	"
PRECIPITATION	"
TRANSIENT	"
DYSPROSIUM	
ANODE SPARK ->	1402
ERBIUM	"
GADOLINIUM	"
HOLMIUM	"
SAMARIUM	"
SODIUM SILICATE	"
YTTERBIUM	"
YTTRIUM	"
EARTH	
ALKALI ->	1122
ALKALINE	"
->	1475
CRYSTAL	"
DIVALENT	"
EUROPIUM	1122
	1475
LUMINESCENCE	1122
	147.
OPTICAL SPECTRA	"
PHOSPHATES	1122
STRUCTURE	1475
SULFATES	"
EFFECT	
ANOMALOUS ->	1677
BORON	"
CHLORATE CELL ->	70
->	1606
CHLORINE	70
CURRENT	"
	1606
CURRENT DENSITY	70
	1606
DENSITY	1677
DIELECTRIC	"
DIFFUSION	"
EFFICIENCY ->	70
	1606
ELECTRETS	1677
ELECTROCRYSTALLI.	1606
HYDRODYNAMIC	70
INSERT	1677
MECHANISM	1606
MUTUAL	70
NITRIDE	1677
ORIENTATION ->	1613
OXYGEN	"
PH	70
	1606
PLANAR	1677
PROCESS	1606
RATE CONSTANT	1613
SILICON	"
	1677
SILVER ELECTRODE	1606
SURFACE CHARGE	1677
TEMPERATURE	70
	1606
THERMAL OXIDATION	1613
TRACE	"
WATER	"
EFFICIENCY	
CARRIER ->	1332
CHLORATE CELL ->	70
->	1606
CHLORINE	70
CURRENT	"
	1606
CURRENT DENSITY	70

PRIMARY TERM — CO-TERM — PAGE NO.

EFFICIENCY (CONTD)
CURRENT DENSITY - 1606
DIODE - - - - - - 1332
EFFECT - - - - - 70
- - - - - 1606
ELECTROCRYSTALLI. "
GALLIUM - - - - - 1332
HEAT - - - - - - "
HYDRODYNAMIC - - 70
LIFETIME - - - - 1332
MECHANISM - - - - 1606
MUTUAL - - - - - 70
PH - - - - - - - "
- - - - - - - 1606
PHOSPHORUS - - - 1332
PHOTOLUMINESCENCE "
PROCESS - - - - - 1606
SILVER ELECTRODE "
TEMPERATURE - - - 70
- - - 1606
ZINC OXIDE - - - 1332

ELECTRET
CHARGE - - - - -> 591
DENSITY - - - - - "
DIELECTRIC - - - "
FEP - - - - - - - "
HOMOCHARGE - - - "
INSERT - - - - - "
SPRAY - - - - - - "
SURFACE - - - - - "
TEFLON - - - - - "
THERMOELECTRET - "

ELECTRETS
ANOMALOUS - - - ->1677
BORON - - - - - - "
DENSITY - - - - - "
DIELECTRIC - - - "
DIFFUSION - - - - "
EFFECT - - - - - "
INSERT - - - - - "
NITRIDE - - - - - "
PLANAR - - - - - "
SILICON - - - - - "
SURFACE CHARGE - "

ELECTRIC
ABSORPTION - - -> 586
COMPOUND - - - - "
CONDUCTIVITY - - "
FORMATION - - - - "
ION IMPLANTATION "
OPTICAL - - - - - "
SILICON CARBIDE - "

ELECTRICAL
AEROSOL - - - - -> 484
ALUMINUM - - - -> 829
ARSINE - - - - ->1646
CERIUM DIOXIDE ->1676
CHEMICAL - - - - 1646
COMMENTS - - - - 1676
COMPOSITIONAL - - "
CONDUCTIVITY - - "
COPPER - - - - - 829
DEPENDENCE - - - 1676
DEPOSIT - - - - - 484
DOPING - - - - - 829
FORMALDEHYDE - - 484
GALLIUM ARSENIDE 1646
HETEROEPITAXY - - "
HYDRAZINE - - - - 484
INDIUM ARSENIDE - 1646
LUMINESCENCE - - 1676
OPTICAL - - - - - 829
PLATING - - - - - 484
PROPERTIES - - - 829
- - - 1646
QUENCHING - - - - 1676
RESISTIVITY - - - 484
SILVER - - - - - "
SPRAY - - - - - - "
SULFIDE - - - - - 829
TEMPERATURE - - - 1676
THEORY - - - - - "
THERMAL - - - - - "
TRIETHYLINDIUM - 1646
VAPOR DEPOSITION "

ELECTRO OXIDATION
ACETONITRILE - ->1451
CARBON - - - - - "
GOLD - - - - - - "
NITRITE IONS - - "
PLATINUM - - - - "

ELECTROANALYSIS
CHEMILUMINESCENCE>1178
ELECTROGENERATE - "
ENERGY DEFICIENT "
LUMINESCENCE - - "
NONAQUEOUS - - - "
SOLVENT - - - - - "
VOLTAMMETRY - - - "

ELECTROCAPILLARY
LEAD ELECTRODE ->1417
MENISCUS - - - - - "
SODIUM SULFATE - "

ELECTROCATALYST
(ACETONITRILE - -> 780
ACTIVATION - - - "
FORMALDEHYDE - ->1125
FORMIC ACID - - - 780
KINETICS - - - - 1125
MECHANISM - - - - "
MERCURY - - - - - 780
MOLYBDENUM - - - 1125
OXIDATION - - - - 780
- - - - 1125
REACTION - - - - "
SULFUR - - - - - "

ELECTROCHEMICAL
ANODE BEHAVIOR -> 191
ANODE DISSOLUTION> 249
DENSITY - - - - - 191
DIFFUSION - - - -> 286
ETCHING - - - - - "
FERRATE - - - - - 249
FILM - - - - - - 286
HIGH CURRENT - - 191
IRON (VI) - - - - 249
MILD - - - - - - 191
POLISHING - - - - "
POTENTIOSTATIC - 249
SILICON - - - - - 286
SODIUM CHLORATE - 191
STEEL - - - - - - "
SYNTHESIS - - - - 249
THIN FILM - - - - 286

ELECTROCHEMISTRY
ADSORPTION - - -> 764
ALCOHOLS - - - ->1048
APROTIC - - - - -> 518
CALCIUM - - - - -> 534
CELL - - - - - - 1048
CHARGER - - - - ->1134
CHLORIDE - - - ->1007
CHROMATE - - - - "
CONTROLLER - - - 1134
CREVICES - - - - 1007
DEHYDROPYRIDINES >1033
DICALCIUM - - - - 534
DIMERIZATION - - 1033
DIMETHYLFORMAMIDE 518
ELECTRODE - - - - "
- - - - 1048
GALVANIC CELL - - 534
- - 764
HEXANOL - - - - - 1048
HIGH POWER - - - 1134
HYDROGEN - - - - 518
- - - - 1048
INSTRUMENT - - - 764
ION - - - - - - - 1007
IRON - - - - - - - "
METHYL - - - - - 1033
MONOCALCIUM - - - 534
MONONUCLEOTIDE - 1033
NICOTINAMIDE - - "
NORMAL - - - - - 1048
OXYGEN - - - - - 1007
PARTICLE SIZE - - 764
POLARIZATION - - 1007
PROPULSION - - - 1134
PYRIDINIUM - - - 1033
REDOX - - - - - - "
REDUCTION - - - - 1007
REVERSIBLE CELL - 518
SIMULATOR - - - - 1134
SOLVENT - - - - - 518
SPECIES - - - - - 1033
STABILITY - - - - 534
STANNATE - - - - "
SUPPLY - - - - - 1134
SURFACE AREA - - 764
THALLIUM - - - - 518
- - - - 1048
VAPORIZATION - - 534

ELECTROCRYSTALLI.
ADSORPTION - - ->1167
CHLORATE CELL - ->1606
CURRENT - - - - - "
CURRENT DENSITY - "
EFFECT - - - - - "
EFFICIENCY - - - "
ELECTRODE - - - - 1167
ELECTRODEPOSITION> 207
EXCHANGE CURRENT "
FILM - - - - - - 1167
ION - - - - - - - "
KINETICS - - - - "
MECHANISM - - - - 207
- - - - 1606
METAL - - - - - - 1167
MONOLAYER - - - - "
PH - - - - - - - 1606
PROCESS - - - - - "
SILVER - - - - - 207
SILVER ELECTRODE 1606
STRUCTURE - - - - 1167
TEMPERATURE - - - 1606
THERMODYNAMICS - 1167

ELECTRODE
ACTIVITY - - - -> 354
ADDITIVE - - - -> 463
ADSORPTION - - -> 474
- - ->1167
- - ->1421
- - ->1570
ALCOHOLS - - - ->1048
ALKALI METAL - -> 994
ALLOY - - - - - -> 247
- - - - - -> 734
ALUMINUM - - - -> 983
ALUMINUM CHLORIDE "
994
ANODE OXIDATION -> 757
ANODIZATION - - - 983
APROTIC - - - - -> 518
ARGON OXYGEN - - 354
ASYMPTOTIC - - -> 521
AUTOMATIC - - - -> 251
BARIUM SULFATE - 463
BATTERY ANODE - - 734
BATTERY FAILURE ->1546
BERYLLIUM - - - - 247
BIPOLAR ELECTRODE> 622
BISMUTH - - - - - 247
CALCIA STABILIZED> 506
CAPACITANCE - - -> 632
- - -> 639
CAPACITY - - - -> 512
- - - - 1546
CARBON MONOXIDE ->1315
CARBONATE - - - - 734
- - - - 994
CELL - - - - - - 1048
CESIUM - - - - -> 727
CHARGING - - - - 757
CHLORIDE - - - - 994
CHRONOCOULOMETRY 1421
CIRCUIT - - - - ->1439
COEFFICIENT - - - 994
CONDUCTANCE - - - 1570
CONTROL - - - - - 354
COULOMETRY - - - "
COUPLING - - - -> 745
CURRENT - - - - - 622
CURRENT DENSITY - 994
CURRENT POTENTIAL>1558
CYCLE - - - - - - 1546
CYCLIC - - - - -> 360
DECOMPOSITION - - 1546
DEPOSITION - - - 474
- - ->1592
- - ->1610
DETERMINATION - ->1462
DIFFUSION - - - - 734
- - - - 1315
DIGITAL - - - - - 745
DIMETHYLANILINE - 757
DIMETHYLFORMAMIDE> 79
518
DISCHARGING - - - 757
DISK - - - - - - 1558
DISSOLUTION - - - 360
- - - 1592
DISSOLVED - - - -> 872
DISTRIBUTION - - 622
DOUBLE LAYER - - 512
- - 632
ELECTROCHEMISTRY 518
1048
ELECTROCRYSTALLI. 1167

ELECTRODE (CONTD)
ELECTROLYTE - - - 506
- - - 727
ELECTROLYTE CELL 632
639
ELECTROOXIDATION 745
EQUIVALENT - - - 1439
EXCHANGE - - - - 994
FILM - - - - - - 1167
FLUORIDE - - - - 247
FORM - - - - - - 1546
FUSED - - - - - - 983
GALLIUM - - - - - 506
GALLIUM SESQUIOX. "
GAS - - - - - - - 251
GAS SENSOR - - - 1315
GOLD - - - - - - 1610
GOLD EVAPORATED - 474
GRAPHITE - - - - 632
- - - - 639
HAMMETT - - - - - 1462
HEMISPHERICAL - - 1592
HEXANOL - - - - - 1048
HYDROGEN - - - - 251
- - - - 518
- - - - 1048
- - - - 1462
HYDROXIDE - - - - 727
IMPEDANCE - - - - 521
INTERFACE - - - - 639
INTERMETALLIC - - 734
ION - - - - - - - 983
- - - - - - - 1167
IRON OXIDE - - - 1592
ISOTHERM - - - - 474
KINETICS - - - - 506
- - - - 994
- - - - 1167
LEAD - - - - - - 483
- - - - - - 474
- - - - - - 1610
LEAD CHLORIDE - - 79
LEAD DIOXIDE - - 1546
LEAD SULFATE - - 483
LIGNIN - - - - - "
LITHIUM - - - - - 247
LITHIUM MAGNESIUM 734
MASS TRANSFER - - 1558
MEASUREMENT - - - 79
- - - 1570
MECHANISM - - - - 360
- - - - 483
- - - - 745
- - - - 1546
MERCURY - - - - - 1421
METAL - - - - - - 1167
MILD - - - - - - 1592
MIXTURE - - - - - 354
MODULATION - - - 1558
MOLTEN - - - - - 983
MOLTEN SALT - - - 247
MONOLAYER - - - - 1167
MORPHOLOGY - - - 463
- - - 757
NICKEL - - - - - 512
NORMAL - - - - - 1048
OHMIC COUPLING - 1439
OPTIC - - - - - - 1610
OXIDATION - - - - 1315
OXYGEN - - - - - 354
- - - - - 506
- - - - - 872
PLATINUM - - - - 354
- - - - 360
- - - - 632
- - - - 872
- - - - 1315
POROUS - - - - - 512
POTASSIUM HYDROX. "
POTENTIAL - - - - 79
- - - - 360
- - - - 622
- - - - 872
POTENTIOSTAT - - 354
PROGRAM - - - - - 360
PROPYLENE - - - - 734
- - - - 994
PSEUDOCOLLECTION 1439
PUMP - - - - - - 251
REACTION - - - - 463
REDEPOSITION - - 360
REDUCTION - - - - 727
REFLECTANCE - - - 474
RESISTANCE - - - 1439
RESISTIVE - - - - 622
REST - - - - - - 872
REVERSIBLE CELL - 518

PRIMARY TERM / CO-TERM	PAGE NO.
ELECTRODE (CONTD)	
RHODIUM	1421
RING	1592
RING DISK	360
	745
	1439
ROOM TEMPERATURE	632
ROTATING	745
	1558
	1592
ROTATING DISK	521
ROUGHENING	360
	639
SALT	983
SIGMA	1462
SILVER	757
SILVER CHLORIDE	"
SILVER HALIDES	632
	639
SILVER OXIDE	727
SIMULATION	745
SINGLE CRYSTAL	474
	1610
SINUSOIDAL	1558
SODIUM CHLORIDE	983
SOLID	506
SOLID ELECTROLYTE	632
	639
SOLID STATE	"
SOLUTION	521
SOLVENT	518
SPARKLESS	251
SPECTROSCOPY	474
STANDARD	79
STEEL	1592
STRUCTURE	727
	1167
SUBSTITUENT	1462
SUBVALENT	983
SULFATE SOLUTION	1592
SURFACE	757
	1570
SWEEP	512
THALLIUM	516
	1048
THERMAL ANALYSIS	1546
THERMODYNAMICS	1167
THIN FILM	1570
TITANIUM CHLORIDE	79
TITRATION	354
TRANSFER	506
	994
TRIANGULAR	512
UNDER POTENTIAL	1610
UNDERPOTENTIAL	474
VOLTAGE	512
VOLTAMMETRY	1421
WARBURG	521
WETTING	639
WIRE ELECTRODE	622
ZIRCONIA	354
	506
ELECTRODEPOSIT	
CARBON	490
COPPER	202
EVAPORATION	"
GOLD	490
NUCLEATION	202
SINGLE CRYSTAL	"
THIN FILM	"
ELECTRODEPOSITION	
ALLOY	776
AMORPHOUS	"
BATTERY	1457
CARBONATE	"
COBALT RHENIUM	776
COPPER	661
CURRENT	"
	"
DISTRIBUTION	"
	"
ELECTROCRYSTALLI.	207
ELECTROLYTE	1457
EXCHANGE CURRENT	207
LITHIUM ELECTRODE	1457
MEASUREMENT	661
MECHANISM	207
PRINTED CIRCUIT	661
PROPYLENE	1457
RECHARGABLE	"
REDOX SYSTEM	661
SILVER	207
WIRE	661
	"
WIRE ELECTRODE	"
ELECTRODISSOLUTI.	
ANODE	1876
BENZOTRIAZOLE	"
CHLORIDE SOLUTION	"
CORROSION	"
INHIBITION	"
IRON	"
NEUTRAL SOLUTION	"
ELECTROETCH	
ALUMINUM OXIDE	1465
ANNEALING	"
ANODE FILM	"
SURFACE GAIN	"
TRANSFORMATION	"
ELECTROGENERATE	
CHEMILUMINESCENCE	1178
ELECTROANALYSIS	"
ENERGY DEFICIENT	"
LUMINESCENCE	"
NONAQUEOUS	"
SOLVENT	"
VOLTAMMETRY	"
ELECTROHYDRODIME.	
ACETONITRILE	881
CHRONOPOTENTIOME.	769
COUPLING	"
CURRENT REVERSAL	"
DIETHYLFUMARATE	881
DMSO	"
ELECTROLYTE	769
ION PAIRS	881
KETONES	769
REDUCTION	881
REDUCTIVE	769
SODIUM ION	881
UNSATURATED	769
VOLTAMMETRY	881
ELECTROINITIATE	
BATTERY	1294
HIGH ENERGY	"
LITHIUM	"
PERCHLORATE	"
POLYMERIZATION	"
TETRAHYDROFURAN	"
ELECTROLESS	
ACID BATH	1023
AGITATION	56
ALUMINA	107
AMINE	1023
BEAM	62
BOND	107
BONDING	"
BORANE	1023
BOROHYDRIDE	56
CATALYST	1461
CIRCUIT	62
COBALT	1023
CONSTANT	887
COPPER	107
	887
	1405
CORROSION	887
DENDRITE	912
DEPOSITION	1023
FORMALDEHYDE	1405
FORMING	67
GLASS	667
	1405
GOLD	56
	62
GROWTH INHIBITION	667
HEAT SINKS	912
HEAT TRANSFER	"
HYPOPHOSPHITE	1023
IMAGING	667
IMPURITY	56
INHIBITION	667
	1461
LEAD	62
METALLIZATION	107
MIXED POTENTIAL	887
MOLTEN ALKALI	107
NICKEL	1023
ORGANIC ACID	67
PARTIAL PROCESS	887
PHOTOLYSIS	67
PLASTICS	1461
PLATING	56
	62
	67
	667
	887
ELECTROLESS (CONTD)	
PLATING	912
	1023
	1405
	1461
PREPARATION	912
PRINTED CIRCUIT	67
PROCEDURE	56
RATE	887
SILICON	62
SILVER GLUTAMATE	67
SILVER SALT	"
SPECIFIC	887
STANDARD	"
SURFACE	107
THICKNESS	56
ULTRA VIOLET	1461
ULTRAVIOLET	667
ELECTROLUMINESCE.	
CRYSTAL GROWTH	1516
DIRECT CURRENT	109
DOPING	1516
EPITAXY	"
GAS PHASE	"
GREEN	109
LEAD DOPED	"
MORPHOLOGY	1516
PHOSPHORS	109
POWDER CELLS	"
STOICHIOMETRY	1516
VAPOR PHASE	"
ZINC SULFIDE	109
ELECTROLYSIS	
AQUEOUS SOLUTION	1311
BIPOLAR	648
CHLORATE	"
DECOMPOSITION	1328
ELECTROLYZER	648
HIGH TEMPERATURE	1328
IMPURITIES	1311
INTERFACE	1328
MASS TRANSPORT	"
MERCURY	1311
PARASITE CURRENT	648
SILICON DIOXIDE	1328
SODIUM CHLORIDE	1311
STABILITY	1328
ELECTROLYTE	
ADSORPTION	987
AGENT	779
ALUMINUM	583
AMMONIUM	977
ANION	987
ANODE	1382
BATTERY	1045
	1457
BEHAVIOR	1460
BROMIDE	977
CALCIA STABILIZED	506
CAPACITOR	583
CARBONATE	1457
CESIUM	727
CHRONOPOTENTIOME.	769
COEFFICIENT	779
CONDUCTANCE	977
CONTAMINATION	1045
COPPER FLUOROBOR.	779
COPPER SULFATE	"
CORROSION	583
COUPLING	769
CURRENT REVERSAL	"
DIFFUSION	779
DIMETHYLFORMAMIDE	977
DISCHARGE	1460
ELECTRODE	506
	727
ELECTRODEPOSITION	1457
ELECTROHYDRODIME.	769
ETCHABILITY	583
GAAS	1382
GAASP	"
GALLIUM	506
GALLIUM SESQUIOX.	"
HYDROCARBON	987
HYDROXIDE	727
INFRARED	1045
INORGANIC	"
IRON	583
ISOTHIOCYANATE	977
KETONES	769
KINETIC	779
KINETICS	506
LIQUID	1045
LITHIUM	"
ELECTROLYTE (CONTD)	
LITHIUM CELL	1460
LITHIUM ELECTRODE	1457
MICROSEGREGATION	583
MOLYBDENUM	1460
MONOHYDRATE	987
NICKEL	977
NONAQUEOUS	"
	1382
	1460
ORGANIC	779
OXIDATION	987
	1382
OXYGEN	506
OXYHALIDE	1045
PARAMETER	779
POTASSIUM	977
PRECIPITATION	583
PROPANE	987
PROPYLENE	1457
RECHARGABLE	"
REDUCTION	727
REDUCTIVE	769
SILVER OXIDE	727
SOLID	506
SOLUTION	977
	1460
STRUCTURE	727
TETRABUTYL	977
TRACE ANALYSIS	1045
TRANSFER	506
TRIFLUOROMETHANE.	987
TUNNEL	583
UNSATURATED	769
VISCOSITY	977
WATER	1045
ZIRCONIA	506
ELECTROLYTE CELL	
CAPACITANCE	632
	639
DOUBLE LAYER	632
ELECTRODE	"
	639
GRAPHITE	632
	639
INTERFACE	"
PLATINUM	632
ROOM TEMPERATURE	"
ROUGHENING	639
SILVER HALIDES	632
	639
SOLID ELECTROLYTE	632
	639
SOLID STATE	"
WETTING	"
ELECTROLYTES	
ACETONE	1563
CRYSTAL GROWTH	"
DISSOLUTION	"
DUTERIUM OXIDE	"
FORMAMIDE	"
POTENTIAL	"
PRECIPITATION	"
TRANSIENT	"
ELECTROLYZER	
BIPOLAR	648
CHLORATE	"
ELECTROLYSIS	"
PARASITE CURRENT	"
ELECTROMIGRATION	
BERYLLIUM	1429
CHRONOPOTENTIOME.	"
DEPENDENCE	"
DEPLETION	"
FLOURIDES	"
GLASSES	"
LITHIUM	"
MOLTEN HALIDES	"
TEMPERATURE	"
ELECTRON	
ACTIVATION	459
ALUMINUM	268
AMMONIA	459
ANION VACANCY	255
ANODE	876
ANODE DISINTERGR.	7
ANODE DISSOLUTION	"
ANODE FILM	268
ANOMALOUS VALENCY	7
ANTI FRENKEL	255
BATTERY	1541
BERYLLIUM	7

PRIMARY TERM — CO-TERM — PAGE NO.

ELECTRON (CONTD)
BREAKDOWN - - - -> 692
CHARACTERISTIC - 7
CHLORIDE - - - - 268
COATING - - - - -> 720
CONCENTRATION - - 459
CONDUCTIVITY - - 255
CRT - - - - - - - 720
CRYSTAL - - - - ->1454
DECOMPOSITION - - 459
DEFECT STRUCTURE 255
DEVICE - - - - - 720
DIFFUSION - - - ->1538
DIODE - - - - - - 692
ENTROPY - - - - - 459
GAAS - - - - - - 692
GRAPHITE SILICATE 720
GROWTH - - - - - 268
IMPATT - - - - - 692
INORGANIC - - - -> 929
ION - - - - - - - 255
IRON OXIDE - - - 929
LEAD - - - - - - 876
LEAD ACID - - - - 1454
- - - - 1541
LEAD CALCIUM - - "
LEAD ELECTRODE - "
LEAD SULFATE - - 1454
LITHIUM - - - - - 459
MICROSCOPE - - - 7
- - - 692
MICROSCOPY - - - 876
- - - 1454
- - - 1538
- - - 1541
NEGATIVE - - - - "
NONAQUEOUS - - - 7
OPACITY - - - - - 268
PALLADIUM - - - - 1538
PENETRATION - - - 720
PHOTOMASK - - - - 929
PITTING - - - - - 268
POLARIZATION - - 7
POLARIZED - - - - 876
POLYMER BONDING - 1541
PRECIPITATION - - 1454
PREMATURE - - - - 692
RESIST - - - - - 929
SCANNING - - - - 7
- - - - 692
- - - - 1454
- - - - 1541
SCHOTTKY - - - - 692
SILICIDE - - - - 1538
SITES - - - - - - 692
SOLUTION - - - - 7
- - - - 1454
SOLVATED - - - - 459
STRUCTURE - - - - 1454
- - - - 1538
THICKNESS - - - - 720
THIN FILM - - - - 929
VOLTAMMETRY - - - 876
YTTRIA DOPED - - 255
ZIRCONIUM OXIDE - "

ELECTRON BEAM
CONTRAST - - - ->1669
DEVELOPER - - - - "
ELECTRON RESIST - "
FUNCTION - - - - "
ION MILLABLE - ->1620
LITHOGRAPHY - - - 1669
METHACRYLATE - - "
PMMA - - - - - - "
POLYMETHYL - - - "
POLYSTYRENE - - - 1620
POSITIVE - - - - "
RATE - - - - - - 1669
RESIST - - - - - 1620
SOLUBILITY - - - 1669
SULFONE - - - - - 1620

ELECTRON MICROSC.
CATALYST - - - -> 738
CHANNELING - - ->1657
DIELECTRIC - - - 738
FLOW - - - - - -> 307
GALLIUM - - - - - 1657
GLASS - - - - - - 307
INDIUM - - - - - 1657
INTEGRATED CIRCU. 307
MICROPROBE - - - 1657
MIXED - - - - - - 38
MOS - - - - - - - 307
PALLADIUM CHLORI. 738
PATTERN - - - - - 1657

ELECTRON MICROSC. (CONTD)
PHOSPHIDE - - - - 1657
PLATING - - - - - 738
SCANNING - - - - 307
- - - - 1657
STANNOUS CHLORIDE 738
SUBSTRATE - - - - "

ELECTRON MOBILITY
CERIUM DIOXIDE -> 126
COMPOSITION - - - "
CONDUCTIVITY - - "
DEPENDENCE - - - "
NONSTOICHIOMETRIC "
TEMPERATURE - - - "

ELECTRON RESIST
CONTRAST - - - ->1669
DEVELOPER - - - - "
ELECTRON BEAM - - "
FUNCTION - - - - "
LITHOGRAPHY - - - "
METHACRYLATE - - "
PMMA - - - - - - "
POLYMETHYL - - - "
RATE - - - - - - "
SOLUBILITY - - - "

ELECTRON RESISTS
LITHOGRAPHY - - ->1500
POLYMER RESISTS - "
X RAY - - - - - - "

ELECTRON SPECTRO.
AUGER - - - - - -> 310
- - - - - -> 827
CLEANING - - - - 310
DENSIFICATION - - 827
GERMANIUM - - - - 310
GLASS FILM - - - 827
OXYGEN - - - - - "
RATIO - - - - - - "
SILICON - - - - - "
SILICON DIOXIDE - "
SPIN ON - - - - - "
STOICHIOMETRY - - "
SURFACE - - - - - 310

ELECTROOPTICAL
ANODE OXIDATION -> 820
COMPOUND - - - - "
DEVICE - - - - - "
DIFFUSION - - - - "
GALLIUM ARSENIDE "
SEMICONDUCTOR - - "
ZINC - - - - - - "

ELECTROOXIDATION
COUPLING - - - -> 745
DIGITAL - - - - - "
ELECTRODE - - - - "
MECHANISM - - - - "
RING DISK - - - - "
ROTATING - - - - "
SIMULATION - - - "

ELECTROPLATED
DEVICE - - - - -> 426
FABRICATION - - - "
GAAS - - - - - - "
HEAT SINKS - - - "
IMPATT - - - - - "
WAFER CURVATURE - "

ELECTROREDUCTION
BRONZE - - - - ->1029
HYDROGEN - - - - "
HYDROGEN PEROXIDE "
OXYGEN - - - - - "
PLATINUM - - - - "
SODIUM - - - - - "
TRACES - - - - - "
TUNGSTEN - - - - "

ELECTROSORPTION
ADSORPTION - - -> 233
CARBON DIOXIDE - "
CARBONYL - - - - "
PLATINUM - - - - "
RADIOMETRY - - - "
REDUCED - - - - - "

ELECTROWINNING
CATHODE - - - - -> 867
COEFFICIENT - - - "
CONVECTION - - - "
EUTECTICS - - - -> 879

ELECTROWINNING (CONTD)
FORCED - - - - - 867
FUSED SALTS - - - 879
HAFNIUM - - - - - "
MASS - - - - - - 867
MODEL CELL - - - "
NATURAL - - - - - "
REACTIVE METALS - 879
TRANSFER - - - - 867

ELEMENTAL
BORIDES - - - - -> 846
BORON - - - - - - "
CHEMICAL - - - - "
MODIFICATION - - "
NONMETAL - - - - "
STRUCTURE - - - - "
TETRAGONAL - - - "
VAPOR DEPOSITION "

ELEVATED
COPPER - - - - -> 651
CORROSION - - - - "
CYCLIC - - - - - "
LITHIUM HYDROXIDE "
TEMPERATURE - - - "
VOLTAMMETRY - - - "

ELLIPSOMETRY
ANODE - - - - - ->1146
ANODE FILM - - ->1186
CATALYSIS - - - - "
CHROMATE - - - - 1146
CORROSION - - - - "
DOUBLE LAYER - ->1596
EVOLUTION - - - - 1186
FILM - - - - - - 1146
FORMATION - - - - 1596
GALVANOSTATIC - - 1186
GOLD - - - - - - 1596
HYSTERESIS - - - "
INHIBITOR - - - - 1146
IRON - - - - - - "
- - - - - ->1393
NIOBIUM - - - - -> 805
OPEN CIRCUIT - - 1146
OXIDATION - - - -> 263
- - - - 805
OXIDE FILM - - - 1596
OXYGEN - - - - - 1186
PASSIVITY - - - - 1146
PHOSPHATES - - - 1393
PLASMA - - - - - 263
- - - - - 805
PLATINUM - - - - 1186
- - - - 1596
POTENTIAL - - - - 1146
REACTION - - - - 1186
REDUCTION - - - - 1596
REFLECTANCE - - - "
REFRACTIVE INDEX 805
1393
SULFURIC ACID - - 1186
SURFACE PROCESS - 1596
TANTALUM - - - - 263
- - - - 805
THICKNESS - - - - 1186
THIN FILMS - - - 1393

EMBRITTLEMENT
BEHAVIOR - - - ->1589
HYDROGEN - - - - "
HYDROGEN ELECTRO. "
IRREVERSIBLE - - "

EMF
ALKALI CHLORIDE -> 991
ALLOY - - - - - ->1245
ALUMINUM - - - - "
BATTERY - - - - - "
BETA ALUMINA - ->1603
BUFFER - - - - - 1245
CADMIUM CHLORIDE > 959
CARBONATE - - - -> 83
CARBONATE ION - -> 885
CERIUM CHLORIDE - 991
CHLORIDE - - - - 1245
FREE ENERGY - - - 959
FUSED NITRATES - 885
GIBBS - - - - - - 959
HIGH PRESSURE - - 1245
ION MOBILITY - - 959
- - "
LITHIUM CHLORIDE "
LITHIUM ION - - - 83
MAGNESIUM - - - - 1245
MEASUREMENT - - - 83

EMF (CONTD)
MEASUREMENT - - - 991
MIXTURE - - - - - "
MOLTEN MIX - - - 959
MOLTEN SALT - - - 991
NUMBER - - - - - 83
NUMBERS - - - - - 991
OXIDE ION - - - - 885
OXYGEN ELECTRODE "
PROPYLENE - - - - 83
SEAWATER - - - - 1245
SOLID ELECTROLYTE 1603
SOLUTION - - - - 83
STABILITY - - - - 885
TRANSFERENCE - - 83
- - 959
- - 991

EMITING
AMMONIA - - - - -> 962
BEHAVIOR - - - - "
DIODES - - - - - "
EPITAXY - - - - - "
GAP - - - - - - - "
IMPURITY - - - - "
LIGHT - - - - - - "
LIQUID PHASE - - "
NITROGEN DOPING - "
SOURCE - - - - - "

EMITTER DIP
BORON - - - - - ->1377
DIFFUSION - - - - "
PHOSPHORUS - - - "

ENCAPSULATION
CRYSTAL GROWTH -> 822
CZOCHRALSKI - - - "
DOPING - - - - ->1350
ENHANCEMENT - - - "
GALLIUM PHOSPHIDE 822
GOLD - - - - - - 1350
IMAGING - - - - - 822
LIQUID - - - - - "
SILICON - - - - - 1350
SOLUBILITY - - - "
X RAY - - - - - - 822

ENERGY DEFICIENT
CHEMILUMINESCENCE>1178
ELECTROANALYSIS - "
ELECTROGENERATE - "
LUMINESCENCE - - "
NONAQUEOUS - - - "
SOLVENT - - - - - "
VOLTAMMETRY - - - "

ENERGY TRANSFER
EUROPIUM - - - -> 305
- - - ->1338
FLUORESCENCE - - "
GLASS - - - - - - "
HIGH PRESSURE - - 305
LAMP - - - - - - "
LEAD - - - - - - 1338
MERCURY - - - - - 305
PHOSPHOR - - - - "
TERBIUM - - - - - "
VANDATE - - - - - "
VAPOR - - - - - - "
YTTRIUM - - - - - "

ENHANCEMENT
DOPING - - - - ->1350
ENCAPSULATION - - "
GOLD - - - - - - "
SILICON - - - - - "
SOLUBILITY - - - "

ENTROPY
ACTIVATION - - -> 459
AMMONIA - - - - - "
CONCENTRATION - - "
DECOMPOSITION - - "
ELECTRON - - - - "
LITHIUM - - - - - "
SOLVATED - - - - "

ENTRY
ADSORPTION - - -> 609
ARSENIC - - - - - "
HYDROGEN - - - - "
PERMEATION - - - "
POTENTIAL - - - - "
STEEL - - - - - - "

PRIMARY TERM / CO-TERM	PAGE NO.
ENVIRONMENT	
ALUMINUM FILM	-> 400
ANODE OXIDATION	"
IMPEDANCE	"
PH	"
POROSITY	"
EPITAXIAL	
APPLICATION	-> 422
CIRCUIT	"
DEVICE	"
INTEGRATED	"
INTERFEROGRAM	-> 150
LAYER	"
MEASUREMENT	422
PHASE SHIFT	150
RESISTANCE	422
RESISTIVITY	"
SILICON	150
	422
SPREADING	"
THICKNESS	150
EPITAXY	
ACCEPTOR	->1208
ALUMINATE	-> 571
AMMONIA	-> 962
ANTIMONY	-> 967
ARSENIC	->1362
BARRIER	->1066
BEHAVIOR	962
CADMIUM	-> 965
CALCULATION	->1357
CAPACITANCE	1066
CRYSTAL GROWTH	-> 439
	->1237
	->1516
DECOMPOSITION	->1383
DEPOSITION	965
	1357
DETECTOR	->1506
DEVICE	-> 563
DIFFUSION	1237
DIODES	962
DOPED	1237
DOPING	967
	1516
ELECTROLUMINESCE.	"
EMITING	962
EQUILIBRIA	->1354
ETCHING	1383
EVALUATION	439
GAAS	"
	1066
	1237
	1506
GAASP	1357
GALLIUM ARSENIDE	571
GAN	1383
GAP	962
GAS PHASE	1354
	1516
GERMANIUM	1237
GROWTH	563
	571
	1362
HALL DATA	1208
HALL EFFECT	1066
HETEROEPITAXY	965
IMPURITY	563
	962
INDIUM PHOSPHIDE	1208
INGAAS	1506
ION IMPLANT	1362
IRON	->1534
IRON OXIDE	"
LAYER	1066
LIGHT	962
LIQUID	439
LIQUID PHASE	962
	1208
MAGNESIUM	571
MEASUREMENT	1066
METALORGANICS	967
MICROWAVE DEVICE	439
MOBILITY	1066
MORPHOLOGY	1516
NITROGEN DOPING	962
OHM	1237
OXIDATION	1534
PHOSPHORUS	1354
PHOTOLUMINESCENCE	1066
	1208
PHOTOSENSITIVITY	965
PROCESSING	563
REDISTRIBUTION	"
SAPPHIRE	965
EPITAXY (CONTD)	
SAPPHIRE	967
SCHOTTKY	1066
SELENIDE	965
SEMICONDUCTOR	563
	1237
SILICON	563
	967
	1354
	1362
SINGLE CRYSTAL	1534
SOURCE	962
	967
SPECTRA	1066
SPINEL	871
STOICHIOMETRY	1516
SULFIDE	965
THERMAL	1383
TRIMETHYLSTIBINE	967
VAPOR	965
VAPOR PHASE	"
	1354
	1357
	1516
WAVEGUIDE	1506
ZINC	1237
EQUATION	
BOUNDARY	-> 313
COMPLEMENT	"
CONDITION	"
DIFFUSION	"
ERROR	"
FLUX STEP	"
FUNCTION	"
PROFILE	"
SEMICONDUCTOR	"
EQUILIBRIA	
ARGON	->1372
CONTROL	"
DIFFUSING	"
EPITAXY	->1354
ETCHING	1372
GAS PHASE	1354
HELIUM	1372
HEXAFLUORIDE	"
INCLUSION	-> 467
INITIATION	"
LANGMUIR SHEATH	1372
MANGANESE	467
NITROGEN	1372
PENTA FLUORIDE	"
PHOSPHORUS	1354
PITTING	467
POTENTIAL PH	"
RATE	1372
REACTION	"
SILICON	1354
STAINLESS STEEL	467
SULFIDE	"
TUNGSTEN	1372
VAPOR PHASE	1354
EQUILIBRIUM	
CHLORINE	-> 919
DECOMPOSITION	"
DEPOSITION	"
HIGH TEMPERATURE	"
HYDROGEN	"
REACTION	"
REDUCTION	"
SILICON	"
EQUIVALENT	
CIRCUIT	->1439
ELECTRODE	"
OHMIC COUPLING	"
PSEUDOCOLLECTION	"
RESISTANCE	"
RING DISK	"
ERBIUM	
ANODE SPARK	->1402
DYSPROSIUM	"
GADOLINIUM	"
HOLMIUM	"
SAMARIUM	"
SODIUM SILICATE	"
YTTERBIUM	"
YTTRIUM	"
ERROR	
BOUNDARY	-> 313
COMPLEMENT	"
CONDITION	"
DIFFUSION	"
ERROR (CONTD)	
EQUATION	313
FLUX STEP	"
FUNCTION	"
PROFILE	"
SEMICONDUCTOR	"
ETCH	
ARSENIC	->1650
ARSENIDE	"
ASYMMETRIC	"
ASYMMETRY	"
COMPOUNDS	"
CRACKING	"
CROSS HATCH	"
GALLIUM	"
GROUP III-V	"
INDIUM	"
PHOSPHIDE	"
SIRTL	"
ETCH SOLUTION	
BUFFER	->1579
FLUORIDE	"
PALLADIUM HYDRIDE	"
PH ELECTRODE	"
ETCHABILITY	
ALUMINUM	-> 583
CAPACITOR	"
CORROSION	"
ELECTROLYTE	"
IRON	"
MICROSEGREGATION	"
PRECIPITATION	"
TUNNEL	"
ETCHANT	
AMMONIUM	->1215
BIPOLAR	"
CHEMICAL	"
GALLIUM ARSENIDE	"
HYDROGEN PEROXIDE	"
HYDROXIDE	"
LEAD SULFIDE	-> 595
LEAD SULFUR	"
PN JUNCTION	"
REMOVAL	1215
SELECTIVE	"
SELENIUM	595
SILICON DIOXIDE	1215
TRANSISTOR	"
ETCHING	
ARGON	->1372
ASSIGNMENT	-> 170
BREAKDOWN	->1229
CARRIER	"
CONTROL	1372
CRYSTAL	->1085
CRYSTAL DEFECTS	170
CRYSTALLOGRAPHY	"
DECOMPOSITION	->1383
DEFECT	1085
DIELECTRIC	1229
DIFFUSING	1372
DIFFUSION	-> 286
DOMAIN	170
ELECTROCHEMICAL	286
EPITAXY	1383
EQUILIBRIA	1372
FERRICYANIDE	-> 455
FERROELECTRIC	170
FILM	286
GALLIUM	1085
GAN	1383
GAP	455
GAS PHASE	-> 293
GENERATION	1229
GMC	170
HELIUM	1372
HEXAFLUORIDE	"
IMPERFECTION	1229
LANGMUIR SHEATH	1372
LED	455
MASK	"
MINORITY	1229
NITROGEN	1372
PENTA FLUORIDE	"
PHOSPHIDE	1085
POLISH	455
RATE	1372
REACTION	"
SAPPHIRE	293
SILICON	286
	1229
SINGLE CRYSTAL	170
ETCHING (CONTD)	
THERMAL	1383
THIN FILM	286
TUNGSTEN	1372
WAFER	1229
EUROPIUM	
ALKALI	->1122
ALKALINE	"
	->1475
ALUMINUM	-> 137
BARIUM	"
CALCIUM	"
CRYSTAL	1475
DIVALENT	"
EARTH	1122
	1475
ENERGY TRANSFER	-> 305
	->1338
FLUORESCENCE	"
GALLIUM	137
GLASS	1338
HIGH PRESSURE	305
LAMP	"
LEAD	1338
LUMINESCENCE	1122
	1475
MERCURY	305
OPTICAL SPECTRA	1475
PHOSPHATES	1122
PHOSPHOR	305
PHOTOLUMINESCENCE	137
SEMICONDUCTOR	"
STRONTIUM	"
STRUCTURE	1475
SULFATES	"
SYNTHESIS	137
TERBIUM	305
VANDATE	"
VAPOR	"
YTTERBIUM	137
YTTRIUM	305
EUTECTIC	
ACCELERATE	-> 778
CORROSION	"
CREVICE	"
FORMATION	"
ION	"
LITHIUM CHLORIDE	"
MONOLAYER	"
NICKEL	"
PITTING	"
POTASSIUM CHLORI.	"
REDUCTION	"
SILVER	"
EUTECTICS	
ELECTROWINNING	-> 879
FUSED SALTS	"
HAFNIUM	"
REACTIVE METALS	"
EVALUATION	
CRYSTAL GROWTH	-> 439
EPITAXY	"
GAAS	"
LIQUID	"
MICROWAVE DEVICE	"
EVAPORATION	
COPPER	-> 202
ELECTRODEPOSIT	"
FLOAT ZONE	->1222
HIGH RESISTIVITY	"
NUCLEATION	202
POLYCRYSTALLINE	1222
POLYDEPOSITION	"
PROCESS	"
PRODUCTION	"
SILICON	"
SINGLE CRYSTAL	202
	1222
THIN FILM	202
VACUUM	1222
EVOLUTION	
ACID	->1609
AMMONIA	-> 230
	1609
ANODE FILM	->1186
CATALYSIS	"
CHROMIUM	-> 225
COBALT	"
COEFFICIENT	230
CORROSION	225
ELLIPSOMETRY	1186

PRIMARY TERM / CO-TERM — PAGE NO.

EVOLUTION (CONTD)
EXCHANGE CURRENT 230
GALVANOSTATIC 1186
HYDROGEN 225
230
1609
LIQUID 230
1609
MANGANESE 225
NITROGEN 230
1609
OVERVOLTAGE 230
OXYGEN 1186
PLATINUM "
REACTION "
1609
SULFURIC ACID 1186
TAFEL SLOPE 230
THICKNESS 1186
TRANSFER 230
VANADIUM 225

EXCHANGE
ALKALI METAL -> 994
ALUMINUM CHLORIDE "
CARBONATE "
CHLORIDE "
COEFFICIENT "
CURRENT DENSITY "
ELECTRODE "
KINETICS "
PROPYLENE "
TRANSFER "

EXCHANGE CURRENT
AMMONIA -> 230
COEFFICIENT "
ELECTROCRYSTALLI.> 207
ELECTRODEPOSITION "
EVOLUTION 230
HYDROGEN "
LIQUID "
MECHANISM 207
NITROGEN 230
OVERVOLTAGE "
SILVER 207
TAFEL SLOPE 230
TRANSFER "

EXISTENCE
CRYSTAL ->1674
HEAT "
INDIUM "
MEASUREMENT "
MONOSELENIDE "
PHASE TRANSITION "
SEMICONDUCTOR "
SPECIFIC "
STRUCTURE "
XRAY "

FABRICATION
DEVICE -> 426
ELECTROPLATED "
GAAS "
HEAT SINKS "
IMPATT "
WATER CURVATURE "

FACET GROWTH
DEMARCATION -> 787
INTERFACE "
SEGREGATION "

FEP
CHARGE -> 591
DENSITY "
DIELECTRIC "
ELECTRET "
HOMOCHARGE "
INSERT "
SPRAY "
SURFACE "
TEFLON "
THERMOELECTRET "

FERRATE
ANODE DISSOLUTION> 249
ELECTROCHEMICAL "
IRON (VI) "
POTENTIOSTATIC "
SYNTHESIS "

FERRICYANIDE
ETCHING -> 455
GAP "
LED "

FERRICYANIDE (CONTD)
MASK 455
POLISH "

FERROELECTRIC
ASSIGNMENT -> 170
CRYSTAL DEFECTS "
CRYSTALLOGRAPHY "
DOMAIN "
ETCHING "
GMO "
SINGLE CRYSTAL "

FET
CHEMICAL ->1103
CONCENTRATION -> 419
DEVICE "
GATE "
GLASS "
INTERFACE "
ION DRIFT "
ION TRAPPING "
MOS 1103
OXIDE 419
PHOSPHORUS "
PHOSPHOSILICATE "
POLARIZATION "
SILICON DIOXIDE 1103
SILICON OXIDE 419
THICKNESS "
THIN FILM 1103
THRESHOLD 419
VAPOR DEPOSITION 1103
VOLTAGE 419

FIBER GROWTH
AC DISCHARGE -> 714
DEPOSITION "
TANTALUM CARBIDE "
VAPOR "

FIELD EFFECT
CORONA CHARGE -> 452
INTERFACE "
MODULATE "
PHOTOLUMINESCENCE "
SEMICONDUCTOR "
TRAP "
ZINC OXIDE "

FILM
ADSORPTION ->1167
AERATION -> 183
ALUMINUM OXIDE ->1019
ANODE ->1146
ANODE OXIDATION ->1152
ANODE OXIDE 1019
ARGON -> 558
BACKSPUTTERING "
BARRIER HEIGHT ->1195
BREAKDOWN -> 809
1195
CHROMATE 1146
COMPOSITE 1019
CONTAMINATION 1195
CONTROL ->1233
->1235
CORROSION 183
1146
CRISTOBALITE ->1081
CRYSTALLIZATION "
CVD 1233
DEPOSITION "
1235
DIELECTRIC 809
1195
DIFFERENTIAL 183
DIFFUSION -> 286
1081
ELECTROCHEMICAL 286
ELECTROCRYSTALLI. 1167
ELECTRODE "
ELLIPSOMETRY 1146
ETCHING 286
FILM THICKNESS 1233
1235
GRAVIMETRY 1019
HALOGEN 809
HELIUM 1233
HYDROGEN CHLORIDE 809
HYDROUS 1019
IMPLANTATION 558
INHIBITOR 1146
INTERFACE 1081
ION 558
1167
IRON 1146

FILM (CONTD)
KINETICS 1167
LASER 1233
1235
LOWERING 1195
METAL 183
1167
METALLIZATION 558
MOISTNESS 183
MONOLAYER 1167
NEON 1233
NETWORK 1081
NEUTRAL 1152
NICKEL "
NICKEL OXIDE "
NITRIDE 1233
OPEN CIRCUIT 1146
OXIDATION 809
PASSIVATING 183
PASSIVITY 1146
1152
PHOSPHORUS 1081
POLYCRYSTALLINE 1235
POTENTIAL 1146
PSEUDOBOEHMITE 1019
RADIOTRACER "
RELIABILITY 809
SILICON 286
1195
1233
1235
SILICON DIOXIDE 558
809
1081
1195
1233
SODIUM 1195
SODIUM INDUCED "
SPUTTERING 558
STRUCTURE 1167
SULFATE 1152
THERMODYNAMICS 1167
THICKNESS 183
THIN FILM 286
TRAPPING 558
VARIABLE 183

FILM THICKNESS
CONTROL ->1233
->1235
CVD 1233
DEPOSITION "
1235
FILM 1233
1235
HELIUM 1233
LASER "
1235
NEON 1233
NITRIDE "
POLYCRYSTALLINE 1235
SILICON 1233
1235
SILICON DIOXIDE 1233

FLOAT ZONE
EVAPORATION ->1222
HIGH RESISTIVITY "
POLYCRYSTALLINE "
POLYDEPOSITION "
PROCESS "
PRODUCTION "
SILICON "
SINGLE CRYSTAL "
VACUUM "

FLOURIDES
BERYLLIUM ->1429
CHRONOPOTENTIOME. "
DEPENDENCE "
DEPLETION "
ELECTROMIGRATION "
GLASSES "
LITHIUM "
MOLTEN HALIDES "
TEMPERATURE "

FLOW
ELECTRON MICROSC.> 307
GLASS "
INTEGRATED CIRCU. "
MOS "
SCANNING "

FLOW REACTOR
CURRENT -> 95
DIMENSION "

FLOW REACTOR (CONTD)
DISTRIBUTION 95
PACKED BED "

FLUORESCENCE
ENERGY TRANSFER ->1378
EUROPIUM "
GLASS "
LEAD "

FLUORESCENT
DELUXE ->1627
HIGH EFFICACY "
LAMPS "
NEW GENERATION "

FLUORIDE
ALLOY -> 247
BERYLLIUM "
BISMUTH "
BUFFER ->1579
ELECTRODE 247
ETCH SOLUTION 1579
LITHIUM 247
MOLTEN SALT "
PALLADIUM HYDRIDE 1579
PH ELECTRODE "

FLUORINE
CONTAMINATION -> 790
GOLD REFRACTORY "
ION "
METALLIZATION "
RETENTION "
SILICON "
SURFACE "
TRANSISTOR "

FLUOROGRAPHITE
BEHAVIOR ->1308
DOUBLE LAYER "
NONAQUEOUS "
POROUS ELECTRODE "
POTENTIAL "

FLUX STEP
BOUNDARY -> 313
COMPLEMENT "
CONDITION "
DIFFUSION "
EQUATION "
ERROR "
FUNCTION "
PROFILE "
SEMICONDUCTOR "

FORCED
CATHODE -> 867
COEFFICIENT "
CONVECTION "
ELECTROWINNING "
MASS "
MODEL CELL "
NATURAL "
TRANSFER "

FORM
BATTERY FAILURE ->1546
CAPACITY "
CYCLE "
DECOMPOSITION "
ELECTRODE "
LEAD DIOXIDE "
MECHANISM "
THERMAL ANALYSIS "

FORMALDEHYDE
AEROSOL -> 484
COPPER ->1405
DEPOSIT 484
ELECTRICAL "
ELECTROCATALYST ->1125
ELECTROLESS 1405
GLASS "
HYDRAZINE 484
KINETICS 1125
MECHANISM "
MOLYBDENUM "
OXIDATION "
PLATING 484
1405
REACTION 1125
RESISTIVITY 484
SILVER "
SPRAY "
SULFUR 1125

PRIMARY TERM / CO-TERM	PAGE NO.
FORMAMIDE	
ACETONE	->1563
CRYSTAL GROWTH	"
DISSOLUTION	"
DUTERIUM OXIDE	"
ELECTROLYTES	"
POTENTIAL	"
PRECIPITATION	"
TRANSIENT	"
FORMATION	
ABSORPTION	-> 586
ACCELERATE	-> 778
ACETONE	->1584
BATTERY	-> 854
CHROMIUM OXIDE	-> 711
COMPOUND	586
CONDUCTIVITY	"
CONSTANT	1584
CORROSION	778
CREVICE	"
DOUBLE LAYER	->1596
ELECTRIC	586
ELLIPSOMETRY	- 1596
EUTECTIC	778
FREE ENERGY	711
GOLD	1596
HYSTERESIS	"
ION	778
ION IMPLANTATION	586
LEAD ACID	854
LEAD ELECTRODE	"
LITHIUM CHLORIDE	778
MIXTURE	1584
MONOLAYER	778
NEGATIVE PLATE	854
NICKEL	778
OPTICAL	586
OXIDE FILM	1596
PITTING	778
PLATINUM	1596
POTASSIUM CHLORI.	778
PRODUCT	1584
REDUCTION	778
	1596
REFLECTANCE	"
SILICON CARBIDE	586
SILVER	778
SILVER HALIDES	1584
SOLID ELECTROLYTE	711
SOLUBILITY	1584
SURFACE PROCESS	1596
WATER	1584
FORMATION CELL	
CESIUM CHLORIDE	-> 104
MOLTEN SALT	"
NICKEL CHLORIDE	"
FORMIC ACID	
ACETONITRILE	-> 780
ACTIVATION	"
ELECTROCATALYST	"
MERCURY	"
OXIDATION	"
FORMING	
ELECTROLESS	-> 67
ORGANIC ACID	"
PHOTOLYSIS	"
PLATING	"
PRINTED CIRCUIT	"
SILVER GLUTAMATE	"
SILVER SALT	"
FRACTOGRAPHY	
CORROSION	->1190
CRACK	"
MORPHOLOGY	"
STAINLESS STEEL	"
STRESS	"
STRIATION	"
SULFURIC ACID	"
TRANSGRANULAR	"
FREE ENERGY	
CADMIUM CHLORIDE	> 959
CHROMIUM OXIDE	-> 711
EMF	959
FORMATION	711
GIBBS	-> 932
	959
ION MOBILITY	"
	"
LATTICE PARAMETER	932
LITHIUM CHLORIDE	959
MISCIBILITY GAP	932
FREE ENERGY (CONTD)	
MODEL	932
MOLTEN MIX	959
PSEUDO BINARY	932
QUASIREGULAR	"
SOLID ELECTROLYTE	711
TRANSFERENCE	959
FREE RADICAL	
BEHAVIOR	-> 345
DIHYDROPYRIDINES	"
DIMERIZATION	"
METHYLNICOTINAMI.	"
NICOTINAMIDE	"
OXIDATION	"
REDOX PATTERN	"
	"
REDUCTION	"
FUEL CELL	
ANODE	->1864
CATALYST	"
HYDRAZINE	"
NICKEL BORIDE	"
SUBSTRATE	"
FUNCTION	
BOUNDARY	-> 313
COMPLEMENT	"
CONDITION	"
CONTRAST	->1669
DEVELOPER	"
DIFFUSION	313
ELECTRON BEAM	1669
ELECTRON RESIST	"
EQUATION	313
ERROR	"
FLUX STEP	"
LITHOGRAPHY	1669
METHACRYLATE	"
PMMA	"
POLYMETHYL	"
PROFILE	313
RATE	1669
SEMICONDUCTOR	313
SOLUBILITY	1669
FUSED	
ALUMINUM	-> 983
ALUMINUM CHLORIDE	"
ANODIZATION	"
ELECTRODE	"
ION	"
MOLTEN	"
SALT	"
SODIUM CHLORIDE	"
SUBVALENT	"
FUSED NITRATES	
CARBONATE ION	-> 885
EMF	"
OXIDE ION	"
OXYGEN ELECTRODE	"
STABILITY	"
FUSED SALT	
ALUMINUM CHLORIDE	> 212
COPPER	"
IRON	"
MELT	"
METAL ION	"
POLAROGRAPHY	"
SILVER	"
SODIUM CHLORIDE	"
SYSTEM	"
VOLTAMMETRY	"
FUSED SALTS	
ELECTROWINNING	-> 879
EUTECTICS	"
HAFNIUM	"
REACTIVE METALS	"
FUSED SILICA	
DEPOSIT	-> 685
DEVICE	"
SILICON FILM	"
THIN FILM	"
TRANSISTOR	"
VACUUM	"
GAAS	
ABSORPTION	->1482
ALLOY	-> 416
ANODE	->1382
BARRIER	->1066
BREAKDOWN	-> 692
GAAS (CONTD)	
CAPACITANCE	1066
CARRIER	1482
CHARACTERIZATION	416
CONCENTRATION	1482
CRYSTAL GROWTH	-> 439
	->1237
DETECTOR	->1506
DEVICE	-> 426
DIFFUSION	1237
DIODE	692
DOPED	1237
DRUDE ZENER	1482
ELECTROLYTE	1382
ELECTRON	692
ELECTROPLATED	426
EPITAXY	439
	1066
	1237
	1506
EVALUATION	439
FABRICATION	426
GAASP	1382
GERMANIUM	1237
GROWTH	416
HALL EFFECT	1066
HEAT SINKS	426
HETEROJUNCTION	416
IMPATT	426
	692
INFRARED	1482
INGAAS	1506
LATTICE MATCH	416
LAYER	1066
LIQUID	439
LPE	416
MEASUREMENT	1066
MICROSCOPE	692
MICROWAVE DEVICE	439
MOBILITY	1066
NONAQUEOUS	1382
OHM	1237
OXIDATION	-> 113
	1382
OXIDE FILM	113
OXYGEN PLASMA	"
PHOTOLUMINESCENCE	1066
PREMATURE	692
REFLECTIVITY	1482
SCANNING	692
SCHOTTKY	"
	1066
SEMICONDUCTOR	1237
	1482
SILICON DOPED	"
SITES	692
SPECTRA	1066
WATER CURVATURE	426
WAVEGUIDE	1506
ZINC	1237
GAASP	
ANODE	->1382
CALCULATION	->1357
DEPOSITION	"
ELECTROLYTE	1382
EPITAXY	1357
GAAS	1382
NONAQUEOUS	"
OXIDATION	"
VAPOR PHASE	1357
GADOLINIUM	
ANODE SPARK	->1402
DYSPROSIUM	"
ERBIUM	"
HOLMIUM	"
SAMARIUM	"
SODIUM SILICATE	"
YTTERBIUM	"
YTTRIUM	"
GALLATE	
ALUMINATES	->1623
HEXAGONAL	"
HOST LATTICE	"
LAMP	"
NEW	"
PHOSPHORS	"
RARE EARTH	"
GALLIUM	
ALUMINUM	-> 137
	->1509
	->1662
AMMONOLYSIS	-> 159
ANTIMONIDE	1662
GALLIUM (CONTD)	
ARSENIC	->1634
	->1650
ARSENIDE	"
	1662
ASYMMETRIC	1650
ASYMMETRY	"
BARIUM	137
CALCIA STABILIZED	> 506
CALCIUM	137
CARRIER	->1332
CHANNELING	->1657
CHARACTERIZATION	159
COEFFICIENT	-> 556
COMPOUND	1634
COMPOUNDS	1650
CONCENTRATION	-> 153
CRACKING	1650
CROSS HATCH	"
CRYSTAL	->1085
CRYSTAL GROWTH	153
	159
	556
CRYSTALLIZATION	1509
DEFECT	1085
DIFFUSION	556
	->1487
DIODE	1332
DOPING	1509
	1634
EFFICIENCY	1332
ELECTRODE	506
ELECTROLYTE	"
ELECTRON MICROSC.	1657
ETCH	1650
ETCHING	1085
EUROPIUM	137
GALLIUM NITRIDE	159
GALLIUM SESQUIOX.	506
GAP	153
GROUP II-VI	1662
GROUP III-V	1650
	1662
HEAT	1332
INDIUM	1650
	1657
	1662
ISOTHERMS	1634
KINETICS	506
LATTICE	1662
LIFETIME	1332
LIQUIDUS	1634
MASKING	1509
MELT	556
MICROPROBE	1657
MISCIBILITY GAP	1662
OXIDATION	1509
OXYGEN	506
PARAMETER	1662
PASSIVATION	1509
PATTERN	1657
PHOSPHIDE	556
	1085
	1650
	1657
	1662
PHOSPHORUS	153
	556
	1332
	1509
	1634
PHOTOLUMINESCENCE	137
	1332
PLANAR JUNCTION	1509
PSEUDOBINARY	1662
SAPPHIRE	159
SCANNING	1657
SEGREGATION	1509
SEMICONDUCTOR	137
	159
	1634
	1662
SILICON	1487
	1634
SILICON DIOXIDE	1487
SIRTL	1650
SOLID	506
SOLID SOLUTION	1662
SOLIDUS	153
STRONTIUM	137
SYNTHESIS	"
SYSTEM	1634
TERNARY	"
TRANSFER	506
VACANCY	153
YTTERBIUM	137
ZINC OXIDE	1332

PRIMARY TERM — CO-TERM — PAGE NO.

GALLIUM (CONTD)
ZIRCONIA - - - - 506

GALLIUM ARSENIDE
ALUMINATE - - - -> 571
AMMONIUM - - - ->1215
ANODE OXIDATION -> 820
ARSINE - - - - - ->1642
- - - - - ->1646
BIPOLAR - - - - - 1215
CHARACTERIZATION 1642
CHEMICAL - - - - 1215
- - - - 1642
- - - - 1646
COMPOUND - - - - 820
DEVICE - - - - - "
DIFFUSION - - - - "
ELECTRICAL - - - 1646
ELECTROOPTICAL - 820
EPITAXY - - - - - 571
ETCHANT - - - - - 1215
GROWTH - - - - - 571
- - - - - 1642
HETEROEPITAXY - - "
- - 1646
HYDROGEN PEROXIDE 1215
HYDROXIDE - - - - "
INDIUM ARSENIDE - 1642
- 1646
MAGNESIUM - - - - 571
PROPERTIES - - - 1646
REMOVAL - - - - - 1215
SELECTIVE - - - - "
SEMICONDUCTOR - - 820
SILICON DIOXIDE - 1215
SPINEL - - - - - 571
TRANSISTOR - - - 1215
TRIETHYLINDIUM - 1642
- 1646
VAPOR DEPOSITION 1642
1646
ZINC - - - - - - 820

GALLIUM NITRIDE
AMMONOLYSIS - - -> 159
CHARACTERIZATION "
CONTRAST - - - ->1202
CRYSTAL GROWTH - 159
DIODE - - - - - - 1202
GALLIUM - - - - - 159
HETEROEXPITAXIAL 1202
JUNCTION - - - - "
LIGHT EMISSION - "
MICROSTRUCTURE - "
PROFILE - - - - - "
SAPPHIRE - - - - 159
SEMICONDUCTOR - - "
STRUCTURE - - - - 1202
VAPOR DEPOSITION "
VOLTAGE - - - - - "

GALLIUM PHOSPHIDE
ANODE OXIDATION ->1665
AQUEOUS - - - - - "
COMPOUND - - - - "
CRYSTAL GROWTH -> 822
CZOCHRALSKI - - - "
ENCAPSULATION - - "
HYDROGEN PEROXIDE 1665
IMAGING - - - - - 822
LIQUID - - - - - "
NATIVE OXIDE - - 1665
SEMICONDUCTORS - "
X RAY - - - - - - 822

GALLIUM SESQUIOX.
CALCIA STABILIZED> 506
ELECTRODE - - - - "
ELECTROLYTE - - - "
GALLIUM - - - - - "
KINETICS - - - - "
OXYGEN - - - - - "
SOLID - - - - - - "
TRANSFER - - - - "
ZIRCONIA - - - - "

GALVANIC CELL
ADSORPTION - - -> 764
BATTERY - - - - -> 315
BATTERY CELL - -> 1
BETA ALUMINA - - "
CALCIUM - - - - -> 534
CARBONATE - - - - 315
CATHODE - - - - - 1
DICALCIUM - - - - 534
ELECTROCHEMISTRY "
764

GALVANIC CELL (CONTD)
INSTRUMENT - - - 764
IRON DOPED - - - 1
IRON SPINEL - - - "
LITHIUM ANODE - - 315
LITHIUM BROMINE - "
MONOCALCIUM - - - 534
MOSS BAUER - - - 1
NONAQUEOUS - - - 315
PARTICLE SIZE - - 764
PROPYLENE - - - - 315
SECONDARY - - - - "
SOLVENT - - - - - "
SPECTROSCOPY - - 1
STABILITY - - - - 534
STANNATE - - - - "
SURFACE AREA - - 764
VAPORIZATION - - 534

GALVANOSTATIC
ANODE FILM - - ->1186
CATALYSIS - - - - "
CONTROL - - - - -> 523
CURRENT - - - - - "
DISK ELECTRODE - "
DISTRIBUTION - - "
ELLIPSOMETRY - - 1186
EVOLUTION - - - - "
OXYGEN - - - - - "
PLATINUM - - - - "
POTENTIOSTATIC - 523
REACTION - - - - 1186
SHORT TIME - - - 523
SULFURIC ACID - - 1186
THICKNESS - - - - "

GAN
DECOMPOSITION - ->1383
EPITAXY - - - - - "
ETCHING - - - - - "
THERMAL - - - - - "

GAP
AMMONIA - - - - -> 962
BEHAVIOR - - - - "
CLOSELY - - - - ->1124
CONCENTRATION - -> 153
CRYSTAL GROWTH - "
DIODES - - - - - 962
EMITTING - - - - - "
EPITAXY - - - - - "
ETCHING - - - - -> 455
FERRICYANIDE - - "
GALLIUM - - - - - 153
IMPURITY - - - - 962
LED - - - - - - - 455
LIGHT - - - - - - 962
LIQUID PHASE - - "
MASK - - - - - - 455
METALLIZATION - - 1124
NITROGEN DOPING - 962
PATTERN - - - - - 1124
PHOSPHORUS - - - 153
POLISH - - - - - 455
SELF ALIGNED - - 1124
SOLIDUS - - - - - 153
SOURCE - - - - - 962
SPACED - - - - - 1124
VACANCY - - - - - 153

GARNET
BERYLLIA - - - ->1240
CERAMIC OXIDE - - "
CRYSTAL - - - - - "
DAMAGE - - - - - "
HARDNESS - - - - "
POLISHING - - - - "
PREPARATION - - - "
SAPPHIRE - - - - "
SPINEL - - - - - "
SURFACE - - - - - "

GAS
AUTOMATIC - - - -> 251
ELECTRODE - - - - "
HYDROGEN - - - -> 13
- - - - 251
LEAD ACID - - - - 13
LEAD CALCIUM - - "
OXYGEN - - - - - "
PUMP - - - - - - 251
RECOMBINATION - - 13
SPARKLESS - - - - 251
SYSTEM - - - - - 13

GAS LIFT
BRINE LEVEL - - ->1286

GAS LIFT (CONTD)
CHLORALKALI CELL 1286
MERCURY TYPE - - "
PUMP - - - - - - "
SCALE UP - - - - "
VOLTAGE - - - - - "

GAS PHASE
CRYSTAL GROWTH ->1516
DOPING - - - - - "
ELECTROLUMINESCE. "
EPITAXY - - - - ->1354
- - - - - 1516
EQUILIBRIA - - - 1354
ETCHING - - - - -> 293
MORPHOLOGY - - - 1516
PHOSPHORUS - - - 1354
SAPPHIRE - - - - 293
SILICON - - - - - 1354
STOICHIOMETRY - - 1516
VAPOR PHASE - - - 1354
- - - 1516

GAS SENSOR
CARBON MONOXIDE ->1315
CHALCOGENIDE - ->1575
DIFFUSION - - - - 1315
ELECTRODE - - - - "
GLASS ELECTRODE - 1575
NITROGEN DIOXIDE "
OXIDATION - - - - 1315
PLATINUM - - - - "

GASEOUS
CARBON FILM - - ->1551
IRON - - - - - - "
OXIDATION - - - - "
PRETREATMENT - - "
THIN FILM - - - - "

GATE
CHARGE - - - - -> 907
CONCENTRATION - -> 419
DEVICE - - - - - "
DIELECTRIC - - - 907
FET - - - - - - - 419
GLASS - - - - - - "
INSULATOR - - - - 907
INTERFACE - - - - 419
ION DRIFT - - - - "
ION TRAPPING - - "
NITRIDE - - - - - 907
OXIDE - - - - - - 419
- - - - - - 907
PHOSPHORUS - - - 419
PHOSPHOSILICATE - "
POLARIZATION - - "
SILICON - - - - - 907
SILICON OXIDE - - 419
STABILITY - - - - 907
THICKNESS - - - - 419
THRESHOLD - - - - "
VOLTAGE - - - - - "

GENERATION
BREAKDOWN - - - ->1229
CAPACITATOR - - -> 849
CARRIER - - - - - "
- - - - - 1229
DIELECTRIC - - - "
ETCHING - - - - - "
IMPERFECTION - - "
MINORITY - - - - 849
- - - - 1229
MOS - - - - - - - 849
SILICON - - - - - "
- - - - - 1229
WAFER - - - - - - "

GERMANIUM
ANOMALOUS - - - ->1212
AUGER - - - - - -> 310
BANDGAP - - - - ->1673
CARRIER MOBILITY 1212
CHEMICAL - - - - 1673
CLEANING - - - - 310
COMPOUND - - - - 1673
CRYSTAL - - - - - "
CRYSTAL GROWTH ->1237
DIFFUSION - - - - "
DISTRIBUTION - - 1212
DOPED - - - - - - 1237
ELECTRON SPECTRO. 310
EPITAXY - - - - - 1237
GAAS - - - - - - "
HALL - - - - - - 1212
IMPURITY - - - - "

GERMANIUM (CONTD)
INHOMOGENEITY - - 1212
METHOD - - - - - "
MOBILITY - - - - "
NITRIDE - - - - - 1673
OHM - - - - - - - 1237
PROPERTIES - - - 1673
RADIAL - - - - - 1212
SEMICONDUCTOR - - "
- - 1237
STRUCTURE - - - - 1673
SURFACE - - - - - 310
SYNTHESIS - - - - 1673
TERNARY - - - - - "
VANDERPAUW - - - 1212
VAPOR DEPOSITION 1673
ZINC - - - - - - 1237
- - - - - - 1673

GERMANIUM NITRIDE
ABSORPTION - - ->1073
ANNEALING - - - - "
GERMANIUM OXIDE - "
GERMANIUM OXYNIT. "
IMPLANTATION - - "
INFRARED - - - - "
ION - - - - - - - "

GERMANIUM OXIDE
ABSORPTION - - ->1073
ANNEALING - - - - "
GERMANIUM NITRIDE "
GERMANIUM OXYNIT. "
IMPLANTATION - - "
INFRARED - - - - "
ION - - - - - - - "

GERMANIUM OXYNIT.
ABSORPTION - - ->1073
ANNEALING - - - - "
GERMANIUM NITRIDE "
GERMANIUM OXIDE - "
IMPLANTATION - - "
INFRARED - - - - "
ION - - - - - - - "

GETTERING
DEVICE PROCESSING> 724
GLASS - - - - - - -> 444
- - - - - - - 724
ION SCATTERING - - 444
MOBILE CHARGE - - 724
PHOSPHOSILICATE - 444
- 724
REMOVAL - - - - - "
SILICON DIOXIDE - "
SODIUM - - - - - "
SOFT JUNCTIONS - 444

GIBBS
CADMIUM CHLORIDE > 959
EMF - - - - - - - "
FREE ENERGY - - -> 932
- - - 959
ION MOBILITY - - "
- - "
LATTICE PARAMETER 932
LITHIUM CHLORIDE 959
MISCIBILITY GAP - 932
MODEL - - - - - - "
MOLTEN MIX - - - 959
PSEUDO BINARY - - 932
QUASIREGULAR - - "
TRANSFERENCE - - 959

GLASS
CONCENTRATION - -> 419
COPPER - - - - - ->1405
DEVICE - - - - - 419
DEVICE PROCESSING> 724
ELECTROLESS - - -> 667
- - - 1405
ELECTRON MICROSC.> 307
ENERGY TRANSFER ->1338
EUROPIUM - - - - "
FET - - - - - - - 419
FLOW - - - - - - - 307
FLUORESCENCE - - 1338
FORMALDEHYDE - - 1405
GATE - - - - - - 419
GETTERING - - - -> 444
- - - - 724
GROWTH INHIBITION 667
IMAGING - - - - - "
INHIBITION - - - "
INTEGRATED CIRCU. 307
INTERFACE - - - - 419

PRIMARY TERM / CO-TERM	PAGE NO.
GLASS (CONTD)	
ION DRIFT	419
ION SCATTERING	444
ION TRAPPING	419
LEAD	1338
MOBILE CHARGE	724
MOS	307
OXIDE	419
PHOSPHORUS	"
PHOSPHOSILICATE	"
	444
	724
PLATING	667
	1405
POLARIZATION	419
REMOVAL	724
SCANNING	307
SILICON DIOXIDE	724
SILICON OXIDE	419
SODIUM	724
SOFT JUNCTIONS	444
THICKNESS	419
THRESHOLD	"
ULTRAVIOLET	667
VOLTAGE	419
GLASS ELECTRODE	
ARSENIC	-> 363
CHALCOGENIDE	"
	->1575
COPPER SULFIDE	363
GAS SENSOR	1575
NITROGEN DIOXIDE	"
SINNERITE	363
GLASS FILM	
ADSORPTION	-> 676
AUGER	-> 827
BOROSILICATE	676
	->1098
DENSIFICATION	827
DEPOSIT	676
DIFFUSION	"
ELECTRON SPECTRO.	827
GLASS METAL	1098
HARDNESS	"
OXYGEN	827
RATIO	"
SILANOL	676
SILICON	827
SILICON DIOXIDE	"
SINTERING	1098
SPECTROSCOPY	676
SPIN ON	827
STOICHIOMETRY	"
STRESS	1098
VAPOR	676
VICKERS	1098
WATER	676
GLASS METAL	
BOROSILICATE	->1098
GLASS FILM	"
HARDNESS	"
SINTERING	"
STRESS	"
VICKERS	"
GLASSES	
BERYLLIUM	->1429
CHRONOPOTENTIOME.	"
DEPENDENCE	"
DEPLETION	"
ELECTROMIGRATION	"
FLOURIDES	"
LITHIUM	"
MOLTEN HALIDES	"
TEMPERATURE	"
GLASSLIKE	
ANODE	-> 749
CARBON	"
CHLORINE ELECTRO.	"
GRAPHITE	"
OXYGEN ELECTRODE	"
PYROLYSIS	"
SURFACE OXIDE	"
GLO	
ASSIGNMENT	-> 170
CRYSTAL DEFECTS	"
CRYSTALLOGRAPHY	"
DOMAIN	"
ETCHING	"
FERROELECTRIC	"
SINGLE CRYSTAL	"

PRIMARY TERM / CO-TERM	PAGE NO.
GOLD	
ACETONITRILE	->1451
AGITATION	-> 56
BEAM	-> 62
BOROHYDRIDE	56
CAPACITANCE	->1318
CARBON	-> 490
	1451
CIRCUIT	62
COPPER	1318
COPPER CHLORIDE	"
DEPOSITION	->1610
DIFFUSION	1318
DOPING	->1350
DOUBLE LAYER	1318
	->1596
ELECTRO OXIDATION	1451
ELECTRODE	1610
ELECTRODEPOSIT	490
ELECTROLESS	56
	62
ELLIPSOMETRY	1596
ENCAPSULATION	1350
ENHANCEMENT	"
FORMATION	1596
HYSTERESIS	"
IMPURITY	56
LEAD	62
	1610
LOW TEMPERATURE	1318
METALLIZATION	->1076
MICROWAVE	"
NITRITE IONS	1451
OPTIC	1610
OXIDE FILM	1596
PLATING	56
	62
PLATINUM	1451
	1596
PROCEDURE	56
REDUCTION	1596
REFLECTANCE	"
RELIABILITY	1076
SILICON	62
	1350
SINGLE CRYSTAL	1318
	1610
SOLID ELECTROLYTE	1318
SOLUBILITY	1350
STABILITY	1076
SURFACE PROCESS	1596
TANTALUM	1076
THERMAL	"
THICKNESS	56
TRANSISTOR	1076
UNDER POTENTIAL	1610
GOLD EVAPORATED	
ADSORPTION	-> 474
DEPOSITION	"
ELECTRODE	"
ISOTHERM	"
LEAD	"
REFLECTANCE	"
SINGLE CRYSTAL	"
SPECTROSCOPY	"
UNDERPOTENTIAL	"
GOLD REFRACTORY	
CONTAMINATION	-> 790
FLUORINE	"
ION	"
METALLIZATION	"
RETENTION	"
SILICON	"
SURFACE	"
TRANSISTOR	"
GRADIENTS	
CONCENTRATION	-> 370
CONVECTIONLESS	"
INTERFEROMETRY	"
TRANSPORT	"
ZINC ANODE	"
ZINC CATHODE	"
GRAIN	
ACIDIC	->1141
ANODE	"
CHLORIDE	"
COLD	"
MICROSCOPY	"
NICKEL	"
POLARIZATION	"
POTENTIOSTATIC	"
SIZE	"
WORK	"

PRIMARY TERM / CO-TERM	PAGE NO.
GRAPHITE	
ANODE	-> 749
CAPACITANCE	-> 632
	-> 639
CARBON	749
CHLORINE ELECTRO.	"
DOUBLE LAYER	632
ELECTRODE	"
	639
ELECTROLYTE CELL	632
	639
GLASSLIKE	749
INTERFACE	639
OXYGEN ELECTRODE	749
PLATINUM	632
PYROLYSIS	749
ROOM TEMPERATURE	632
ROUGHENING	639
SILVER HALIDES	632
	639
SOLID ELECTROLYTE	632
	639
SOLID STATE	"
SURFACE OXIDE	749
WETTING	639
GRAPHITE ANODE	
ACTIVE	-> 220
CARBON OXIDE	->1289
CHLORALKALI CELL	220
CHLORINE	"
CHLORINE ELECTRO.	1289
CONSUMPTION	220
CORROSION	"
PH	"
TAFEL	1289
GRAPHITE BED	
AMALGAM	-> 343
COMPARISON	"
CRUSHED	"
DECOMPOSITION	"
SODIUM HYDROXIDE	"
TOWER	"
GRAPHITE SILICATE	
COATING	-> 720
CRT	"
DEVICE	"
ELECTRON	"
PENETRATION	"
THICKNESS	"
GRAVIMETRY	
ALUMINUM OXIDE	->1019
ANODE OXIDE	"
COMPOSITE	"
FILM	"
HYDROUS	"
PSEUDOBOEHMITE	"
RADIOTRACER	"
GREEN	
DIRECT CURRENT	-> 109
ELECTROLUMINESCE.	"
LEAD DOPED	"
PHOSPHORS	"
POWDER CELLS	"
ZINC SULFIDE	"
GRID	
ACTIVE	-> 531
ALLOY	->1526
BATTERY	531
	1526
BISMUTH	"
CALCIUM	"
CALCIUM LEAD	"
CORROSION	531
LEAD ACID	"
LEAD ANTIMONY	"
MATERIAL	"
PROTECTION	"
THICKNESS	"
TIN	1526
GROUP II-VI	
ALUMINUM	->1662
ANTIMONIDE	"
ARSENIDE	"
GALLIUM	"
GROUP III-V	"
INDIUM	"
LATTICE	"
MISCIBILITY GAP	"
PARAMETER	"
PHOSPHIDE	"

PRIMARY TERM / CO-TERM	PAGE NO.
GROUP II-VI (CONTD)	
PSEUDOBINARY	1662
SEMICONDUCTOR	"
SOLID SOLUTION	"
GROUP III-V	
ALUMINUM	->1662
ANTIMONIDE	"
ARSENIC	->1650
ARSENIDE	"
	1662
ASYMMETRIC	1650
ASYMMETRY	"
COMPOUNDS	"
CRACKING	"
CROSS MATCH	"
ETCH	"
GALLIUM	"
	1662
GROUP II-VI	"
INDIUM	1650
	1662
LATTICE	"
MISCIBILITY GAP	"
PARAMETER	"
PHOSPHIDE	1650
	1662
PSEUDOBINARY	"
SEMICONDUCTOR	"
SIRTL	1650
SOLID SOLUTION	1662
GROWING	
ANALYSIS	->1671
CRYSTAL	"
ZONE LEVELING	"
ZONE MELTING	"
GROWTH	
ALLOY	-> 416
	-> 538
ALUMINATE	-> 571
ALUMINUM	-> 268
	->1228
	->1322
ANODE FILM	268
ARSENIC	->1362
ARSINE	->1642
BAYERITE	1322
CHARACTERIZATION	416
	1642
CHEMICAL	"
CHLORIDE	268
COBALT IRON	538
COBALTOUS IRON	"
CRITICAL	-> 329
DENDRITE	"
DEVICE	-> 563
DIFFUSION	538
ELECTRON	268
EPITAXY	563
	571
	1362
GAAS	416
GALLIUM ARSENIDE	571
	1642
HETEROEPITAXY	"
HETEROJUNCTION	416
HYDROLYSIS	1322
IMPURITY	563
INDIUM ARSENIDE	1642
INDUCTION TIME	329
ION IMPLANT	1362
LATTICE MATCH	416
LPE	"
MAGNESIUM	571
NUCLEATION	1322
OPACITY	268
OVERPOTENTIAL	329
OXIDE	538
OXIDE FILM	1322
PITTING	268
PROCESSING	563
PSEUDOBOEHMITE	1322
QUARTZ	1228
REDISTRIBUTION	563
SEMICONDUCTOR	"
SILICON	"
	1228
	1362
SPINEL	571
THERMODYNAMICS	1228
TRANSPORT	"
TRIETHYLINDIUM	1642
VAPOR DEPOSITION	"
WHISKER	1228
X RAY	"

PRIMARY TERM — CO-TERM — PAGE NO.

GROWTH (CONTD)
YIELD - - - - - - 329
ZINC - - - - - - "

GROWTH INHIBITION
ELECTROLESS - - -> 667
GLASS - - - - - - "
IMAGING - - - - - "
INHIBITION - - - - "
PLATING - - - - - "
ULTRAVIOLET - - - "

HAFNIUM
ELECTROWINNING -> 879
EUTECTICS - - - - "
FUSED SALTS - - - "
REACTIVE METALS - "

HALIDES
ALUMINUM - - - -> 773
CHLOROALUMINATE - "
CHRONOPOTENTIOME. "
MELT - - - - - - "
MOLTEN - - - - - "
OXIDATION - - - - "

HALL
ANOMALOUS - - - ->1212
CARRIER MOBILITY "
DISTRIBUTION - - "
GERMANIUM - - - - "
IMPURITY - - - - "
INHOMOGENEITY - - "
METHOD - - - - - "
MOBILITY - - - - "
RADIAL - - - - - "
SEMICONDUCTOR - - "
VANDERPAUW - - - "

HALL DATA
ACCEPTOR - - - ->1208
EPITAXY - - - - - "
INDIUM PHOSPHIDE "
LIQUID PHASE - - "
PHOTOLUMINESCENCE "

HALL EFFECT
BARRIER - - - - ->1066
CAPACITANCE - - - "
EPITAXY - - - - - "
GAAS - - - - - - "
LAYER - - - - - - "
MEASUREMENT - - - "
MOBILITY - - - - "
PHOTOLUMINESCENCE "
SCHOTTKY - - - - "
SPECTRA - - - - - "

HALOGEN
BREAKDOWN - - - -> 809
DIELECTRIC - - - "
FILM - - - - - - "
HYDROGEN CHLORIDE "
OXIDATION - - - - "
RELIABILITY - - - "
SILICON DIOXIDE - "

HAMMETT
DETERMINATION - ->1462
ELECTRODE - - - - "
HYDROGEN - - - - "
SIGMA - - - - - - "
SUBSTITUENT - - - "

HARDNESS
BERYLLIA - - - ->1240
BOROSILICATE - ->1098
CERAMIC OXIDE - - 1240
CRYSTAL - - - - - "
DAMAGE - - - - - "
GARNET - - - - - "
GLASS FILM - - - 1098
GLASS METAL - - - "
POLISHING - - - - 1240
PREPARATION - - - "
SAPPHIRE - - - - "
SINTERING - - - - 1098
SPINEL - - - - - 1240
STRESS - - - - - 1098
SURFACE - - - - - 1240
VICKERS - - - - - 1098

HEAT
CARRIER - - - - ->1332
CRYSTAL - - - - ->1674
DIODE - - - - - - 1332
EFFICIENCY - - - "
EXISTENCE - - - - 1674
GALLIUM - - - - - 1332
INDIUM - - - - - 1674
LIFETIME - - - - 1332
MEASUREMENT - - - 1674
MONOSELENIDE - - "
PHASE TRANSITION "
PHOSPHORUS - - - 1332
PHOTOLUMINESCENCE "
SEMICONDUCTOR - - 1674
SPECIFIC - - - - "
STRUCTURE - - - - "
XRAY - - - - - - "
ZINC OXIDE - - - 1332

HEAT SINKS
DENDRITE - - - -> 912
DEVICE - - - - -> 426
ELECTROLESS - - - 912
ELECTROPLATED - - 426
FABRICATION - - - "
GAAS - - - - - - "
HEAT TRANSFER - - 912
IMPATT - - - - - 426
PLATING - - - - - 912
PREPARATION - - - "
WATER CURVATURE - 426

HEAT TRANSFER
DENDRITE - - - -> 912
ELECTROLESS - - - "
HEAT SINKS - - - "
PLATING - - - - - "
PREPARATION - - - "

HELIUM
ANALYZER - - - -> 689
ARGON - - - - - ->1372
CONTROL - - - - ->1233
- - - - - 1372
CVD - - - - - - 1233
DEFECT - - - - - 689
DEPOSITION - - - 1233
DIFFUSING - - - - 1372
EQUILIBRIA - - - "
ETCHING - - - - - "
FILM - - - - - - 1233
FILM THICKNESS - "
HEXAFLUORIDE - - 1372
LANGMUIR SHEATH - "
LASER - - - - - - 689
- - - - - - 1233
NEON - - - - - - "
NITRIDE - - - - - "
NITROGEN - - - - 689
- - - - 1372
PENTA FLUORIDE - "
RATE - - - - - - "
REACTION - - - - "
SILICON - - - - - 689
- - - - - 1233
SILICON DIOXIDE - "
SLICE - - - - - - 689
SURFACE - - - - - "
TUNGSTEN - - - - 1372

HEMISPHERICAL
DEPOSITION - - ->1592
DISSOLUTION - - - "
ELECTRODE - - - - "
IRON OXIDE - - - "
MILD - - - - - - "
RING - - - - - - "
ROTATING - - - - "
STEEL - - - - - - "
SULFATE SOLUTION "

HETEROEPITAXY
ARSINE - - - - ->1642
- - - - ->1646
CADMIUM - - - - -> 965
CHARACTERIZATION 1642
CHEMICAL - - - - "
- - - - 1646
DEPOSITION - - - 965
ELECTRICAL - - - 1646
EPITAXY - - - - - 965
GALLIUM ARSENIDE 1642
1646
GROWTH - - - - - 1642
INDIUM ARSENIDE - "
- 1646
INSULATOR - - - ->1345
PHOTOSENSITIVITY 965
PROPERTIES - - - 1646
SAPPHIRE - - - - 965

HETEROEPITAXY (CONTD)
SAPPHIRE - - - - 1345
SELENIDE - - - - 965
SEMICONDUCTOR - - 1345
SILICON - - - - - "
SPINEL - - - - - "
SULFIDE - - - - - 965
THIN FILM - - - - 1345
TRIETHYLINDIUM - 1642
- 1646
VAPOR - - - - - - 965
VAPOR DEPOSITION 1642
1646
VAPOR PHASE - - - 965

HETEROEXPITAXIAL
CONTRAST - - - ->1202
DIODE - - - - - - "
GALLIUM NITRIDE - "
JUNCTION - - - - "
LIGHT EMISSION - "
MICROSTRUCTURE - "
PROFILE - - - - - "
STRUCTURE - - - - "
VAPOR DEPOSITION "
VOLTAGE - - - - - "

HETEROGENEOUS
CLUSTER - - - - ->1090
CRISTOBALITE - - "
OXYGEN - - - - - "
PRECIPITATION - - "
SILICON - - - - - "
SILICON OXIDES - "
VACANCY - - - - - "

HETEROJUNCTION
ALLOY - - - - - -> 416
CHARACTERIZATION "
GAAS - - - - - - "
GROWTH - - - - - "
LATTICE MATCH - - "
LPE - - - - - - - "

HEXAFLUORIDE
ARGON - - - - - ->1372
CONTROL - - - - - "
DIFFUSING - - - - "
EQUILIBRIA - - - "
ETCHING - - - - - "
HELIUM - - - - - "
LANGMUIR SHEATH - "
NITROGEN - - - - "
PENTA FLUORIDE - "
RATE - - - - - - "
REACTION - - - - "
TUNGSTEN - - - - "

HEXAGONAL
ALUMINATES - - ->1623
GALLATE - - - - - "
HOST LATTICE - - "
LAMP - - - - - - "
NEW - - - - - - - "
PHOSPHORS - - - - "
RARE EARTH - - - "

HEXANOL
ALCOHOLS - - - ->1048
CELL - - - - - - "
ELECTROCHEMISTRY "
ELECTRODE - - - - "
HYDROGEN - - - - "
NORMAL - - - - - "
THALLIUM - - - - "

HIGH CURRENT
ANODE BEHAVIOR -> 191
DENSITY - - - - - "
ELECTROCHEMICAL - "
MILD - - - - - - "
POLISHING - - - - "
SODIUM CHLORATE - "
STEEL - - - - - - "

HIGH EFFICACY
DELUXE - - - - ->1627
FLUORESCENT - - - "
LAMPS - - - - - - "
NEW GENERATION - "

HIGH ENERGY
BATTERY - - - - ->1294
ELECTROINITIATE - "
LITHIUM - - - - - "
PERCHLORATE - - - "
POLYMERIZATION - "

HIGH ENERGY (CONTD)
TETRAHYDROFURAN - 1294

HIGH POWER
CHARGER - - - - ->1134
CONTROLLER - - - "
ELECTROCHEMISTRY "
PROPULSION - - - "
SIMULATOR - - - - "
SUPPLY - - - - - "

HIGH PRESSURE
ALLOY - - - - - ->1245
ALUMINUM - - - - "
BATTERY - - - - - "
BETA ALUMINA - -> 596
BUFFER - - - - - 1245
CHLORIDE - - - - "
CRYSTAL GROWTH - 596
ENF - - - - - - - 1245
ENERGY TRANSFER -> 305
EUROPIUM - - - - "
LAMP - - - - - - "
MAGNESIUM - - - - 1245
MEMBRANE - - - - 596
MERCURY - - - - - 305
PHOSPHOR - - - - "
SEAWATER - - - - 1245
SODIUM - - - - - 596
TERBIUM - - - - - 305
VANDATE - - - - - "
VAPOR - - - - - - "
YTTRIUM - - - - - "

HIGH RESISTIVITY
EVAPORATION - - ->1222
FLOAT ZONE - - - "
POLYCRYSTALLINE - "
POLYDEPOSITION - "
PROCESS - - - - - "
PRODUCTION - - - "
SILICON - - - - - "
SINGLE CRYSTAL - "
VACUUM - - - - - "

HIGH TEMPERATURE
BEHAVIOR - - - -> 122
- - - -> 163
CALCIUM DOPED - - 122
CERIUM DIOXIDE - "
CHEMISORPTION - - 163
CHLORINE - - - -> 919
DECOMPOSITION - - "
- - ->1328
DEPOSITION - - - 919
DIELECTRIC - - - 122
- - - 163
DIFFUSION - - - - "
DOPING - - - - - "
ELECTROLYSIS - - 1328
EQUILIBRIUM - - - 919
HYDROGEN - - - - "
INTERFACE - - - - 1328
IRON - - - - - -> 665
IRON PYRITE - - - "
IRON SULFIDE - - "
LITHIUM - - - - - 163
- - - - - 665
MASS TRANSPORT - 1328
MOLTEN SALT - - - 665
POLYCRYSTALLINE - 163
REACTION - - - - 919
REDUCTION - - - - "
SECONDARY CELL - 665
SILICON - - - - - 919
SILICON DIOXIDE - 1328
SODIUM - - - - - 163
STABILITY - - - - 1328
SULFIDE - - - - - 665
ZINC OXIDE - - - 163

HISTOPATHOLOGY
ALLOY - - - - - ->1129
ALUMINUM - - - - "
CORROSION - - - - "
IMPLANTABLE - - - "
INVITRO - - - - - "
INVIVO - - - - - "
MAGNESIUM - - - - "
POWER - - - - - - "
SOURCE - - - - - "
ZINC - - - - - - "

HOFMANN LOEFFLER
AMINES - - - - -> 378
CATION RADICAL - "
OXIDATION - - - - "

PRIMARY TERM / CO-TERM	PAGE NO.
HOFMANN LOEFFLER (CONTD)	
SECONDARY	378
HOLE	
CALCIA STABILIZED	793
CONDUCTION	"
COULOMETRY	"
OXYGEN	"
PERMEATION	"
SOLID STATE	"
TITRATION	"
WUSTITE	"
ZIRCONIA	"
HOLMIUM	
ANODE SPARK	->1402
DYSPROSIUM	"
ERBIUM	"
GADOLINIUM	"
SAMARIUM	"
SODIUM SILICATE	"
YTTERBIUM	"
YTTRIUM	"
HOMOCHARGE	
CHARGE	-> 591
DENSITY	"
DIELECTRIC	"
ELECTRET	"
FEP	"
INSERT	"
SPRAY	"
SURFACE	"
TEFLON	"
THERMOELECTRET	"
HOST LATTICE	
ALUMINATES	->1623
GALLATE	"
HEXAGONAL	"
LAMP	"
NEW	"
PHOSPHORS	"
RARE EARTH	"
HYDRAZINE	
AEROSOL	-> 484
ANODE	->1264
CATALYST	"
DEPOSIT	484
ELECTRICAL	"
FORMALDEHYDE	"
FUEL CELL	1264
NICKEL BORIDE	"
PLATING	484
RESISTIVITY	"
SILVER	"
SPRAY	"
SUBSTRATE	1264
HYDROCARBON	
ADSORPTION	-> 987
ANION	"
ELECTROLYTE	"
MONOHYDRATE	"
OXIDATION	"
PROPANE	"
TRIFLUOROMETHANE	"
HYDRODYNAMIC	
CHLORATE CELL	-> 70
CHLORINE	"
CURRENT	"
CURRENT DENSITY	"
EFFECT	"
EFFICIENCY	"
MUTUAL	"
PH	"
TEMPERATURE	"
HYDROGEN	
ACID	->1609
ADSORPTION	-> 609
ALCOHOLS	->1048
AMMONIA	-> 230
	1609
ANODE OXIDATION	-> 782
APROTIC	-> 516
ARSENIC	609
AUTOMATIC	-> 251
BEHAVIOR	->1589
BRONZE	->1029
CELL	1048
CHLORINE	-> 919
CHROMIUM	-> 225
COBALT	"
COEFFICIENT	230
HYDROGEN (CONTD)	
CORROSION	225
DECOMPOSITION	919
DEPOSITION	"
DETERMINATION	->1462
DIMETHYLFORMAMIDE	518
ELECTROCHEMISTRY	"
	1048
ELECTRODE	251
	518
	1048
	1462
ELECTROREDUCTION	1029
EMBRITTLEMENT	1589
ENTRY	609
EQUILIBRIUM	919
EVOLUTION	225
	230
	1609
EXCHANGE CURRENT	230
GAS	-> 13
	251
HAMMETT	1462
HEXANOL	1048
HIGH TEMPERATURE	919
HYDROGEN ELECTRO.	1589
HYDROGEN PEROXIDE	1029
IMPLANTATION	-> 784
INTERFACE	"
IRREVERSIBLE	1589
LEAD ACID	13
LEAD CALCIUM	"
LIQUID	230
	1609
MANGANESE	225
MOS STRUCTURE	784
NITROGEN	230
	1609
NORMAL	1048
OVERVOLTAGE	230
OXYGEN	13
	784
	1029
PERMEATION	609
PLATINIZED	782
PLATINUM	1029
POTENTIAL	609
PUMP	251
REACTION	919
	1609
RECOMBINATION	13
REDUCTION	919
REVERSIBLE CELL	518
SIGMA	1462
SILICON	784
	919
SILICON DIOXIDE	784
SODIUM	1029
SOLVENT	518
SPARKLESS	251
STEEL	609
SUBSTITUENT	1462
SURFACE STATE	784
SYSTEM	13
TAFEL SLOPE	230
THALLIUM	518
	1048
TRACES	1029
TRANSFER	230
TUNGSTEN	1029
TUNGSTEN OXIDE	782
TUNGSTEN TRIOXIDE	"
VANADIUM	225
HYDROGEN CHLORIDE	
BREAKDOWN	-> 809
DIELECTRIC	"
FILM	"
HALOGEN	"
OXIDATION	"
RELIABILITY	"
SILICON DIOXIDE	"
HYDROGEN ELECTRO.	
BEHAVIOR	->1589
EMBRITTLEMENT	"
HYDROGEN	"
IRREVERSIBLE	"
HYDROGEN FLUORIDE	
ANODE OXIDATION	-> 195
BUFFERED	"
CONCENTRATION	"
ION IMPLANTATION	"
OXIDE DISSOLUTION	"
PROFILE	"
TANTALUM	"
HYDROGEN PEROXIDE	
AMMONIUM	->1215
ANODE OXIDATION	->1665
AQUEOUS	"
BIPOLAR	1215
BRONZE	->1029
CHEMICAL	1215
COMPOUND	1665
ELECTROREDUCTION	1029
ETCHANT	1215
GALLIUM ARSENIDE	"
GALLIUM PHOSPHIDE	1665
HYDROGEN	1029
HYDROXIDE	1215
NATIVE OXIDE	1665
OXYGEN	1029
PLATINUM	"
REMOVAL	1215
SELECTIVE	"
SEMICONDUCTORS	1665
SILICON DIOXIDE	1215
SODIUM	1029
TRACES	"
TRANSISTOR	1215
TUNGSTEN	1029
HYDROGEN SULFIDE	
ALLOY	-> 889
ATMOSPHERE	"
COBALT IRON	"
KINETICS	"
PARABOLIC	"
SULFIDATION	"
HYDROLYSIS	
ALUMINUM	->1322
BAYERITE	"
GROWTH	"
NUCLEATION	"
OXIDE FILM	"
PSEUDOBOEHMITE	"
HYDROTHERMAL	
ALUMINUM	-> 303
LITHIUM	"
LUMINESCENCE	"
MANGANOUS	"
ORTHOSILICATE	"
PHOSPHOR	"
HYDROUS	
ALUMINUM OXIDE	->1019
ANODE OXIDE	"
COMPOSITE	"
FILM	"
GRAVIMETRY	"
PSEUDOBOEHMITE	"
RADIOTRACER	"
HYDROXIDE	
AMMONIUM	->1215
BIPOLAR	"
CESIUM	-> 727
CHEMICAL	1215
ELECTRODE	727
ELECTROLYTE	"
ETCHANT	1215
GALLIUM ARSENIDE	"
HYDROGEN PEROXIDE	"
REDUCTION	727
REMOVAL	1215
SELECTIVE	"
SILICON DIOXIDE	"
SILVER OXIDE	727
STRUCTURE	"
TRANSISTOR	1215
HYPOPHOSPHITE	
ACID BATH	->1023
AMINE	"
BORANE	"
COBALT	"
DEPOSITION	"
ELECTROLESS	"
NICKEL	"
PLATING	"
HYSTERESIS	
DOUBLE LAYER	->1596
ELLIPSOMETRY	"
FORMATION	"
GOLD	"
OXIDE FILM	"
PLATINUM	"
REDUCTION	"
REFLECTANCE	"
SURFACE PROCESS	"
IMAGING	
CHLOROSTILBENES	->1667
CRYSTAL GROWTH	-> 822
CZOCHRALSKI	"
ELECTROLESS	-> 667
ENCAPSULATION	822
GALLIUM PHOSPHIDE	"
GLASS	667
GROWTH INHIBITION	"
INHIBITION	"
IRRADIATION	1667
LIQUID	822
LIQUID CRYSTAL	1667
NEMATIC	"
PLATING	667
STILBENES	1667
ULTRAVIOLET	667
	1667
X RAY	822
IMMERSION	
METAL ELECTRODE	-> 618
METHOD	"
OPEN CIRCUIT	"
SCRAPE	"
ZERO CHARGE	"
IMPATT	
BREAKDOWN	-> 692
DEVICE	-> 426
DIODE	692
ELECTRON	"
ELECTROPLATED	426
FABRICATION	"
GAAS	"
	692
HEAT SINKS	426
MICROSCOPE	692
PREMATURE	"
SCANNING	"
SCHOTTKY	"
SITES	"
WATER CURVATURE	426
IMPEDANCE	
AC	-> 375
ALKALINE	"
ALUMINUM FILM	-> 400
ANODE OXIDATION	"
ASYMPTOTIC	-> 521
BETA ALUMINA	->1314
CATHODE	375
CONDUCTANCE	1314
CONDUCTIVITY	375
CURRENT	1314
DC	375
DISCHARGED	"
ELECTRODE	521
ENVIRONMENT	400
IONIC CONDUCTANC.	375
LECLANCHE CELL	"
MANGANESE DIOXIDE	"
MEASUREMENT	"
MERCURY OXIDE	"
PH	400
POROSITY	"
PULSE	1314
RESISTANCE	375
ROTATING DISK	521
SOLUTION	"
UNDISCHARGED	375
WARBURG	521
IMPERFECTION	
BREAKDOWN	->1229
CARRIER	"
COPPER	-> 289
DIELECTRIC	1229
DISPLACEMENT	289
ETCHING	1229
GENERATION	"
MINORITY	"
SILICON	289
	1229
SUBSTRATE	289
TOPOGRAPHY	"
WAFER	1229
X RAY	289
INPLANT	
ANODE	-> 45
ION	"
RANGE PROFILE	"
TANTALUM OXIDE	"
INPLANTABLE	
ALLOY	->1129

PRIMARY TERM / CO-TERM — PAGE NO.

IMPLANTABLE (CONTD)
ALUMINUM - - - - 1129
CORROSION - - - - "
HISTOPATHOLOGY - "
INVITRO - - - - - "
INVIVO - - - - - "
MAGNESIUM - - - - "
POWER - - - - - - "
SOURCE - - - - - "
ZINC - - - - - - "

IMPLANTATION
ABSORPTION - - ->1073
ANNEALING - - - - "
ARGON - - - - - -> 558
BACKSPUTTERING - "
FILM - - - - - - "
GERMANIUM NITRIDE 1073
GERMANIUM OXIDE - "
GERMANIUM OXYNIT. "
HYDROGEN - - - -> 784
INFRARED - - - - 1073
INTERFACE - - - - 784
ION - - - - - - - 558
- - - - - - - 1073
METALLIZATION - - 558
MOS STRUCTURE - - 784
OXYGEN - - - - - "
SILICON - - - - - "
SILICON DIOXIDE - 558
- 784
SPUTTERING - - - 558
SURFACE STATE - - 784
TRAPPING - - - - 558

IMPURITIES
AQUEOUS SOLUTION >1311
ELECTROLYSIS - - "
MERCURY - - - - - "
SODIUM CHLORIDE - "

IMPURITY
AGITATION - - - -> 56
AMMONIA - - - - -> 962
ANODE OXIDATION -> 860
ANOMALOUS - - - ->1212
BEHAVIOR - - - - 962
BOROHYDRIDE - - - 56
CALCULATION - - -> 588
CARRIER MOBILITY 1212
CONCENTRATION - -> 132
DEPENDENCE - - - "
DEVICE - - - - -> 563
DIFFUSION - - - - 132
DIODES - - - - - 962
DISSOLUTION - - - 860
DISTRIBUTION - - 132
- - 1212
DOPED OXIDE - - - 132
ELECTROLESS - - - 56
EMITING - - - - - 962
EPITAXY - - - - - 563
- - - - - 962
GAP - - - - - - - "
GERMANIUM - - - - 1212
GOLD - - - - - - 56
GROWTH - - - - - 563
HALL - - - - - - 1212
INHOMOGENEITY - - "
ION IMPLANT - - - 860
LAYER - - - - - - 132
LIGHT - - - - - - 962
LIQUID PHASE - - "
METHOD - - - - - 1212
MOBILITY - - - - "
NITROGEN DOPING - 962
NUMERICAL - - - - 588
OXIDATION - - - - "
- - - ->1107
PHOSPHORUS - - - 132
PLATING - - - - - 56
PROCEDURE - - - - "
PROCESSING - - - 563
RADIAL - - - - - 1212
REDISTRIBUTION - 563
- 588
RF HEATING - - - 1107
SEMICONDUCTOR - - 563
- - 588
- - 1212
SILICON - - - - - 132
- - - - - 563
- - - - - 588
- - - - - 1107
SILICON DIOXIDE - 588
SOURCE - - - - - 962
TANTALUM OXIDE - 860

IMPURITY (CONTD)
TEMPERATURE - - - 132
THERMAL - - - - - 588
- - - - - 1107
THICKNESS - - - - 56
VANDERPAUW - - - 1212
VAPOR DEPOSITION 132

INCLUSION
EQUILIBRIA - - -> 467
INITIATION - - - "
MANGANESE - - - - "
PITTING - - - - - "
POTENTIAL PH - - "
STAINLESS STEEL - "
SULFIDE - - - - - "

INDIUM
ALUMINUM - - - ->1662
ANTIMONIDE - - - "
ARSENIC - - - - ->1650
ARSENIDE - - - - "
- - - - 1662
ASYMMETRIC - - - 1650
ASYMMETRY - - - - "
CHANNELING - - ->1657
COMPOUNDS - - - - 1650
CRACKING - - - - "
CROSS HATCH - - - "
CRYSTAL - - - - ->1674
CRYSTAL GROWTH -> 835
ELECTRON MICROSC. 1657
ETCH - - - - - - 1650
EXISTENCE - - - - 1674
GALLIUM - - - - - 1650
- - - - - 1657
- - - - - 1662
GROUP II-VI - - - "
GROUP III-V - - - 1650
- - - 1662
HEAT - - - - - - 1674
LATTICE - - - - - 1662
MEASUREMENT - - - 1674
MICROPROBE - - - 1657
MISCIBILITY GAP - 1662
MONOSELENIDE - - 1674
PARAMETER - - - - 1662
PATTERN - - - - - 1657
PHASE EQUILIBRIUM 835
PHASE TRANSITION 1674
PHOSPHIDE - - - - 835
- - - - 1650
- - - - 1657
- - - - 1662
PHOSPHORUS - - - 835
PSEUDOBINARY - - 1662
SCANNING - - - - 1657
SEMICONDUCTOR - - 1662
- - 1674
SIRTL - - - - - - 1650
SOLID SOLUTION - 1662
SPECIFIC - - - - 1674
STRUCTURE - - - - "
VAPOR PRESSURE - 835
XRAY - - - - - - 1674

INDIUM ANTIMONIDE
BEHAVIOR - - - -> 448
CONVERGING - - - "
INTERFACE - - - - "
PRESSURE INDUCED "
SEGREGATION - - - "
SOLIDIFICATION - "
STATIONARY - - - "
VERTICAL ZONE - - "

INDIUM ARSENIDE
ARSINE - - - - ->1642
- - - - ->1646
CHARACTERIZATION 1642
CHEMICAL - - - - "
- - - - 1646
ELECTRICAL - - - "
GALLIUM ARSENIDE 1642
1646
GROWTH - - - - - 1642
HETEROEPITAXY - - "
- - 1646
PROPERTIES - - - "
TRIETHYLINDIUM - 1642
- 1646
VAPOR DEPOSITION 1642
1646

INDIUM PHOSPHIDE
ACCEPTOR - - - ->1208
EPITAXY - - - - - "

INDIUM PHOSPHIDE (CONTD)
HALL DATA - - - - 1208
LIQUID PHASE - - "
PHOTOLUMINESCENCE "

INDUCED
DEFECTS - - - - -> 989
PROCESS - - - - - "
SILICON - - - - - "
SOFT JUNCTIONS - "

INDUCTION TIME
CRITICAL - - - -> 329
DENDRITE - - - - "
GROWTH - - - - - "
OVERPOTENTIAL - - "
YIELD - - - - - - "
ZINC - - - - - - "

INFRARED
ABSORPTION - - -> 434
- - ->1073
- - ->1482
ACTIVATION - - - 434
ANALYSIS - - - - "
ANNEALING - - - - 1073
BATTERY - - - - ->1045
CARRIER - - - - - 1482
CONCENTRATION - - 434
- - 1482
CONTAMINATION - - 1045
DRUDE ZENER - - - 1482
ELECTROLYTE - - - 1045
GAAS - - - - - - 1482
GERMANIUM NITRIDE 1073
GERMANIUM OXIDE - "
GERMANIUM OXYNIT. "
IMPLANTATION - - "
INORGANIC - - - - 1045
INTERACTION - - - 434
ION - - - - - - - 1073
LIQUID - - - - - 1045
LITHIUM - - - - - "
MOISTURE - - - - 434
OXYHALIDE - - - - 1045
PHOSPHORUS - - - 434
PSG FILM - - - - "
REFLECTIVITY - - 1482
RESISTANCE - - - 434
SEMICONDUCTOR - - 1482
SILICON DOPED - - "
TRACE ANALYSIS - 1045
WATER - - - - - - 434
- - - - - 1045

INFRARED DEVICE
ANTIMONY - - - ->1523
CHALCOGENIDES - - "
DOPING - - - - - "
JUNCTION - - - - "
LEAD - - - - - - "
TELLURIDE - - - - "
TERNARIES - - - - "
TIN - - - - - - - "

INGAAS
DETECTOR - - - ->1506
EPITAXY - - - - - "
GAAS - - - - - - "
WAVEGUIDE - - - - "

INHIBITION
ALKALINE - - - -> 605
ANODE - - - - - ->1276
ANODE DISSOLUTION 605
BENZOTRIAZOLE - - "
- - 1276
CATALYST - - - ->1461
CHLORIDE - - - - 605
CHLORIDE SOLUTION 1276
CORROSION - - - - 605
- - - - 1276
ELECTRODISSOLUTI. "
ELECTROLESS - - -> 667
- - - 1461
GLASS - - - - - - 667
GROWTH INHIBITION "
IMAGING - - - - - "
IRON - - - - - - 605
- - - - - - 1276
NEUTRAL SOLUTION "
PLASTICS - - - - 1461
PLATING - - - - - 667
- - - - - 1461
SOLUTION - - - - 605
ULTRA VIOLET - - 1461
ULTRAVIOLET - - - 667

INHIBITOR
ANODE - - - - - ->1146
CHROMATE - - - - "
CORROSION - - - - "
ELLIPSOMETRY - - "
FILM - - - - - - "
IRON - - - - - - "
OPEN CIRCUIT - - "
PASSIVITY - - - - "
POTENTIAL - - - - "

INHOMOGENEITY
ANOMALOUS - - - ->1212
CARRIER MOBILITY "
DISTRIBUTION - - "
GERMANIUM - - - - "
HALL - - - - - - "
IMPURITY - - - - "
METHOD - - - - - "
MOBILITY - - - - "
RADIAL - - - - - "
SEMICONDUCTOR - - "
VANDERPAUW - - - "

INITIATION
EQUILIBRIA - - -> 467
INCLUSION - - - - "
MANGANESE - - - - "
PITTING - - - - - "
POTENTIAL PH - - "
STAINLESS STEEL - "
SULFIDE - - - - - "

INORGANIC
BATTERY - - - - ->1045
CONTAMINATION - - "
ELECTROLYTE - - - "
ELECTRON - - - -> 929
INFRARED - - - - 1045
IRON OXIDE - - -> 925
- - - 929
LASER - - - - - - 925
LIQUID - - - - - 1045
LITHIUM - - - - - "
MASK - - - - - - 925
OXYHALIDE - - - - 1045
PHOTOMASK - - - - 929
PHOTORESIST - - - 925
RESIST - - - - - 929
THIN FILM - - - - 925
- - - - 929
TRACE ANALYSIS - 1045
WATER - - - - - - "

INSERT
ANOMALOUS - - - ->1677
BORON - - - - - - "
CHARGE - - - - -> 591
DENSITY - - - - - "
- - - - - 1677
DIELECTRIC - - - 591
- - - 1677
DIFFUSION - - - - "
EFFECT - - - - - "
ELECTRET - - - - 591
ELECTRETS - - - - 1677
FEP - - - - - - - 591
HOMOCHARGE - - - "
NITRIDE - - - - - 1677
PLANAR - - - - - "
SILICON - - - - - "
SPRAY - - - - - - 591
SURFACE - - - - - "
SURFACE CHARGE - 1677
TEFLON - - - - - 591
THERMOELECTRET - "

INSOLUBLE
COLORED FILMS - ->1555
COMPOUND - - - - "
RADICAL - - - - - "
VIOLOGEN - - - - "

INSTABILITY
CRYSTAL GROWTH -> 380
CZOCHRALSKI - - - "
DOPED GERMANIUM - "
OSCILLATORY - - - "
SUPERCOOLING - - "

INSTRUMENT
ADSORPTION - - -> 764
ELECTROCHEMISTRY "
GALVANIC CELL - - "
PARTICLE SIZE - - "
SURFACE AREA - - "

PRIMARY TERM / CO-TERM	PAGE NO.
INSULATOR	
CHARGE ->	907
DIELECTRIC	"
GATE	"
HETEROEPITAXY ->	1345
NITRIDE	907
OXIDE	"
SAPPHIRE	1345
SEMICONDUCTOR	"
SILICON	907
	1345
SPINEL	"
STABILITY	907
THIN FILM	1345
INTEGRATED	
APPLICATION ->	422
CARBON ->	146
CIRCUIT	"
	422
CONTAMINATION	146
DEVICE	422
DOPING	146
EPITAXIAL	422
MEASUREMENT	"
RESIDUE	146
RESISTANCE	422
RESISTIVITY	"
SILICON	146
	422
SPREADING	"
SURFACE	146
INTEGRATED CIRCU.	
ELECTRON MICROSC.>	307
FLOW	"
GLASS	"
MOS	"
SCANNING	"
INTEGRATION	
BIPOLAR ->	1119
COMPLEMENTARY	"
DEVICE	"
ISOLATED	"
MONOLITHIC	"
MOS	"
SEMICONDUCTOR	"
TRANSISTOR	"
INTERACTION	
ABSORPTION ->	434
ACTIVATION	"
ANALYSIS	"
BINARY ->	500
CONCENTRATION	434
COULOMBIC	500
INFRARED	434
LITHIUM CHLORIDE	500
MOISTURE	434
MOLTEN SALT	500
PHOSPHORUS	434
POTASSIUM CHLOR.	500
PSG FILM	434
RESISTANCE	"
SURFACE TENSION	500
WATER	434
INTERFACE	
BEHAVIOR ->	448
CAPACITANCE ->	639
CONCENTRATION ->	419
CONVERGING	448
CORONA CHARGE ->	452
CRISTOBALITE ->1081	
CRYSTALLIZATION	"
DECOMPOSITION ->1328	
DEMARCATION ->	787
DEVICE	419
DIFFUSION	1081
ELECTRODE	639
ELECTROLYSIS	1328
ELECTROLYTE CELL	639
FACET GROWTH	787
FET	419
FIELD EFFECT	452
FILM	1081
GATE	419
GLASS	"
GRAPHITE	639
HIGH TEMPERATURE	1328
HYDROGEN ->	784
IMPLANTATION	"
INDIUM ANTIMONIDE	448
ION DRIFT	419
ION TRAPPING	"
MASS TRANSPORT	1328
INTERFACE (CONTD)	
MODULATE	452
MOS STRUCTURE	784
NETWORK	1081
OXIDE	419
OXYGEN	784
PHOSPHORUS	419
	1081
PHOSPHOSILICATE	419
PHOTOLUMINESCENCE	452
POLARIZATION	419
PRESSURE INDUCED	448
ROUGHENING	639
SEGREGATION	448
	787
SEMICONDUCTOR	452
SILICON	784
SILICON DIOXIDE	"
	1081
	1328
SILICON OXIDE	419
SILVER HALIDES	639
SOLID ELECTROLYTE	"
SOLID STATE	"
SOLIDIFICATION	448
STABILITY	1328
STATIONARY	448
SURFACE STATE	784
THICKNESS	419
THRESHOLD	"
TRAP	452
VERTICAL ZONE	448
VOLTAGE	419
WETTING	639
ZINC OXIDE	452
INTERFEROGRAM	
EPITAXIAL ->	150
LAYER	"
PHASE SHIFT	"
SILICON	"
THICKNESS	"
INTERFEROMETRY	
CONCENTRATION ->	370
CONVECTIONLESS	"
GRADIENTS	"
TRANSPORT	"
ZINC ANODE	"
ZINC CATHODE	"
INTERMETALLIC	
ALLOY ->	734
BATTERY ANODE	"
CARBONATE	"
DIFFUSION	"
ELECTRODE	"
LITHIUM MAGNESIUM	"
PROPYLENE	"
INVITRO	
ALLOY ->1129	
ALUMINUM	"
CORROSION	"
HISTOPATHOLOGY	"
IMPLANTABLE	"
INVIVO	"
MAGNESIUM	"
POWER	"
SOURCE	"
ZINC	"
INVIVO	
ALLOY ->1129	
ALUMINUM	"
CORROSION	"
HISTOPATHOLOGY	"
IMPLANTABLE	"
INVITRO	"
MAGNESIUM	"
POWER	"
SOURCE	"
ZINC	"
ION	
ABSORPTION ->1073	
ACCELERATE ->	778
ADSORPTION ->1167	
ALUMINUM ->	983
ALUMINUM CHLORIDE	"
ANION VACANCY ->	255
ANNEALING	1073
ANODE ->	45
	550
ANODIZATION	983
ANTI FRENKEL	255
ARGON ->	558
ION (CONTD)	
BACKSCATTERING	550
BACKSPUTTERING	558
CHLORIDE ->1007	
CHROMATE	"
CONDUCTIVITY	255
CONTAMINANT ->1617	
CONTAMINATION ->	790
CORROSION	778
CREVICE	"
CREVICES	1007
DEFECT STRUCTURE	255
DEPTH PROFILE	1617
ELECTROCHEMISTRY	1007
ELECTROCRYSTALLI.	1167
ELECTRODE	983
	1167
ELECTRON	255
EUTECTIC	778
FILM	558
	1167
FLUORINE	790
FORMATION	778
FUSED	983
GERMANIUM NITRIDE	1073
GERMANIUM OXIDE	"
GERMANIUM OXYNIT.	"
GOLD REFRACTORY	7
IMPLANT	45
IMPLANTATION	558
	1073
INFRARED	"
IRON	1007
KINETICS	1167
LITHIUM CHLORIDE	778
MASS SPECTROMETRY	1617
METAL	1167
METALLIZATION	558
	790
MICROCIRCUIT	1617
MICROPROBE	"
MOLTEN	983
MONOLAYER	778
	1167
NICKEL	778
OXIDE	550
OXYGEN	1007
PITTING	778
POLARIZATION	1007
POTASSIUM CHLORI.	778
RANGE PROFILE	45
REDUCTION	778
	1007
RETENTION	790
RUTHERFORD	550
SALT	983
SCATTERING	550
SECONDARY	1617
SILICON	550
	790
SILICON DIOXIDE	558
SILVER	778
SILVER CHLORIDE	1617
SODIUM CHLORIDE	983
SPUTTERING	558
	1617
STRUCTURE	1167
SUBVALENT	983
SURFACE	790
	1617
TANTALUM	550
TANTALUM OXIDE	45
THERMODYNAMICS	1167
THIN FILM	550
TRANSISTOR	790
TRAPPING	558
YTTRIA DOPED	255
ZIRCONIUM OXIDE	"
ION DRIFT	
CONCENTRATION ->	419
DEVICE	"
FET	"
GATE	"
GLASS	"
INTERFACE	"
ION TRAPPING	"
OXIDE	"
PHOSPHORUS	"
PHOSPHOSILICATE	"
POLARIZATION	"
SILICON OXIDE	"
THICKNESS	"
THRESHOLD	"
VOLTAGE	"
ION IMPLANT	
ALUMINUM ->1281	
ANODE	"
ANODE OXIDATION ->	860
	865
ARSENIC ->1362	
BEHAVIOR	865
BORON ->	705
DIFFUSION	"
DISSOLUTION	860
EPITAXY	1362
GROWTH	"
IMPURITY	860
MARKER	865
METAL ATOMS	1281
MOBILITY	"
NOBEL GASES	865
OXIDATION	705
	1281
RUTHERFORD	"
SEGREGATION	705
SILICON	1362
TANTALUM	865
TANTALUM OXIDE	860
ION IMPLANTATION	
ABSORPTION ->	586
ANODE OXIDATION ->	195
BUFFERED	"
COMPOUND	586
CONCENTRATION	195
CONDUCTIVITY	586
ELECTRIC	"
FORMATION	"
HYDROGEN FLUORIDE	195
OPTICAL	586
OXIDE DISSOLUTION	195
PROFILE	"
SILICON CARBIDE	586
TANTALUM	195
ION MILLABLE	
ELECTRON BEAM ->1620	
POLYSTYRENE	"
POSITIVE	"
RESIST	"
SULFONE	"
ION MOBILITY	
CADMIUM CHLORIDE >	959
	> "
EMF	"
	"
FREE ENERGY	"
	"
GIBBS	"
	"
ION MOBILITY	"
	"
LITHIUM CHLORIDE	"
	"
MOLTEN MIX	"
	"
TRANSFERENCE	"
	"
ION PAIRS	
ACETONITRILE ->	881
DIETHYLFUMARATE	"
DMSO	"
ELECTROHYDRODIME.	"
REDUCTION	"
SODIUM ION	"
VOLTAMMETRY	"
ION SCATTERING	
GETTERING ->	444
GLASS	"
PHOSPHOSILICATE	"
SOFT JUNCTIONS	"
ION TRAPPING	
CONCENTRATION ->	419
DEVICE	"
FET	"
GATE	"
GLASS	"
INTERFACE	"
ION DRIFT	"
OXIDE	"
PHOSPHORUS	"
PHOSPHOSILICATE	"
POLARIZATION	"
SILICON OXIDE	"
THICKNESS	"
THRESHOLD	"
VOLTAGE	"

PRIMARY TERM / CO-TERM — PAGE NO.

IONIC
CERIUM DIOXIDE ->1198
CONDUCTIVITY - - "
DEPENDENCE - - - "
NONSTOICHIOMETRIC "
NUMBER - - - - - "
OXYGEN - - - - - "
PRESSURE - - - - "
TEMPERATURE - - - "
TRANSFERENCE - - "

IONIC CONDUCTANC.
AC - - - - - - -> 375
ALKALINE - - - - "
CATHODE - - - - - "
CONDUCTIVITY - - "
DC - - - - - - - "
DISCHARGED - - - "
IMPEDANCE - - - - "
LECLANCHE CELL - "
MANGANESE DIOXIDE "
MEASUREMENT - - - "
MERCURY OXIDE - - "
RESISTANCE - - - "
UNDISCHARGED - - "

IRON
AGENT - - - - - ->1013
ALKALINE - - - -> 605
ALUMINUM - - - -> 583
ALUMINUM CHLORIDE> 212
ANODE - - - - - ->1146
- - - - - ->1276
ANODE DISSOLUTION 605
BENZOTRIAZOLE - - "
- - 1276
CAPACITOR - - - - 583
CARBON - - - - -> 527
CARBON FILM - - ->1551
CATHODE - - - - - 1013
CHELATING - - - - "
CHLORIDE - - - - 605
- - - ->1007
CHLORIDE SOLUTION 1276
CHROMATE - - - - 1007
- - - - 1146
CHROMIUM - - - ->1192
COPPER - - - - - 212
CORROSION - - - - 583
- - - - 605
- - - - 1146
- - - - 1192
- - - - 1276
COVERAGE - - - - 1013
CREVICES - - - - 1007
DEPOSITION - - - 527
ELECTROCHEMISTRY 1007
ELECTRODISSOLUTI. 1276
ELECTROLYTE - - - 583
ELLIPSOMETRY - - 1146
- - ->1393
EPITAXY - - - - ->1534
ETCHABILITY - - - 583
FILM - - - - - - 1146
FUSED SALT - - - 212
GASEOUS - - - - - 1551
HIGH TEMPERATURE > 665
INHIBITION - - - 605
- - - 1276
INHIBITOR - - - - 1146
ION - - - - - - - 1007
IRON OXIDE - - - 527
- - - 1534
IRON PYRITE - - - 665
IRON SULFIDE - - "
LITHIUM - - - - - "
MELT - - - - - - 212
METAL ION - - - - "
MICROSEGREGATION 583
MOLTEN SALT - - - 665
MOLYBDENUM - - - 1192
NEUTRAL SOLUTION 1276
OPEN CIRCUIT - - 1146
OXIDATION - - - - 1534
- - - - 1551
OXYGEN - - - - - 1007
PASSIVATED - - - 1013
PASSIVATION - - - 527
PASSIVITY - - - - 1146
PENTACARBONYL - -> 832
PHOSPHATES - - - 1393
PITTING - - - - - 1192
PLATINUM - - - - 527
POLARIZATION - - 1007
POLAROGRAPHY - - 212
POTENTIAL - - - - 1013
- - - - 1146

IRON (CONTD)
POTENTIOSTATIC - 527
PRECIPITATION - - 583
PRETREATMENT - - 1551
PULSING - - - - - 1013
REDUCTION - - - - 1007
REFRACTIVE INDEX 1393
RESISTANCE - - - 1192
RING ELECTRODE - 827
SECONDARY CELL - 665
SILVER - - - - - 212
SINGLE CRYSTAL - 1534
SODIUM CHLORIDE - 212
SOLUTION - - - - 605
STAINLESS STEEL - 1192
STEELS - - - - - 527
SULFIDE - - - - - 665
SYSTEM - - - - - 212
TEMPERATURE - - - 1192
THIN FILM - - - - 1551
THIN FILMS - - - 1393
TRANSIENT - - - - 527
TUNNEL - - - - - 583
VAPOR PRESSURE - 832
VOLTAMMETRY - - - 212

IRON (VI)
ANODE DISSOLUTION> 249
ELECTROCHEMICAL - "
FERRATE - - - - - "
POTENTIOSTATIC - "
SYNTHESIS - - - - "

IRON DOPED
BATTERY CELL - -> 1
BETA ALUMINA - - "
CATHODE - - - - - "
GALVANIC CELL - - "
IRON SPINEL - - - "
MOSS BAUER - - - "
SPECTROSCOPY - - "

IRON OXIDE
ANODE DEPOSITION > 37
CARBON - - - - -> 527
CATHODE - - - - -> 42
DEPOSITION - - - 527
- - - ->1592
DISSOLUTION - - - "
ELECTRODE - - - - "
ELECTRON - - - -> 929
EPITAXY - - - - ->1534
HEMISPHERICAL - - 1592
INORGANIC - - - -> 925
- - - - 929
IRON - - - - - - 527
- - - - - - 1534
IRON OXYHYDROXIDE 37
LASER - - - - - - 925
MASK - - - - - - "
MILD - - - - - - 1592
OXIDATION - - - - 1534
PASSIVATION - - - 527
PASSIVITY - - - - 37
PERCHLORATE - - - "
PHOTOMASK - - - - 929
PHOTORESIST - - - 925
PLATINUM - - - - 37
- - - - 42
- - - - 527
POTENTIOSTATIC - "
REDUCTION - - - - 42
RESIST - - - - - 929
RING - - - - - - 1592
RING ELECTRODE - 527
ROTATING - - - - 1592
SINGLE CRYSTAL - 1534
STEEL - - - - - - 1592
STEELS - - - - - 527
SULFATE SOLUTION 1592
THIN FILM - - - - 42
- - - - 925
- - - - 929
TRANSIENT - - - - 527

IRON OXYHYDROXIDE
ANODE DEPOSITION > 37
IRON OXIDE - - - "
PASSIVITY - - - - "
PERCHLORATE - - - "
PLATINUM - - - - "

IRON PYRITE
HIGH TEMPERATURE > 665
IRON - - - - - - "
IRON SULFIDE - - "
LITHIUM - - - - - "

IRON PYRITE (CONTD)
MOLTEN SALT - - - 665
SECONDARY CELL - "
SULFIDE - - - - - "

IRON SPINEL
BATTERY CELL - -> 1
BETA ALUMINA - - "
CATHODE - - - - - "
GALVANIC CELL - - "
IRON DOPED - - - "
MOSS BAUER - - - "
SPECTROSCOPY - - "

IRON SULFIDE
HIGH TEMPERATURE > 665
IRON - - - - - - "
IRON PYRITE - - - "
LITHIUM - - - - - "
MOLTEN SALT - - - "
SECONDARY CELL - "
SULFIDE - - - - - "

IRRADIATION
CHLOROSTILBENES ->1667
IMAGING - - - - - "
LIQUID CRYSTAL - "
NEMATIC - - - - - "
STILBENES - - - - "
ULTRAVIOLET - - - "

IRREVERSIBLE
BEHAVIOR - - - ->1589
EMBRITTLEMENT - - "
HYDROGEN - - - - "
HYDROGEN ELECTRO. "

ISOLATED
BIPOLAR - - - - ->1119
COMPLEMENTARY - - "
DEVICE - - - - - "
INTEGRATION - - - "
MONOLITHIC - - - "
MOS - - - - - - - "
SEMICONDUCTOR - - "
TRANSISTOR - - - "

ISOTHERM
ADSORPTION - - -> 474
DEPOSITION - - - "
ELECTRODE - - - - "
GOLD EVAPORATED - "
LEAD - - - - - - "
REFLECTANCE - - - "
SINGLE CRYSTAL - "
SPECTROSCOPY - - "
UNDERPOTENTIAL - "

ISOTHERMS
ARSENIC - - - - ->1634
COMPOUND - - - - "
DOPING - - - - - "
GALLIUM - - - - - "
LIQUIDUS - - - - "
PHOSPHORUS - - - "
SEMICONDUCTOR - - "
SILICON - - - - - "
SYSTEM - - - - - "
TERNARY - - - - - "

ISOTHIOCYANATE
AMMONIUM - - - -> 977
BROMIDE - - - - - "
CONDUCTANCE - - - "
DIMETHYLFORMAMIDE "
ELECTROLYTE - - - "
NICKEL - - - - - "
NONAQUEOUS - - - "
POTASSIUM - - - - "
SOLUTION - - - - "
TETRABUTYL - - - "
VISCOSITY - - - - "

JUNCTION
ANODE - - - - - -> 280
ANTIMONY - - - ->1523
BIPOLAR - - - - - 280
CHALCOGENIDES - - 1523
CONTRAST - - - ->1202
CRYSTAL DEFECT - 280
DECORATION - - - "
DIODE - - - - - - 1202
DOPING - - - - - 1523
GALLIUM NITRIDE - 1202
HETEROEXPITAXIAL "
INFRARED DEVICE - 1523
LEAD - - - - - - "

JUNCTION (CONTD)
LEAKAGE - - - - - 280
LIGHT EMISSION - 1202
MICROSTRUCTURE - "
NPN - - - - - - - 280
PROFILE - - - - - 1202
STRUCTURE - - - - "
TELLURIDE - - - - 1823
TERNARIES - - - - "
TIN - - - - - - - "
TRANSISTOR - - - 280
VAPOR DEPOSITION 1202
VOLTAGE - - - - - "

KETONES
CHRONOPOTENTIOME.> 769
COUPLING - - - - "
CURRENT REVERSAL "
ELECTROHYDRODIME. "
ELECTROLYTE - - - "
REDUCTIVE - - - - "
UNSATURATED - - - "

KINETIC
AGENT - - - - - -> 779
COEFFICIENT - - - "
COPPER FLUOROBOR. "
COPPER SULFATE - "
DIFFUSION - - - - "
ELECTROLYTE - - - "
ORGANIC - - - - - "
PARAMETER - - - - "

KINETICS
ADSORPTION - - ->1167
ALKALI METAL - -> 994
ALLOY - - - - - -> 889
- - - - - ->1051
ALUMINIDE - - - - "
ALUMINUM CHLORIDE 994
ATMOSPHERE - - - 889
CALCIA STABILIZED> 506
CARBONATE - - - - 994
CHLORIDE - - - - "
COATING - - - - - 1051
COBALT IRON - - - 889
COEFFICIENT - - - 994
CURRENT DENSITY - "
DIFFUSION - - - - 1051
ELECTROCATALYST ->1125
ELECTROCRYSTALLI. 1167
ELECTRODE - - - - 506
- - - - 994
- - - - 1167
ELECTROLYTE - - - 506
EXCHANGE - - - - 994
FILM - - - - - - 1167
FORMALDEHYDE - - 1125
GALLIUM - - - - - 506
GALLIUM SESQUIOX. "
HYDROGEN SULFIDE 889
ION - - - - - - - 1167
MECHANISM - - - - 1125
METAL - - - - - - 1167
MOLYBDENUM - - - 1125
MONOLAYER - - - - 1167
NICKEL - - - - - 1051
OXIDATION - - - - 1125
OXYGEN - - - - - 506
PACK - - - - - - 1051
PARABOLIC - - - - 889
PROPYLENE - - - - 994
PROTECTIVE - - - 1051
REACTION - - - - 1125
SOLID - - - - - - 506
STRUCTURE - - - - 1167
SULFIDATION - - - 889
SULFUR - - - - - 1125
THERMODYNAMICS - 1051
- 1167
TRANSFER - - - - 506
- - - - 994
ZIRCONIA - - - - 506

KRAMERS KRONIG
ABSORPTION - - ->1496
CRYSTAL QUALITY - "
OPTICAL INTERFER. "
REFRACTIVE INDEX "
SILICON FILM - - "
THIN FILM - - - - "

LACQUER FILM
CHROME COATING -> 29
DELAMINATION - - "
ORGANIC - - - - - "
STEEL - - - - - - "

PRIMARY TERM / CO-TERM	PAGE NO.
LACQUER FILM	(CONTD)
UNDERCUTTING	29
LAMP	
ALUMINATES	->1623
ENERGY TRANSFER	-> 305
EUROPIUM	"
GALLATE	1623
HEXAGONAL	"
HIGH PRESSURE	305
HOST LATTICE	1623
MERCURY	305
NEW	1623
PHOSPHOR	305
PHOSPHORS	1623
RARE EARTH	"
TERBIUM	305
VANDATE	"
VAPOR	"
YTTRIUM	"
LAMPS	
COLOR RENDITION	-> 407
DELUXE	->1627
DISTRIBUTION	407
FLUORESCENT	1627
HIGH EFFICACY	"
MERCURY VAPOR	407
NEW GENERATION	1627
OPTIMIZED	407
PHOSPHORS	"
POWER	"
SPECTRAL	"
LANGMUIR SHEATH	
ARGON	->1372
CONTROL	"
DIFFUSING	"
EQUILIBRIA	"
ETCHING	"
HELIUM	"
HEXAFLUORIDE	"
NITROGEN	"
PENTA FLUORIDE	"
RATE	"
REACTION	"
TUNGSTEN	"
LANTHANUM	
ALUMINATE	-> 142
CANDOLUMINESCENCE	"
PHOSPHORS	"
TRANSITION ION	"
WILLEMITE	"
ZINC PHOSPHATE	"
LASER	
ANALYZER	-> 689
CONTROL	->1233
	->1235
CVD	1233
DEFECT	689
DEPOSITION	1233
	1235
FILM	1233
	1235
FILM THICKNESS	1233
	1235
HELIUM	689
	1233
INORGANIC	-> 925
IRON OXIDE	"
MASK	"
NEON	1233
NITRIDE	"
NITROGEN	689
PHOTORESIST	925
POLYCRYSTALLINE	1235
SILICON	689
	1233
	1235
SILICON DIOXIDE	1233
SLICE	689
SURFACE	"
THIN FILM	925
LATTICE	
ALUMINUM	->1662
ANTIMONIDE	"
ARSENIDE	"
GALLIUM	"
GROUP II-VI	"
GROUP III-V	"
INDIUM	"
MISCIBILITY GAP	"
PARAMETER	"
PHOSPHIDE	"
LATTICE	(CONTD)
PSEUDOBINARY	1662
SEMICONDUCTOR	"
SOLID SOLUTION	"
LATTICE MATCH	
ALLOY	-> 416
CHARACTERIZATION	"
GAAS	"
GROWTH	"
HETEROJUNCTION	"
LPE	"
LATTICE PARAMETER	
FREE ENERGY	-> 932
GIBBS	"
MISCIBILITY GAP	"
MODEL	"
PSEUDO BINARY	"
QUASIREGULAR	"
LAYER	
BARRIER	->1066
CAPACITANCE	"
CONCENTRATION	-> 132
DEPENDENCE	"
DIFFUSION	"
DISTRIBUTION	"
DOPED OXIDE	"
EPITAXIAL	-> 150
EPITAXY	1066
GAAS	"
HALL EFFECT	"
IMPURITY	132
INTERFEROGRAM	150
MEASUREMENT	1066
MOBILITY	"
PHASE SHIFT	150
PHOSPHORUS	132
PHOTOLUMINESCENCE	1066
SCHOTTKY	"
SILICON	132
	150
SPECTRA	1066
TEMPERATURE	132
THICKNESS	150
VAPOR DEPOSITION	132
LEAD	
ADDITIVE	-> 463
ADSORPTION	-> 474
ANODE	-> 876
ANTIMONY	->1523
BARIUM SULFATE	463
BEAM	-> 62
CHALCOGENIDES	1523
CIRCUIT	62
DEPOSITION	474
	->1610
DOPING	1523
ELECTRODE	463
	474
	1610
ELECTROLESS	62
ELECTRON	876
ENERGY TRANSFER	->1338
EUROPIUM	"
FLUORESCENCE	"
GLASS	"
GOLD	62
	1610
GOLD EVAPORATED	474
INFRARED DEVICE	1523
ISOTHERM	474
JUNCTION	1523
LEAD SULFATE	463
LIGNIN	"
MECHANISM	"
MICROSCOPY	876
MORPHOLOGY	463
OPTIC	1610
PLATING	62
POLARIZED	876
REACTION	463
REFLECTANCE	474
SILICON	62
SINGLE CRYSTAL	474
	1610
SPECTROSCOPY	474
TELLURIDE	1523
TERNARIES	"
TIN	"
UNDER POTENTIAL	1610
UNDERPOTENTIAL	474
VOLTAMMETRY	876
LEAD ACID	
ACTIVE	-> 531
BATTERY	"
	-> 854
	->1541
CORROSION	531
CRYSTAL	->1454
ELECTRON	"
	1541
FORMATION	854
GAS	-> 13
GRID	531
HYDROGEN	13
LEAD ANTIMONY	531
LEAD CALCIUM	13
	1541
LEAD ELECTRODE	854
	1541
LEAD SULFATE	1454
MATERIAL	531
MICROSCOPY	1454
	1541
NEGATIVE	"
NEGATIVE PLATE	854
OXYGEN	13
POLYMER BONDING	1541
PRECIPITATION	1454
PROTECTION	531
RECOMBINATION	13
SCANNING	1454
	1541
SOLUTION	1454
STRUCTURE	"
SYSTEM	13
THICKNESS	531
LEAD ANTIMONY	
ACTIVE	-> 531
BATTERY	"
CORROSION	"
GRID	"
LEAD ACID	"
MATERIAL	"
PROTECTION	"
THICKNESS	"
LEAD CALCIUM	
BATTERY	->1541
ELECTRON	"
GAS	-> 13
HYDROGEN	"
LEAD ACID	"
	1541
LEAD ELECTRODE	"
MICROSCOPY	"
NEGATIVE	"
OXYGEN	13
POLYMER BONDING	1541
RECOMBINATION	13
SCANNING	1541
SYSTEM	13
LEAD CARBONATE	
BASIC	-> 253
COMPOSITION	"
LEAD OXIDE	"
LEAD SULFATE	"
VARIABLE	"
LEAD CHLORIDE	
ANTHRACENE	->1341
COMPOSITE	"
CONVERSION	"
DIMETHYLFORMAMIDE>	79
ELECTRODE	"
LIGHT	1341
LUMINESCENCE	"
MEASUREMENT	79
POTENTIAL	"
STANDARD	"
TITANIUM CHLORIDE	"
VISIBLE	1341
X RAY	"
LEAD DIOXIDE	
BATTERY FAILURE	->1546
CAPACITY	"
CYCLE	"
DECOMPOSITION	"
ELECTRODE	"
FORM	"
MECHANISM	"
THERMAL ANALYSIS	"
LEAD DOPED	
DIRECT CURRENT	-> 109
ELECTROLUMINESCE.	"
LEAD DOPED	(CONTD)
GREEN	109
PHOSPHORS	"
POWDER CELLS	"
ZINC SULFIDE	"
LEAD ELECTRODE	
BATTERY	-> 854
	->1541
ELECTROCAPILLARY	>1417
ELECTRON	1541
FORMATION	854
LEAD ACID	"
	1541
LEAD CALCIUM	"
MENISCUS	1417
MICROSCOPY	1541
NEGATIVE	"
NEGATIVE PLATE	854
POLYMER BONDING	1541
SCANNING	"
SODIUM SULFATE	1417
LEAD OXIDE	
BASIC	-> 253
COMPOSITION	"
LEAD CARBONATE	"
LEAD SULFATE	"
VARIABLE	"
LEAD SULFATE	
ADDITIVE	-> 463
BARIUM SULFATE	"
BASIC	-> 253
COMPOSITION	"
CRYSTAL	->1454
ELECTRODE	463
ELECTRON	1454
LEAD	463
LEAD ACID	1454
LEAD CARBONATE	253
LEAD OXIDE	"
LIGNIN	463
MECHANISM	"
MICROSCOPY	1454
MORPHOLOGY	463
PRECIPITATION	1454
REACTION	463
SCANNING	1454
SOLUTION	"
STRUCTURE	"
VARIABLE	253
LEAD SULFIDE	
ETCHANT	-> 595
LEAD SULFUR	"
PN JUNCTION	"
SELENIUM	"
LEAD SULFUR	
ETCHANT	-> 595
LEAD SULFIDE	"
PN JUNCTION	"
SELENIUM	"
LEAKAGE	
ANODE	-> 280
BIPOLAR	"
CRYSTAL DEFECT	"
DECORATION	"
JUNCTION	"
NPN	"
TRANSISTOR	"
LECLANCHE CELL	
AC	-> 375
ALKALINE	"
CATHODE	"
CONDUCTIVITY	"
DC	"
DISCHARGED	"
IMPEDANCE	"
IONIC CONDUCTANC.	"
MANGANESE DIOXIDE	"
MEASUREMENT	"
MERCURY OXIDE	"
RESISTANCE	"
UNDISCHARGED	"
LED	
ETCHING	-> 455
FERRICYANIDE	"
GAP	"
MASK	"
POLISH	"

PRIMARY TERM / CO-TERM — PAGE NO.

LENGTH
CAPACITOR - - - ->1219
CARRIER - - - - - "
DEEP - - - - - - "
DEPLETION - - - - "
DIFFUSION - - - - "
LIFETIME - - - - "
MINORITY - - - - "
MOS - - - - - - - "
SILICON - - - - - "
STEADY STATE - - "

LEWIS ACID
CONDUCTIVITY - -> 91
DIMETHYLFORMAMIDE "
DISSOCIATION - - "
PROTONIC ACID - - "

LIFETIME
CAPACITOR - - - ->1219
CARRIER - - - - - "
- - - - ->1332
DEEP - - - - - - 1219
DEPLETION - - - - "
DIFFUSION - - - - "
DIODE - - - - - - 1332
EFFICIENCY - - - "
GALLIUM - - - - - "
HEAT - - - - - - "
LENGTH - - - - - 1219
MINORITY - - - - "
MOS - - - - - - - "
PHOSPHORUS - - - 1332
PHOTOLUMINESCENCE "
SILICON - - - - - 1219
STEADY STATE - - "
ZINC OXIDE - - - 1332

LIGHT
AMMONIA - - - - -> 962
ANTHRACENE - - ->1341
BEHAVIOR - - - - 962
COMPOSITE - - - - 1341
CONVERSION - - - "
DIODES - - - - - 962
EMITING - - - - - "
EPITAXY - - - - - "
GAP - - - - - - - "
IMPURITY - - - - "
LEAD CHLORIDE - - 1341
LIQUID PHASE - - 962
LUMINESCENCE - - 1341
NITROGEN DOPING - 962
SOURCE - - - - - "
VISIBLE - - - - - 1341
X RAY - - - - - - "

LIGHT EMISSION
CONTRAST - - - ->1202
DIODE - - - - - - "
GALLIUM NITRIDE - "
HETEROEXPITAXIAL "
JUNCTION - - - - "
MICROSTRUCTURE - "
PROFILE - - - - - "
STRUCTURE - - - - "
VAPOR DEPOSITION "
VOLTAGE - - - - - "

LIGNIN
ADDITIVE - - - -> 463
BARIUM SULFATE - "
ELECTRODE - - - - "
LEAD - - - - - - "
LEAD SULFATE - - "
MECHANISM - - - - "
MORPHOLOGY - - - "
REACTION - - - - "

LIMITING CURRENT
CURRENT DISTRIBU.> 241
MASS TRANSFER - - "
ROTATING - - - - "
SPHERE - - - - - "

LINEAR SWEEP
LITHIUM FLUORIDE > 86
MOLTEN FLUORIDE - "
POTASSIUM - - - - "
SODIUM FLUORIDE - "
THORIUM - - - - - "
URANIUM - - - - - "
VOLTAMMETRY - - - "

LIQUID
ACID - - - - - - ->1609
AMMONIA - - - - -> 230

LIQUID (CONTD)
AMMONIA - - - - - 1609
BATTERY - - - - ->1045
COEFFICIENT - - - 230
CONTAMINATION - - 1045
CRYSTAL GROWTH -> 439
-> 822
CZOCHRALSKI - - - "
ELECTROLYTE - - - 1045
ENCAPSULATION - - 822
EPITAXY - - - - - 439
EVALUATION - - - "
EVOLUTION - - - - 230
- - - - 1609
EXCHANGE CURRENT 230
GAAS - - - - - - 439
GALLIUM PHOSPHIDE 822
HYDROGEN - - - - 230
- - - - 1609
IMAGING - - - - - 822
INFRARED - - - - 1045
INORGANIC - - - - "
LITHIUM - - - - - "
MICROWAVE DEVICE 439
NITROGEN - - - - 230
- - - - 1609
OVERVOLTAGE - - - 230
OXYHALIDE - - - - 1045
REACTION - - - - 1609
TAFEL SLOPE - - - 230
TRACE ANALYSIS - 1045
TRANSFER - - - - 230
WATER - - - - - - 1045
X RAY - - - - - - 822

LIQUID CRYSTAL
CHLOROSTILBENES ->1667
IMAGING - - - - - "
IRRADIATION - - - "
NEMATIC - - - - - "
STILBENES - - - - "
ULTRAVIOLET - - - "

LIQUID PHASE
ACCEPTOR - - - ->1208
AMMONIA - - - - -> 962
BEHAVIOR - - - - "
DIODES - - - - - "
EMITING - - - - - "
EPITAXY - - - - - "
- - - - - 1208
GAP - - - - - - - 962
HALL DATA - - - - 1208
IMPURITY - - - - 962
INDIUM PHOSPHIDE 1208
LIGHT - - - - - - 962
NITROGEN DOPING - "
PHOTOLUMINESCENCE 1208
SOURCE - - - - - 962

LIQUIDUS
ARSENIC - - - - ->1634
COMPOUND - - - - "
DOPING - - - - - "
GALLIUM - - - - - "
ISOTHERMS - - - - "
PHOSPHORUS - - - "
SEMICONDUCTOR - - "
SILICON - - - - - "
SYSTEM - - - - - "
TERNARY - - - - - "

LIQUIDUS TEMPERA.
CALCULATION - - ->1258
MOLTEN SALT - - - "
PHASE DIAGRAM - - "

LITHIUM
ACTIVATION - - -> 459
ALLOY - - - - - -> 247
ALUMINUM - - - -> 303
AMMONIA - - - - - 459
BATTERY - - - - ->1045
- - - - ->1294
BEHAVIOR - - - -> 163
BERYLLIUM - - - - 247
- - - ->1429
BISMUTH - - - - - 247
CHEMISORPTION - - 163
CHLORIDE - - - ->1298
CHRONOPOTENTIONE. 1429
CONCENTRATION - - 459
CONDUCTANCE - - - 1298
CONTAMINATION - - 1045
DECOMPOSITION - - 459
DENSITY - - - - - 1298
DEPENDENCE - - - 1429

LITHIUM (CONTD)
DEPLETION - - - - 1429
DIELECTRIC - - - 163
DIFFUSION - - - - "
DOPING - - - - - "
ELECTRODE - - - - 247
ELECTROINITIATE - 1294
ELECTROLYTE - - - 1045
ELECTROMIGRATION 1429
ELECTRON - - - - 459
ENTROPY - - - - - "
FLOURIDES - - - - 1429
FLUORIDE - - - - 247
GLASSES - - - - - 1429
HIGH ENERGY - - - 1294
HIGH TEMPERATURE 163
> 665
HYDROTHERMAL - - 303
INFRARED - - - - 1045
INORGANIC - - - - "
IRON - - - - - - 665
IRON PYRITE - - - "
IRON SULFIDE - - "
LIQUID - - - - - 1045
LUMINESCENCE - - 303
MANGANESE - - - - 1298
MANGANOUS - - - - 303
MELT - - - - - - 1298
MOLTEN HALIDES - 1429
MOLTEN SALT - - - 247
- - - 665
ORTHOSILICATE - - 303
OXYHALIDE - - - - 1045
PERCHLORATE - - - 1294
PHOSPHOR - - - - 303
POLYCRYSTALLINE - 163
POLYMERIZATION - 1294
POTASSIUM - - - - 1298
RUBIDIUM - - - - "
SECONDARY CELL - 665
SODIUM - - - - - 163
- - - - - 1298
SOLVATED - - - - 459
SULFIDE - - - - - 665
TEMPERATURE - - - 1429
TETRAHYDROFUHAN - 1294
TRACE ANALYSIS - 1045
WATER - - - - - - "
ZINC OXIDE - - - 163

LITHIUM ANODE
BATTERY - - - - -> 315
CARBONATE - - - - "
GALVANIC CELL - - "
LITHIUM BROMINE - "
NONAQUEOUS - - - "
PROPYLENE - - - - "
SECONDARY - - - - "
SOLVENT - - - - - "

LITHIUM BROMINE
BATTERY - - - - -> 315
CARBONATE - - - - "
GALVANIC CELL - - "
LITHIUM ANODE - - "
NONAQUEOUS - - - "
PROPYLENE - - - - "
SECONDARY - - - - "
SOLVENT - - - - - "

LITHIUM CELL
BEHAVIOR - - - ->1460
DISCHARGE - - - - "
ELECTROLYTE - - - "
MOLYBDENUM - - - "
NONAQUEOUS - - - "
SOLUTION - - - - "

LITHIUM CELLS
BATTERY - - - - -> 656
BEHAVIOR - - - - "
CARBONATE - - - - "
CATHODE - - - - - "
COPPER - - - - - "
MANGANESE - - - - "
MOLYBDENUM - - - "
PROPYLENE - - - - "
TETRAHYDROFURAN - "

LITHIUM CHLORIDE
ACCELERATE - - -> 778
BINARY - - - - -> 500
CADMIUM CHLORIDE > 959
CORROSION - - - - 778
COULOMBIC - - - - 500
CREVICE - - - - - 778
EMF - - - - - - - 959

LITHIUM CHLORIDE (CONTD)
EUTECTIC - - - - 778
FORMATION - - - - "
FREE ENERGY - - - 959
GIBBS - - - - - - "
INTERACTION - - - 500
ION - - - - - - - 778
ION MOBILITY - - 959
- - "
MOLTEN MIX - - - "
MOLTEN SALT - - - 500
MONOLAYER - - - - 778
NICKEL - - - - - "
PITTING - - - - - "
POSTASSIUM CHLOR. 500
POTASSIUM CHLORI. 778
REDUCTION - - - - "
SILVER - - - - - "
SURFACE TENSION - 500
TRANSFERENCE - - 959

LITHIUM ELECTRODE
BATTERY - - - - ->1457
CARBONATE - - - - "
ELECTRODEPOSITION "
ELECTROLYTE - - - "
PROPYLENE - - - - "
RECHARGABLE - - - "

LITHIUM FLUORIDE
LINEAR SWEEP - -> 86
MOLTEN FLUORIDE - "
POTASSIUM - - - - "
SODIUM FLUORIDE - "
THORIUM - - - - - "
URANIUM - - - - - "
VOLTAMMETRY - - - "

LITHIUM HYDROXIDE
COPPER - - - - -> 651
CORROSION - - - - "
CYCLIC - - - - - "
ELEVATED - - - - "
TEMPERATURE - - - "
VOLTAMMETRY - - - "

LITHIUM ION
CARBONATE - - - - -> 83
EMF - - - - - - - "
MEASUREMENT - - - "
NUMBER - - - - - "
PROPYLENE - - - - "
SOLUTION - - - - "
TRANSFERENCE - - "

LITHIUM MAGNESIUM
ALLOY - - - - - -> 734
BATTERY ANODE - - "
CARBONATE - - - - "
DIFFUSION - - - - "
ELECTRODE - - - - "
INTERMETALLIC - - "
PROPYLENE - - - - "

LITHOGRAPHY
CONTRAST - - - ->1669
DEVELOPER - - - - "
ELECTRON BEAM - - "
ELECTRON RESIST - "
ELECTRON RESISTS >1500
FUNCTION - - - - 1669
METHACRYLATE - - "
PMMA - - - - - - "
POLYMER RESISTS - 1500
POLYMETHYL - - - 1669
RATE - - - - - - "
SOLUBILITY - - - "
X RAY - - - - - - 1500

LOW PRESSURE
ATMOSPHERE - - -> 943
LOW TEMPERATURE - "
MAGNESIUM - - - - "
NITROGEN - - - - "
THERMAL NITRIDAT. "

LOW TEMPERATURE
ATMOSPHERE - - -> 943
CAPACITANCE - - ->1318
COPPER - - - - - "
COPPER CHLORIDE - "
DIFFUSION - - - - "
DOUBLE LAYER - - "
GOLD - - - - - - "
LOW PRESSURE - - 943
MAGNESIUM - - - - "
NITROGEN - - - - "

PRIMARY TERM / CO-TERM	PAGE NO.
LOW TEMPERATURE (CONTD)	
SINGLE CRYSTAL	1318
SOLID ELECTROLYTE	"
THERMAL NITRIDAT.	943
LOWERING	
BARRIER HEIGHT	->1195
BREAKDOWN	"
CONTAMINATION	"
DIELECTRIC	"
FILM	"
SILICON	"
SILICON DIOXIDE	"
SODIUM	"
SODIUM INDUCED	"
LPE	
ALLOY	-> 416
CHARACTERIZATION	"
GAAS	"
GROWTH	"
HETEROJUNCTION	"
LATTICE MATCH	"
LUMINESCENCE	
ALKALI	->1122
ALKALINE	"
	->1475
ALUMINUM	-> 303
ANTHRACENE	->1341
BARIUM CALCIUM	->1631
BARIUM MAGNESIUM	"
BORATES	"
CALCIUM	"
CALCIUM MAGNESIUM	"
CALCIUM STRONTIUM	"
CERIUM DIOXIDE	->1676
CHEMILUMINESCENCE>	1178
COMMENTS	1676
COMPOSITE	1341
COMPOSITIONAL	1676
CONDUCTIVITY	"
CONVERSION	1341
CRYSTAL	1475
DEPENDENCE	1676
DIVALENT	1475
EARTH	1122
	1475
ELECTRICAL	1676
ELECTROANALYSIS	1178
ELECTROGENERATE	"
ENERGY DEFICIENT	"
EUROPIUM	1122
	1475
HYDROTHERMAL	303
LEAD CHLORIDE	1341
LIGHT	"
LITHIUM	303
MAGNESIUM STRONT.	1631
MANGANOUS	303
NONAQUEOUS	1178
OPTICAL SPECTRA	1475
ORTHOSILICATE	303
PHOSPHATES	1122
PHOSPHOR	303
QUENCHING	1676
SOLVENT	1178
STRUCTURE	1475
SULFATES	"
TEMPERATURE	1676
TERBIUM	1631
THEORY	1676
THERMAL	"
THERMAL QUENCHING>	312
VISIBLE	1341
VOLTAMMETRY	1178
X RAY	1341
MAGNESIUM	
ALLOY	->1129
	->1245
ALUMINATE	-> 871
ALUMINUM	1129
	1245
ATMOSPHERE	-> 943
BATTERY	1245
BUFFER	"
CHLORIDE	"
CORROSION	1129
EMF	1245
EPITAXY	571
GALLIUM ARSENIDE	"
GROWTH	"
HIGH PRESSURE	1245
HISTOPATHOLOGY	1129
IMPLANTABLE	"
INVITRO	"
MAGNESIUM (CONTD)	
INVIVO	1129
LOW PRESSURE	943
LOW TEMPERATURE	"
NITROGEN	"
POWER	1129
SEAWATER	1245
SOURCE	1129
SPINEL	571
THERMAL NITRIDAT.	943
ZINC	1129
MAGNESIUM STRONT.	
BARIUM CALCIUM	->1631
BARIUM MAGNESIUM	"
BORATES	"
CALCIUM	"
CALCIUM MAGNESIUM	"
CALCIUM STRONTIUM	"
LUMINESCENCE	"
TERBIUM	"
MANGANESE	
BATTERY	-> 656
BEHAVIOR	"
CARBONATE	"
CATHODE	"
CHLORIDE	->1298
CHROMIUM	-> 225
COBALT	"
CONDUCTANCE	1298
COPPER	656
CORROSION	225
DENSITY	1298
EQUILIBRIA	-> 467
EVOLUTION	225
HYDROGEN	"
INCLUSION	467
INITIATION	"
LITHIUM	1298
LITHIUM CELLS	656
MELT	1298
MOLYBDENUM	656
PITTING	467
POTASSIUM	1298
POTENTIAL PH	467
PROPYLENE	656
RUBIDIUM	1298
SODIUM	"
STAINLESS STEEL	467
SULFIDE	"
TETRAHYDROFURAN	656
VANADIUM	225
MANGANESE DIOXIDE	
AC	-> 375
ALKALINE	"
CATHODE	"
CONDUCTIVITY	"
DC	"
DISCHARGED	"
IMPEDANCE	"
IONIC CONDUCTANC.	"
LECLANCHE CELL	"
MEASUREMENT	"
MERCURY OXIDE	"
RESISTANCE	"
UNDISCHARGED	"
MANGANOUS	
ALUMINUM	-> 303
HYDROTHERMAL	"
LITHIUM	"
LUMINESCENCE	"
ORTHOSILICATE	"
PHOSPHOR	"
MARKER	
ANODE OXIDATION	-> 865
BEHAVIOR	"
ION IMPLANT	"
NOBEL GASES	"
TANTALUM	"
MASK	
ACOUSTIC WAVE	->1503
CONTACT PRINT	"
ETCHING	-> 455
FERRICYANIDE	"
GAP	"
INORGANIC	-> 925
IRON OXIDE	"
LASER	"
LED	455
PHOTO RESIST	1503
PHOTOLITHOGRAPHY	"
PHOTORESIST	925
MASK (CONTD)	
POLISH	455
SUBMICRON LINE	1503
THIN FILM	925
MASKING	
ALUMINUM	->1509
CRYSTALLIZATION	"
DOPING	"
GALLIUM	"
OXIDATION	"
PASSIVATION	"
PHOSPHORUS	"
PLANAR JUNCTION	"
SEGREGATION	"
MASS	
CATHODE	-> 867
COEFFICIENT	"
CONVECTION	"
ELECTROWINNING	"
FORCED	"
MODEL CELL	"
NATURAL	"
TRANSFER	"
MASS SPECTROMETRY	
CONTAMINANT	->1617
DEPTH PROFILE	"
ION	"
MICROCIRCUIT	"
MICROPROBE	"
SECONDARY	"
SILVER CHLORIDE	"
SPUTTERING	"
SURFACE	"
MASS TRANSFER	
COMPONENT	->1000
CONVECTIVE	"
CORROSION	"
CRACK	"
CURRENT	->1448
CURRENT DISTRIBU.>	241
CURRENT POTENTIAL>	1558
DIFFUSION	1000
DISK	1558
DISTRIBUTION	1448
ELECTRODE	1558
LIMITING CURRENT	241
MINOR	1000
MODULATION	1558
MOLTEN SALT	1000
PLANE	1448
PROPAGATING	1000
ROTATING	241
	1558
ROTATING DISK	1448
SINUSOIDAL	1558
SPHERE	241
MASS TRANSPORT	
DECOMPOSITION	->1328
ELECTROLYSIS	"
HIGH TEMPERATURE	"
INTERFACE	"
SILICON DIOXIDE	"
STABILITY	"
MATERIAL	
ACTIVE	-> 531
BATTERY	"
CORROSION	"
GRID	"
LEAD ACID	"
LEAD ANTIMONY	"
PROTECTION	"
THICKNESS	"
MEASUREMENT	
AC	-> 375
ADSORPTION	->1570
ALKALI CHLORIDE	-> 991
ALKALINE	375
APPLICATION	-> 422
BARRIER	->1066
CAPACITANCE	"
CARBONATE	-> 83
CATHODE	375
CERIUM CHLORIDE	991
CHARACTERIZATION >	669
CIRCUIT	422
CONDUCTANCE	1570
CONDUCTIVITY	375
CONTACT ANGLE	669
COPPER	-> 661
CRYSTAL	->1674
MEASUREMENT (CONTD)	
CURRENT	661
	"
DC	375
DEVICE	422
DIMETHYLFORMAMIDE>	79
DISCHARGED	375
DISTRIBUTION	661
	"
ELECTRODE	79
	1570
ELECTRODEPOSITION	661
EMF	83
	991
EPITAXIAL	422
EPITAXY	1066
EXISTENCE	1674
GAAS	1066
HALL EFFECT	"
HEAT	1674
IMPEDANCE	375
INDIUM	1674
INTEGRATED	422
IONIC CONDUCTANC.	375
LAYER	1066
LEAD CHLORIDE	79
LECLANCHE CELL	375
LITHIUM ION	83
MANGANESE DIOXIDE	375
MERCURY OXIDE	"
MIXTURE	991
MOBILITY	1066
MOLTEN SALT	991
MONOSELENIDE	1674
NUMBER	83
NUMBERS	991
PHASE TRANSITION	1674
PHOTOLUMINESCENCE	1066
POTENTIAL	79
PRINTED CIRCUIT	661
PROPYLENE	83
REDOX SYSTEM	661
RESISTANCE	375
	422
RESISTIVITY	"
SCHOTTKY	1066
SEMICONDUCTOR	1674
SILICON	422
SILICON DIOXIDE	669
SOLUTION	83
SPECIFIC	1674
SPECTRA	1066
SPREADING	422
STANDARD	79
STRUCTURE	1674
SURFACE	669
	1570
THERMAL	669
THIN FILM	1570
TITANIUM CHLORIDE	79
TRANSFERENCE	83
	991
UNDISCHARGED	375
WIRE	661
	"
WIRE ELECTRODE	"
XRAY	1674
MECHANISM	
ADDITIVE	-> 463
BARIUM SULFATE	"
BATTERY FAILURE	->1546
CAPACITY	"
CHLORATE CELL	->1606
COUPLING	-> 745
CURRENT	1606
CURRENT DENSITY	"
CYCLE	1546
CYCLIC	-> 360
DECOMPOSITION	1546
DIGITAL	745
DISSOLUTION	360
EFFECT	1606
EFFICIENCY	"
ELECTROCATALYST	->1125
ELECTROCRYSTALLI.>	207
	1606
ELECTRODE	360
	463
	745
	1546
ELECTRODEPOSITION	207
ELECTROOXIDATION	745
EXCHANGE CURRENT	207
FORM	1546
FORMALDEHYDE	1125
KINETICS	"

PRIMARY TERM — CO-TERM — PAGE NO.

MECHANISM (CONTD)
LEAD - - - - - - 463
LEAD DIOXIDE - - 1546
LEAD SULFATE - - 463
LIGNIN - - - - - "
MOLYBDENUM - - - 1125
MORPHOLOGY - - - 463
OXIDATION - - - - 1125
PH - - - - - - - - 1606
PLATINUM - - - - 360
POTENTIAL - - - - "
PROCESS - - - - - 1606
PROGRAM - - - - - 360
REACTION - - - - 463
- - - - 1125
REDEPOSITION - - 360
RING DISK - - - - "
- - - - 745
ROTATING - - - - "
ROUGHENING - - - 360
SILVER - - - - - 207
SILVER ELECTRODE 1606
SIMULATION - - - 745
SULFUR - - - - - 1125
TEMPERATURE - - - 1606
THERMAL ANALYSIS 1546

MELT
ALUMINUM - - - -> 773
ALUMINUM CHLORIDE> 212
CHLORIDE - - - ->1298
CHLOROALUMINATE - 773
CHRONOPOTENTIOME. "
COEFFICIENT - - -> 556
CONDUCTANCE - - - 1298
COPPER - - - - - 212
CRYSTAL GROWTH - 556
DENSITY - - - - - 1298
DIFFUSION - - - - 556
FUSED SALT - - - 212
GALLIUM - - - - - 556
HALIDES - - - - - 773
IRON - - - - - - 212
LITHIUM - - - - - 1298
MANGANESE - - - - "
METAL ION - - - - 212
MOLTEN - - - - - 773
OXIDATION - - - - "
PHOSPHIDE - - - - 556
PHOSPHORUS - - - "
POLAROGRAPHY - - 212
POTASSIUM - - - - 1298
RUBIDIUM - - - - "
SILVER - - - - - 212
SODIUM - - - - - 1298
SODIUM CHLORIDE - 212
SYSTEM - - - - - "
VOLTAMMETRY - - - "

MEMBRANE
BETA ALUMINA - -> 596
CRYSTAL GROWTH - "
HIGH PRESSURE - - "
SODIUM - - - - - "

MENISCUS
ELECTROCAPILLARY >1417
LEAD ELECTRODE - "
SODIUM SULFATE - "

MERCURY
ACETONITRILE - -> 780
ACTIVATION - - - "
ADSORPTION - - ->1421
AQUEOUS SOLUTION >1311
BATTERY - - - - -> 175
CADMIUM - - - - - "
CELL - - - - - - "
CHARGE ACCEPTANCE "
CHRONOCOULOMETRY 1421
COMPUTER - - - - 175
CONTROLLED - - - "
ELECTROCATALYST - 780
ELECTRODE - - - - 1421
ELECTROLYSIS - - 1311
ENERGY TRANSFER -> 305
EUROPIUM - - - - "
FORMIC ACID - - - 780
HIGH PRESSURE - - 305
IMPURITIES - - - 1311
LAMP - - - - - - 305
NICKEL - - - - - 175
OXIDATION - - - - 780
PHOSPHOR - - - - 305
PULSE CHARGING - 175
RHODIUM - - - - - 1421
SODIUM CHLORIDE - 1311

MERCURY (CONTD)
TERBIUM - - - - - 305
VANDATE - - - - - "
VAPOR - - - - - - "
VOLTAMMETRY - - - 1421
YTTRIUM - - - - - 305

MERCURY OXIDE
AC - - - - - - - -> 375
ALKALINE - - - - "
CATHODE - - - - - "
CONDUCTIVITY - - "
DC - - - - - - - "
DISCHARGED - - - "
IMPEDANCE - - - - "
IONIC CONDUCTANC. "
LECLANCHE CELL - "
MANGANESE DIOXIDE "
MEASUREMENT - - - "
RESISTANCE - - - "
UNDISCHARGED - - "

MERCURY TYPE
BRINE LEVEL - - ->1286
CHLORALKALI CELL "
GAS LIFT - - - - "
PUMP - - - - - - "
SCALE UP - - - - "
VOLTAGE - - - - - "

MERCURY VAPOR
COLOR RENDITION -> 407
DISTRIBUTION - - "
LAMPS - - - - - - "
OPTIMIZED - - - - "
PHOSPHORS - - - - "
POWER - - - - - - "
SPECTRAL - - - - "

METAL
ACTIVITY - - - -> 543
ADSORPTION - - ->1167
AERATION - - - -> 183
CHROMIUM - - - - 543
CORROSION - - - - 183
DEPOSITION - - ->1160
DIFFERENTIAL - - 183
ELECTROCRYSTALLI. 1167
ELECTRODE - - - - "
FILM - - - - - - 183
- - - - - - 1167
ION - - - - - - - "
KINETICS - - - - "
MOISTNESS - - - - 183
MONOLAYER - - - - 1167
NICKEL - - - - - 543
NOBLE - - - - - - 1160
OPEN CIRCUIT - - "
OXYGEN - - - - - 543
PALLADIUM - - - - 1160
PASSIVATING - - - 183
PHOTOCATALYTIC - 1160
PHOTOGRAPHY - - - "
SEMICONDUCTOR - - "
STRUCTURE - - - - 1167
SYSTEM - - - - - 543
THERMODYNAMICS - 1167
THICKNESS - - - - 183
TITANIUM DIOXIDE 1160
VARIABLE - - - - 183

METAL ATOMS
ALUMINUM - - - ->1281
ANODE - - - - - - "
ION IMPLANT - - - "
MOBILITY - - - - "
OXIDATION - - - - "
RUTHERFORD - - - "

METAL ELECTRODE
INMERSION - - - -> 618
METHOD - - - - - "
OPEN CIRCUIT - - "
SCRAPE - - - - - "
ZERO CHARGE - - - "

METAL ION
ALUMINUM CHLORIDE> 212
COPPER - - - - - "
FUSED SALT - - - "
IRON - - - - - - "
MELT - - - - - - "
POLAROGRAPHY - - "
SILVER - - - - - "
SODIUM CHLORIDE - "
SYSTEM - - - - - "
VOLTAMMETRY - - - "

METALLIZATION
ALUMINA - - - - -> 107
ARGON - - - - - -> 558
BACKSPUTTERING - "
BOND - - - - - - 107
BONDING - - - - - "
CHEMICAL - - - -> 298
CLOSELY - - - - ->1124
CONTAMINATION - -> 790
COPPER - - - - - 107
DEPOSITION - - - 298
ELECTROLESS - - - 107
FILM - - - - - - 558
FLUORINE - - - - 790
GAP - - - - - - - 1124
GOLD - - - - - ->1076
GOLD REFRACTORY - 790
IMPLANTATION - - 558
ION - - - - - - - "
- - - - - - - 790
MICROWAVE - - - - 1076
MOLTEN ALKALI - - 107
PATTERN - - - - - 1124
RELIABILITY - - - 1076
RETENTION - - - - 790
SELF ALIGNED - - 1124
SEMICONDUCTOR - - 298
SILICON - - - - - 790
SILICON DIOXIDE - 558
SPACED - - - - - 1124
SPUTTERING - - - 558
STABILITY - - - - 1076
SURFACE - - - - - 107
- - - - - - 790
TANTALUM - - - - 1076
THERMAL - - - - - "
TRANSISTOR - - - 790
- - - 1076
TRAPPING - - - - 558
TUNGSTEN - - - - 298
VAPOR - - - - - - "

METALORGANICS
ANTIMONY - - - -> 967
DOPING - - - - - "
EPITAXY - - - - - "
SAPPHIRE - - - - "
SILICON - - - - - "
SOURCE - - - - - "
TRIMETHYLSTIBINE "

METHACRYLATE
CONTRAST - - - ->1669
DEVELOPER - - - - "
ELECTRON BEAM - - "
ELECTRON RESIST - "
FUNCTION - - - - "
LITHOGRAPHY - - - "
PMMA - - - - - - "
POLYMETHYL - - - "
RATE - - - - - - "
SOLUBILITY - - - "

METHOD
ANOMALOUS - - - ->1212
CARRIER MOBILITY "
CATHODOCHROMICS -> 815
DISTRIBUTION - - 1212
GERMANIUM - - - - "
HALL - - - - - - "
INMERSION - - - -> 618
IMPURITY - - - - 1212
INHOMOGENEITY - - "
METAL ELECTRODE - 618
MOBILITY - - - - 1212
OPEN CIRCUIT - - 618
PHOTOCHROMICS - - 815
RADIAL - - - - - 1212
SCRAPE - - - - - 618
SEMICONDUCTOR - - 1212
SODALITE - - - - 815
STRUCTURE CONVER. "
SYNTHESIS - - - - "
VANDERPAUW - - - 1212
ZERO CHARGE - - - 618

METHYL
DEHYDROPYRIDINES >1033
DIMERIZATION - - "
ELECTROCHEMISTRY "
MONONUCLEOTIDE - "
NICOTINAMIDE - - "
PYRIDINIUM - - - "
REDOX - - - - - - "
SPECIES - - - - - "

METHYLNICOTINAMI.
BEHAVIOR - - - -> 345
DIHYDROPYRIDINES "
DIMERIZATION - - "
FREE RADICAL - - "
NICOTINAMIDE - - "
OXIDATION - - - - "
REDOX PATTERN - - "
- - "
REDUCTION - - - - "

MEV
CONTAMINANTS - -> 172
DETECTION - - - - "
SCATTERING - - - "
SENSITIVITY - - - "
SURFACE ANALYSIS "

MICROANALYSIS
BORON - - - - - -> 593
CONTAMINATION - - "
NUCLEAR - - - - - "
OXYGEN - - - - - "
SOLVENTS - - - - "
SURFACE - - - - - "

MICROCIRCUIT
CONTAMINANT - - ->1617
DEPTH PROFILE - - "
ION - - - - - - - "
MASS SPECTROMETRY "
MICROPROBE - - - "
SECONDARY - - - - "
SILVER CHLORIDE - "
SPUTTERING - - - "
SURFACE - - - - - "

MICROPROBE
CHANNELING - - ->1657
CONTAMINANT - - ->1617
DEPTH PROFILE - - "
ELECTRON MICROSC. 1657
GALLIUM - - - - - "
INDIUM - - - - - "
ION - - - - - - - 1617
MASS SPECTROMETRY "
MICROCIRCUIT - - "
PATTERN - - - - - 1657
PHOSPHIDE - - - - "
SCANNING - - - - "
SECONDARY - - - - 1617
SILVER CHLORIDE - "
SPUTTERING - - - "
SURFACE - - - - - "

MICROSCOPE
ANODE DISINTEGR.> 7
ANODE DISSOLUTION "
ANOMALOUS VALENCY "
BERYLLIUM - - - - "
BREAKDOWN - - - -> 692
CHARACTERISTIC - 7
DIODE - - - - - - 692
ELECTRON - - - - 7
- - - - 692
GAAS - - - - - - "
IMPATT - - - - - "
NONAQUEOUS - - - 7
POLARIZATION - - "
PREMATURE - - - - 692
SCANNING - - - - 7
- - - - 692
SCHOTTKY - - - - "
SITES - - - - - - "
SOLUTION - - - - 7

MICROSCOPY
ACIDIC - - - - ->1141
ANODE - - - - - -> 876
- - - - - 1141
BATTERY - - - - ->1541
CESIUM HYDROXIDE > 17
CHLORIDE - - - - 1141
COLD - - - - - - "
CRYSTAL - - - - ->1454
DIFFUSION - - - ->1538
ELECTRON - - - - 876
- - - - 1454
- - - - 1538
- - - - 1941
GRAIN - - - - - - 1141
LEAD - - - - - - 876
LEAD ACID - - - - 1454
- - - - 1541
LEAD CALCIUM - - "
LEAD ELECTRODE - "
LEAD SULFATE - - 1454

PRIMARY TERM / CO-TERM	PAGE NO.
MICROSCOPY (CONTD)	
NEGATIVE	1541
NICKEL	1141
PALLADIUM	1538
PARTICLE SIZE	17
POLARIZATION	1141
POLARIZED	876
POLYMER BONDING	1541
POTASSIUM HYDROX.	17
POTENTIOSTATIC	1141
PRECIPITATION	1454
SCANNING	"
	1541
SILICIDE	1538
SILVER OXIDE	17
SIZE	1141
SOLUTION	1454
STRUCTURE	17
	1454
	1538
VOLTAMMETRY	876
WORK	1141
MICROSEGREGATION	
ALUMINUM	-> 583
CAPACITOR	"
CORROSION	"
ELECTROLYTE	"
ETCHABILITY	"
IRON	"
PRECIPITATION	"
TUNNEL	"
MICROSTRUCTURE	
ALLOY	-> 718
ALUMINUM COPPER	"
CONTRAST	->1202
DIODE	"
GALLIUM NITRIDE	"
HETEROEXPITAXIAL	"
JUNCTION	"
LIGHT EMISSION	"
OXIDATION	718
PROFILE	1202
STRUCTURE	"
TWO PHASE	718
VAPOR DEPOSITION	1202
VOLTAGE	"
MICROWAVE	
GOLD	->1076
METALLIZATION	"
RELIABILITY	"
STABILITY	"
TANTALUM	"
THERMAL	"
TRANSISTOR	"
MICROWAVE DEVICE	
CRYSTAL GROWTH	-> 439
EPITAXY	"
EVALUATION	"
GAAS	"
LIQUID	"
MILD	
ANODE BEHAVIOR	-> 191
DENSITY	"
DEPOSITION	->1592
DISSOLUTION	"
ELECTROCHEMICAL	191
ELECTRODE	1592
HEMISPHERICAL	"
HIGH CURRENT	191
IRON OXIDE	1592
POLISHING	191
RING	1592
ROTATING	"
SODIUM CHLORATE	191
STEEL	"
	1592
SULFATE SOLUTION	"
MINOR	
COMPONENT	->1000
CONVECTIVE	"
CORROSION	"
CRACK	"
DIFFUSION	"
MASS TRANSFER	"
MOLTEN SALT	"
PROPAGATING	"
MINORITY	
BREAKDOWN	->1229
CAPACITATOR	-> 849
CAPACITOR	->1219
MINORITY (CONTD)	
CARRIER	849
	-> 973
	1219
	1229
DEEP	1219
DEPLETION	"
DIELECTRIC	1229
DIFFUSION	973
	1219
ETCHING	1229
GENERATION	849
	1229
INPERFECTION	"
LENGTH	1219
LIFETIME	"
MOS	849
	1219
PHOTOVOLTAGE	973
SILICON	849
	973
	1219
	1229
SOLAR CELL	973
STEADY STATE	1219
SURFACE	973
WAFER	1229
MISCIBILITY GAP	
ALUMINUM	->1662
ANTIMONIDE	"
ARSENIDE	"
FREE ENERGY	-> 932
GALLIUM	1662
GIBBS	932
GROUP II-VI	1662
GROUP III-V	"
INDIUM	"
LATTICE	"
LATTICE PARAMETER	932
MODEL	"
PARAMETER	1662
PHOSPHIDE	"
PSEUDO BINARY	932
PSEUDOBINARY	1662
QUASIREGULAR	932
SEMICONDUCTOR	1662
SOLID SOLUTION	"
MIXED	
CATALYST	-> 738
DIELECTRIC	"
ELECTRON MICROSC.	"
PALLADIUM CHLORI.	"
PLATING	"
STANNOUS CHLORIDE	"
SUBSTRATE	"
MIXED POTENTIAL	
CONSTANT	-> 887
COPPER	"
CORROSION	"
ELECTROLESS	"
PARTIAL PROCESS	"
PLATING	"
RATE	"
SPECIFIC	"
STANDARD	"
MIXTURE	
ACETONE	->1584
ACTIVITY	-> 354
ALKALI CHLORIDE	-> 991
ARGON OXYGEN	354
CERIUM CHLORIDE	991
CONSTANT	1584
CONTROL	354
COULOMETRY	"
ELECTRODE	"
EMF	991
FORMATION	1584
MEASUREMENT	991
MOLTEN SALT	"
NUMBERS	"
OXYGEN	354
PLATINUM	"
POTENTIOSTAT	"
PRODUCT	1584
SILVER HALIDES	"
SOLUBILITY	"
TITRATION	354
TRANSFERENCE	991
WATER	1584
ZIRCONIA	354
MOBILE CHARGE	
DEVICE PROCESSING	> 724
MOBILE CHARGE (CONTD)	
GETTERING	724
GLASS	"
PHOSPHOSILICATE	"
REMOVAL	"
SILICON DIOXIDE	"
SODIUM	"
MOBILITY	
ALUMINUM	->1281
ANODE	"
ANOMALOUS	->1212
BARRIER	->1066
CAPACITANCE	"
CARRIER MOBILITY	1212
DISTRIBUTION	"
EPITAXY	1066
GAAS	"
GERMANIUM	1212
HALL	"
HALL EFFECT	1066
IMPURITY	1212
INHOMOGENEITY	"
ION IMPLANT	1281
LAYER	1066
MEASUREMENT	"
METAL ATOMS	1281
METHOD	1212
OXIDATION	1281
PHOTOLUMINESCENCE	1066
RADIAL	1212
RUTHERFORD	1281
SCHOTTKY	1066
SEMICONDUCTOR	1212
SPECTRA	1066
VANDERPAUW	1212
MODEL	
FREE ENERGY	-> 932
GIBBS	"
LATTICE PARAMETER	"
MISCIBILITY GAP	"
PSEUDO BINARY	"
QUASIREGULAR	"
MODEL CELL	
CATHODE	-> 867
COEFFICIENT	"
CONVECTION	"
ELECTROWINNING	"
FORCED	"
MASS	"
NATURAL	"
TRANSFER	"
MODIFICATION	
BORIDES	-> 846
BORON	"
CHEMICAL	"
ELEMENTAL	"
NONMETAL	"
STRUCTURE	"
TETRAGONAL	"
VAPOR DEPOSITION	"
MODULATE	
CORONA CHARGE	-> 452
FIELD EFFECT	"
INTERFACE	"
PHOTOLUMINESCENCE	"
SEMICONDUCTOR	"
TRAP	"
ZINC OXIDE	"
MODULATION	
CURRENT POTENTIAL	>1558
DISK	"
ELECTRODE	"
MASS TRANSFER	"
ROTATING	"
SINUSOIDAL	"
MOISTNESS	
AERATION	-> 183
CORROSION	"
DIFFERENTIAL	"
FILM	"
METAL	"
PASSIVATING	"
THICKNESS	"
VARIABLE	"
MOISTURE	
ABSORPTION	-> 434
ACTIVATION	"
ANALYSIS	"
CONCENTRATION	"
MOISTURE (CONTD)	
INFRARED	434
INTERACTION	"
PHOSPHORUS	"
PSG FILM	"
RESISTANCE	"
WATER	"
MOLECULE	
BEAM	-> 899
DEPOSITION	"
PYROLYSIS	"
SAMPLE	"
SILANE	"
SILICON	"
SPECTROMETRY	"
MOLTEN	
ALUMINUM	-> 773
	-> 983
ALUMINUM CHLORIDE	"
ANODIZATION	"
CHLOROALUMINATE	773
CHRONOPOTENTIOME.	"
ELECTRODE	983
FUSED	"
HALIDES	773
ION	983
MELT	773
OXIDATION	"
SALT	983
SODIUM CHLORIDE	"
SUBVALENT	"
MOLTEN ALKALI	
ALUMINA	-> 107
BOND	"
BONDING	"
COPPER	"
ELECTROLESS	"
METALLIZATION	"
SURFACE	"
MOLTEN FLUORIDE	
LINEAR SWEEP	-> 86
LITHIUM FLUORIDE	"
POTASSIUM	"
SODIUM FLUORIDE	"
THORIUM	"
URANIUM	"
VOLTAMMETRY	"
MOLTEN HALIDES	
BERYLLIUM	->1429
CHRONOPOTENTIOME.	"
DEPENDENCE	"
DEPLETION	"
ELECTROMIGRATION	"
FLOURIDES	"
GLASSES	"
LITHIUM	"
TEMPERATURE	"
MOLTEN MIX	
CADMIUM CHLORIDE	> 959
EMF	"
FREE ENERGY	"
GIBBS	"
ION MOBILITY	"
	"
LITHIUM CHLORIDE	"
TRANSFERENCE	"
MOLTEN SALT	
ALKALI CHLORIDE	-> 991
ALLOY	-> 247
BERYLLIUM	"
BINARY	-> 500
BISMUTH	247
CALCULATION	->1258
CERIUM CHLORIDE	991
CESIUM CHLORIDE	-> 104
COMPONENT	->1000
CONVECTIVE	"
CORROSION	"
COULOMBIC	500
CRACK	1000
DIFFUSION	"
ELECTRODE	247
EMF	991
FLUORIDE	247
FORMATION CELL	104
HIGH TEMPERATURE	> 665
INTERACTION	500
IRON	665
IRON PYRITE	"
IRON SULFIDE	"

PRIMARY TERM / CO-TERM — PAGE NO.

MOLTEN SALT (CONTD)
LIQUIDUS TEMPERA. 1258
LITHIUM - - - - - 247
- - - - - 685
LITHIUM CHLORIDE 500
MASS TRANSFER - - 1080
MEASUREMENT - - - 991
MINOR - - - - - - 1000
MIXTURE - - - - - 991
NICKEL CHLORIDE - 104
NUMBERS - - - - - 991
PHASE DIAGRAM - - 1258
POTASSIUM CHLOR. 500
PROPAGATING - - - 1000
SECONDARY CELL - 685
SULFIDE - - - - - "
SURFACE TENSION - 500
TRANSFERENCE - - 991

MOLYBDENUM
BATTERY - - - - -> 656
BEHAVIOR - - - - "
- - - ->1460
CARBONATE - - - - 656
CATHODE - - - - - "
CHROMIUM - - - ->1192
COPPER - - - - - 656
CORROSION - - - - 1192
DISCHARGE - - - - 1460
ELECTROCATALYST ->1125
ELECTROLYTE - - - 1460
FORMALDEHYDE - - - 1125
IRON - - - - - - 1192
KINETICS - - - - 1125
LITHIUM CELL - - 1460
LITHIUM CELLS - - 656
MANGANESE - - - - "
MECHANISM - - - - 1125
NONAQUEOUS - - - 1460
OXIDATION - - - - 1125
PITTING - - - - - 1192
PROPYLENE - - - - 656
REACTION - - - - 1125
RESISTANCE - - - 1192
SOLUTION - - - - 1460
STAINLESS STEEL - 1192
SULFUR - - - - - 1125
TEMPERATURE - - - 1192
TETRAHYDROFURAN - 656

MONOCALCIUM
CALCIUM - - - - -> 534
DICALCIUM - - - - "
ELECTROCHEMISTRY "
GALVANIC CELL - - "
STABILITY - - - - "
STANNATE - - - - "
VAPORIZATION - - "

MONOHYDRATE
ADSORPTION - - -> 987
ANION - - - - - - "
ELECTROLYTE - - - "
HYDROCARBON - - - "
OXIDATION - - - - "
PROPANE - - - - - "
TRIFLUOROMETHANE. "

MONOLAYER
ACCELERATE - - -> 778
ADSORPTION - - ->1167
CORROSION - - - - 778
CREVICE - - - - - "
ELECTROCRYSTALLI. 1167
ELECTRODE - - - - "
EUTECTIC - - - - 778
FILM - - - - - - 1167
FORMATION - - - - 778
ION - - - - - - - "
- - - - - - - 1167
KINETICS - - - - "
LITHIUM CHLORIDE 778
METAL - - - - - - 1167
NICKEL - - - - - 778
PITTING - - - - - "
POTASSIUM CHLORI. "
REDUCTION - - - - "
SILVER - - - - - "
STRUCTURE - - - - 1167
THERMODYNAMICS - "

MONOLITHIC
BIPOLAR - - - - ->1119
COMPLEMENTARY - - "
DEVICE - - - - - "
INTEGRATION - - - "
ISOLATED - - - - "

MONOLITHIC (CONTD)
MOS - - - - - - - 1119
SEMICONDUCTOR - - "
TRANSISTOR - - - "

MONONUCLEOTIDE
DEHYDROPYRIDINES >1033
DIMERIZATION - - "
ELECTROCHEMISTRY "
METHYL - - - - - "
NICOTINAMIDE - - "
PYRIDINIUM - - - "
REDOX - - - - - - "
SPECIES - - - - - "

MONOSELENIDE
CRYSTAL - - - - ->1674
EXISTENCE - - - - "
HEAT - - - - - - "
INDIUM - - - - - "
MEASUREMENT - - - "
PHASE TRANSITION "
SEMICONDUCTOR - - "
SPECIFIC - - - - "
STRUCTURE - - - - "
XRAY - - - - - - "

MORPHOLOGY
ADDITIVE - - - -> 463
ANODE OXIDATION -> 757
BARIUM SULFATE - 463
CHARGING - - - - 757
CORROSION - - - ->1190
CRACK - - - - - - "
CRYSTAL GROWTH ->1516
DIMETHYLANILINE - 757
DISCHARGING - - - "
DOPING - - - - - 1516
ELECTRODE - - - - 463
- - - - 757
ELECTROLUMINESCE. 1516
EPITAXY - - - - - "
FRACTOGRAPHY - - 1190
GAS PHASE - - - - 1516
LEAD - - - - - - 463
LEAD SULFATE - - "
LIGNIN - - - - - "
MECHANISM - - - - "
REACTION - - - - "
SILVER - - - - - 757
SILVER CHLORIDE - "
STAINLESS STEEL - 1190
STOICHIOMETRY - - 1516
STRESS - - - - - 1190
STRIATION - - - - "
SULFURIC ACID - - "
SURFACE - - - - - 757
TRANSGRANULAR - - 1190
VAPOR PHASE - - - 1516

MOS
BIPOLAR - - - - ->1119
CAPACITATOR - - -> 849
CAPACITOR - - - ->1219
CARRIER - - - - - 849
- - - - - 1219
CHEMICAL - - - ->1103
COMPLEMENTARY - - 1119
DEEP - - - - - - 1219
DEPLETION - - - - "
DEVICE - - - - - 1119
DIFFUSION - - - - 1219
ELECTRON MICROSC.> 307
FET - - - - - - - 1103
FLOW - - - - - - 307
GENERATION - - - 849
GLASS - - - - - - 307
INTEGRATED CIRCU. "
INTEGRATION - - - 1119
ISOLATED - - - - "
LENGTH - - - - - 1219
LIFETIME - - - - "
MINORITY - - - - 849
- - - - 1219
MONOLITHIC - - - 1119
SCANNING - - - - 307
SEMICONDUCTOR - - 1119
SILICON - - - - - 849
- - - - 1219
SILICON DIOXIDE - 1103
STEADY STATE - - 1219
THIN FILM - - - - 1103
TRANSISTOR - - - 1119
VAPOR DEPOSITION 1103

MOS STRUCTURE
HYDROGEN - - - -> 784

MOS STRUCTURE (CONTD)
IMPLANTATION - - 784
INTERFACE - - - - "
OXYGEN - - - - - "
SILICON - - - - - "
SILICON DIOXIDE - "
SURFACE STATE - - "

MOSS BAUER
BATTERY CELL - -> 1
BETA ALUMINA - - "
CATHODE - - - - - "
GALVANIC CELL - - "
IRON DOPED - - - "
IRON SPINEL - - - "
SPECTROSCOPY - - "

MUTUAL
CHLORATE CELL - -> 70
CHLORINE - - - - "
CURRENT - - - - - "
CURRENT DENSITY - "
EFFECT - - - - - "
EFFICIENCY - - - "
HYDRODYNAMIC - - "
PH - - - - - - - "
TEMPERATURE - - - "

NATIVE OXIDE
ANODE OXIDATION ->1665
AQUEOUS - - - - - "
COMPOUND - - - - "
GALLIUM PHOSPHIDE "
HYDROGEN PEROXIDE "
SEMICONDUCTORS - "

NATURAL
CATHODE - - - - -> 867
COEFFICIENT - - - "
CONVECTION - - - "
ELECTROWINNING - "
FORCED - - - - - "
MASS - - - - - - "
MODEL CELL - - - "
TRANSFER - - - - "

NEGATIVE
BATTERY - - - - ->1541
ELECTRON - - - - "
LEAD ACID - - - - "
LEAD CALCIUM - - "
LEAD ELECTRODE - "
MICROSCOPY - - - "
POLYMER BONDING - "
SCANNING - - - - "

NEGATIVE PLATE
BATTERY - - - - -> 854
FORMATION - - - - "
LEAD ACID - - - - "
LEAD ELECTRODE - "

NEMATIC
CHLOROSTILBENES ->1667
IMAGING - - - - - "
IRRADIATION - - - "
LIQUID CRYSTAL - "
STILBENES - - - - "
ULTRAVIOLET - - - "

NEON
CONTROL - - - - ->1233
CVD - - - - - - - "
DEPOSITION - - - "
FILM - - - - - - "
FILM THICKNESS - "
HELIUM - - - - - "
LASER - - - - - - "
NITRIDE - - - - - "
SILICON - - - - - "
SILICON DIOXIDE - "

NETWORK
CRISTOBALITE - ->1081
CRYSTALLIZATION - "
DIFFUSION - - - - "
FILM - - - - - - "
INTERFACE - - - - "
PHOSPHORUS - - - "
SILICON DIOXIDE - "

NEUTRAL
ANODE OXIDATION ->1152
FILM - - - - - - "
NICKEL - - - - - "
NICKEL OXIDE - - "
PASSIVITY - - - - "

NEUTRAL (CONTD)
SULFATE - - - - - 1152

NEUTRAL SOLUTION
ANODE - - - - - ->1276
BENZOTRIAZOLE - - "
CHLORIDE SOLUTION "
CORROSION - - - - "
ELECTRODISSOLUTI. "
INHIBITION - - - "
IRON - - - - - - "

NEUTRON
ACTIVATION - - -> 681
CONTAMINATION - - "
DEFORMATION - - - "
DEPOSIT - - - - - "
DICHLOROSILANE - - "
OXYGEN - - - - - "
POLYCRYSTALLINE - "
SILICON FILM - - "
VAPOR - - - - - - "

NEW
ALUMINATES - - ->1623
GALLATE - - - - - "
HEXAGONAL - - - - "
HOST LATTICE - - "
LAMP - - - - - - "
PHOSPHORS - - - - "
RARE EARTH - - - "

NEW GENERATION
DELUXE - - - - ->1627
FLUORESCENT - - - "
HIGH EFFICACY - - "
LAMPS - - - - - - "

NICKEL
ACCELERATE - - -> 778
ACID BATH - - - ->1023
ACIDIC - - - - ->1141
ACTIVITY - - - -> 543
ALLOY - - - - - -> 800
- - - - - ->1051
- - - - - ->1137
ALUMINIDE - - - - 1051
ALUMINUM - - - - 800
AMINE - - - - - - 1023
AMMONIUM - - - -> 977
ANODE - - - - - - 1141
ANODE OXIDATION ->1152
BATTERY - - - - -> 175
BORANE - - - - - 1023
BROMIDE - - - - - 977
CADMIUM - - - - - 175
CAPACITY - - - -> 512
CELL - - - - - - 175
CHARGE ACCEPTANCE "
CHLORIDE - - - - 1141
CHROMIUM - - - - 543
COATING - - - - - 800
- - - - - 1051
COBALT - - - - - 1023
COLD - - - - - - 1141
COMPUTER - - - - 175
CONDUCTANCE - - - 977
CONTROLLED - - - 175
COPPER - - - - - 1137
CORROSION - - - - 778
CREVICE - - - - - "
CURVE - - - - - - 1137
DEGRADATION - - - 800
DEPLETION - - - - "
DEPOSITION - - - 1023
DIFFUSION - - - - 800
- - - - 1051
DIMETHYLFORMAMIDE 977
DOUBLE LAYER - - 512
ELECTRODE - - - - "
ELECTROLESS - - - 1023
ELECTROLYTE - - - 977
EUTECTIC - - - - 778
FILM - - - - - - 1152
FORMATION - - - - 778
GRAIN - - - - - - 1141
HYPOPHOSPHITE - - 1023
ION - - - - - - - 778
ISOTHIOCYANATE - 977
KINETICS - - - - 1051
LITHIUM CHLORIDE 778
MERCURY - - - - - 175
METAL - - - - - - 543
MICROSCOPY - - - 1141
MONOLAYER - - - - 778
NEUTRAL - - - - - 1152
NICKEL OXIDE - - "

PRIMARY TERM / CO-TERM	PAGE NO.
NICKEL (CONTD)	
NONAQUEOUS	977
OXIDATION	800
OXYGEN	543
PACK	1051
PASSIVITY	1137
	1152
PITTING	778
	1137
PLATING	1023
POLARIZATION	1137
	1141
POROUS	512
POTASSIUM	977
POTASSIUM CHLORI.	778
POTASSIUM HYDROX.	512
POTENTIAL	1137
POTENTIOSTATIC	"
	1141
PROTECTIVE	1051
PULSE CHARGING	175
REDUCTION	778
SILVER	"
SIZE	1141
SODIUM CHLORIDE	1137
SOLUTION	977
SPALLING	800
SULFATE	1152
SUPERALLOY	800
SWEEP	512
SYSTEM	543
TETRABUTYL	977
THERMODYNAMICS	1051
TRIANGULAR	512
VISCOSITY	977
VOLTAGE	512
WORK	1141
NICKEL ALLOY	
AIR ->	118
OXIDATION	"
WATER VAPOR	"
NICKEL BORIDE	
ANODE	->1264
CATALYST	"
FUEL CELL	"
HYDRAZINE	"
SUBSTRATE	"
NICKEL CHLORIDE	
CESIUM CHLORIDE ->	104
FORMATION CELL	"
MOLTEN SALT	"
NICKEL IRON	
ALLOY ->	386
DIFFUSION MODEL	"
NICKEL OXIDE	"
OXIDATION	"
NICKEL OXIDE	
ALLOY ->	386
ANODE OXIDATION	->1152
BEHAVIOR ->	318
DIFFUSION MODEL	386
FILM	1152
NEUTRAL	"
NICKEL	"
NICKEL IRON	386
OXIDATION	"
PASSIVITY	1152
REDOX COUPLE	318
SEMICONDUCTOR	"
SULFATE	1152
NICOTINAMIDE	
BEHAVIOR ->	345
DEHYDROPYRIDINES	>1033
DIHYDROPYRIDINES	345
DIMERIZATION	"
	1033
ELECTROCHEMISTRY	"
FREE RADICAL	345
METHYL	1033
METHYLNICOTINAMI.	345
MONONUCLEOTIDE	1033
OXIDATION	345
PYRIDINIUM	1033
REDOX	"
REDOX PATTERN	345
	"
REDUCTION	"
SPECIES	1033
NIOBIUM	
ELLIPSOMETRY ->	805
NIOBIUM (CONTD)	
OXIDATION	805
PLASMA	"
REFRACTIVE INDEX	"
TANTALUM	"
NITRATE	
ALUMINUM	->1271
ANODE	"
CHLORIDE	"
PITTING	"
SOLUTION	"
STRAINING	"
NITRIDE	
ANOMALOUS	->1677
BANDGAP	->1673
BORON	1677
CHARGE ->	907
CHEMICAL	1673
COMPOUND	"
CONTROL	->1233
CRYSTAL	1673
CVD	1233
DENSITY	1677
DEPOSITION	1233
DIELECTRIC	907
	1677
DIFFUSION	"
EFFECT	"
ELECTRETS	"
FILM	1233
FILM THICKNESS	"
GATE	907
GERMANIUM	1673
HELIUM	1233
INSERT	1677
INSULATOR	907
LASER	1233
NEON	"
OXIDE	907
PLANAR	1677
PROPERTIES	1673
SILICON	907
	1233
	1677
SILICON DIOXIDE	1233
STABILITY	907
STRUCTURE	1673
SURFACE CHARGE	1677
SYNTHESIS	1673
TERNARY	"
VAPOR DEPOSITION	"
ZINC	"
NITRITE IONS	
ACETONITRILE	->1451
CARBON	"
ELECTRO OXIDATION	"
GOLD	"
PLATINUM	"
NITROGEN	
ACID	->1609
AMMONIA	-> 230
	1609
ANALYZER	-> 689
ARGON	->1372
ATMOSPHERE	-> 943
COEFFICIENT	230
CONTROL	1372
DEFECT	689
DIFFUSING	1372
EQUILIBRIA	"
ETCHING	"
EVOLUTION	230
	1609
EXCHANGE CURRENT	230
HELIUM	689
	1372
HEXAFLUORIDE	"
HYDROGEN	230
	1609
LANGMUIR SHEATH	1372
LASER	689
LIQUID	230
	1609
LOW PRESSURE	943
LOW TEMPERATURE	"
MAGNESIUM	"
OVERVOLTAGE	230
PENTA FLUORIDE	1372
RATE	"
REACTION	"
	1609
SILICON	689
SLICE	"
NITROGEN (CONTD)	
SURFACE	689
TAFEL SLOPE	230
THERMAL NITRIDAT.	943
TRANSFER	230
TUNGSTEN	1372
NITROGEN DIOXIDE	
CHALCOGENIDE	->1575
GAS SENSOR	"
GLASS ELECTRODE	"
NITROGEN DOPING	
AMMONIA ->	962
BEHAVIOR	"
DIODES	"
EMITING	"
EPITAXY	"
GAP	"
IMPURITY	"
LIGHT	"
LIQUID PHASE	"
SOURCE	"
NOBEL GASES	
ANODE OXIDATION ->	865
BEHAVIOR	"
ION IMPLANT	"
MARKER	"
TANTALUM	"
NOBLE	
DEPOSITION	->1160
METAL	"
OPEN CIRCUIT	"
PALLADIUM	"
PHOTOCATALYTIC	"
PHOTOGRAPHY	"
SEMICONDUCTOR	"
TITANIUM DIOXIDE	"
NONAQUEOUS	
AMMONIUM ->	977
ANODE	->1382
ANODE DISINTEGRA.	>1604
ANODE DISINTERGR.	> 7
ANODE DISSOLUTION	"
ANOMALOUS VALENCY	"
BATTERY ->	315
BEHAVIOR	->1308
	->1460
BERYLLIUM	7
	1604
BROMIDE	977
CARBONATE	315
CHARACTERISTIC	7
CHARACTERISTICS	1604
CHEMILUMINESCENCE	>1178
CONDUCTANCE	977
DIMETHYLFORMAMIDE	"
DISCHARGE	1460
DOUBLE LAYER	1308
ELECTROANALYSIS	1178
ELECTROGENERATE	"
ELECTROLYTE	977
	1382
	1460
ELECTRON	7
ENERGY DEFICIENT	1178
FLUOROGRAPHITE	1308
GAAS	1382
GAASP	"
GALVANIC CELL	315
ISOTHIOCYANATE	977
LITHIUM ANODE	315
LITHIUM BROMINE	"
LITHIUM CELL	1460
LUMINESCENCE	1178
MICROSCOPE	7
MOLYBDENUM	1460
NICKEL	977
OXIDATION	1382
POLARIZATION	7
	1604
POROUS ELECTRODE	1308
POTASSIUM	977
POTENTIAL	1308
PROPYLENE	315
SCANNING	7
SECONDARY	315
SOLUTION	7
	977
	1460
	1604
SOLVENT	315
	1178
TETRABUTYL	977
NONAQUEOUS (CONTD)	
VISCOSITY	977
VOLTAMMETRY	1178
NONMETAL	
BORIDES ->	846
BORON	"
CHEMICAL	"
ELEMENTAL	"
MODIFICATION	"
STRUCTURE	"
TETRAGONAL	"
VAPOR DEPOSITION	"
NONSTOICHIOMETRIC	
CERIUM DIOXIDE ->	126
	>1198
COMPOSITION	126
CONDUCTIVITY	"
	1198
DEPENDENCE	126
	1198
ELECTRON MOBILITY	126
IONIC	1198
NUMBER	"
OXYGEN	"
PRESSURE	"
TEMPERATURE	126
	1198
TRANSFERENCE	"
NORMAL	
ALCOHOLS ->	1048
CELL	"
ELECTROCHEMISTRY	"
ELECTRODE	"
HEXANOL	"
HYDROGEN	"
THALLIUM	"
NPN	
ANODE ->	280
BIPOLAR	"
CRYSTAL DEFECT	"
DECORATION	"
JUNCTION	"
LEAKAGE	"
TRANSISTOR	"
NUCLEAR	
BORON ->	593
CONTAMINATION	"
MICROANALYSIS	"
OXYGEN	"
SOLVENTS	"
SURFACE	"
NUCLEATION	
ALUMINUM ->	1322
BAYERITE	"
COPPER ->	202
ELECTRODEPOSIT	"
EVAPORATION	"
GROWTH	1322
HYDROLYSIS	"
OXIDE FILM	"
PSEUDOBOEHMITE	"
SINGLE CRYSTAL	202
THIN FILM	"
NUMBER	
CARBONATE ->	83
CERIUM DIOXIDE	->1198
CONDUCTIVITY	"
DEPENDENCE	"
EMF	83
IONIC	1198
LITHIUM ION	83
MEASUREMENT	"
NONSTOICHIOMETRIC	1198
OXYGEN	"
PRESSURE	"
PROPYLENE	83
SOLUTION	"
TEMPERATURE	1198
TRANSFERENCE	83
	1198
NUMBERS	
ALKALI CHLORIDE ->	991
CERIUM CHLORIDE	"
EMF	"
MEASUREMENT	"
MIXTURE	"
MOLTEN SALT	"
TRANSFERENCE	"

PRIMARY TERM — CO-TERM — PAGE NO.

NUMERICAL
CALCULATION - - -> 588
IMPURITY - - - - "
OXIDATION - - - - "
REDISTRIBUTION - "
SEMICONDUCTOR - - "
SILICON - - - - - "
SILICON DIOXIDE - "
THERMAL - - - - - "

OHM
CRYSTAL GROWTH ->1237
DIFFUSION - - - - "
DOPED - - - - - - "
EPITAXY - - - - - "
GAAS - - - - - - "
GERMANIUM - - - - "
SEMICONDUCTOR - - "
ZINC - - - - - - "

OHMIC COUPLING
CIRCUIT - - - - ->1439
ELECTRODE - - - - "
EQUIVALENT - - - "
PSEUDOCOLLECTION "
RESISTANCE - - - "
RING DISK - - - - "

OPACITY
ALUMINUM - - - -> 268
ANODE FILM - - - "
CHLORIDE - - - - "
ELECTRON - - - - "
GROWTH - - - - - "
PITTING - - - - - "

OPEN CIRCUIT
ANODE - - - - - ->1146
CHROMATE - - - - "
CORROSION - - - - "
DEPOSITION - - ->1160
ELLIPSOMETRY - - 1146
FILM - - - - - - "
IMMERSION - - - -> 618
INHIBITOR - - - - 1146
IRON - - - - - - "
METAL - - - - - - 1160
METAL ELECTRODE - 618
METHOD - - - - - "
NOBLE - - - - - - 1160
PALLADIUM - - - - "
PASSIVITY - - - - 1146
PHOTOCATALYTIC - 1160
PHOTOGRAPHY - - - "
POTENTIAL - - - - 1146
SCRAPE - - - - - 618
SEMICONDUCTOR - - 1160
TITANIUM DIOXIDE "
ZERO CHARGE - - - 618

OPTIC
DEPOSITION - - ->1610
ELECTRODE - - - - "
GOLD - - - - - - "
LEAD - - - - - - "
SINGLE CRYSTAL - "
UNDER POTENTIAL - "

OPTICAL
ABSORPTION - - -> 586
ALUMINUM - - - -> 829
COMPOUND - - - - 586
CONDUCTIVITY - - "
COPPER - - - - - 829
DOPING - - - - - "
ELECTRIC - - - - 586
ELECTRICAL - - - 829
FORMATION - - - - 586
ION IMPLANTATION "
PROPERTIES - - - 829
SILICON CARBIDE - 586
SULFIDE - - - - - 829

OPTICAL INTERFER.
ABSORPTION - - ->1496
CRYSTAL QUALITY - "
KRAMERS KRONIG - "
REFRACTIVE INDEX "
SILICON FILM - - "
THIN FILM - - - - "

OPTICAL SPECTRA
ALKALINE - - - ->1475
CRYSTAL - - - - - "
DIVALENT - - - - "
EARTH - - - - - - "
EUROPIUM - - - - "

PRIMARY TERM — CO-TERM — PAGE NO.

OPTICAL SPECTRA (CONTD)
LUMINESCENCE - - 1475
STRUCTURE - - - - "
SULFATES - - - - "

OPTIMIZED
COLOR RENDITION -> 407
DISTRIBUTION - - "
LAMPS - - - - - - "
MERCURY VAPOR - - "
PHOSPHORS - - - - "
POWER - - - - - - "
SPECTRAL - - - - "

ORGANIC
AGENT - - - - - -> 779
CHROME COATING -> 29
COEFFICIENT - - - 779
COPPER FLUOROBOR. "
COPPER SULFATE - "
DELAMINATION - - 29
DIFFUSION - - - - 779
ELECTROLYTE - - - "
KINETIC - - - - - "
LACQUER FILM - - 29
PARAMETER - - - - 779
STEEL - - - - - - 29
UNDERCUTTING - - "

ORGANIC ACID
ELECTROLESS - - -> 67
FORMING - - - - - "
PHOTOLYSIS - - - "
PLATING - - - - - "
PRINTED CIRCUIT - "
SILVER GLUTAMATE "
SILVER SALT - - - "

ORIENTATION
EFFECT - - - - ->1613
OXYGEN - - - - - "
RATE CONSTANT - - "
SILICON - - - - - "
THERMAL OXIDATION "
TRACE - - - - - - "
WATER - - - - - - "

ORTHOSILICATE
ALUMINUM - - - -> 303
HYDROTHERMAL - - "
LITHIUM - - - - - "
LUMINESCENCE - - "
MANGANOUS - - - - "
PHOSPHOR - - - - "

OSCILLATORY
CRYSTAL GROWTH -> 380
CZOCHRALSKI - - - "
DOPED GERMANIUM - "
INSTABILITY - - - "
SUPERCOOLING - - "

OVERPOTENTIAL
CRITICAL - - - -> 329
DENDRITE - - - - "
GROWTH - - - - - "
INDUCTION TIME - "
YIELD - - - - - - "
ZINC - - - - - - "

OVERVOLTAGE
AMMONIA - - - - -> 230
COEFFICIENT - - - "
EVOLUTION - - - - "
EXCHANGE CURRENT "
HYDROGEN - - - - "
LIQUID - - - - - "
NITROGEN - - - - "
TAFEL SLOPE - - - "
TRANSFER - - - - "

OXIDATION
ACETONITRILE - -> 780
ACTIVATION - - - "
ADSORPTION - - -> 987
AIR - - - - - - -> 118
ALLOY - - - - - -> 386
- - - - - -> 718
- - - - - -> 800
ALUMINUM - - - -> 773
- - - - 800
- - - ->1281
- - - ->1509
ALUMINUM COPPER - 718
AMINES - - - - -> 378
ANION - - - - - - 987
ANODE - - - - - - 1281

PRIMARY TERM — CO-TERM — PAGE NO.

OXIDATION (CONTD)
ANODE - - - - - ->1382
BEHAVIOR - - - -> 345
BORON - - - - - -> 705
BREAKDOWN - - - -> 809
CALCULATION - - -> 588
CARBON FILM - - ->1551
CARBON MONOXIDE ->1315
CATION RADICAL - 370
CHLOROALUMINATE - 773
CHROMIUM - - - -> 952
CHROMIUM OXIDE -> 945
- 952
CHRONOPOTENTIOME. 773
COATING - - - - - 800
CRYSTALLIZATION - 1509
DEGRADATION - - - 800
DEPLETION - - - - "
DIELECTRIC - - - 809
DIFFUSION - - - - 705
- - - - 800
- - - - 1315
DIFFUSION MODEL - 386
DIHYDROPYRIDINES 345
DIMERIZATION - - "
DOPING - - - - - 1509
ELECTROCATALYST - 780
->1125
ELECTRODE - - - - 1315
ELECTROLYTE - - - 987
- - - 1382
ELLIPSOMETRY - -> 263
- -> 805
EPITAXY - - - - ->1534
FILM - - - - - - 809
FORMALDEHYDE - - 1125
FORMIC ACID - - - 780
FREE RADICAL - - 345
GAAS - - - - - -> 113
- - - - - - 1382
GAASP - - - - - - "
GALLIUM - - - - - 1509
GAS SENSOR - - - 1315
GASEOUS - - - - - 1551
HALIDES - - - - - 773
HALOGEN - - - - - 809
HOFMANN LOEFFLER 378
HYDROCARBON - - - 987
HYDROGEN CHLORIDE 889
IMPURITY - - - - 588
- - - ->1107
ION IMPLANT - - - 705
- - - 1281
IRON - - - - - - 1534
- - - - - - 1551
IRON OXIDE - - - 1534
KINETICS - - - - 1125
MASKING - - - - - 1509
MECHANISM - - - - 1125
MELT - - - - - - 773
MERCURY - - - - - 780
METAL ATOMS - - - 1281
METHYLNICOTINAMI. 345
MICROSTRUCTURE - 718
MOBILITY - - - - 1281
MOLTEN - - - - - 773
MOLYBDENUM - - - 1125
MONOHYDRATE - - - 987
NICKEL - - - - - 800
NICKEL ALLOY - - 118
NICKEL IRON - - - 386
NICKEL OXIDE - - "
NICOTINAMIDE - - 345
NIOBIUM - - - - - 805
NONAQUEOUS - - - 1382
NUMERICAL - - - - 588
OXIDE FILM - - - 113
OXYGEN - - - - - 945
OXYGEN ATOMS - - 952
OXYGEN PLASMA - - 113
PASSIVATION - - - 1509
PHOSPHORUS - - - "
PLANAR JUNCTION - "
PLASMA - - - - - 263
- - - - - 805
PLATINUM - - - - 1315
PRETREATMENT - - 1551
PROPANE - - - - - 987
REACTION - - - - 1125
REDISTRIBUTION - 588
REDOX PATTERN - - 345
- - "
REDUCTION - - - - "
REFRACTIVE INDEX 805
RELIABILITY - - - 809
RF HEATING - - - 1107
RUTHERFORD - - - 1281

PRIMARY TERM — CO-TERM — PAGE NO.

OXIDATION (CONTD)
SECONDARY - - - - 376
SEGREGATION - - - 705
- - - 1509
SEMICONDUCTOR - - 588
SILICON - - - - - "
- - - - - 1107
SILICON DIOXIDE - 588
- 809
SINGLE CRYSTAL - 1534
SPALLING - - - - 800
SPECTROSCOPY - -> 673
SULFUR - - - - - 1125
SUPERALLOY - - - 800
SURFACE - - - - - 673
TANTALUM - - - - 263
- - - - 805
THERMAL - - - - - 588
- - - - - 1107
THIN FILM - - - - 1551
TRIFLUOROMETHANE. 987
TWO PHASE - - - - 718
VAPORIZATION - - 945
- - 952
WATER VAPOR - - - 118
X RAY - - - - - - 673

OXIDE
ALLOY - - - - - -> 538
ANODE - - - - - -> 550
BACKSCATTERING - "
CHARGE - - - - -> 907
COBALT IRON - - - 538
COBALTOUS IRON - "
CONCENTRATION - -> 419
DEVICE - - - - - "
DIELECTRIC - - - 907
DIFFUSION - - - - 538
FET - - - - - - - 419
GATE - - - - - - "
- - - - - - 907
GLASS - - - - - - 419
GROWTH - - - - - 538
INSULATOR - - - - 907
INTERFACE - - - - 419
ION - - - - - - - 550
ION DRIFT - - - - 419
ION TRAPPING - - "
NITRIDE - - - - - 907
PHOSPHORUS - - - 419
PHOSPHOSILICATE - "
POLARIZATION - - "
RUTHERFORD - - - 550
SCATTERING - - - "
SILICON - - - - - "
- - - - - 907
SILICON OXIDE - - 419
STABILITY - - - - 907
TANTALUM - - - - 550
THICKNESS - - - - 419
THIN FILM - - - - 550
THRESHOLD - - - - 419
VOLTAGE - - - - - "

OXIDE DISSOLUTION
ANODE OXIDATION -> 195
BUFFERED - - - - "
CONCENTRATION - - "
HYDROGEN FLUORIDE "
ION IMPLANTATION "
PROFILE - - - - - "
TANTALUM - - - - "

OXIDE FILM
ALUMINUM - - - ->1322
BAYERITE - - - - "
DOUBLE LAYER - ->1596
ELLIPSOMETRY - - "
FORMATION - - - - "
GAAS - - - - - -> 113
GOLD - - - - - - 1596
GROWTH - - - - - 1322
HYDROLYSIS - - - "
HYSTERESIS - - - 1596
NUCLEATION - - - 1322
OXIDATION - - - - 113
OXYGEN PLASMA - - "
PLATINUM - - - - 1596
PSEUDOBOEHMITE - 1322
REDUCTION - - - - 1596
REFLECTANCE - - - "
SURFACE PROCESS - "

OXIDE ION
CARBONATE ION - -> 885
EMF - - - - - - - "
FUSED NITRATES - "

PRIMARY TERM / CO-TERM	PAGE NO.
OXIDE ION (CONTD)	
OXYGEN ELECTRODE	885
STABILITY - - - -	"
OXYGEN	
ACTIVATION - - ->	681
ACTIVITY - - - ->	354
- - - ->	543
ANODE FILM - - ->	1186
ARGON OXYGEN - -	354
AUGER - - - - - ->	34
- - - - - ->	827
BORON - - - - - ->	593
BRONZE - - - - ->	1029
CALCIA STABILIZED>	506
>	793
CATALYSIS - - - -	1186
CERIUM DIOXIDE ->1198	
CHLORIDE - - - ->1007	
CHLORINE - - - -	34
CHROMATE - - - -	1007
CHROMIUM - - - -	543
CHROMIUM OXIDE ->	945
CLUSTER - - - - ->1090	
COMPOSITION - - -	34
CONDUCTION - - -	793
CONDUCTIVITY - -	1198
CONTAMINATION - -	593
- -	681
CONTROL - - - - -	354
COULOMETRY - - -	"
- - -	793
CREVICES - - - -	1007
CRISTOBALITE - -	1090
DEFORMATION - - -	681
DENSIFICATION - -	827
DEPENDENCE - - -	1198
DEPOSIT - - - - -	681
DICHLOROSILANE -	"
DISSOLVED - - - ->	872
EFFECT - - - - ->1613	
ELECTROCHEMISTRY	1007
ELECTRODE - - - -	354
- - - -	506
- - - -	872
ELECTROLYTE - - -	506
ELECTRON SPECTRO.	827
ELECTROREDUCTION	1029
ELLIPSOMETRY - -	1186
EVOLUTION - - - -	"
GALLIUM - - - - -	506
GALLIUM SESQUIOX.	"
GALVANOSTATIC - -	1186
GAS - - - - - - ->	13
GLASS FILM - - -	827
HETEROGENEOUS - -	1090
HOLE - - - - - -	793
HYDROGEN - - - -	13
- - - ->	784
- - - -	1029
HYDROGEN PEROXIDE	"
IMPLANTATION - -	784
INTERFACE - - - -	"
ION - - - - - - -	1007
IONIC - - - - - -	1198
IRON - - - - - -	1007
KINETICS - - - -	506
LEAD ACID - - - -	13
LEAD CALCIUM - -	"
METAL - - - - - -	543
MICROANALYSIS - -	593
MIXTURE - - - - -	354
MOS STRUCTURE - -	784
NEUTRON - - - - -	681
NICKEL - - - - -	543
NONSTOICHIOMETRIC	1198
NUCLEAR - - - - -	593
NUMBER - - - - -	1198
ORIENTATION - - -	1613
OXIDATION - - - -	945
PERMEATION - - -	793
PLATINUM - - - -	354
- - - -	872
- - - -	1029
- - - -	1186
PLATINUM ANODE -	34
POLARIZATION - -	1007
POLYCRYSTALLINE -	681
POTENTIAL - - - -	872
POTENTIOSTAT - -	354
PRECIPITATION - -	1090
PRESSURE - - - -	1198
RATE CONSTANT - -	1613
RATIO - - - - - -	827
REACTION - - - -	1186
RECOMBINATION - -	13
REDUCTION - - - -	1007

PRIMARY TERM / CO-TERM	PAGE NO.
OXYGEN (CONTD)	
REST - - - - - -	872
SILICON - - - - -	784
- - - - -	827
- - - - -	1090
- - - - -	1613
SILICON DIOXIDE -	784
-	827
SILICON FILM - -	681
SILICON OXIDES -	1090
SODIUM - - - - -	1029
SOLID - - - - - -	506
SOLID STATE - - -	793
SOLVENTS - - - -	593
SPECTROSCOPY - -	34
SPIN ON - - - - -	827
STOICHIOMETRY - -	"
SULFURIC ACID - -	1186
SURFACE - - - - -	34
- - - - -	593
SURFACE STATE - -	784
SYSTEM - - - - -	13
- - - - -	543
TEMPERATURE - - -	1198
THERMAL OXIDATION	1613
THICKNESS - - - -	1186
TITRATION - - - -	354
- - - -	793
TRACE - - - - - -	1613
TRACES - - - - -	1029
TRANSFER - - - -	506
TRANSFERENCE - -	1198
TUNGSTEN - - - -	1029
VACANCY - - - - -	1090
VAPOR - - - - - -	681
VAPORIZATION - -	945
WATER - - - - - -	1613
WUSTITE - - - - -	793
ZIRCONIA - - - -	354
- - - -	506
- - - -	793
OXYGEN ATOMS	
CHROMIUM - - - ->	952
CHROMIUM OXIDE -	"
OXIDATION - - - -	"
VAPORIZATION - -	"
OXYGEN ELECTRODE	
ANODE - - - - - ->	749
CARBON - - - - -	"
CARBONATE ION - ->	885
CHLORINE ELECTRO.	749
EMF - - - - - - -	885
FUSED NITRATES -	"
GLASSLIKE - - - -	749
GRAPHITE - - - -	"
OXIDE ION - - - -	885
PYROLYSIS - - - -	749
STABILITY - - - -	885
SURFACE OXIDE - -	749
OXYGEN PLASMA	
GAAS - - - - - ->	113
OXIDATION - - - -	"
OXIDE FILM - - -	"
OXYHALIDE	
BATTERY - - - - ->1045	
CONTAMINATION - -	"
ELECTROLYTE - - -	"
INFRARED - - - -	"
INORGANIC - - - -	"
LIQUID - - - - -	"
LITHIUM - - - - -	"
TRACE ANALYSIS -	"
WATER - - - - - -	"
PACK	
ALLOY - - - - - ->1051	
ALUMINIDE - - - -	"
COATING - - - - -	"
DIFFUSION - - - -	"
KINETICS - - - -	"
NICKEL - - - - -	"
PROTECTIVE - - -	"
THERMODYNAMICS -	"
PACKED BED	
CURRENT - - - - ->	95
DIMENSION - - - -	"
DISTRIBUTION - -	"
FLOW REACTOR - -	"
PALLADIUM	
CORROSION - - - ->	645
DEPOSITION - - ->1160	

PRIMARY TERM / CO-TERM	PAGE NO.
PALLADIUM (CONTD)	
DIFFUSION - - - ->1538	
DISSOLUTION - - -	645
ELECTRON - - - -	1538
METAL - - - - - -	1160
MICROSCOPY - - -	1538
NOBLE - - - - - -	1160
OPEN CIRCUIT - -	"
PHOTOCATALYTIC -	"
PHOTOGRAPHY - - -	"
RING DISK - - - -	645
SEMICONDUCTOR - -	1160
SILICIDE - - - -	1538
STRUCTURE - - - -	"
TITANIUM DIOXIDE	1160
PALLADIUM CHLORI.	
CATALYST - - - ->	738
DIELECTRIC - - -	"
ELECTRON MICROSC.	"
MIXED - - - - - -	"
PLATING - - - - -	"
STANNOUS CHLORIDE	"
SUBSTRATE - - - -	"
PALLADIUM HYDRIDE	
BUFFER - - - - ->1579	
ETCH SOLUTION - -	"
FLUORIDE - - - -	"
PH ELECTRODE - -	"
PARA DIHALOSUBST.	
BENZENES - - - ->	516
COMPOUND - - - -	"
POLAROGRAPHY - -	"
RELATED - - - - -	"
PARABOLIC	
ALLOY - - - - - - ->	889
ATMOSPHERE - - -	"
COBALT IRON - - -	"
HYDROGEN SULFIDE	"
KINETICS - - - -	"
SULFIDATION - - -	"
PARAMETER	
AGENT - - - - - ->	779
ALUMINUM - - - ->1662	
ANTIMONIDE - - -	"
ARSENIDE - - - -	"
COEFFICIENT - - -	779
COPPER FLUOROBOR.	"
COPPER SULFATE -	"
DIFFUSION - - - -	"
ELECTROLYTE - - -	"
GALLIUM - - - - -	1662
GROUP II-VI - - -	"
GROUP III-V - - -	"
INDIUM - - - - -	"
KINETIC - - - - -	779
LATTICE - - - - -	1662
MISCIBILITY GAP -	"
ORGANIC - - - - -	779
PHOSPHIDE - - - -	1662
PSEUDOBINARY - -	"
SEMICONDUCTOR - -	"
SOLID SOLUTION -	"
PARASITE CURRENT	
BIPOLAR - - - - ->	648
CHLORATE - - - -	"
ELECTROLYSIS - -	"
ELECTROLYZER - -	"
PARTIAL PROCESS	
CONSTANT - - - ->	887
COPPER - - - - -	"
CORROSION - - - -	"
ELECTROLESS - - -	"
MIXED POTENTIAL -	"
PLATING - - - - -	"
RATE - - - - - -	"
SPECIFIC - - - -	"
STANDARD - - - -	"
PARTICLE	
ARRANGEMENT - - ->	894
CATHODOLUMINESCE.	"
CRT - - - - - - -	"
DISTRIBUTION - -	"
PHOSPHOR - - - -	"
SIZE - - - - - -	"
TELEVISION - - -	"
PARTICLE SIZE	
ADSORPTION - - ->	764
CESIUM HYDROXIDE >	17

PRIMARY TERM / CO-TERM	PAGE NO.
PARTICLE SIZE (CONTD)	
ELECTROCHEMISTRY	764
GALVANIC CELL - -	"
INSTRUMENT - - -	"
MICROSCOPY - - -	17
POTASSIUM HYDROX.	"
SILVER OXIDE - -	"
STRUCTURE - - - -	"
SURFACE AREA - -	764
PASSIVATED	
AGENT - - - - - ->1013	
CATHODE - - - - -	"
CHELATING - - - -	"
COVERAGE - - - -	"
IRON - - - - - -	"
POTENTIAL - - - -	"
PULSING - - - - -	"
PASSIVATING	
AERATION - - - ->	183
CORROSION - - - -	"
DIFFERENTIAL - -	"
FILM - - - - - -	"
METAL - - - - - -	"
MOISTNESS - - - -	"
THICKNESS - - - -	"
VARIABLE - - - -	"
PASSIVATION	
ALUMINUM - - - ->1509	
CARBON - - - - ->	527
CRYSTALLIZATION -	1509
DEPOSITION - - -	527
DOPING - - - - -	1509
GALLIUM - - - - -	"
IRON - - - - - -	527
IRON OXIDE - - -	"
MASKING - - - - -	1509
OXIDATION - - - -	"
PHOSPHORUS - - -	"
PLANAR JUNCTION -	"
PLATINUM - - - -	527
POTENTIOSTATIC -	"
RING ELECTRODE -	"
SEGREGATION - - -	1509
STEELS - - - - -	527
TRANSIENT - - - -	"
PASSIVITY	
ALLOY - - - - - ->1137	
ANODE - - - - - ->1146	
ANODE DEPOSITION >	37
ANODE OXIDATION ->1152	
CHROMATE - - - -	1146
COPPER - - - - -	1137
CORROSION - - - -	1146
CURVE - - - - - -	1137
ELLIPSOMETRY - -	1146
FILM - - - - - -	"
- - - - - -	1152
INHIBITOR - - - -	1146
IRON - - - - - -	"
IRON OXIDE - - -	37
IRON OXYHYDROXIDE	"
NEUTRAL - - - - -	1152
NICKEL - - - - -	1137
- - - - -	1152
NICKEL OXIDE - -	"
OPEN CIRCUIT - -	1146
PERCHLORATE - - -	37
PITTING - - - - -	1137
PLATINUM - - - -	37
POLARIZATION - -	1137
POTENTIAL - - - -	"
- - - -	1146
POTENTIOSTATIC -	1137
SODIUM CHLORIDE -	"
SULFATE - - - - -	1152
PATTERN	
CHANNELING - - ->1657	
CLOSELY - - - - ->1124	
ELECTRON MICROSC.	1657
GALLIUM - - - - -	"
GAP - - - - - - -	1124
INDIUM - - - - -	1657
METALLIZATION - -	1124
MICROPROBE - - -	1657
PHOSPHIDE - - - -	"
SCANNING - - - -	"
SELF ALIGNED - -	1124
SPACED - - - - -	"
PENETRATION	
COATING - - - - ->	720
CRT - - - - - - -	"

PRIMARY TERM / CO-TERM — PAGE NO.

PENETRATION (CONTD)
DEVICE - - - - - 720
ELECTRON - - - - "
GRAPHITE SILICATE "
THICKNESS - - - - "

PENTA FLUORIDE
ARGON - - - - - ->1372
CONTROL - - - - - "
DIFFUSING - - - - "
EQUILIBRIA - - - "
ETCHING - - - - - "
HELIUM - - - - - "
HEXAFLUORIDE - - "
LANGMUIR SHEATH - "
NITROGEN - - - - "
RATE - - - - - - "
REACTION - - - - "
TUNGSTEN - - - - "

PENTACARBONYL
IRON - - - - - -> 832
VAPOR PRESSURE - "

PERCHLORATE
ANODE DEPOSITION > 37
BATTERY - - - - ->1294
ELECTROINITIATE - "
HIGH ENERGY - - - "
IRON OXIDE - - - 37
IRON OXYHYDROXIDE "
LITHIUM - - - - - 1294
PASSIVITY - - - - 37
PLATINUM - - - - "
POLYMERIZATION - 1294
TETRAHYDROFURAN - "

PERMEATION
ADSORPTION - - -> 609
ARSENIC - - - - - "
CALCIA STABILIZED> 793
CONDUCTION - - - "
COULOMETRY - - - "
ENTRY - - - - - - 609
HOLE - - - - - - 793
HYDROGEN - - - - 609
OXYGEN - - - - - 793
POTENTIAL - - - - 609
SOLID STATE - - - 793
STEEL - - - - - - 609
TITRATION - - - - 793
WUSTITE - - - - - "
ZIRCONIA - - - - "

PH
ACTIVE - - - - -> 220
ALUMINUM FILM - -> 400
ANODE OXIDATION - "
CHLORALKALI CELL 220
CHLORATE CELL - -> 70
- ->1606
CHLORINE - - - - 70
- - - - 220
CONSUMPTION - - - "
CORROSION - - - - "
CURRENT - - - - - 70
- - - - - 1606
CURRENT DENSITY - 70
- 1606
EFFECT - - - - - 70
- - - - - 1606
EFFICIENCY - - - 70
- - - 1606
ELECTROCRYSTALLI. "
ENVIRONMENT - - - 460
GRAPHITE ANODE - 220
HYDRODYNAMIC - - 70
IMPEDANCE - - - - 400
MECHANISM - - - - 1606
MUTUAL - - - - - 70
POROSITY - - - - 400
PROCESS - - - - - 1606
SILVER ELECTRODE "
TEMPERATURE - - - 70
- - - 1606

PH ELECTRODE
BUFFER - - - - ->1579
ETCH SOLUTION - - "
FLUORIDE - - - - "
PALLADIUM HYDRIDE "

PHASE DIAGRAM
CALCULATION - - ->1258
LIQUIDUS TEMPERA. "
MOLTEN SALT - - - "

PHASE EQUILIBRIUM
CRYSTAL GROWTH -> 835
INDIUM - - - - - "
PHOSPHIDE - - - - "
PHOSPHORUS - - - "
VAPOR PRESSURE - "

PHASE SHIFT
EPITAXIAL - - - -> 150
INTERFEROGRAM - - "
LAYER - - - - - - "
SILICON - - - - - "
THICKNESS - - - - "

PHASE TRANSITION
CRYSTAL - - - - ->1674
EXISTENCE - - - - "
HEAT - - - - - - "
INDIUM - - - - - "
MEASUREMENT - - - "
MONOSELENIDE - - "
SEMICONDUCTOR - - "
SPECIFIC - - - - "
STRUCTURE - - - - "
XRAY - - - - - - "

PHENYLNITROPROPE.
DIMERIZATION - ->1412
DIMETHYLFORMAMIDE "
VOLTAMMETRY - - - "

PHOSPHATES
ALKALI - - - - ->1122
ALKALINE - - - - "
EARTH - - - - - - "
ELLIPSOMETRY - ->1393
EUROPIUM - - - - 1122
IRON - - - - - - 1393
LUMINESCENCE - - 1122
REFRACTIVE INDEX 1393
THIN FILMS - - - "

PHOSPHIDE
ALUMINUM - - - ->1662
ANTIMONIDE - - - "
ARSENIC - - - - ->1650
ARSENIDE - - - - "
- - - - 1662
ASYMMETRIC - - - 1650
ASYMMETRY - - - - "
CHANNELING - - ->1657
COEFFICIENT - - -> 556
COMPOUNDS - - - - 1650
CRACKING - - - - "
CROSS HATCH - - - "
CRYSTAL - - - - ->1085
CRYSTAL GROWTH - 556
-> 835
DEFECT - - - - - 1085
DIFFUSION - - - - 556
ELECTRON MICROSC. 1657
ETCH - - - - - - 1650
ETCHING - - - - - 1085
GALLIUM - - - - - 556
- - - - - 1085
- - - - - 1650
- - - - - 1657
- - - - - 1662
GROUP II-VI - - - "
GROUP III-V - - - 1650
- - - 1662
INDIUM - - - - - 835
- - - - - 1650
- - - - - 1657
- - - - - 1662
LATTICE - - - - - "
MELT - - - - - - 556
MICROPROBE - - - 1657
MISCIBILITY GAP - 1662
PARAMETER - - - - "
PATTERN - - - - - 1657
PHASE EQUILIBRIUM 835
PHOSPHORUS - - - 556
- - - 835
PSEUDOBINARY - - 1662
SCANNING - - - - 1657
SEMICONDUCTOR - - 1662
SIRTL - - - - - - 1650
SOLID SOLUTION - 1662
VAPOR PRESSURE - 835

PHOSPHOR
ALUMINUM - - - -> 303
ARRANGEMENT - - -> 894
CATHODOLUMINESCE. "
CRT - - - - - - - "
DISTRIBUTION - - "

PHOSPHOR (CONTD)
ENERGY TRANSFER -> 305
EUROPIUM - - - - "
HIGH PRESSURE - - "
HYDROTHERMAL - - 303
LAMP - - - - - - 305
LITHIUM - - - - - 303
LUMINESCENCE - - "
MANGANOUS - - - - "
MERCURY - - - - - 305
ORTHOSILICATE - - 303
PARTICLE - - - - 094
SIZE - - - - - - "
TELEVISION - - - "
TERBIUM - - - - - 305
VANDATE - - - - - "
VAPOR - - - - - - "
YTTRIUM - - - - - "

PHOSPHORS
ALUMINATE - - - -> 142
ALUMINATES - - ->1623
CANDOLUMINESCENCE 142
COLOR RENDITION -> 407
DIRECT CURRENT -> 109
DISTRIBUTION - - 407
ELECTROLUMINESCE. 109
GALLATE - - - - - 1623
GREEN - - - - - - 109
HEXAGONAL - - - - 1623
HOST LATTICE - - "
LAMP - - - - - - "
LAMPS - - - - - - 407
LANTHANUM - - - - 142
LEAD DOPED - - - 109
MERCURY VAPOR - - 407
NEW - - - - - - - 1623
OPTIMIZED - - - - 407
POWDER CELLS - - 109
POWER - - - - - - 407
RARE EARTH - - - 1623
SPECTRAL - - - - 407
TRANSITION ION - 142
WILLEMITE - - - - "
ZINC PHOSPHATE - "
ZINC SULFIDE - - 109

PHOSPHORUS
ABSORPTION - - -> 434
ACTIVATION - - - "
ALUMINUM - - - ->1509
ANALYSIS - - - - 434
ARSENIC - - - - ->1634
BORON - - - - - ->1377
CARRIER - - - - ->1332
COEFFICIENT - - -> 556
COMPOUND - - - - 1634
CONCENTRATION - -> 132
- -> 153
- -> 419
- - 434
CRISTOBALITE - ->1081
CRYSTAL GROWTH - 153
- 556
-> 835
CRYSTALLIZATION - 1081
- 1509
DEPENDENCE - - - 132
DEVICE - - - - - 419
DIFFUSION - - - - 132
- - - - 556
- - - - 1081
- - - - 1377
DIODE - - - - - - 1332
DISTRIBUTION - - 132
DOPED OXIDE - - - "
DOPING - - - - - 1509
- - - - - 1634
EFFICIENCY - - - 1332
EMITTER DIP - - - 1377
EPITAXY - - - - ->1354
EQUILIBRIA - - - "
FET - - - - - - - 419
FILM - - - - - - 1081
GALLIUM - - - - - 153
- - - - - 556
- - - - - 1332
- - - - - 1509
- - - - - 1634
GAP - - - - - - - 153
GAS PHASE - - - - 1354
GATE - - - - - - 419
GLASS - - - - - - "
HEAT - - - - - - 1332
IMPURITY - - - - 132
INDIUM - - - - - 835
INFRARED - - - - 434

PHOSPHORUS (CONTD)
INTERACTION - - - 434
INTERFACE - - - - 419
- - - - 1081
ION DRIFT - - - - 419
ION TRAPPING - - "
ISOTHERMS - - - - 1634
LAYER - - - - - - 132
LIFETIME - - - - 1332
LIQUIDUS - - - - 1634
MASKING - - - - - 1509
MELT - - - - - - 556
MOISTURE - - - - 434
NETWORK - - - - - 1081
OXIDATION - - - - 1509
OXIDE - - - - - - 419
PASSIVATION - - - 1509
PHASE EQUILIBRIUM 835
PHOSPHIDE - - - - 556
- - - - 835
PHOSPHOSILICATE - 419
PHOTOLUMINESCENCE 1332
PLANAR JUNCTION - 1509
POLARIZATION - - 419
PSG FILM - - - - 434
RESISTANCE - - - "
SEGREGATION - - - 1509
SEMICONDUCTOR - - 1634
SILICON - - - - - 132
- - - - - 1354
- - - - - 1634
SILICON DIOXIDE - 1081
SILICON OXIDE - - 419
SOLIDUS - - - - - 153
SYSTEM - - - - - 1634
TEMPERATURE - - - 132
TERNARY - - - - - 1634
THICKNESS - - - - 419
THRESHOLD - - - - "
VACANCY - - - - - 153
VAPOR DEPOSITION 132
VAPOR PHASE - - - 1354
VAPOR PRESSURE - 835
VOLTAGE - - - - - 419
WATER - - - - - - 434
ZINC OXIDE - - - 1332

PHOSPHOSILICATE
CATALYZE - - - ->1115
COMPOUND - - - - "
CONCENTRATION - -> 419
CRISTOBALITE - - 1115
CRYSTALLIZATION - "
DEVICE - - - - - 419
DEVICE PROCESSING> 724
FET - - - - - - - 419
GATE - - - - - - "
GETTERING - - - -> 444
- - - - 724
GLASS - - - - - - 419
- - - - - - 444
- - - - - - 724
INTERFACE - - - - 419
ION DRIFT - - - - "
ION SCATTERING - 444
ION TRAPPING - - 419
MOBILE CHARGE - - 724
OXIDE - - - - - - 419
PHOSPHORUS - - - "
POLARIZATION - - "
QUARTZ - - - - - 1115
REMOVAL - - - - - 724
SILICON DIOXIDE - "
- 1115
SILICON OXIDE - - 419
SODIUM - - - - - 724
SOFT JUNCTIONS - 444
THICKNESS - - - - 419
THIN FILM - - - - 1115
THRESHOLD - - - - 419
VOLTAGE - - - - - "

PHOTO RESIST
ACOUSTIC WAVE - ->1503
CONTACT PRINT - - "
MASK - - - - - - - "
PHOTOLITHOGRAPHY "
SUBMICRON LINE - "

PHOTOCATALYTIC
DEPOSITION - - ->1160
METAL - - - - - - "
NOBLE - - - - - - "
OPEN CIRCUIT - - "
PALLADIUM - - - - "
PHOTOGRAPHY - - - "
SEMICONDUCTOR - - "

PRIMARY TERM / CO-TERM	PAGE NO.
PHOTOCATALYTIC (CONTD)	
TITANIUM DIOXIDE	1160
PHOTOCHROMICS	
CATHODOCHROMICS ->	815
METHOD	"
SODALITE	"
STRUCTURE CONVER.	"
SYNTHESIS	"
PHOTOGRAPHY	
DEPOSITION ->	1160
METAL	"
NOBLE	"
OPEN CIRCUIT	"
PALLADIUM	"
PHOTOCATALYTIC	"
SEMICONDUCTOR	"
TITANIUM DIOXIDE	"
PHOTOLITHOGRAPHY	
ACOUSTIC WAVE ->	1503
CONTACT PRINT	"
MASK	"
PHOTO RESIST	"
SUBMICRON LINE	"
PHOTOLUMINESCENCE	
ACCEPTOR ->	1208
ALUMINUM ->	137
BARIUM	"
BARRIER ->	1066
CALCIUM	137
CAPACITANCE	1066
CARRIER ->	1332
CORONA CHARGE ->	452
DIODE	1332
EFFICIENCY	"
EPITAXY	1066
	1208
EUROPIUM	137
FIELD EFFECT	452
GAAS	1066
GALLIUM	137
	1332
HALL DATA	1208
HALL EFFECT	1066
HEAT	1332
INDIUM PHOSPHIDE	1208
INTERFACE	452
LAYER	1066
LIFETIME	1332
LIQUID PHASE	1208
MEASUREMENT	1066
MOBILITY	"
MODULATE	452
PHOSPHORUS	1332
SCHOTTKY	1066
SEMICONDUCTOR	137
	452
SPECTRA	1066
STRONTIUM	137
SYNTHESIS	"
TRAP	452
YTTERBIUM	137
ZINC OXIDE	452
	1332
PHOTOLYSIS	
ELECTROLESS ->	67
FORMING	"
ORGANIC ACID	"
PLATING	"
PRINTED CIRCUIT	"
SILVER GLUTAMATE	"
SILVER SALT	"
PHOTOMASK	
ELECTRON ->	929
INORGANIC	"
IRON OXIDE	"
RESIST	"
THIN FILM	"
PHOTORESIST	
INORGANIC ->	925
IRON OXIDE	"
LASER	"
MASK	"
THIN FILM	"
PHOTOSENSITIVITY	
CADMIUM ->	965
DEPOSITION	"
EPITAXY	"
HETEROEPITAXY	"
SAPPHIRE	"
PHOTOSENSITIVITY (CONTD)	
SELENIDE	965
SULFIDE	"
VAPOR	"
VAPOR PHASE	"
PHOTOVOLTAGE	
CARRIER ->	973
DIFFUSION	"
MINORITY	"
SILICON	"
SOLAR CELL	"
SURFACE	"
PITTING	
ACCELERATE ->	778
ALLOY ->	1137
ALUMINUM ->	268
	1271
ANODE	"
ANODE FILM	268
CHLORIDE	"
	1271
CHROMIUM ->	1192
COPPER	1137
CORROSION	778
	1192
CREVICE	778
CURVE	1137
ELECTRON	268
EQUILIBRIA ->	467
EUTECTIC	778
FORMATION	"
GROWTH	268
INCLUSION	467
INITIATION	"
ION	778
IRON	1192
LITHIUM CHLORIDE	778
MANGANESE	467
MOLYBDENUM	1192
MONOLAYER	778
NICKEL	"
	1137
NITRATE	1271
OPACITY	268
PASSIVITY	1137
POLARIZATION	"
POTASSIUM CHLORI.	778
POTENTIAL	1137
POTENTIAL PH	467
POTENTIOSTATIC	1137
REDUCTION	778
RESISTANCE	1192
SILVER	778
SODIUM CHLORIDE	1137
SOLUTION	1271
STAINLESS STEEL	467
	1192
STRAINING	1271
SULFIDE	467
TEMPERATURE	1192
PLANAR	
ANOMALOUS ->	1677
BORON	"
DENSITY	"
DIELECTRIC	"
DIFFUSION	"
EFFECT	"
ELECTRETS	"
INSERT	"
NITRIDE	"
SILICON	"
SURFACE CHARGE	"
PLANAR JUNCTION	
ALUMINUM ->	1509
CRYSTALLIZATION	"
DOPING	"
GALLIUM	"
MASKING	"
OXIDATION	"
PASSIVATION	"
PHOSPHORUS	"
SEGREGATION	"
PLANAR SOURCE	
ANOMALUS ->	722
BORON DIFFUSION	"
BORON NITRIDE	"
SILICON	"
PLANE	
CURRENT ->	1448
DISTRIBUTION	"
MASS TRANSFER	"
PLANE (CONTD)	
ROTATING DISK	1448
PLASMA	
ELLIPSOMETRY ->	263
->	805
NIOBIUM	"
OXIDATION	263
	805
REFRACTIVE INDEX	"
TANTALUM	263
	805
PLASTICS	
CATALYST ->	1461
ELECTROLESS	"
INHIBITION	"
PLATING	"
ULTRA VIOLET	"
PLATING	
ACID BATH ->	1023
AEROSOL ->	484
AGITATION ->	56
AMINE	1023
BEAM ->	62
BORANE	1023
BOROHYDRIDE	56
CATALYST ->	738
	1461
CIRCUIT	62
COBALT	1023
CONSTANT ->	887
COPPER	"
	1405
CORROSION	887
DENDRITE ->	912
DEPOSIT	484
DEPOSITION	1023
DIELECTRIC	738
ELECTRICAL	484
ELECTROLESS	56
	62
->	67
->	667
	887
	912
	1023
	1405
	1461
ELECTRON MICROSC.	738
FORMALDEHYDE	484
	1405
FORMING	67
GLASS	667
	1405
GOLD	56
	62
GROWTH INHIBITION	667
HEAT SINKS	912
HEAT TRANSFER	"
HYDRAZINE	484
HYPOPHOSPHITE	1023
IMAGING	667
IMPURITY	56
INHIBITION	667
	1461
LEAD	62
MIXED	738
MIXED POTENTIAL	887
NICKEL	1023
ORGANIC ACID	67
PALLADIUM CHLORI.	738
PARTIAL PROCESS	887
PHOTOLYSIS	67
PLASTICS	1461
PREPARATION	912
PRINTED CIRCUIT	67
PROCEDURE	56
RATE	887
RESISTIVITY	484
SILICON	62
SILVER	484
SILVER GLUTAMATE	67
SILVER SALT	"
SPECIFIC	887
SPRAY	484
STANDARD	887
STANNOUS CHLORIDE	738
SUBSTRATE	"
THICKNESS	56
ULTRA VIOLET	1461
ULTRAVIOLET	667
PLATINIZED	
ANODE OXIDATION ->	782
HYDROGEN	"
PLATINIZED (CONTD)	
TUNGSTEN OXIDE	782
TUNGSTEN TRIOXIDE	"
PLATINUM	
ACETONITRILE ->	1451
ACTIVITY ->	354
ADSORPTION ->	233
ANODE DEPOSITION	37
ANODE FILM ->	1186
ARGON OXYGEN	354
BRONZE ->	1029
CAPACITANCE ->	632
CARBON ->	527
	1451
CARBON DIOXIDE	233
CARBON MONOXIDE ->	1315
CARBONYL	233
CATALYSIS	1186
CATHODE ->	42
CONTROL	354
COULOMETRY	"
CYCLIC ->	360
DEPOSITION	527
DIFFUSION	1315
DISSOLUTION	360
DISSOLVED ->	872
DOUBLE LAYER	632
->	1596
ELECTRO OXIDATION	1451
ELECTRODE	354
	360
	632
	872
	1315
ELECTROLYTE CELL	632
ELECTROREDUCTION	1029
ELECTROSORPTION	233
ELLIPSOMETRY	1186
	1596
EVOLUTION	1186
FORMATION	1596
GALVANOSTATIC	1186
GAS SENSOR	1315
GOLD	1451
	1596
GRAPHITE	632
HYDROGEN	1029
HYDROGEN PEROXIDE	"
HYSTERESIS	1596
IRON	527
IRON OXIDE	37
	42
	527
IRON OXYHYDROXIDE	37
MECHANISM	360
MIXTURE	354
NITRITE IONS	1451
OXIDATION	1315
OXIDE FILM	1596
OXYGEN	354
	872
	1029
	1186
PASSIVATION	527
PASSIVITY	37
PERCHLORATE	"
POTENTIAL	360
	872
POTENTIOSTAT	354
POTENTIOSTATIC	527
PROGRAM	360
RADIOMETRY	233
REACTION	1186
REDEPOSITION	360
REDUCED	233
REDUCTION	42
	1596
REFLECTANCE	"
REST	872
RING DISK	360
RING ELECTRODE	527
ROOM TEMPERATURE	632
ROUGHENING	360
SILVER HALIDES	632
SODIUM	1029
SOLID ELECTROLYTE	632
STEELS	527
SULFURIC ACID	1186
SURFACE PROCESS	1596
THICKNESS	1186
THIN FILM	42
TITRATION	354
TRACES	1029
TRANSIENT	527
TUNGSTEN	1029
ZIRCONIA	354

PRIMARY TERM / CO-TERM	PAGE NO.
PLATINUM ANODE	
AUGER ->	34
CHLORINE	"
COMPOSITION	"
OXYGEN	"
SPECTROSCOPY	"
SURFACE	"
PMMA	
CONTRAST ->1669	
DEVELOPER	"
ELECTRON BEAM	"
ELECTRON RESIST	"
FUNCTION	"
LITHOGRAPHY	"
METHACRYLATE	"
POLYMETHYL	"
RATE	"
SOLUBILITY	"
PN JUNCTION	
ETCHANT -> 595	
LEAD SULFIDE	"
LEAD SULFUR	"
SELENIUM	"
POLARIZATION	
ACIDIC ->1141	
ALLOY ->1137	
ALUMINUM OXIDE -> 700	
ANODE 1141	
ANODE DISINTEGRA.>1604	
ANODE DISINTEGRA.> 7	
ANODE DISSOLUTION	"
ANOMALOUS VALENCY	"
BERYLLIUM	"
1604	
CHARACTERISTIC - 7	
CHARACTERISTICS - 1604	
CHARGE MOTION - 700	
CHLORIDE ->1007	
1141	
CHROMATE 1007	
COLD 1141	
CONCENTRATION -> 419	
CONTAMINATION 700	
COPPER 1137	
CREVICES 1007	
CURVE 1137	
DEVICE 419	
ELECTROCHEMISTRY 1007	
ELECTRON 7	
FET 419	
GATE	"
GLASS	"
GRAIN 1141	
INTERFACE 419	
ION 1007	
ION DRIFT 419	
ION TRAPPING	"
IRON 1007	
MICROSCOPE 7	
MICROSCOPY 1141	
NICKEL 1137	
1141	
NONAQUEOUS 7	
1604	
OXIDE 419	
OXYGEN 1007	
PASSIVITY 1137	
PHOSPHORUS 419	
PHOSPHOSILICATE	"
PITTING 1137	
POTENTIAL	"
POTENTIOSTATIC	"
1141	
REDUCTION 1007	
SCANNING 7	
SILICON DIOXIDE 700	
SILICON OXIDE 419	
SIZE 1141	
SODIUM 700	
SODIUM CHLORIDE 1137	
SOLUTION 7	
1604	
THICKNESS 419	
THRESHOLD	"
VOLTAGE	"
WORK 1141	
POLARIZED	
ANODE -> 876	
ELECTRON	"
LEAD	"
MICROSCOPY	"
VOLTAMMETRY	"
POLAROGRAPHY	
ALUMINUM CHLORIDE> 212	
BENZENES -> 516	
COMPOUND	"
COPPER 212	
FUSED SALT	"
IRON	"
MELT	"
METAL ION	"
PARA DIHALOSUBST. 516	
RELATED	"
SILVER 212	
SODIUM CHLORIDE	"
SYSTEM	"
VOLTAMMETRY	"
POLISH	
ETCHING -> 455	
FERRICYANIDE	"
GAP	"
LED	"
MASK	"
POLISHING	
ANODE BEHAVIOR -> 191	
BERYLLIA ->1240	
CADMIUM SULFIDE ->1064	
CERAMIC OXIDE 1240	
CHEMOMECHANICAL 1064	
CRYSTAL 1240	
DAMAGE	"
DENSITY 191	
ELECTROCHEMICAL	"
GARNET 1240	
HARDNESS	"
HIGH CURRENT 191	
MILD	"
PREPARATION 1240	
SAPPHIRE	"
SODIUM CHLORATE 191	
SPINEL 1240	
STEEL 191	
SURFACE 1240	
POLYCRYSTALLINE	
ACTIVATION -> 681	
ANALYTICAL -> 972	
BEHAVIOR -> 163	
BORON 972	
CHEMISORPTION 163	
CONTAMINATION 681	
CONTROL ->1235	
DEFORMATION 681	
DEPOSIT	"
DEPOSITION 1235	
DETERMINATION 972	
DICHLOROSILANE 681	
DIELECTRIC 163	
DIFFUSION	"
DOPING	"
EVAPORATION ->1222	
FILM 1235	
FILM THICKNESS	"
FLOAT ZONE 1222	
HIGH RESISTIVITY	"
HIGH TEMPERATURE 163	
LASER 1235	
LITHIUM 163	
NEUTRON 681	
OXYGEN	"
POLYDEPOSITION 1222	
PROCESS	"
PRODUCTION	"
SHEET RESISTIVITY 972	
SILICON 1222	
1235	
SILICON FILM 681	
972	
SINGLE CRYSTAL 1222	
SODIUM 163	
VACUUM 1222	
VAPOR 681	
ZINC OXIDE 163	
POLYDEPOSITION	
EVAPORATION ->1222	
FLOAT ZONE	"
HIGH RESISTIVITY	"
POLYCRYSTALLINE	"
PROCESS	"
PRODUCTION	"
SILICON	"
SINGLE CRYSTAL	"
VACUUM	"
POLYMER BONDING	
BATTERY ->1541	
POLYMER BONDING (CONTD)	
ELECTRON 1541	
LEAD ACID	"
LEAD CALCIUM	"
LEAD ELECTRODE	"
MICROSCOPY	"
NEGATIVE	"
SCANNING	"
POLYMER RESISTS	
ELECTRON RESISTS >1500	
LITHOGRAPHY	"
X RAY	"
POLYMERIZATION	
BATTERY ->1294	
ELECTROINITIATE	"
HIGH ENERGY	"
LITHIUM	"
PERCHLORATE	"
TETRAHYDROFURAN	"
POLYMETHYL	
CONTRAST ->1669	
DEVELOPER	"
ELECTRON BEAM	"
ELECTRON RESIST	"
FUNCTION	"
LITHOGRAPHY	"
METHACRYLATE	"
PMMA	"
RATE	"
SOLUBILITY	"
POLYSTYRENE	
ELECTRON BEAM ->1620	
ION MILLABLE	"
POSITIVE	"
RESIST	"
SULFONE	"
POROSITY	
ALUMINUM FILM -> 400	
ANODE OXIDATION	"
ENVIRONMENT	"
IMPEDANCE	"
PH	"
POROUS	
CAPACITY -> 512	
DOUBLE LAYER	"
ELECTRODE	"
NICKEL	"
POTASSIUM HYDROX.	"
SWEEP	"
TRIANGULAR	"
VOLTAGE	"
POROUS ELECTRODE	
BEHAVIOR ->1308	
DOUBLE LAYER	"
FLUOROGRAPHITE	"
NONAQUEOUS	"
POTENTIAL	"
POSITIVE	
ELECTRON BEAM ->1620	
ION MILLABLE	"
POLYSTYRENE	"
RESIST	"
SULFONE	"
POTASSIUM CHLOR.	
BINARY -> 500	
COULOMBIC	"
INTERACTION	"
LITHIUM CHLORIDE	"
MOLTEN SALT	"
SURFACE TENSION	"
POTASSIUM	
AMMONIUM -> 977	
BROMIDE	"
CHLORIDE ->1298	
CONDUCTANCE 977	
1298	
DENSITY	"
DIMETHYLFORMAMIDE 977	
ELECTROLYTE	"
ISOTHIOCYANATE	"
LINEAR SWEEP -> 86	
LITHIUM 1298	
LITHIUM FLUORIDE 86	
MANGANESE 1298	
MELT	"
MOLTEN FLUORIDE 86	
NICKEL 977	
POTASSIUM (CONTD)	
NONAQUEOUS 977	
RUBIDIUM 1298	
SODIUM	"
SODIUM FLUORIDE 86	
SOLUTION 977	
TETRABUTYL	"
THORIUM 86	
URANIUM	"
VISCOSITY 977	
VOLTAMMETRY 86	
POTASSIUM CHLORI.	
ACCELERATE -> 778	
CORROSION	"
CREVICE	"
EUTECTIC	"
FORMATION	"
ION	"
LITHIUM CHLORIDE	"
MONOLAYER	"
NICKEL	"
PITTING	"
REDUCTION	"
SILVER	"
POTASSIUM HYDROX.	
CAPACITY -> 512	
->1444	
CESIUM HYDROXIDE > 17	
DOUBLE LAYER 512	
1444	
ELECTRODE 512	
MICROSCOPY 17	
NICKEL 512	
PARTICLE SIZE 17	
POROUS 512	
SILVER 1444	
SILVER OXIDE 17	
SPECTROGRAPHY 1444	
STRUCTURE 17	
SWEEP 512	
SWEEP RATE 1444	
TEMPERATURE	"
TRIANGLE	"
TRIANGULAR 512	
VOLTAGE	"
VOLTAMMETRY 1444	
POTENTIAL	
ACETONE ->1563	
ACTIVITY -> 884	
ADSORPTION -> 609	
AGENT ->1013	
ALLOY ->1137	
AMALGAMS 884	
ANODE ->1146	
ARSENIC 609	
BEHAVIOR ->1308	
BIPOLAR ELECTRODE> 622	
CATHODE 1013	
CHELATING	"
CHROMATE 1146	
COEFFICIENT 884	
COPPER 1137	
COPPER ELECTRODE > 18	
CORROSION 1146	
COVERAGE 1013	
CRYSTAL GROWTH 1563	
CURRENT 622	
CURVE 1137	
CYCLIC -> 360	
DILUTE 884	
DIMETHYLFORMAMIDE> 79	
DISSOLUTION 360	
1563	
DISSOLVED -> 872	
DISTRIBUTION 622	
DOUBLE LAYER 1308	
DUTERIUM OXIDE 1563	
ELECTRODE 79	
360	
622	
872	
ELECTROLYTES 1563	
ELLIPSOMETRY 1146	
ENTRY 609	
FILM 1146	
FLUOROGRAPHITE 1308	
FORMAMIDE 1563	
HYDROGEN 609	
INHIBITOR 1146	
IRON 1013	
1146	
LEAD CHLORIDE 79	
MEASUREMENT	"
MECHANISM 360	

PRIMARY TERM / CO-TERM	PAGE NO.
POTENTIAL (CONTD)	
NICKEL	1137
NONAQUEOUS	1308
OPEN CIRCUIT	1146
OXYGEN	872
PASSIVATED	1013
PASSIVITY	1137
	1146
PERMEATION	609
PITTING	1137
PLATINUM	360
	872
POLARIZATION	1137
POROUS ELECTRODE	1308
POTENTIOSTATIC	1137
PRECIPITATION	1563
PROGRAM	360
PULSING	1013
REDEPOSITION	360
RESISTIVE	622
REST	872
RING DISK	360
ROUGHENING	"
SINGLE CRYSTAL	18
SODIUM CHLORIDE	1137
STANDARD	18
	79
	884
STEEL	609
THALLIUM	884
TITANIUM CHLORIDE	79
TRANSIENT	1563
WIRE ELECTRODE	622
POTENTIAL PH	
EQUILIBRIA	467
INCLUSION	"
INITIATION	"
MANGANESE	"
PITTING	"
STAINLESS STEEL	"
SULFIDE	"
POTENTIOSTAT	
ACTIVITY	354
ARGON OXYGEN	"
CONTROL	"
COULOMETRY	"
ELECTRODE	"
MIXTURE	"
OXYGEN	"
PLATINUM	"
TITRATION	"
ZIRCONIA	"
POTENTIOSTATIC	
ACIDIC	1141
ALLOY	1137
ANODE	1141
ANODE DISSOLUTION	249
CARBON	527
CHLORIDE	1141
COLD	"
CONTROL	523
COPPER	1137
CURRENT	523
CURVE	1137
DEPOSITION	527
DISK ELECTRODE	523
DISTRIBUTION	"
ELECTROCHEMICAL	249
FERRATE	"
GALVANOSTATIC	523
GRAIN	1141
IRON	527
IRON (VI)	249
IRON OXIDE	527
MICROSCOPY	1141
NICKEL	1137
	1141
PASSIVATION	527
PASSIVITY	1137
PITTING	"
PLATINUM	527
POLARIZATION	1137
	1141
POTENTIAL	1137
RING ELECTRODE	527
SHORT TIME	523
SIZE	1141
SODIUM CHLORIDE	1137
STEELS	527
SYNTHESIS	249
TRANSIENT	527
WORK	1141
POWDER CELLS	
DIRECT CURRENT	109
ELECTROLUMINESCE	"
GREEN	"
LEAD DOPED	"
PHOSPHORS	"
ZINC SULFIDE	"
POWER	
ALLOY	1129
ALUMINUM	"
COLOR RENDITION	407
CORROSION	1129
DISTRIBUTION	407
HISTOPATHOLOGY	1129
IMPLANTABLE	"
INVITRO	"
INVIVO	"
LAMPS	407
MAGNESIUM	1129
MERCURY VAPOR	407
OPTIMIZED	"
PHOSPHORS	"
SOURCE	1129
SPECTRAL	407
ZINC	1129
PRECIPITATION	
ACETONE	1563
ALUMINUM	583
CAPACITOR	"
CLUSTER	1090
CORROSION	583
CRISTOBALITE	1090
CRYSTAL	1454
CRYSTAL GROWTH	1563
DISSOLUTION	"
DUTERIUM OXIDE	"
ELECTROLYTE	583
ELECTROLYTES	1563
ELECTRON	1454
ETCHABILITY	583
FORMAMIDE	1563
HETEROGENEOUS	1090
IRON	583
LEAD ACID	1454
LEAD SULFATE	"
MICROSCOPY	"
MICROSEGREGATION	583
OXYGEN	1090
POTENTIAL	1563
SCANNING	1454
SILICON	1090
SILICON OXIDES	"
SOLUTION	1454
STRUCTURE	"
TRANSIENT	1563
TUNNEL	583
VACANCY	1090
PREMATURE	
BREAKDOWN	692
DIODE	"
ELECTRON	"
GAAS	"
IMPATT	"
MICROSCOPE	"
SCANNING	"
SCHOTTKY	"
SITES	"
PREPARATION	
BERYLLIA	1240
BOAT	1112
BORON ARSENIDE	412
CERAMIC OXIDE	1240
CONDUCTION	412
CRYSTAL	1240
CVD	1112
DAMAGE	1240
DECOMPOSITION	412
DENDRITE	912
ELECTROLESS	"
GARNET	1240
HARDNESS	"
HEAT SINKS	912
HEAT TRANSFER	"
PLATING	"
POLISHING	1240
PROPERTY	412
	1112
QUARTZ	"
REDUCTION	"
SAPPHIRE	1240
SEMICONDUCTOR	412
	1112
SILICON	"
PREPARATION (CONTD)	
SPINEL	1240
SUBSTRATE	412
SURFACE	1240
TRICHLOROSILANE	1112
TUBE	"
PRESSURE	
CERIUM DIOXIDE	1198
CONDUCTIVITY	"
DEPENDENCE	"
IONIC	"
NONSTOICHIOMETRIC	"
NUMBER	"
OXYGEN	"
TEMPERATURE	"
TRANSFERENCE	"
PRESSURE INDUCED	
BEHAVIOR	448
CONVERGING	"
INDIUM ANTIMONIDE	"
INTERFACE	"
SEGREGATION	"
SOLIDIFICATION	"
STATIONARY	"
VERTICAL ZONE	"
PRETREATMENT	
CARBON FILM	1551
GASEOUS	"
IRON	"
OXIDATION	"
THIN FILM	"
PRINTED CIRCUIT	
COPPER	661
CURRENT	"
	"
DISTRIBUTION	"
	"
ELECTRODEPOSITION	"
ELECTROLESS	67
FORMING	"
MEASUREMENT	661
ORGANIC ACID	67
PHOTOLYSIS	"
PLATING	"
REDOX SYSTEM	661
SILVER GLUTAMATE	67
SILVER SALT	"
WIRE	661
	"
WIRE ELECTRODE	"
PROCEDURE	
AGITATION	56
BOROHYDRIDE	"
ELECTROLESS	"
GOLD	"
IMPURITY	"
PLATING	"
THICKNESS	"
PROCESS	
CHLORATE CELL	1606
CURRENT	"
CURRENT DENSITY	"
DEFECTS	969
EFFECT	1606
EFFICIENCY	"
ELECTROCRYSTALLI	"
EVAPORATION	1222
FLOAT ZONE	"
HIGH RESISTIVITY	"
INDUCED	969
MECHANISM	1606
PH	"
POLYCRYSTALLINE	1222
POLYDEPOSITION	"
PRODUCTION	"
SILICON	969
	1222
SILVER ELECTRODE	1606
SINGLE CRYSTAL	1222
SOFT JUNCTIONS	969
TEMPERATURE	1606
VACUUM	1222
PROCESSING	
DEVICE	563
EPITAXY	"
GROWTH	"
IMPURITY	"
REDISTRIBUTION	"
SEMICONDUCTOR	"
SILICON	"
PRODUCT	
ACETONE	1584
CONSTANT	"
FORMATION	"
MIXTURE	"
SILVER HALIDES	"
SOLUBILITY	"
WATER	"
PRODUCTION	
EVAPORATION	1222
FLOAT ZONE	"
HIGH RESISTIVITY	"
POLYCRYSTALLINE	"
POLYDEPOSITION	"
PROCESS	"
SILICON	"
SINGLE CRYSTAL	"
VACUUM	"
PROFILE	
ANODE OXIDATION	195
BOUNDARY	313
BUFFERED	195
COMPLEMENT	313
CONCENTRATION	195
CONDITION	313
CONTRAST	1202
DIFFUSION	313
DIODE	1202
EQUATION	313
ERROR	"
FLUX STEP	"
FUNCTION	"
GALLIUM NITRIDE	1202
HETEROEXPITAXIAL	"
HYDROGEN FLUORIDE	195
ION IMPLANTATION	"
JUNCTION	1202
LIGHT EMISSION	"
MICROSTRUCTURE	"
OXIDE DISSOLUTION	195
SEMICONDUCTOR	313
STRUCTURE	1202
TANTALUM	195
VAPOR DEPOSITION	1202
VOLTAGE	"
PROGRAM	
CYCLIC	360
DISSOLUTION	"
ELECTRODE	"
MECHANISM	"
PLATINUM	"
POTENTIAL	"
REDEPOSITION	"
RING DISK	"
ROUGHENING	"
PROPAGATING	
COMPONENT	1000
CONVECTIVE	"
CORROSION	"
CRACK	"
DIFFUSION	"
MASS TRANSFER	"
MINOR	"
MOLTEN SALT	"
PROPANE	
ADSORPTION	987
ANION	"
ELECTROLYTE	"
HYDROCARBON	"
MONOHYDRATE	"
OXIDATION	"
TRIFLUOROMETHANE	"
PROPERTIES	
ALUMINUM	829
ARSINE	1646
BANDGAP	1673
CHEMICAL	1646
	1673
COMPOUND	"
COPPER	829
CRYSTAL	1673
DOPING	829
ELECTRICAL	"
	1646
GALLIUM ARSENIDE	"
GERMANIUM	1673
HETEROEPITAXY	1646
INDIUM ARSENIDE	"
NITRIDE	1673
OPTICAL	829
STRUCTURE	1673

PRIMARY TERM / CO-TERM — PAGE NO.

PROPERTIES (CONTD)
SULFIDE - - - - - 829
SYNTHESIS - - - - 1673
TERNARY - - - - - "
TRIETHYLINDIUM - 1646
VAPOR DEPOSITION - "
1673
ZINC - - - - - - "

PROPERTY
BOAT - - - - - ->1112
BORON ARSENIDE -> 412
CONDUCTION - - - "
CVD - - - - - - - 1112
DECOMPOSITION - - 412
PREPARATION - - - "
- - - 1112
QUARTZ - - - - - "
REDUCTION - - - - "
SEMICONDUCTOR - - 412
- - 1112
SILICON - - - - - "
SUBSTRATE - - - - 412
TRICHLOROSILANE - 1112
TUBE - - - - - - "

PROPULSION
CHARGER - - - - ->1134
CONTROLLER - - - "
ELECTROCHEMISTRY "
HIGH POWER - - - "
SIMULATOR - - - - "
SUPPLY - - - - - "

PROPYLENE
ALKALI METAL - -> 994
ALLOY - - - - - -> 734
ALUMINUM CHLORIDE 994
BATTERY - - - - -> 315
- - - - -> 656
- - - - ->1457
BATTERY ANODE - - 734
BEHAVIOR - - - - 656
CARBONATE - - - -> 83
- - - - 315
- - - - 656
- - - - 734
- - - - 994
- - - - 1457
CATHODE - - - - - 656
CHLORIDE - - - - 994
COEFFICIENT - - - "
COPPER - - - - - 656
CURRENT DENSITY - 994
DIFFUSION - - - - 734
ELECTRODE - - - - "
- - - - 994
ELECTRODEPOSITION 1457
ELECTROLYTE - - - "
EMF - - - - - - - 83
EXCHANGE - - - - 994
GALVANIC CELL - - 315
INTERMETALLIC - - 734
KINETICS - - - - 994
LITHIUM ANODE - - 315
LITHIUM BROMINE - "
LITHIUM CELLS - - 656
LITHIUM ELECTRODE 1457
LITHIUM ION - - - 83
LITHIUM MAGNESIUM 734
MANGANESE - - - - 656
MEASUREMENT - - - 83
MOLYBDENUM - - - 656
NONAQUEOUS - - - 315
NUMBER - - - - - 83
RECHARGABLE - - - 1457
SECONDARY - - - - 315
SOLUTION - - - - 83
SOLVENT - - - - - 315
TETRAHYDROFURAN - 656
TRANSFER - - - - 994
TRANSFERENCE - - 83

PROTECTION
ACTIVE - - - - -> 531
BATTERY - - - - - "
CORROSION - - - - "
GRID - - - - - - "
LEAD ACID - - - - "
LEAD ANTIMONY - - "
MATERIAL - - - - "
THICKNESS - - - - "

PROTECTIVE
ALLOY - - - - - ->1051
ALUMINIDE - - - - "
COATING - - - - - "

PROTECTIVE (CONTD)
DIFFUSION - - - - 1051
KINETICS - - - - "
NICKEL - - - - - "
PACK - - - - - - "
THERMODYNAMICS - "

PROTONIC ACID
CONDUCTIVITY - -> 91
DIMETHYLFORMAMIDE "
DISSOCIATION - - "
LEWIS ACID - - - "

PSEUDO BINARY
FREE ENERGY - - -> 932
GIBBS - - - - - - "
LATTICE PARAMETER "
MISCIBILITY GAP - "
MODEL - - - - - - "
QUASIREGULAR - - "

PSEUDOBINARY
ALUMINUM - - - ->1662
ANTIMONIDE - - - "
ARSENIDE - - - - "
GALLIUM - - - - - "
GROUP II-VI - - - "
GROUP III-V - - - "
INDIUM - - - - - "
LATTICE - - - - - "
MISCIBILITY GAP - "
PARAMETER - - - - "
PHOSPHIDE - - - - "
SEMICONDUCTOR - - "
SOLID SOLUTION - "

PSEUDOBOEHMITE
ALUMINUM - - - ->1322
ALUMINUM OXIDE ->1019
ANODE OXIDE - - - "
BAYERITE - - - - 1322
COMPOSITE - - - - 1019
FILM - - - - - - "
GRAVIMETRY - - - "
GROWTH - - - - - 1322
HYDROLYSIS - - - "
HYDROUS - - - - - 1019
NUCLEATION - - - 1322
OXIDE FILM - - - "
RADIOTRACER - - - 1019

PSEUDOCOLLECTION
CIRCUIT - - - - ->1439
ELECTRODE - - - - "
EQUIVALENT - - - "
OHMIC COUPLING - "
RESISTANCE - - - "
RING DISK - - - - "

PSG FILM
ABSORPTION - - -> 434
ACTIVATION - - - "
ANALYSIS - - - - "
CONCENTRATION - - "
INFRARED - - - - "
INTERACTION - - - "
MOISTURE - - - - "
PHOSPHORUS - - - "
RESISTANCE - - - "
WATER - - - - - - "

PULSE
BETA ALUMINA - ->1314
CONDUCTANCE - - - "
CURRENT - - - - - "
IMPEDANCE - - - - "

PULSE CHARGING
BATTERY - - - - -> 175
CADMIUM - - - - - "
CELL - - - - - - "
CHARGE ACCEPTANCE "
COMPUTER - - - - "
CONTROLLED - - - "
MERCURY - - - - - "
NICKEL - - - - - "

PULSING
AGENT - - - - - ->1013
CATHODE - - - - - "
CHELATING - - - - "
COVERAGE - - - - "
IRON - - - - - - "
PASSIVATED - - - "
POTENTIAL - - - - "

PUMP
AUTOMATIC - - - -> 251
BRINE LEVEL - - ->1286
CHLORALKALI CELL "
ELECTRODE - - - - 251
GAS - - - - - - - "
GAS LIFT - - - - 1286
HYDROGEN - - - - 251
MERCURY TYPE - - 1286
SCALE UP - - - - "
SPARKLESS - - - - 251
VOLTAGE - - - - - 1286

PYRIDINIUM
DEHYDROPYRIDINES >1033
DIMERIZATION - - "
ELECTROCHEMISTRY "
METHYL - - - - - "
MONONUCLEOTIDE - "
NICOTINAMIDE - - "
REDOX - - - - - - "
SPECIES - - - - - "

PYROLYSIS
ANODE - - - - - -> 749
BEAM - - - - - -> 899
CARBON - - - - - 749
CHLORINE ELECTRO. "
DEPOSITION - - - 899
GLASSLIKE - - - - 749
GRAPHITE - - - - "
MOLECULE - - - - 899
OXYGEN ELECTRODE 749
SAMPLE - - - - - 899
SILANE - - - - - "
SILICON - - - - - "
SPECTROMETRY - - "
SURFACE OXIDE - - 749

QUARTZ
ALUMINUM - - - ->1228
BOAT - - - - - ->1112
CATALYZE - - - ->1115
COMPOUND - - - - "
CRISTOBALITE - - "
CRYSTALLIZATION - "
CVD - - - - - - - 1112
GROWTH - - - - - 1228
PHOSPHOSILICATE - 1115
PREPARATION - - - 1112
PROPERTY - - - - "
REDUCTION - - - - "
SEMICONDUCTOR - - "
SILICON - - - - - "
- - - - - 1228
SILICON DIOXIDE - 1115
THERMODYNAMICS - 1228
THIN FILM - - - - 1115
TRANSPORT - - - - 1228
TRICHLOROSILANE - 1112
TUBE - - - - - - "
WHISKER - - - - - 1228
X RAY - - - - - - "

QUASIREGULAR
FREE ENERGY - - -> 932
GIBBS - - - - - - "
LATTICE PARAMETER "
MISCIBILITY GAP - "
MODEL - - - - - - "
PSEUDO BINARY - - "

QUENCHING
CERIUM DIOXIDE ->1676
COMMENTS - - - - "
COMPOSITIONAL - - "
CONDUCTIVITY - - "
DEPENDENCE - - - "
ELECTRICAL - - - "
LUMINESCENCE - - "
TEMPERATURE - - - "
THEORY - - - - - "
THERMAL - - - - - "

RADIAL
ANOMALOUS - - - ->1212
CARRIER MOBILITY "
DISTRIBUTION - - "
GERMANIUM - - - - "
HALL - - - - - - "
IMPURITY - - - - "
INHOMOGENEITY - - "
METHOD - - - - - "
MOBILITY - - - - "
SEMICONDUCTOR - - "
VANDERPAUW - - - "

RADICAL
COLORED FILMS - ->1555
COMPOUND - - - - "
INSOLUBLE - - - - "
VIOLOGEN - - - - "

RADIOMETRY
ADSORPTION - - -> 233
CARBON DIOXIDE - "
CARBONYL - - - - "
ELECTROSORPTION - "
PLATINUM - - - - "
REDUCED - - - - - "

RADIOTRACER
ALUMINUM OXIDE ->1019
ANODE OXIDE - - - "
COMPOSITE - - - - "
FILM - - - - - - "
GRAVIMETRY - - - "
HYDROUS - - - - - "
PSEUDOBOEHMITE - "

RANGE PROFILE
ANODE - - - - - -> 45
IMPLANT - - - - - "
ION - - - - - - - "
TANTALUM OXIDE - "

RARE EARTH
ALUMINATES - - ->1623
GALLATE - - - - - "
HEXAGONAL - - - - "
HOST LATTICE - - "
LAMP - - - - - - "
NEW - - - - - - - "
PHOSPHORS - - - - "

RATE
AMALGAM - - - - -> 340
ARGON - - - - - ->1372
CONSTANT - - - -> 887
CONTRAST - - - ->1669
CONTROL - - - - - 1372
COPPER - - - - - 887
CORROSION - - - - "
DECOMPOSITION - - 340
DEVELOPER - - - - 1669
DIFFUSING - - - - 1372
ELECTROLESS - - - 887
ELECTRON BEAM - - 1669
ELECTRON RESIST - "
EQUILIBRIA - - - 1372
ETCHING - - - - - "
FUNCTION - - - - 1669
HELIUM - - - - - 1372
HEXAFLUORIDE - - "
LANGMUIR SHEATH - "
LITHOGRAPHY - - - 1669
METHACRYLATE - - "
MIXED POTENTIAL - 887
NITROGEN - - - - 1372
PARTIAL PROCESS - 887
PENTA FLUORIDE - 1372
PLATING - - - - - 887
PMMA - - - - - - 1669
POLYMETHYL - - - "
REACTION - - - - 1372
SODIUM HYDROXIDE 340
SOLUBILITY - - - 1669
SPECIFIC - - - - 887
STANDARD - - - - "
TOWER - - - - - - 340
TUNGSTEN - - - - 1372

RATE CONSTANT
EFFECT - - - - ->1613
ORIENTATION - - - "
OXYGEN - - - - - "
SILICON - - - - - "
THERMAL OXIDATION "
TRACE - - - - - - "
WATER - - - - - - "

RATIO
AUGER - - - - - -> 827
DENSIFICATION - - "
ELECTRON SPECTRO. "
GLASS FILM - - - "
OXYGEN - - - - - "
SILICON - - - - - "
SILICON DIOXIDE - "
SPIN ON - - - - - "
STOICHIOMETRY - - "

REACTION
ACID - - - - - ->1609

PRIMARY TERM / CO-TERM — PAGE NO.

REACTION (CONTD)
ADDITIVE - - - -> 463
ALUMINUM - - - -> 430
AMMONIA - - - - - 1609
ANODE FILM - - ->1186
ARGON - - - - - ->1372
BARIUM SULFATE - 463
CATALYSIS - - - - 1186
CHLORINE - - - -> 919
CONTROL - - - - - 1372
DECOMPOSITION - - 919
DEPOSITION - - - "
DIFFRACTION - - - 430
DIFFUSING - - - - 1372
ELECTROCATALYST ->1125
ELECTRODE - - - - 463
ELLIPSOMETRY - - 1186
EQUILIBRIA - - - 1372
EQUILIBRIUM - - - 919
ETCHING - - - - - 1372
EVOLUTION - - - - 1186
- - - - 1609
FORMALDEHYDE - - 1125
GALVANOSTATIC - - 1186
HELIUM - - - - - 1372
HEXAFLUORIDE - - "
HIGH TEMPERATURE 919
HYDROGEN - - - - "
- - - - 1609
KINETICS - - - - 1125
LANGMUIR SHEATH - 1372
LEAD - - - - - - 463
LEAD SULFATE - - "
LIGNIN - - - - - "
LIQUID - - - - - 1609
MECHANISM - - - - 463
- - - - 1125
MOLYBDENUM - - - "
MORPHOLOGY - - - 463
NITROGEN - - - - 1372
- - - - 1609
OXIDATION - - - - 1125
OXYGEN - - - - - 1186
PENTA FLUORIDE - 1372
PLATINUM - - - - 1186
RATE - - - - - - 1372
REDUCTION - - - - 919
SILICA - - - - - 430
SILICON - - - - - 919
SUBSTRATE - - - - 430
SULFUR - - - - - 1125
SULFURIC ACID - - 1186
THICKNESS - - - - "
TUNGSTEN - - - - 1372

REACTIVE METALS
ELECTROWINNING -> 879
EUTECTICS - - - - "
FUSED SALTS - - - "
HAFNIUM - - - - - "

RECHARGABLE
BATTERY - - - - - ->1457
CARBONATE - - - - "
ELECTRODEPOSITION "
ELECTROLYTE - - - "
LITHIUM ELECTRODE "
PROPYLENE - - - - "

RECOMBINATION
GAS - - - - - - -> 13
HYDROGEN - - - - "
LEAD ACID - - - - "
LEAD CALCIUM - - "
OXYGEN - - - - - "
SYSTEM - - - - - "

REDEPOSITION
CYCLIC - - - - -> 360
DISSOLUTION - - - "
ELECTRODE - - - - "
MECHANISM - - - - "
PLATINUM - - - - "
POTENTIAL - - - - "
PROGRAM - - - - - "
RING DISK - - - - "
ROUGHENING - - - "

REDISTRIBUTION
CALCULATION - - -> 588
DEVICE - - - - -> 563
EPITAXY - - - - - "
GROWTH - - - - - "
IMPURITY - - - - "
- - - - 588
NUMERICAL - - - - "
OXIDATION - - - - "

REDISTRIBUTION (CONTD)
PROCESSING - - - 563
SEMICONDUCTOR - - "
- - 588
SILICON - - - - - 563
- - - - - 588
SILICON DIOXIDE - "
THERMAL - - - - - "

REDOX
DEHYDROPYRIDINES >1033
DIMERIZATION - - "
ELECTROCHEMISTRY "
METHYL - - - - - "
MONONUCLEOTIDE - "
NICOTINAMIDE - - "
PYRIDINIUM - - - "
SPECIES - - - - - "

REDOX COUPLE
BEHAVIOR - - - -> 318
NICKEL OXIDE - - "
SEMICONDUCTOR - - "

REDOX PATTERN
BEHAVIOR - - - -> 345
- - - ->
DIHYDROPYRIDINES "
"
DIMERIZATION - - "
- - "
FREE RADICAL - - "
- - "
METHYLNICOTINAMI. "
"
NICOTINAMIDE - - "
- - "
OXIDATION - - - - "
- - - - "
REDOX PATTERN - - "
- - "
REDUCTION - - - - "
- - - - "

REDOX SYSTEM
COPPER - - - - -> 661
CURRENT - - - - - "
- - - - - "
DISTRIBUTION - - "
- - "
ELECTRODEPOSITION "
MEASUREMENT - - - "
PRINTED CIRCUIT - "
WIRE - - - - - - "
- - - - - - "
WIRE ELECTRODE - "

REDUCED
ADSORPTION - - -> 233
CARBON DIOXIDE - "
CARBONYL - - - - "
ELECTROSORPTION - "
PLATINUM - - - - "
RADIOMETRY - - - "

REDUCTION
ACCELERATE - - -> 778
ACETONITRILE - -> 881
BEHAVIOR - - - -> 345
BOAT - - - - - ->1112
CATHODE - - - - -> 42
CESIUM - - - - -> 727
CHLORIDE - - - ->1007
CHLORINE - - - -> 919
CHROMATE - - - - 1007
CORROSION - - - - 778
CREVICE - - - - - "
CREVICES - - - - 1007
CVD - - - - - - - 1112
DECOMPOSITION - - 919
DEPOSITION - - - "
DIETHYLFUMARATE - 881
DIHYDROPYRIDINES 345
DIMERIZATION - - "
DMSO - - - - - - 881
DOUBLE LAYER - ->1596
ELECTROCHEMISTRY 1007
ELECTRODE - - - - 727
ELECTROHYDRODIME. 881
ELECTROLYTE - - - 727
ELLIPSOMETRY - - 1596
EQUILIBRIUM - - - 919
EUTECTIC - - - - 778
FORMATION - - - - "
- - - - 1596
FREE RADICAL - - 345
GOLD - - - - - - 1596

REDUCTION (CONTD)
HIGH TEMPERATURE 919
HYDROGEN - - - - "
HYDROXIDE - - - - 727
HYSTERESIS - - - 1596
ION - - - - - - - 778
- - - - - - - 1007
ION PAIRS - - - - 881
IRON - - - - - - 1007
IRON OXIDE - - - 42
LITHIUM CHLORIDE 778
METHYLNICOTINAMI. 345
MONOLAYER - - - - 778
NICKEL - - - - - "
NICOTINAMIDE - - 345
OXIDATION - - - - "
OXIDE FILM - - - 1596
OXYGEN - - - - - 1007
PITTING - - - - - 778
PLATINUM - - - - 42
- - - - 1596
POLARIZATION - - 1007
POTASSIUM CHLORI. 778
PREPARATION - - - 1112
PROPERTY - - - - "
QUARTZ - - - - - "
REACTION - - - - 919
REDOX PATTERN - - 345
- - "
REFLECTANCE - - - 1596
SEMICONDUCTOR - - 1112
SILICON - - - - - 919
- - - - - 1112
SILVER - - - - - 778
SILVER OXIDE - - 727
SODIUM ION - - - 881
STRUCTURE - - - - 727
SURFACE PROCESS - 1596
THIN FILM - - - - 42
TRICHLOROSILANE - 1112
TUBE - - - - - - "
VOLTAMMETRY - - - 881

REDUCTIVE
CHRONOPOTENTIOME.> 769
COUPLING - - - - "
CURRENT REVERSAL "
ELECTROHYDRODIME. "
ELECTROLYTE - - - "
KETONES - - - - - "
UNSATURATED - - - "

REFLECTANCE
ADSORPTION - - -> 474
DEPOSITION - - - "
DOUBLE LAYER - ->1596
ELECTRODE - - - - 474
ELLIPSOMETRY - - 1596
FORMATION - - - - "
GOLD - - - - - - "
GOLD EVAPORATED - 474
HYSTERESIS - - - 1596
ISOTHERM - - - - 474
LEAD - - - - - - "
OXIDE FILM - - - 1596
PLATINUM - - - - "
REDUCTION - - - - "
SINGLE CRYSTAL - 474
SPECTROSCOPY - - "
SURFACE PROCESS - 1596
UNDERPOTENTIAL - 474

REFLECTIVITY
ABSORPTION - - ->1482
CARRIER - - - - - "
CONCENTRATION - - "
DRUDE ZENER - - - "
GAAS - - - - - - "
INFRARED - - - - "
SEMICONDUCTOR - - "
SILICON DOPED - - "

REFRACTIVE INDEX
ABSORPTION - - ->1496
CRYSTAL QUALITY - "
ELLIPSOMETRY - -> 805
- ->1393
IRON - - - - - - "
KRAMERS KRONIG - 1496
NIOBIUM - - - - - 805
OPTICAL INTERFER. 1496
OXIDATION - - - - 805
PHOSPHATES - - - 1393
PLASMA - - - - - 805
SILICON FILM - - 1496
TANTALUM - - - - 805
THIN FILM - - - - 1496

REFRACTIVE INDEX (CONTD)
THIN FILMS - - - 1393

RELATED
BENZENES - - - -> 516
COMPOUND - - - - "
PARA DIHALOSUBST. "
POLAROGRAPHY - - "

RELIABILITY
BREAKDOWN - - - -> 809
DIELECTRIC - - - "
FILM - - - - - - "
GOLD - - - - - ->1076
HALOGEN - - - - - 809
HYDROGEN CHLORIDE "
METALLIZATION - - 1076
MICROWAVE - - - - "
OXIDATION - - - - 809
SILICON DIOXIDE - "
STABILITY - - - - 1076
TANTALUM - - - - "
THERMAL - - - - - "
TRANSISTOR - - - "

REMOVAL
AMMONIUM - - - ->1215
BIPOLAR - - - - - "
CHEMICAL - - - - "
DEVICE PROCESSING> 724
ETCHANT - - - - - 1215
GALLIUM ARSENIDE "
GETTERING - - - - 724
GLASS - - - - - - "
HYDROGEN PEROXIDE 1215
HYDROXIDE - - - - "
MOBILE CHARGE - - 724
PHOSPHOSILICATE - "
SELECTIVE - - - - 1215
SILICON DIOXIDE - 724
- 1215
SODIUM - - - - - 724
TRANSISTOR - - - 1215

REPASSIVATION
CORROSION - - - -> 599
CRACKING - - - - "
TITANIUM ALLOY - "
TRIBOELLIPSOMETRY "

RESIDUE
CARBON - - - - -> 146
CIRCUIT - - - - - "
CONTAMINATION - - "
DOPING - - - - - "
INTEGRATED - - - "
SILICON - - - - - "
SURFACE - - - - - "

RESIST
ELECTRON - - - -> 929
ELECTRON BEAM - ->1620
INORGANIC - - - - 929
ION MILLABLE - - 1620
IRON OXIDE - - - 929
PHOTOMASK - - - - "
POLYSTYRENE - - - 1620
POSITIVE - - - - "
SULFONE - - - - - "
THIN FILM - - - - 929

RESISTANCE
ABSORPTION - - -> 434
AC - - - - - - - -> 375
ACTIVATION - - - 434
ALKALINE - - - - 375
ANALYSIS - - - - 434
APPLICATION - - -> 422
CATHODE - - - - - 375
CHROMIUM - - - ->1192
CIRCUIT - - - - - 422
- - - - ->1439
CONCENTRATION - - 434
CONDUCTIVITY - - 375
CORROSION - - - - 1192
DC - - - - - - - 375
DEVICE - - - - - 422
DISCHARGED - - - 375
ELECTRODE - - - - 1439
EPITAXIAL - - - - 422
EQUIVALENT - - - 1439
IMPEDANCE - - - - 375
INFRARED - - - - 434
INTEGRATED - - - 422
INTERACTION - - - 434
IONIC CONDUCTANC. 375
IRON - - - - - - 1192

PRIMARY TERM / CO-TERM — PAGE NO.

RESISTANCE (CONTD)
LECLANCHE CELL - 375
MANGANESE DIOXIDE "
MEASUREMENT - - - "
- - - 422
MERCURY OXIDE - - 375
MOISTURE - - - - 434
MOLYBDENUM - - - 1192
OHMIC COUPLING - 1439
PHOSPHORUS - - - 434
PITTING - - - - - 1192
PSEUDOCOLLECTION 1439
PSG FILM - - - - 434
RESISTIVITY - - - 422
RING DISK - - - - 1439
SILICON - - - - - 422
SPREADING - - - - "
STAINLESS STEEL - 1192
TEMPERATURE - - - "
UNDISCHARGED - - 375
WATER - - - - - - 434

RESISTIVE
BIPOLAR ELECTRODE> 622
CURRENT - - - - - "
DISTRIBUTION - - "
ELECTRODE - - - - "
POTENTIAL - - - - "
WIRE ELECTRODE - "

RESISTIVITY
AEROSOL - - - - -> 484
APPLICATION - - -> 422
CIRCUIT - - - - - "
DEPOSIT - - - - - 484
DEVICE - - - - - 422
ELECTRICAL - - - 484
EPITAXIAL - - - - 422
FORMALDEHYDE - - 484
HYDRAZINE - - - - "
INTEGRATED - - - 422
MEASUREMENT - - - "
PLATING - - - - - 484
RESISTANCE - - - 422
SILICON - - - - - "
SILVER - - - - - 484
SPRAY - - - - - - "
SPREADING - - - - 422

REST
DISSOLVED - - - -> 872
ELECTRODE - - - - "
OXYGEN - - - - - "
PLATINUM - - - - "
POTENTIAL - - - - "

RETENTION
CONTAMINATION - -> 790
FLUORINE - - - - "
GOLD REFRACTORY - "
ION - - - - - - - "
METALLIZATION - - "
SILICON - - - - - "
SURFACE - - - - - "
TRANSISTOR - - - "

REVERSIBLE CELL
APROTIC - - - - -> 518
DIMETHYLFORMAMIDE "
ELECTROCHEMISTRY "
ELECTRODE - - - - "
HYDROGEN - - - - "
SOLVENT - - - - - "
THALLIUM - - - - "

RF HEATING
IMPURITY - - - ->1107
OXIDATION - - - - "
SILICON - - - - - "
THERMAL - - - - - "

RHODIUM
ADSORPTION - - ->1421
CHRONOCOULOMETRY "
ELECTRODE - - - - "
MERCURY - - - - - "
VOLTAMMETRY - - - "

RING
DEPOSITION - - ->1592
DISSOLUTION - - - "
ELECTRODE - - - - "
HEMISPHERICAL - - "
IRON OXIDE - - - "
MILD - - - - - - "
ROTATING - - - - "
STEEL - - - - - - "

RING (CONTD)
SULFATE SOLUTION 1592

RING DISK
CIRCUIT - - - - ->1439
CORROSION - - - -> 645
COUPLING - - - -> 745
CYCLIC - - - - -> 360
DIGITAL - - - - - 745
DISSOLUTION - - - 360
- - - 645
ELECTRODE - - - - 360
- - - - 745
- - - - 1439
ELECTROOXIDATION 745
EQUIVALENT - - - 1439
MECHANISM - - - - 360
- - - - 745
OHMIC COUPLING - 1439
PALLADIUM - - - - 645
PLATINUM - - - - 360
POTENTIAL - - - - "
PROGRAM - - - - - "
PSEUDOCOLLECTION 1439
REDEPOSITION - - 360
RESISTANCE - - - 1439
ROTATING - - - - 745
ROUGHENING - - - 360
SIMULATION - - - 745

RING ELECTRODE
CARBON - - - - -> 827
DEPOSITION - - - "
IRON - - - - - - "
IRON OXIDE - - - "
PASSIVATION - - - "
PLATINUM - - - - "
POTENTIOSTATIC - "
STEELS - - - - - "
TRANSIENT - - - - "

ROOM TEMPERATURE
CAPACITANCE - - -> 632
DOUBLE LAYER - - "
ELECTRODE - - - - "
ELECTROLYTE CELL "
GRAPHITE - - - - "
PLATINUM - - - - "
SILVER HALIDES - "
SOLID ELECTROLYTE "

ROTATING
COUPLING - - - -> 745
CURRENT DISTRIBU.> 241
CURRENT POTENTIAL>1558
DEPOSITION - - ->1592
DIGITAL - - - - - 745
DISK - - - - - - 1558
DISSOLUTION - - - 1592
ELECTRODE - - - - 745
- - - - 1558
- - - - 1592
ELECTROOXIDATION 745
HEMISPHERICAL - - 1592
IRON OXIDE - - - "
LIMITING CURRENT 241
MASS TRANSFER - - "
- - 1558
MECHANISM - - - - 745
MILD - - - - - - 1592
MODULATION - - - 1558
RING - - - - - - 1592
RING DISK - - - - 745
SIMULATION - - - "
SINUSOIDAL - - - 1558
SPHERE - - - - - 241
STEEL - - - - - - 1592
SULFATE SOLUTION "

ROTATING DISK
ASYMPTOTIC - - -> 521
CURRENT - - - - ->1448
DISTRIBUTION - - "
ELECTRODE - - - - 521
IMPEDANCE - - - - "
MASS TRANSFER - - 1448
PLANE - - - - - - "
SOLUTION - - - - 521
WARBURG - - - - - "

ROUGHENING
CAPACITANCE - - -> 639
CYCLIC - - - - -> 360
DISSOLUTION - - - "
ELECTRODE - - - - "
- - - - 639
ELECTROLYTE CELL "

ROUGHENING (CONTD)
GRAPHITE - - - - 639
INTERFACE - - - - "
MECHANISM - - - - 360
PLATINUM - - - - "
POTENTIAL - - - - "
PROGRAM - - - - - "
REDEPOSITION - - "
RING DISK - - - - "
SILVER HALIDES - 639
SOLID ELECTROLYTE "
SOLID STATE - - - "
WETTING - - - - - "

RUBIDIUM
CHLORIDE - - - ->1298
CONDUCTANCE - - - "
DENSITY - - - - - "
LITHIUM - - - - - "
MANGANESE - - - - "
MELT - - - - - - "
POTASSIUM - - - - "
SODIUM - - - - - "

RUTHERFORD
ALUMINUM - - - - ->1281
ANODE - - - - - -> 550
- - - - - - 1281
BACKSCATTERING - 550
ION - - - - - - - "
ION IMPLANT - - - 1281
METAL ATOMS - - - "
MOBILITY - - - - "
OXIDATION - - - - "
OXIDE - - - - - - 550
SCATTERING - - - "
SILICON - - - - - "
TANTALUM - - - - "
THIN FILM - - - - "

SALT
ALUMINUM - - - -> 983
ALUMINUM CHLORIDE "
ANODIZATION - - - "
ELECTRODE - - - - "
FUSED - - - - - - "
ION - - - - - - - "
MOLTEN - - - - - "
SODIUM CHLORIDE - "
SUBVALENT - - - - "

SAMARIUM
ANODE SPARK - - ->1402
DYSPROSIUM - - - "
ERBIUM - - - - - "
GADOLINIUM - - - "
HOLMIUM - - - - - "
SODIUM SILICATE - "
YTTERBIUM - - - - "
YTTRIUM - - - - - "

SAMPLE
BEAM - - - - - -> 899
DEPOSITION - - - "
MOLECULE - - - - "
PYROLYSIS - - - - "
SILANE - - - - - "
SILICON - - - - - "
SPECTROMETRY - - "

SAPPHIRE
AMMONOLYSIS - - -> 159
ANTIMONY - - - - -> 967
BERYLLIA - - - ->1240
CADMIUM - - - - -> 965
CERAMIC OXIDE - - 1240
CHARACTERIZATION 159
CRYSTAL - - - - - 1240
CRYSTAL GROWTH - 159
DAMAGE - - - - - 1240
DEPOSITION - - - 965
DOPING - - - - - 967
EPITAXY - - - - - 965
- - - - - 967
ETCHING - - - - -> 293
GALLIUM - - - - - 159
GALLIUM NITRIDE - "
GARNET - - - - - 1240
GAS PHASE - - - - 293
HARDNESS - - - - 1240
HETEROEPITAXY - - 965
- ->1345
INSULATOR - - - - "
METALORGANICS - - 967
PHOTOSENSITIVITY 965
POLISHING - - - - 1240
PREPARATION - - - "

SAPPHIRE (CONTD)
SELENIDE - - - - 965
SEMICONDUCTOR - - 159
- - 1345
SILICON - - - - - 967
- - - - - 1345
SOURCE - - - - - 967
SPINEL - - - - - 1240
- - - - - 1345
SULFIDE - - - - - 965
SURFACE - - - - - 1240
THIN FILM - - - - 1345
TRIMETHYLSTIBINE 967
VAPOR - - - - - - 965
VAPOR PHASE - - - "

SCALE UP
BRINE LEVEL - - ->1286
CHLORALKALI CELL "
GAS LIFT - - - - "
MERCURY TYPE - - "
PUMP - - - - - - "
VOLTAGE - - - - - "

SCANNING
ANODE DISINTEGR.> 7
ANODE DISSOLUTION "
ANOMALOUS VALENCY "
BATTERY - - - - ->1541
BERYLLIUM - - - - 7
BREAKDOWN - - - -> 692
CHANNELING - - ->1657
CHARACTERISTIC - 7
CRYSTAL - - - - ->1454
DIODE - - - - - - 692
ELECTRON - - - - 7
- - - - 692
- - - - 1454
- - - - 1541
ELECTRON MICROSC.> 307
1657
FLOW - - - - - - 307
GAAS - - - - - - 692
GALLIUM - - - - - 1657
GLASS - - - - - - 307
IMPATT - - - - - 692
INDIUM - - - - - 1657
INTEGRATED CIRCU. 307
LEAD ACID - - - - 1454
- - - - 1541
LEAD CALCIUM - - "
LEAD ELECTRODE - "
LEAD SULFATE - - 1454
MICROPROBE - - - 1657
MICROSCOPE - - - 7
- - - 692
MICROSCOPY - - - 1454
- - - 1541
MOS - - - - - - - 307
NEGATIVE - - - - 1541
NONAQUEOUS - - - 7
PATTERN - - - - - 1657
PHOSPHIDE - - - - "
POLARIZATION - - 7
POLYMER BONDING - 1541
PRECIPITATION - - 1454
PREMATURE - - - - 692
SCHOTTKY - - - - "
SITES - - - - - - "
SOLUTION - - - - 7
- - - - 1454
STRUCTURE - - - - "

SCATTERING
ANODE - - - - - -> 550
BACKSCATTERING - "
CONTAMINANTS - -> 172
DETECTION - - - - "
ION - - - - - - - 550
MEV - - - - - - - 172
OXIDE - - - - - - 550
RUTHERFORD - - - "
SENSITIVITY - - - 172
SILICON - - - - - 550
SURFACE ANALYSIS 172
TANTALUM - - - - 550
THIN FILM - - - - "

SCHOTTKY
BARRIER - - - - ->1066
BREAKDOWN - - - -> 692
CAPACITANCE - - - 1066
DIODE - - - - - - 692
ELECTRON - - - - "
EPITAXY - - - - - 1066
GAAS - - - - - - 692
- - - - - - 1066

PRIMARY TERM CO-TERM	PAGE NO.
SCHOTTKY (CONTD)	
HALL EFFECT	1066
IMPATT	692
LAYER	1066
MEASUREMENT	"
MICROSCOPE	692
MOBILITY	1066
PHOTOLUMINESCENCE	"
PREMATURE	692
SCANNING	"
SITES	"
SPECTRA	1066
SCRAPE	
IMMERSION	-> 618
METAL ELECTRODE	"
METHOD	"
OPEN CIRCUIT	"
ZERO CHARGE	"
SEAWATER	
ALLOY	->1245
ALUMINUM	"
BATTERY	"
BUFFER	"
CHLORIDE	"
EMF	"
HIGH PRESSURE	"
MAGNESIUM	"
SECONDARY	
AMINES	-> 378
BATTERY	-> 315
CARBONATE	"
CATION RADICAL	378
CONTAMINANT	->1617
DEPTH PROFILE	"
GALVANIC CELL	315
HOFMANN LOEFFLER	378
ION	1617
LITHIUM ANODE	315
LITHIUM BROMINE	"
MASS SPECTROMETRY	1617
MICROCIRCUIT	"
MICROPROBE	"
NONAQUEOUS	315
OXIDATION	378
PROPYLENE	315
SILVER CHLORIDE	1617
SOLVENT	315
SPUTTERING	1617
SURFACE	"
SECONDARY BATTERY	
ACETONITRILE	-> 851
BATTERY	"
COPPER	"
SECONDARY CELL	
HIGH TEMPERATURE	> 665
IRON	"
IRON PYRITE	"
IRON SULFIDE	"
LITHIUM	"
MOLTEN SALT	"
SULFIDE	"
SEGREGATION	
ALUMINUM	->1509
BEHAVIOR	-> 448
BORON	-> 705
CONVERGING	448
CRYSTALLIZATION	1509
DEMARCATION	-> 787
DIFFUSION	705
DOPING	1509
FACET GROWTH	787
GALLIUM	1509
INDIUM ANTIMONIDE	448
INTERFACE	"
	787
ION IMPLANT	705
MASKING	1509
OXIDATION	705
	1509
PASSIVATION	"
PHOSPHORUS	"
PLANAR JUNCTION	"
PRESSURE INDUCED	448
SOLIDIFICATION	"
STATIONARY	"
VERTICAL ZONE	"
SELECTIVE	
AMMONIUM	->1215
BIPOLAR	"
CHEMICAL	"

PRIMARY TERM CO-TERM	PAGE NO.
SELECTIVE (CONTD)	
ETCHANT	1215
GALLIUM ARSENIDE	"
HYDROGEN PEROXIDE	"
HYDROXIDE	"
REMOVAL	"
SILICON DIOXIDE	"
TRANSISTOR	"
SELENIDE	
CADMIUM	-> 965
DEPOSITION	"
EPITAXY	"
HETEROEPITAXY	"
PHOTOSENSITIVITY	"
SAPPHIRE	"
SULFIDE	"
VAPOR	"
VAPOR PHASE	"
SELENIUM	
ETCHANT	-> 595
LEAD SULFIDE	"
LEAD SULFUR	"
PN JUNCTION	"
SELF ALIGNED	
CLOSELY	->1124
GAP	"
METALLIZATION	"
PATTERN	"
SPACED	"
SEMICONDUCTOR	
ABSORPTION	->1482
ALUMINUM	-> 137
	->1662
ANNONOLYSIS	-> 159
ANODE OXIDATION	-> 820
ANOMALOUS	->1212
ANTIMONIDE	1662
ARSENIC	->1634
ARSENIDE	1662
BARIUM	137
BEHAVIOR	-> 318
BIPOLAR	->1119
BOAT	->1112
BORON ARSENIDE	-> 412
BOUNDARY	-> 313
CALCIUM	137
CALCULATION	-> 588
CARRIER	1482
CARRIER MOBILITY	1212
CHARACTERIZATION	159
CHEMICAL	-> 298
COMPLEMENT	313
COMPLEMENTARY	1119
COMPOUND	820
	1634
CONCENTRATION	1482
CONDITION	313
CONDUCTION	412
CORONA CHARGE	-> 452
CRYSTAL	->1674
CRYSTAL GROWTH	159
	->1237
CVD	1112
DECOMPOSITION	412
DEPOSITION	298
	->1160
DEVICE	-> 563
	820
	1119
DIFFUSION	313
	820
	1237
DISTRIBUTION	1212
DOPED	1237
DOPING	1634
DRUDE ZENER	1482
ELECTROOPTICAL	820
EPITAXY	563
	1237
EQUATION	313
ERROR	"
EUROPIUM	137
EXISTENCE	1674
FIELD EFFECT	452
FLUX STEP	313
FUNCTION	"
GAAS	1237
	1482
GALLIUM	137
	159
	1634
	1662
GALLIUM ARSENIDE	820

PRIMARY TERM CO-TERM	PAGE NO.
SEMICONDUCTOR (CONTD)	
GALLIUM NITRIDE	159
GERMANIUM	1212
	1237
GROUP II-VI	1662
GROUP III-V	"
GROWTH	563
HALL	1212
HEAT	1674
HETEROEPITAXY	->1345
IMPURITY	563
	588
	1212
INDIUM	1662
	1674
INFRARED	1482
INHOMOGENEITY	1212
INSULATOR	1345
INTEGRATION	1119
INTERFACE	452
ISOLATED	1119
ISOTHERMS	1634
LATTICE	1662
LIQUIDUS	1634
MEASUREMENT	1674
METAL	1160
METALLIZATION	298
METHOD	1212
MISCIBILITY GAP	1662
MOBILITY	1212
MODULATE	452
MONOLITHIC	1119
MONOSELENIDE	1674
MOS	1119
NICKEL OXIDE	318
NOBLE	1160
NUMERICAL	588
OHM	1237
OPEN CIRCUIT	1160
OXIDATION	588
PALLADIUM	1160
PARAMETER	1662
PHASE TRANSITION	1674
PHOSPHIDE	1662
PHOSPHORUS	1634
PHOTOCATALYTIC	1160
PHOTOGRAPHY	"
PHOTOLUMINESCENCE	137
	452
PREPARATION	412
	1112
PROCESSING	563
PROFILE	313
PROPERTY	412
	1112
PSEUDOBINARY	1662
QUARTZ	1112
RADIAL	1212
REDISTRIBUTION	563
	588
REDOX COUPLE	318
REDUCTION	1112
REFLECTIVITY	1482
SAPPHIRE	159
	1345
SILICON	563
	588
	1112
	1345
	1634
SILICON DIOXIDE	588
SILICON DOPED	1482
SOLID SOLUTION	1662
SPECIFIC	1674
SPINEL	1345
STRONTIUM	137
STRUCTURE	1674
SUBSTRATE	412
SYNTHESIS	137
SYSTEM	1634
TERNARY	"
THERMAL	588
THIN FILM	1345
TITANIUM DIOXIDE	1160
TRANSISTOR	1119
TRAP	452
TRICHLOROSILANE	1112
TUBE	"
TUNGSTEN	298
VANDERPAUW	1212
VAPOR	298
XRAY	1674
YTTERBIUM	137
ZINC	820
	1237
ZINC OXIDE	452

PRIMARY TERM CO-TERM	PAGE NO.
SEMICONDUCTORS	
ANODE OXIDATION	->1665
AQUEOUS	"
COMPOUND	"
GALLIUM PHOSPHIDE	"
HYDROGEN PEROXIDE	"
NATIVE OXIDE	"
SENSITIVITY	
CONTAMINANTS	-> 172
DETECTION	"
MEV	"
SCATTERING	"
SURFACE ANALYSIS	"
SHEET RESISTIVITY	
ANALYTICAL	-> 972
BORON	"
DETERMINATION	"
POLYCRYSTALLINE	"
SILICON FILM	"
SHORT TIME	
CONTROL	-> 523
CURRENT	"
DISK ELECTRODE	"
DISTRIBUTION	"
GALVANOSTATIC	"
POTENTIOSTATIC	"
SIGMA	
DETERMINATION	->1462
ELECTRODE	"
HAMMETT	"
HYDROGEN	"
SUBSTITUENT	"
SILANE	
BEAM	-> 899
DEPOSITION	"
MOLECULE	"
PYROLYSIS	"
SAMPLE	"
SILICON	"
SPECTROMETRY	"
SILANOL	
ADSORPTION	-> 676
BOROSILICATE	"
DEPOSIT	"
DIFFUSION	"
GLASS FILM	"
SPECTROSCOPY	"
VAPOR	"
WATER	"
SILICA	
ALUMINUM	-> 430
DIFFRACTION	"
REACTION	"
SUBSTRATE	"
SILICIDE	
DIFFUSION	->1538
ELECTRON	"
MICROSCOPY	"
PALLADIUM	"
STRUCTURE	"
SILICON	
ALUMINUM	->1228
ANALYZER	-> 689
ANODE	-> 550
ANOMALOUS	->1677
ANOMALUS	-> 722
ANTIMONY	-> 967
APPLICATION	-> 422
ARSENIC	->1362
	->1634
AUGER	-> 827
BACKSCATTERING	550
BARRIER HEIGHT	->1195
BEAM	-> 62
	-> 899
BOAT	->1112
BORON	1677
BORON DIFFUSION	722
BORON NITRIDE	"
BREAKDOWN	1195
	->1229
CALCULATION	-> 588
CAPACITATOR	-> 849
CAPACITOR	->1219
CARBON	-> 146
CARRIER	849
	-> 973
	1219

PRIMARY TERM / CO-TERM — PAGE NO.

SILICON (CONTD)
CARRIER - - - - - 1229
CHARGE - - - - -> 907
CHLORINE - - - -> 919
CIRCUIT - - - - - 62
- - - - - 146
- - - - - 422
CLUSTER - - - - ->1090
COMPOUND - - - - 1634
CONCENTRATION - -> 132
CONTAMINATION - - 146
- -> 790
- - 1195
CONTROL - - - - ->1233
- - - - ->1235
COPPER - - - - -> 289
CRISTOBALITE - - 1090
CVD - - - - - - - 1112
- - - - - - - 1233
DECOMPOSITION - - 919
DEEP - - - - - - 1219
DEFECT - - - - - 689
DEFECTS - - - - -> 969
DENSIFICATION - - 827
DENSITY - - - - - 1677
DEPENDENCE - - - 132
DEPLETION - - - - 1219
DEPOSITION - - - 899
- - - 919
- - - 1233
- - - 1235
DEVICE - - - - - 422
- - - - -> 563
DIELECTRIC - - - 907
- - - 1195
- - - 1229
- - - 1677
DIFFUSION - - - - 132
- - - -> 286
- - - - 973
- - - - 1219
- - - ->1487
- - - - 1677
DISPLACEMENT - - 289
DISTRIBUTION - - 132
DOPED OXIDE - - - "
DOPING - - - - - 146
- - - - - 967
- - - - ->1350
- - - - - 1634
EFFECT - - - - ->1613
- - - - - 1677
ELECTRETS - - - - "
ELECTROCHEMICAL - 286
ELECTROLESS - - - 62
ELECTRON SPECTRO. 827
ENCAPSULATION - - 1350
ENHANCEMENT - - - "
EPITAXIAL - - - -> 150
- - - - 422
EPITAXY - - - - - 563
- - - - - 967
- - - - ->1354
- - - - - 1362
EQUILIBRIA - - - 1354
EQUILIBRIUM - - - 919
ETCHING - - - - - 286
- - - - - 1229
EVAPORATION - - ->1222
FILM - - - - - - 286
- - - - - - 1195
- - - - - - 1233
- - - - - - 1235
FILM THICKNESS - 1233
- 1235
FLOAT ZONE - - - 1222
FLUORINE - - - - 790
GALLIUM - - - - - 1487
- - - - - 1634
GAS PHASE - - - - 1354
GATE - - - - - - 907
GENERATION - - - 849
- - - 1229
GLASS FILM - - - 827
GOLD - - - - - - 62
- - - - - 1350
GOLD REFRACTORY - 790
GROWTH - - - - - 563
- - - - 1228
- - - - - 1362
HELIUM - - - - - 689
- - - - - 1233
HETEROEPITAXY - ->1345
HETEROGENEOUS - - 1090
HIGH RESISTIVITY 1222
HIGH TEMPERATURE 919
HYDROGEN - - - -> 784

SILICON (CONTD)
HYDROGEN - - - - 919
IMPERFECTION - - 289
- - 1229
IMPLANTATION - - 784
IMPURITY - - - - 132
- - - - 563
- - - - 588
- - - ->1107
INDUCED - - - - - 969
INSERT - - - - - 1677
INSULATOR - - - - 907
- - - - 1345
INTEGRATED - - - 146
- - - 422
INTERFACE - - - - 784
INTERFEROGRAM - - 150
ION - - - - - - - 550
- - - - - - - 790
ION IMPLANT - - - 1362
ISOTHERMS - - - - 1634
LASER - - - - - - 689
- - - - - - 1233
- - - - - - 1235
LAYER - - - - - - 132
- - - - - - 150
LEAD - - - - - - 62
LENGTH - - - - - 1219
LIFETIME - - - - "
LIQUIDUS - - - - 1634
LOWERING - - - - 1195
MEASUREMENT - - - 422
METALLIZATION - - 790
METALORGANICS - - 967
MINORITY - - - - 849
- - - - 973
- - - - 1219
- - - - 1229
MOLECULE - - - - 899
MOS - - - - - - - 849
- - - - - - - 1219
MOS STRUCTURE - - 784
NEON - - - - - - 1233
NITRIDE - - - - - 907
- - - - - 1233
- - - - - 1677
NITROGEN - - - - 689
NUMERICAL - - - - 588
ORIENTATION - - - 1613
OXIDATION - - - - 588
- - - - 1107
OXIDE - - - - - - 550
- - - - - - 907
OXYGEN - - - - - 784
- - - - - 827
- - - - - 1090
- - - - - 1613
PHASE SHIFT - - - 150
PHOSPHORUS - - - 132
- - - 1354
- - - 1634
PHOTOVOLTAGE - - 973
PLANAR - - - - - 1677
PLANAR SOURCE - - 722
PLATING - - - - - 62
POLYCRYSTALLINE - 1222
- 1235
POLYDEPOSITION - 1222
PRECIPITATION - - 1090
PREPARATION - - - 1112
PROCESS - - - - - 969
- - - - - 1222
PROCESSING - - - 563
PRODUCTION - - - 1222
PROPERTY - - - - 1112
PYROLYSIS - - - - 899
QUARTZ - - - - - 1112
- - - - - 1228
RATE CONSTANT - - 1613
RATIO - - - - - - 827
REACTION - - - - 919
REDISTRIBUTION - 563
- 588
REDUCTION - - - - 919
- - - - 1112
RESIDUE - - - - - 146
RESISTANCE - - - 422
RESISTIVITY - - - "
RETENTION - - - - 790
RF HEATING - - - 1107
RUTHERFORD - - - 550
SAMPLE - - - - - 899
SAPPHIRE - - - - 967
- - - - 1345
SCATTERING - - - 550
SEMICONDUCTOR - - 563
- - 588

SILICON (CONTD)
SEMICONDUCTOR - - 1112
- - 1345
- - 1634
SILANE - - - - - 899
SILICON DIOXIDE - 588
- 784
- 827
- 1195
- 1233
- 1487
SILICON OXIDES - 1090
SINGLE CRYSTAL - 1222
SLICE - - - - - - 689
SODIUM - - - - - 1195
SODIUM INDUCED - "
SOFT JUNCTIONS - 969
SOLAR CELL - - - 973
SOLUBILITY - - - 1350
SOURCE - - - - - 967
SPECTROMETRY - - 899
SPIN ON - - - - - 827
SPINEL - - - - - 1345
SPREADING - - - - 422
STABILITY - - - - 907
STEADY STATE - - 1219
STOICHIOMETRY - - 827
SUBSTRATE - - - - 289
SURFACE - - - - - 146
- - - - - 689
- - - - - 790
- - - - - 973
SURFACE CHARGE - 1677
SURFACE STATE - - 784
SYSTEM - - - - - 1634
TANTALUM - - - - 550
TEMPERATURE - - - 132
TERNARY - - - - - 1634
THERMAL - - - - - 588
- - - - - 1107
THERMAL OXIDATION 1613
THERMODYNAMICS - 1228
THICKNESS - - - - 150
THIN FILM - - - - 286
- - - - 550
- - - - 1345
TOPOGRAPHY - - - 289
TRACE - - - - - - 1613
TRANSISTOR - - - 790
TRANSPORT - - - - 1228
TRICHLOROSILANE - 1112
TRIMETHYLSTIBINE 967
TUBE - - - - - - 1112
VACANCY - - - - - 1090
VACUUM - - - - - 1222
VAPOR DEPOSITION 132
VAPOR PHASE - - - 1354
WAFER - - - - - - 1229
WATER - - - - - - 1613
WHISKER - - - - - 1228
X RAY - - - - - - 289
- - - - - - 1228

SILICON CARBIDE
ABSORPTION - - -> 586
COMPOUND - - - - "
CONDUCTIVITY - - "
ELECTRIC - - - - "
FORMATION - - - - "
ION IMPLANTATION "
OPTICAL - - - - - "

SILICON DIOXIDE
ALUMINUM OXIDE -> 700
AMMONIUM - - - ->1215
ARGON - - - - - -> 558
AUGER - - - - - -> 827
BACKSPUTTERING - 558
BARRIER HEIGHT ->1195
BIPOLAR - - - - - 1215
BREAKDOWN - - - -> 809
- - - - 1195
CALCULATION - - -> 588
CATALYZE - - - ->1115
CHARACTERIZATION > 669
CHARGE MOTION - - 700
CHEMICAL - - - ->1103
- - - - 1215
COMPOUND - - - - 1115
CONTACT ANGLE - - 669
CONTAMINATION - - 700
- - 1195
CONTROL - - - - ->1233
CRISTOBALITE - ->1081
- - 1115
CRYSTALLIZATION - 1081
- 1115

SILICON DIOXIDE (CONTD)
CVD - - - - - - - 1233
DECOMPOSITION - ->1328
DENSIFICATION - - 827
DEPOSITION - - - 1233
DEVICE PROCESSING> 724
DIELECTRIC - - - 809
- - - 1195
DIFFUSION - - - - 1081
- - - - ->1487
ELECTROLYSIS - - 1328
ELECTRON SPECTRO. 827
ETCHANT - - - - - 1215
FET - - - - - - - 1103
FILM - - - - - - 558
- - - - - - 809
- - - - - - 1081
- - - - - - 1195
- - - - - - 1233
FILM THICKNESS - "
GALLIUM - - - - - 1487
GALLIUM ARSENIDE 1215
GETTERING - - - - 724
GLASS - - - - - - "
GLASS FILM - - - 827
HALOGEN - - - - - 809
HELIUM - - - - - 1233
HIGH TEMPERATURE 1328
HYDROGEN - - - -> 784
HYDROGEN CHLORIDE 809
HYDROGEN PEROXIDE 1215
HYDROXIDE - - - - "
IMPLANTATION - - 558
- - 784
IMPURITY - - - - 588
INTERFACE - - - - 784
- - - - 1081
- - - - 1328
ION - - - - - - - 558
LASER - - - - - - 1233
LOWERING - - - - 1195
MASS TRANSPORT - 1328
MEASUREMENT - - - 669
METALLIZATION - - 558
MOBILE CHARGE - - 724
MOS - - - - - - - 1103
MOS STRUCTURE - - 784
NEON - - - - - - 1233
NETWORK - - - - - 1081
NITRIDE - - - - - 1233
NUMERICAL - - - - 588
OXIDATION - - - - "
- - - - 809
OXYGEN - - - - - 784
- - - - - 827
PHOSPHORUS - - - 1081
PHOSPHOSILICATE - 724
- 1115
POLARIZATION - - 700
QUARTZ - - - - - 1115
RATIO - - - - - - 827
REDISTRIBUTION - 588
RELIABILITY - - - 809
REMOVAL - - - - - 724
- - - - - 1215
SELECTIVE - - - - "
SEMICONDUCTOR - - 588
SILICON - - - - - "
- - - - - 784
- - - - - 827
- - - - - 1195
- - - - - 1233
- - - - - 1487
SODIUM - - - - - 700
- - - - - 724
- - - - - 1195
SODIUM INDUCED - "
SPIN ON - - - - - 827
SPUTTERING - - - 558
STABILITY - - - - 1328
STOICHIOMETRY - - 827
SURFACE - - - - - 669
SURFACE STATE - - 784
THERMAL - - - - - 588
- - - - - 669
THIN FILM - - - - 1103
- - - - 1115
TRANSISTOR - - - 1215
TRAPPING - - - - 558
VAPOR DEPOSITION 1103

SILICON DOPED
ABSORPTION - - ->1482
CARRIER - - - - - "
CONCENTRATION - - "
DRUDE ZENER - - - "
GAAS - - - - - - "

PRIMARY TERM / CO-TERM	PAGE NO.
SILICON DOPED (CONTD)	
INFRARED	1482
REFLECTIVITY	"
SEMICONDUCTOR	"
SILICON FILM	
ABSORPTION	->1496
ACTIVATION	-> 681
ANALYTICAL	-> 972
BORON	"
CONTAMINATION	681
CRYSTAL QUALITY	1496
DEFORMATION	681
DEPOSIT	"
	-> 685
DETERMINATION	972
DEVICE	685
DICHLOROSILANE	681
FUSED SILICA	685
KRAMERS KRONIG	1496
NEUTRON	681
OPTICAL INTERFER.	1496
OXYGEN	681
POLYCRYSTALLINE	"
	972
REFRACTIVE INDEX	1496
SHEET RESISTIVITY	972
THIN FILM	685
	1496
TRANSISTOR	685
VACUUM	"
VAPOR	681
SILICON OXIDE	
CONCENTRATION	-> 419
DEVICE	"
FET	"
GATE	"
GLASS	"
INTERFACE	"
ION DRIFT	"
ION TRAPPING	"
OXIDE	"
PHOSPHORUS	"
PHOSPHOSILICATE	"
POLARIZATION	"
THICKNESS	"
THRESHOLD	"
VOLTAGE	"
SILICON OXIDES	
CLUSTER	->1090
CRISTOBALITE	"
HETEROGENEOUS	"
OXYGEN	"
PRECIPITATION	"
SILICON	"
VACANCY	"
SILVER	
ACCELERATE	-> 778
AEROSOL	-> 484
ALUMINUM CHLORIDE>	212
ANODE OXIDATION ->	757
CAPACITY	->1444
CHARGING	757
COPPER	212
CORROSION	778
CREVICE	"
DEPOSIT	484
DIMETHYLANILINE	757
DISCHARGING	"
DOUBLE LAYER	1444
ELECTRICAL	484
ELECTROCRYSTALLI.>	207
ELECTRODE	757
ELECTRODEPOSITION	207
EUTECTIC	778
EXCHANGE CURRENT	207
FORMALDEHYDE	484
FORMATION	778
FUSED SALT	212
HYDRAZINE	484
ION	778
IRON	212
LITHIUM CHLORIDE	778
MECHANISM	207
MELT	212
METAL ION	"
MONOLAYER	778
MORPHOLOGY	757
NICKEL	778
PITTING	"
PLATING	484
POLAROGRAPHY	212
POTASSIUM CHLORI.	778
POTASSIUM HYDROX.	1444
SILVER (CONTD)	
REDUCTION	778
RESISTIVITY	484
SILVER CHLORIDE	757
SODIUM CHLORIDE	212
SPECTROGRAPHY	1444
SPRAY	484
SURFACE	757
SWEEP RATE	1444
SYSTEM	212
TEMPERATURE	1444
TRIANGLE	"
VOLTAMMETRY	212
	1444
SILVER CHLORIDE	
ANODE OXIDATION ->	757
CHARGING	"
CONTAMINANT	->1617
DEPTH PROFILE	"
DIMETHYLANILINE	757
DISCHARGING	"
ELECTRODE	"
ION	1617
MASS SPECTROMETRY	"
MICROCIRCUIT	"
MICROPROBE	"
MORPHOLOGY	757
SECONDARY	1617
SILVER	757
SPUTTERING	1617
SURFACE	757
	1617
SILVER ELECTRODE	
CHLORATE CELL	->1606
CURRENT	"
CURRENT DENSITY	"
EFFECT	"
EFFICIENCY	"
ELECTROCRYSTALLI.	"
MECHANISM	"
PH	"
PROCESS	"
TEMPERATURE	"
SILVER GLUTAMATE	
ELECTROLESS	-> 67
FORMING	"
ORGANIC ACID	"
PHOTOLYSIS	"
PLATING	"
PRINTED CIRCUIT	"
SILVER SALT	"
SILVER HALIDES	
ACETONE	->1584
CAPACITANCE	-> 632
	-> 639
CONSTANT	1584
DOUBLE LAYER	632
ELECTRODE	"
	639
ELECTROLYTE CELL	632
	639
FORMATION	1584
GRAPHITE	632
	639
INTERFACE	"
MIXTURE	1584
PLATINUM	632
PRODUCT	1584
ROOM TEMPERATURE	632
ROUGHENING	639
SOLID ELECTROLYTE	632
	639
SOLID STATE	"
SOLUBILITY	1584
WATER	"
WETTING	639
SILVER OXIDE	
CESIUM	-> 727
CESIUM HYDROXIDE >	17
ELECTRODE	727
ELECTROLYTE	"
HYDROXIDE	"
MICROSCOPY	17
PARTICLE SIZE	"
POTASSIUM HYDROX.	"
REDUCTION	727
STRUCTURE	17
	727
SILVER SALT	
ELECTROLESS	-> 67
FORMING	"
SILVER SALT (CONTD)	
ORGANIC ACID	67
PHOTOLYSIS	"
PLATING	"
PRINTED CIRCUIT	"
SILVER GLUTAMATE	"
SIMULATION	
COUPLING	-> 745
DIGITAL	"
ELECTRODE	"
ELECTROOXIDATION	"
MECHANISM	"
RING DISK	"
ROTATING	"
SIMULATOR	
CHARGER	->1134
CONTROLLER	"
ELECTROCHEMISTRY	"
HIGH POWER	"
PROPULSION	"
SUPPLY	"
SINGLE CRYSTAL	
ADSORPTION	-> 474
ASSIGNMENT	-> 170
CAPACITANCE	->1318
COPPER	-> 202
	1318
COPPER CHLORIDE	"
COPPER ELECTRODE >	18
CRYSTAL DEFECTS	170
CRYSTALLOGRAPHY	"
DEPOSITION	474
	->1610
DIFFUSION	1318
DOMAIN	170
DOUBLE LAYER	1318
ELECTRODE	474
	1610
ELECTRODEPOSIT	202
EPITAXY	->1534
ETCHING	170
EVAPORATION	202
	->1222
FERROELECTRIC	170
FLOAT ZONE	1222
GMC	170
GOLD	1318
	1610
GOLD EVAPORATED	474
HIGH RESISTIVITY	1222
IRON	1534
IRON OXIDE	"
ISOTHERM	474
LEAD	"
	1610
LOW TEMPERATURE	1318
NUCLEATION	202
OPTIC	1610
OXIDATION	1534
POLYCRYSTALLINE	1222
POLYDEPOSITION	"
POTENTIAL	18
PROCESS	1222
PRODUCTION	"
REFLECTANCE	474
SILICON	1222
SOLID ELECTROLYTE	1318
SPECTROSCOPY	474
STANDARD	18
THIN FILM	202
UNDER POTENTIAL	1610
UNDERPOTENTIAL	474
VACUUM	1222
SINNERITE	
ARSENIC	-> 363
CHALCOGENIDE	"
COPPER SULFIDE	"
GLASS ELECTRODE	"
SINTERING	
BOROSILICATE	->1098
GLASS FILM	"
GLASS METAL	"
HARDNESS	"
STRESS	"
VICKERS	"
SINUSOIDAL	
CURRENT POTENTIAL>1558	
DISK	"
ELECTRODE	"
MASS TRANSFER	"
MODULATION	"
SINUSOIDAL (CONTD)	
ROTATING	1558
SIRTL	
ARSENIC	->1650
ARSENIDE	"
ASYMMETRIC	"
ASYMMETRY	"
COMPOUNDS	"
CRACKING	"
CROSS HATCH	"
ETCH	"
GALLIUM	"
GROUP III-V	"
INDIUM	"
PHOSPHIDE	"
SITES	
BREAKDOWN	-> 692
DIODE	"
ELECTRON	"
GAAS	"
IMPATT	"
MICROSCOPE	"
PREMATURE	"
SCANNING	"
SCHOTTKY	"
SIZE	
ACIDIC	->1141
ANODE	"
ARRANGEMENT	-> 894
CATHODOLUMINESCE.	"
CHLORIDE	1141
COLD	"
CRT	894
DISTRIBUTION	"
GRAIN	1141
MICROSCOPY	"
NICKEL	"
PARTICLE	894
PHOSPHOR	"
POLARIZATION	1141
POTENTIOSTATIC	"
TELEVISION	894
WORK	1141
SLICE	
ANALYZER	-> 689
DEFECT	"
HELIUM	"
LASER	"
NITROGEN	"
SILICON	"
SURFACE	"
SODALITE	
CATHODOCHROMICS	-> 815
METHOD	"
PHOTOCHROMICS	"
STRUCTURE CONVER.	"
SYNTHESIS	"
SODIUM	
ALUMINUM OXIDE	-> 700
AMALGAM	-> 337
BARRIER HEIGHT	->1195
BEHAVIOR	-> 163
BETA ALUMINA	-> 596
BREAKDOWN	1195
BRONZE	->1029
	->1530
CHARGE MOTION	700
CHEMISORPTION	163
CHLORIDE	->1298
CONDUCTANCE	"
CONDUCTIVITY	1530
CONTAMINATION	700
	1195
CRYSTAL GROWTH	596
DECOMPOSITION	337
DENSITY	1298
DEVICE PROCESSING>	724
DIELECTRIC	163
	1195
DIFFUSION	163
DOPING	"
ELECTROREDUCTION	1029
FILM	1195
GETTERING	724
GLASS	"
HIGH PRESSURE	596
HIGH TEMPERATURE	163
HYDROGEN	1029
HYDROGEN PEROXIDE	"
LITHIUM	163
	1298

PRIMARY TERM / CO-TERM — PAGE NO.

SODIUM (CONTD)
LOWERING - - - - 1195
MANGANESE - - - - 1298
MELT - - - - - - "
MEMBRANE - - - - 596
MOBILE CHARGE - - 724
OXYGEN - - - - - 1029
PHOSPHOSILICATE - 724
PLATINUM - - - - 1029
POLARIZATION - - 700
POLYCRYSTALLINE - 163
POTASSIUM - - - - 1298
REMOVAL - - - - - 724
RUBIDIUM - - - - 1298
SILICON - - - - - 1195
SILICON DIOXIDE - 700
- 724
- 1195
SODIUM INDUCED - "
SODIUM ION - - - 1530
TOWER - - - - - - 337
TRACES - - - - - 1029
TUNGSTEN - - - - "
- - - - 1530
ZINC OXIDE - - - 163

SODIUM CHLORATE
ANODE BEHAVIOR -> 191
DENSITY - - - - - "
ELECTROCHEMICAL - "
HIGH CURRENT - - "
MILD - - - - - - "
POLISHING - - - - "
STEEL - - - - - - "

SODIUM CHLORIDE
ALLOY - - - - - ->1137
ALUMINUM - - - -> 983
ALUMINUM CHLORIDE> 212
983
ANODIZATION - - - "
AQUEOUS SOLUTION >1311
COPPER - - - - - 212
- - - - - 1137
CURVE - - - - - - "
ELECTRODE - - - - 983
ELECTROLYSIS - - 1311
FUSED - - - - - - 983
FUSED SALT - - - 212
IMPURITIES - - - 1311
ION - - - - - - - 983
IRON - - - - - - 212
MELT - - - - - - "
MERCURY - - - - - 1311
METAL ION - - - - 212
MOLTEN - - - - - 983
NICKEL - - - - - 1137
PASSIVITY - - - - "
PITTING - - - - - "
POLARIZATION - - "
POLAROGRAPHY - - 212
POTENTIAL - - - - 1137
POTENTIOSTATIC - "
SALT - - - - - - 983
SILVER - - - - - 212
SUBVALENT - - - - 983
SYSTEM - - - - - 212
VOLTAMMETRY - - - "

SODIUM FLUORIDE
LINEAR SWEEP - -> 86
LITHIUM FLUORIDE "
MOLTEN FLUORIDE - "
POTASSIUM - - - - "
THORIUM - - - - - "
URANIUM - - - - - "
VOLTAMMETRY - - - "

SODIUM HYDROXIDE
AMALGAN - - - - -> 340
- - - - -> 343
COMPARISON - - - "
CRUSHED - - - - - "
DECOMPOSITION - - 340
- - 343
GRAPHITE BED - - "
RATE - - - - - - 340
TOWER - - - - - - "
- - - - - - 343

SODIUM INDUCED
BARRIER HEIGHT ->1195
BREAKDOWN - - - - "
CONTAMINATION - - "
DIELECTRIC - - - "
FILM - - - - - - "
LOWERING - - - - "

SODIUM INDUCED (CONTD)
SILICON - - - - - 1195
SILICON DIOXIDE - "
SODIUM - - - - - "

SODIUM ION
ACETONITRILE - -> 881
BRONZE - - - - ->1530
CONDUCTIVITY - - "
DIETHYLFUMARATE - 881
DMSO - - - - - - "
ELECTROHYDRODIME. "
ION PAIRS - - - - "
REDUCTION - - - - "
SODIUM - - - - - 1530
TUNGSTEN - - - - "
VOLTAMMETRY - - - 881

SODIUM SILICATE
ANODE SPARK - - ->1402
DYSPROSIUM - - - "
ERBIUM - - - - - "
GADOLINIUM - - - "
HOLMIUM - - - - - "
SAMARIUM - - - - "
YTTERBIUM - - - - "
YTTRIUM - - - - - "

SODIUM SULFATE
ELECTROCAPILLARY >1417
LEAD ELECTRODE - "
MENISCUS - - - - "

SOFT JUNCTIONS
DEFECTS - - - - -> 969
GETTERING - - - -> 444
GLASS - - - - - - "
INDUCED - - - - - 969
ION SCATTERING - 444
PHOSPHOSILICATE - "
PROCESS - - - - - 969
SILICON - - - - - "

SOLAR CELL
CARRIER - - - - -> 973
DIFFUSION - - - - "
MINORITY - - - - "
PHOTOVOLTAGE - - "
SILICON - - - - - "
SURFACE - - - - - "

SOLID
ALUMINUM - - - ->1239
BROMIDE - - - - - "
CALCIA STABILIZED> 506
ELECTRODE - - - - "
ELECTROLYTE - - - "
GALLIUM - - - - - "
GALLIUM SESQUIOX. "
KINETICS - - - - "
OXYGEN - - - - - "
TRANSFER - - - - "
VAPOR PRESSURE - 1239
ZIRCONIA - - - - 506

SOLID ELECTROLYTE
BETA ALUMINA - ->1603
CAPACITANCE - - -> 632
- - -> 639
- - ->1318
CHROMIUM OXIDE -> 711
COPPER - - - - - 1318
COPPER CHLORIDE - "
DIFFUSION - - - - "
DOUBLE LAYER - - 632
- - 1318
ELECTRODE - - - - 632
- - - - 639
ELECTROLYTE CELL 632
639
EMF - - - - - - - 1603
FORMATION - - - - 711
FREE ENERGY - - - "
GOLD - - - - - - 1318
GRAPHITE - - - - 632
- - - - 639
INTERFACE - - - - "
LOW TEMPERATURE - 1318
PLATINUM - - - - 632
ROOM TEMPERATURE "
ROUGHENING - - - 639
SILVER HALIDES - 632
- 639
SINGLE CRYSTAL - 1318
SOLID STATE - - - 639
WETTING - - - - - "

SOLID SOLUTION
ALUMINUM - - - -> 327
- - - ->1662
ALUMINUM SELINIDE 327
ANTIMONIDE - - - 1662
ARSENIDE - - - - "
COPPER - - - - - 327
GALLIUM - - - - - 1662
GROUP II-VI - - - "
GROUP III-V - - - "
INDIUM - - - - - "
LATTICE - - - - - "
MISCIBILITY GAP - "
PARAMETER - - - - "
PHOSPHIDE - - - - "
PSEUDOBINARY - - "
SEMICONDUCTOR - - "
ZINC SELINIDE - - 327
ZINC SULFIDE - - "

SOLID STATE
CALCIA STABILIZED> 793
CAPACITANCE - - -> 639
CONDUCTION - - - 793
COULOMETRY - - - "
ELECTRODE - - - - 639
ELECTROLYTE CELL "
GRAPHITE - - - - "
HOLE - - - - - - 793
INTERFACE - - - - 639
OXYGEN - - - - - 793
PERMEATION - - - "
ROUGHENING - - - 639
SILVER HALIDES - "
SOLID ELECTROLYTE "
TITRATION - - - - 793
WETTING - - - - - 639
WUSTITE - - - - - 793
ZIRCONIA - - - - "

SOLICIFICATION
BEHAVIOR - - - -> 448
CONVERGING - - - "
INDIUM ANTIMONIDE "
INTERFACE - - - - "
PRESSURE INDUCED "
SEGREGATION - - - "
STATIONARY - - - "
VERTICAL ZONE - - "

SOLIDUS
CONCENTRATION - -> 153
CRYSTAL GROWTH - "
GALLIUM - - - - - "
GAP - - - - - - - "
PHOSPHORUS - - - "
VACANCY - - - - - "

SOLUBILITY
ACETONE - - - - ->1584
CONSTANT - - - - "
CONTRAST - - - ->1669
DEVELOPER - - - - "
DOPING - - - - ->1350
ELECTRON BEAM - - 1669
ELECTRON RESIST - "
ENCAPSULATION - - 1350
ENHANCEMENT - - - "
FORMATION - - - - 1584
FUNCTION - - - - 1669
GOLD - - - - - - 1350
LITHOGRAPHY - - - 1669
METHACRYLATE - - "
MIXTURE - - - - - 1584
PMMA - - - - - - 1669
POLYMETHYL - - - "
PRODUCT - - - - - 1584
RATE - - - - - - 1669
SILICON - - - - - 1350
SILVER HALIDES - 1584
WATER - - - - - - "

SOLUTION
ALKALINE - - - -> 605
ALUMINUM - - - ->1271
AMMONIUM - - - -> 977
ANODE - - - - - - 1271
ANODE DISINTEGRA.>1604
ANODE DISINTERGR.> 7
ANODE DISSOLUTION "
605
ANOMALOUS VALENCY 7
ASYMPTOTIC - - -> 521
BEHAVIOR - - - ->1460
BENZOTRIAZOLE - - 605
BERYLLIUM - - - - 7
- - - - 1604

SOLUTION (CONTD)
BROMIDE - - - - - 977
CARBONATE - - - -> 83
CHARACTERISTIC - 7
CHARACTERISTICS - 1604
CHLORIDE - - - - 605
- - - - 1271
CONDUCTANCE - - - 977
CORROSION - - - - 605
CRYSTAL - - - - ->1454
DIMETHYLFORMAMIDE 977
DISCHARGE - - - - 1460
ELECTRODE - - - - 521
ELECTROLYTE - - - 977
- - - 1460
ELECTRON - - - - 7
- - - - 1454
EMF - - - - - - - 83
IMPEDANCE - - - - 521
INHIBITION - - - 605
IRON - - - - - - "
ISOTHIOCYANATE - 977
LEAD ACID - - - - 1454
LEAD SULFATE - - "
LITHIUM CELL - - 1460
LITHIUM ION - - - 83
MEASUREMENT - - - "
MICROSCOPE - - - 7
MICROSCOPY - - - 1454
MOLYBDENUM - - - 1460
NICKEL - - - - - 977
NITRATE - - - - - 1271
NONAQUEOUS - - - 7
- - - 977
- - - 1460
- - - 1604
NUMBER - - - - - 83
PITTING - - - - - 1271
POLARIZATION - - 7
- - 1604
POTASSIUM - - - - 977
PRECIPITATION - - 1454
PROPYLENE - - - - 83
ROTATING DISK - - 521
SCANNING - - - - 7
- - - - 1454
STRAINING - - - - 1271
STRUCTURE - - - - 1454
TETRABUTYL - - - 977
TRANSFERENCE - - 83
VISCOSITY - - - - 977
WARBURG - - - - - 521

SOLVATED
ACTIVATION - - -> 459
AMMONIA - - - - - "
CONCENTRATION - - "
DECOMPOSITION - - "
ELECTRON - - - - "
ENTROPY - - - - - "
LITHIUM - - - - - "

SOLVENT
APROTIC - - - - -> 518
BATTERY - - - - -> 315
CARBONATE - - - - "
CHEMILUMINESCENCE>1178
DIMETHYLFORMAMIDE 518
ELECTROANALYSIS - 1178
ELECTROCHEMISTRY 518
ELECTRODE - - - - "
ELECTROGENERATE - 1178
ENERGY DEFICIENT "
GALVANIC CELL - - 315
HYDROGEN - - - - 518
LITHIUM ANODE - - 315
LITHIUM BROMINE - "
LUMINESCENCE - - 1178
NONAQUEOUS - - - 315
- - - 1178
PROPYLENE - - - - 315
REVERSIBLE CELL - 518
SECONDARY - - - - 315
THALLIUM - - - - 518
VOLTAMMETRY - - - 1178

SOLVENTS
BORON - - - - - -> 593
CONTAMINATION - - "
MICROANALYSIS - - "
NUCLEAR - - - - - "
OXYGEN - - - - - "
SURFACE - - - - - "

SOURCE
ALLOY - - - - - ->1129
ALUMINUM - - - - "

PRIMARY TERM / CO-TERM	PAGE NO.
SOURCE (CONTD)	
AMMONIA ->	962
ANTIMONY ->	967
BEHAVIOR	962
CORROSION	1129
DIODES	962
DOPING	967
EMITTING	962
EPITAXY	"
	967
GAP	962
HISTOPATHOLOGY	1129
IMPLANTABLE	"
IMPURITY	962
INVITRO	1129
INVIVO	"
LIGHT	962
LIQUID PHASE	"
MAGNESIUM	1129
METALORGANICS	967
NITROGEN DOPING	962
POWER	1129
SAPPHIRE	967
SILICON	"
TRIMETHYLSTIBINE	"
ZINC	1129
SPACED	
CLOSELY ->	1124
GAP	"
METALLIZATION	"
PATTERN	"
SELF ALIGNED	"
SPALLING	
ALLOY ->	800
ALUMINUM	"
COATING	"
DEGRADATION	"
DEPLETION	"
DIFFUSION	"
NICKEL	"
OXIDATION	"
SUPERALLOY	"
SPARKLESS	
AUTOMATIC ->	251
ELECTRODE	"
GAS	"
HYDROGEN	"
PUMP	"
SPECIES	
DEHYDROPYRIDINES	1033
DIMERIZATION	"
ELECTROCHEMISTRY	"
METHYL	"
MONONUCLEOTIDE	"
NICOTINAMIDE	"
PYRIDINIUM	"
REDOX	"
SPECIFIC	
CONSTANT ->	887
COPPER	"
CORROSION	"
CRYSTAL ->	1674
ELECTROLESS	887
EXISTENCE	1674
HEAT	"
INDIUM	"
MEASUREMENT	"
MIXED POTENTIAL	887
MONOSELENIDE	1674
PARTIAL PROCESS	887
PHASE TRANSITION	1674
PLATING	887
RATE	"
SEMICONDUCTOR	1674
STANDARD	887
STRUCTURE	1674
XRAY	"
SPECTRA	
BARRIER ->	1066
CAPACITANCE	"
EPITAXY	"
GAAS	"
HALL EFFECT	"
LAYER	"
MEASUREMENT	"
MOBILITY	"
PHOTOLUMINESCENCE	"
SCHOTTKY	"
SPECTRAL	
COLOR RENDITION ->	407
SPECTRAL (CONTD)	
DISTRIBUTION	407
LAMPS	"
MERCURY VAPOR	"
OPTIMIZED	"
PHOSPHORS	"
POWER	"
SPECTROGRAPHY	
CAPACITY ->	1444
DOUBLE LAYER	"
POTASSIUM HYDROX.	"
SILVER	"
SWEEP RATE	"
TEMPERATURE	"
TRIANGLE	"
VOLTAMMETRY	"
SPECTROMETRY	
BEAM ->	899
DEPOSITION	"
MOLECULE	"
PYROLYSIS	"
SAMPLE	"
SILANE	"
SILICON	"
SPECTROSCOPY	
ADSORPTION ->	474
->	676
AUGER ->	34
BATTERY CELL ->	1
BETA ALUMINA	"
BOROSILICATE	676
CATHODE	1
CHLORINE	34
COMPOSITION	"
DEPOSIT	676
DEPOSITION	474
DIFFUSION	676
ELECTRODE	474
GALVANIC CELL	1
GLASS FILM	676
GOLD EVAPORATED	474
IRON DOPED	1
IRON SPINEL	"
ISOTHERM	474
LEAD	"
MOSS BAUER	1
OXIDATION ->	673
OXYGEN	34
PLATINUM ANODE	"
REFLECTANCE	474
SILANOL	676
SINGLE CRYSTAL	474
SURFACE	34
	673
UNDERPOTENTIAL	474
VAPOR	676
WATER	"
X RAY	673
SPHERE	
CURRENT DISTRIBU.	241
LIMITING CURRENT	"
MASS TRANSFER	"
ROTATING	"
SPIN ON	
AUGER ->	827
DENSIFICATION	"
ELECTRON SPECTRO.	"
GLASS FILM	"
OXYGEN	"
RATIO	"
SILICON	"
SILICON DIOXIDE	"
STOICHIOMETRY	"
SPINEL	
ALUMINATE ->	571
BERYLLIA ->	1240
CERAMIC OXIDE	"
CRYSTAL	"
DAMAGE	"
EPITAXY	571
GALLIUM ARSENIDE	"
GARNET	1240
GROWTH	571
HARDNESS	1240
HETEROEPITAXY ->	1345
INSULATOR	"
MAGNESIUM	571
POLISHING	1240
PREPARATION	"
SAPPHIRE	"
	1345
SPINEL (CONTD)	
SEMICONDUCTOR	1345
SILICON	"
SURFACE	1240
THIN FILM	1345
SPRAY	
AEROSOL ->	484
CHARGE ->	591
DENSITY	"
DEPOSIT	484
DIELECTRIC	591
ELECTRET	"
ELECTRICAL	484
FEP	591
FORMALDEHYDE	484
HOMOCHARGE	591
HYDRAZINE	484
INSERT	591
PLATING	484
RESISTIVITY	"
SILVER	"
SURFACE	591
TEFLON	"
THERMOELECTRET	"
SPREADING	
APPLICATION ->	422
CIRCUIT	"
DEVICE	"
EPITAXIAL	"
INTEGRATED	"
MEASUREMENT	"
RESISTANCE	"
RESISTIVITY	"
SILICON	"
SPUTTERING	
AMORPHOUSNESS ->	394
ANODIZATION	"
ARGON ->	558
BACKSPUTTERING	"
CONTAMINANT ->	1617
DEPTH PROFILE	"
FILM	558
IMPLANTATION	"
ION	"
	1617
MASS SPECTROMETRY	"
METALLIZATION	558
MICROCIRCUIT	1617
MICROPROBE	"
SECONDARY	"
SILICON DIOXIDE	558
SILVER CHLORIDE	1617
SURFACE	"
THIN FILM	394
TIN	"
TRAPPING	558
STABILITY	
CALCIUM ->	534
CARBONATE ION ->	885
CHARGE ->	907
DECOMPOSITION ->	1328
DICALCIUM	534
DIELECTRIC	907
ELECTROCHEMISTRY	534
ELECTROLYSIS	1328
EMF	885
FUSED NITRATES	"
GALVANIC CELL	534
GATE	907
GOLD ->	1076
HIGH TEMPERATURE	1328
INSULATOR	907
INTERFACE	1328
MASS TRANSPORT	"
METALLIZATION	1076
MICROWAVE	"
MONOCALCIUM	534
NITRIDE	907
OXIDE	"
OXIDE ION	885
OXYGEN ELECTRODE	"
RELIABILITY	1076
SILICON	907
SILICON DIOXIDE	1328
STANNATE	534
TANTALUM	1076
THERMAL	"
TRANSISTOR	"
VAPORIZATION	534
STAINLESS STEEL	
CHROMIUM ->	1192
CORROSION ->	1190
STAINLESS STEEL (CONTD)	
CORROSION	1192
CRACK	1190
EQUILIBRIA ->	467
FRACTOGRAPHY	1190
INCLUSION	467
INITIATION	"
IRON	1192
MANGANESE	467
MOLYBDENUM	1192
MORPHOLOGY	1190
PITTING	467
	1192
POTENTIAL PH	467
RESISTANCE	1192
STRESS	1190
STRIATION	"
SULFIDE	467
SULFURIC ACID	1190
TEMPERATURE	1192
TRANSGRANULAR	1190
STANDARD	
ACTIVITY ->	884
AMALGAMS	"
COEFFICIENT	"
CONSTANT ->	887
COPPER	"
COPPER ELECTRODE	18
CORROSION	887
DILUTE	884
DIMETHYLFORMAMIDE	79
ELECTRODE	"
ELECTROLESS	887
LEAD CHLORIDE	79
MEASUREMENT	"
MIXED POTENTIAL	887
PARTIAL PROCESS	"
PLATING	"
POTENTIAL	18
	79
	884
RATE	887
SINGLE CRYSTAL	18
SPECIFIC	887
THALLIUM	884
TITANIUM CHLORIDE	79
STANNATE	
CALCIUM ->	534
DICALCIUM	"
ELECTROCHEMISTRY	"
GALVANIC CELL	"
MONOCALCIUM	"
STABILITY	"
VAPORIZATION	"
STANNOUS CHLORIDE	
CATALYST ->	738
DIELECTRIC	"
ELECTRON MICROSC.	"
MIXED	"
PALLADIUM CHLORI.	"
PLATING	"
SUBSTRATE	"
STATIONARY	
BEHAVIOR ->	448
CONVERGING	"
INDIUM ANTIMONIDE	"
INTERFACE	"
PRESSURE INDUCED	"
SEGREGATION	"
SOLIDIFICATION	"
VERTICAL ZONE	"
STEADY STATE	
CAPACITOR ->	1219
CARRIER	"
DEEP	"
DEPLETION	"
DIFFUSION	"
LENGTH	"
LIFETIME	"
MINORITY	"
MOS	"
SILICON	"
STEEL	
ADSORPTION ->	609
ANODE BEHAVIOR ->	191
ARSENIC	609
CHROME COATING ->	29
DELAMINATION	"
DENSITY	191
DEPOSITION ->	1592
DISSOLUTION	"

PRIMARY TERM / CO-TERM — PAGE NO.

STEEL (CONTD)
ELECTROCHEMICAL - 191
ELECTRODE - - - - 1592
ENTRY - - - - - - 609
HEMISPHERICAL - - 1592
HIGH CURRENT - - 191
HYDROGEN - - - - 609
IRON OXIDE - - - 1592
LACQUER FILM - - 29
MILD - - - - - - 191
- - - - - - 1592
ORGANIC - - - - - 29
PERMEATION - - - 609
POLISHING - - - - 191
POTENTIAL - - - - 609
RING - - - - - - 1592
ROTATING - - - - "
SODIUM CHLORATE - 191
SULFATE SOLUTION 1592
UNDERCUTTING - - 29

STEELS
CARBON - - - - -> 527
DEPOSITION - - - "
IRON - - - - - - "
IRON OXIDE - - - "
PASSIVATION - - - "
PLATINUM - - - - "
POTENTIOSTATIC - "
RING ELECTRODE - "
TRANSIENT - - - - "

STILBENES
CHLOROSTILBENES ->1667
IMAGING - - - - - "
IRRADIATION - - - "
LIQUID CRYSTAL - "
NEMATIC - - - - - "
ULTRAVIOLET - - - "

STOICHIOMETRY
AUGER - - - - - -> 827
CRYSTAL GROWTH ->1516
DENSIFICATION - - 827
DOPING - - - - - 1516
ELECTROLUMINESCE. "
ELECTRON SPECTRO. 827
EPITAXY - - - - - 1516
GAS PHASE - - - - "
GLASS FILM - - - 827
MORPHOLOGY - - - 1516
OXYGEN - - - - - 827
RATIO - - - - - - "
SILICON - - - - - "
SILICON DIOXIDE - "
SPIN ON - - - - - "
VAPOR PHASE - - - 1516

STRAINING
ALUMINUM - - - ->1271
ANODE - - - - - - "
CHLORIDE - - - - "
NITRATE - - - - - "
PITTING - - - - - "
SOLUTION - - - - "

STRESS
BOROSILICATE - ->1098
CORROSION - - - ->1190
CRACK - - - - - - "
FRACTOGRAPHY - - "
GLASS FILM - - - 1098
GLASS METAL - - - "
HARDNESS - - - - "
MORPHOLOGY - - - 1190
SINTERING - - - - 1098
STAINLESS STEEL - 1190
STRIATION - - - - "
SULFURIC ACID - - "
TRANSGRANULAR - - "
VICKERS - - - - - 1098

STRIATION
CORROSION - - - ->1190
CRACK - - - - - - "
FRACTOGRAPHY - - "
MORPHOLOGY - - - "
STAINLESS STEEL - "
STRESS - - - - - "
SULFURIC ACID - - "
TRANSGRANULAR - - "

STRONTIUM
ALUMINUM - - - -> 137
BARIUM - - - - - "
CALCIUM - - - - - "
EUROPIUM - - - - "

STRONTIUM (CONTD)
GALLIUM - - - - - 137
PHOTOLUMINESCENCE "
SEMICONDUCTOR - - "
SYNTHESIS - - - - "
YTTERBIUM - - - - "

STRUCTURE
ADSORPTION - - ->1167
ALKALINE - - - ->1475
BANDGAP - - - - ->1673
BORIDES - - - - -> 846
BORON - - - - - - "
CESIUM - - - - -> 727
CESIUM HYDROXIDE > 17
CHEMICAL - - - - 846
- - - - 1673
COMPOUND - - - - "
CONTRAST - - - ->1202
CRYSTAL - - - - ->1454
- - - - - 1475
- - - - - 1673
- - - - ->1674
DIFFUSION - - - ->1538
DIODE - - - - - - 1202
DIVALENT - - - - 1475
EARTH - - - - - - "
ELECTROCRYSTALLI. 1167
ELECTRODE - - - - 727
- - - - 1167
ELECTROLYTE - - - 727
ELECTRON - - - - 1454
- - - - 1538
ELEMENTAL - - - - 846
EUROPIUM - - - - 1475
EXISTENCE - - - - 1674
FILM - - - - - - 1167
GALLIUM NITRIDE - 1202
GERMANIUM - - - - 1673
HEAT - - - - - - 1674
HETEROEXPITAXIAL 1202
HYDROXIDE - - - - 727
INDIUM - - - - - 1674
ION - - - - - - 1167
JUNCTION - - - - 1202
KINETICS - - - - 1167
LEAD ACID - - - - 1454
LEAD SULFATE - - "
LIGHT EMISSION - 1202
LUMINESCENCE - - 1475
MEASUREMENT - - - 1674
METAL - - - - - - 1167
MICROSCOPY - - - 17
- - - 1454
- - - 1538
MICROSTRUCTURE - 1202
MODIFICATION - - 846
MONOLAYER - - - - 1167
MONOSELENIDE - - 1674
NITRIDE - - - - - 1673
NONMETAL - - - - 846
OPTICAL SPECTRA - 1475
PALLADIUM - - - - 1538
PARTICLE SIZE - - 17
PHASE TRANSITION 1674
POTASSIUM HYDROX. 17
PRECIPITATION - - 1454
PROFILE - - - - - 1202
PROPERTIES - - - 1673
REDUCTION - - - - 727
SCANNING - - - - 1454
SEMICONDUCTOR - - 1674
SILICIDE - - - - 1538
SILVER OXIDE - - 17
- - 727
SOLUTION - - - - 1454
SPECIFIC - - - - 1674
SULFATES - - - - 1475
SYNTHESIS - - - - 1673
TERNARY - - - - - "
TETRAGONAL - - - 846
THERMODYNAMICS - 1167
VAPOR DEPOSITION 846
1202
1673
VOLTAGE - - - - - 1202
XRAY - - - - - - 1674
ZINC - - - - - - 1673

STRUCTURE CONVER.
CATHODOCHROMICS -> 815
METHOD - - - - - "
PHOTOCHROMICS - - "
SODALITE - - - - "
SYNTHESIS - - - - "

SUBMICRON LINE
ACOUSTIC WAVE - ->1503
CONTACT PRINT - - "
MASK - - - - - - "
PHOTO RESIST - - "
PHOTOLITHOGRAPHY "

SUBSTITUENT
DETERMINATION - ->1462
ELECTRODE - - - - "
HAMMETT - - - - - "
HYDROGEN - - - - "
SIGMA - - - - - - "

SUBSTRATE
ALUMINUM - - - -> 430
ANODE - - - - - ->1264
BORON ARSENIDE -> 412
CATALYST - - - -> 738
- - - - 1264
CONDUCTION - - - 412
COPPER - - - - -> 289
DECOMPOSITION - - 412
DIELECTRIC - - - 738
DIFFRACTION - - - 430
DISPLACEMENT - - 289
ELECTRON MICROSC. 738
FUEL CELL - - - - 1264
HYDRAZINE - - - - "
IMPERFECTION - - 289
MIXED - - - - - - 738
NICKEL BORIDE - - 1264
PALLADIUM CHLORI. 738
PLATING - - - - - "
PREPARATION - - - 412
PROPERTY - - - - "
REACTION - - - - 430
SEMICONDUCTOR - - 412
SILICA - - - - - 430
SILICON - - - - - 289
STANNOUS CHLORIDE 738
TOPOGRAPHY - - - 289
X RAY - - - - - - "

SUBVALENT
ALUMINUM - - - -> 983
ALUMINUM CHLORIDE "
ANODIZATION - - - "
ELECTRODE - - - - "
FUSED - - - - - - "
ION - - - - - - - "
MOLTEN - - - - - "
SALT - - - - - - "
SODIUM CHLORIDE - "

SULFATE
ANODE OXIDATION ->1152
FILM - - - - - - "
NEUTRAL - - - - - "
NICKEL - - - - - "
NICKEL OXIDE - - "
PASSIVITY - - - - "

SULFATE SOLUTION
DEPOSITION - - ->1592
DISSOLUTION - - - "
ELECTRODE - - - - "
HEMISPHERICAL - - "
IRON OXIDE - - - "
MILD - - - - - - "
RING - - - - - - "
ROTATING - - - - "
STEEL - - - - - - "

SULFATES
ALKALINE - - - ->1475
CRYSTAL - - - - - "
DIVALENT - - - - "
EARTH - - - - - - "
EUROPIUM - - - - "
LUMINESCENCE - - "
OPTICAL SPECTRA - "
STRUCTURE - - - - "

SULFIDATION
ALLOY - - - - - -> 889
ATMOSPHERE - - - "
COBALT IRON - - - "
HYDROGEN SULFIDE "
KINETICS - - - - "
PARABOLIC - - - - "

SULFIDE
ALUMINUM - - - -> 829
CADMIUM - - - - -> 965
COPPER - - - - - 829
DEPOSITION - - - 965

SULFIDE (CONTD)
DOPING - - - - - 829
ELECTRICAL - - - "
EPITAXY - - - - - 965
EQUILIBRIA - - -> 467
HETEROEPITAXY - - 965
HIGH TEMPERATURE > 665
INCLUSION - - - - 467
INITIATION - - - "
IRON - - - - - - 665
IRON PYRITE - - - "
IRON SULFIDE - - "
LITHIUM - - - - - "
MANGANESE - - - - 467
MOLTEN SALT - - - 665
OPTICAL - - - - - 829
PHOTOSENSITIVITY 965
PITTING - - - - - 467
POTENTIAL PH - - "
PROPERTIES - - - 829
SAPPHIRE - - - - 965
SECONDARY CELL - 665
SELENIDE - - - - 965
STAINLESS STEEL - 467
VAPOR - - - - - - 965
VAPOR PHASE - - - "

SULFONE
ELECTRON BEAM - ->1620
ION MILLABLE - - "
POLYSTYRENE - - - "
POSITIVE - - - - "
RESIST - - - - - "

SULFUR
ELECTROCATALYST ->1125
FORMALDEHYDE - - "
KINETICS - - - - "
MECHANISM - - - - "
MOLYBDENUM - - - "
OXIDATION - - - - "
REACTION - - - - "

SULFURIC ACID
ANODE FILM - - ->1186
CATALYSIS - - - - "
CORROSION - - - ->1190
CRACK - - - - - - "
ELLIPSOMETRY - - 1186
EVOLUTION - - - - "
FRACTOGRAPHY - - 1190
GALVANOSTATIC - - 1186
MORPHOLOGY - - - 1190
OXYGEN - - - - - 1186
PLATINUM - - - - "
REACTION - - - - "
STAINLESS STEEL - 1190
STRESS - - - - - "
STRIATION - - - - "
THICKNESS - - - - 1186
TRANSGRANULAR - - 1190

SUPERALLOY
ALLOY - - - - - -> 800
ALUMINUM - - - - "
COATING - - - - - "
DEGRADATION - - - "
DEPLETION - - - - "
DIFFUSION - - - - "
NICKEL - - - - - "
OXIDATION - - - - "
SPALLING - - - - "

SUPERCOOLING
CRYSTAL GROWTH -> 380
CZOCHRALSKI - - - "
DOPED GERMANIUM - "
INSTABILITY - - - "
OSCILLATORY - - - "

SUPPLY
CHARGER - - - - ->1134
CONTROLLER - - - "
ELECTROCHEMISTRY "
HIGH POWER - - - "
PROPULSION - - - "
SIMULATOR - - - - "

SURFACE
ADSORPTION - - -> 848
- - - ->1570
ALUMINA - - - - -> 107
ANALYZER - - - -> 689
ANODE OXIDATION -> 757
AUGER - - - - - -> 34
- - - - - - -> 310
BERYLLIA - - - ->1240

PRIMARY TERM CO-TERM	PAGE NO.
SURFACE (CONTD)	
BOND	107
BONDING	"
BORON	-> 593
CARBON	-> 146
CARRIER	-> 973
CERAMIC OXIDE	1240
CHARACTERIZATION	> 669
CHARGE	-> 591
CHARGING	757
CHLORINE	34
	848
CIRCUIT	146
CLEANING	310
COMPOSITION	34
CONDUCTANCE	1570
CONTACT ANGLE	669
CONTAMINANT	->1617
CONTAMINATION	146
	593
	-> 790
COPPER	107
CRYSTAL	1240
DAMAGE	"
DEFECT	689
DENSITY	591
DEPTH PROFILE	1617
DIELECTRIC	591
DIFFUSION	973
DIMETHYLANILINE	757
DISCHARGING	"
DOPING	146
ELECTRET	591
ELECTRODE	757
	1570
ELECTROLESS	107
ELECTRON SPECTRO.	310
FEP	591
FLUORINE	790
GARNET	1240
GERMANIUM	310
GOLD REFRACTORY	790
HARDNESS	1240
HELIUM	689
HOMOCHARGE	591
INSERT	"
INTEGRATED	146
ION	790
	1617
LASER	689
MASS SPECTROMETRY	1617
MEASUREMENT	669
	1570
METALLIZATION	107
	790
MICROANALYSIS	593
MICROCIRCUIT	1617
MICROPROBE	"
MINORITY	973
MOLTEN ALKALI	107
MORPHOLOGY	757
NITROGEN	689
NUCLEAR	593
OXIDATION	-> 673
OXYGEN	34
	593
PHOTOVOLTAGE	973
PLATINUM ANODE	34
POLISHING	1240
PREPARATION	"
RESIDUE	146
RETENTION	790
SAPPHIRE	1240
SECONDARY	1617
SILICON	146
	689
	790
	973
SILICON DIOXIDE	669
SILVER	757
SILVER CHLORIDE	"
	1617
SLICE	689
SOLAR CELL	973
SOLVENTS	593
SPECTROSCOPY	34
	673
SPINEL	1240
SPRAY	591
SPUTTERING	1617
TEFLON	591
THERMAL	669
THERMOELECTRET	591
THIN FILM	1570
TITANIUM	848
TRANSISTOR	790
X RAY	673

PRIMARY TERM CO-TERM	PAGE NO.
SURFACE ANALYSIS	
CONTAMINANTS	-> 172
DETECTION	"
MEV	"
SCATTERING	"
SENSITIVITY	"
SURFACE AREA	
ADSORPTION	-> 764
ELECTROCHEMISTRY	"
GALVANIC CELL	"
INSTRUMENT	"
PARTICLE SIZE	"
SURFACE CHARGE	
ANOMALOUS	->1677
BORON	"
DENSITY	"
DIELECTRIC	"
DIFFUSION	"
EFFECT	"
ELECTRETS	"
INSERT	"
NITRIDE	"
PLANAR	"
SILICON	"
SURFACE GAIN	
ALUMINUM OXIDE	->1465
ANNEALING	"
ANODE FILM	"
ELECTROETCH	"
TRANSFORMATION	"
SURFACE OXIDE	
ANODE	-> 749
CARBON	"
CHLORINE ELECTRO.	"
GLASSLIKE	"
GRAPHITE	"
OXYGEN ELECTRODE	"
PYROLYSIS	"
SURFACE PROCESS	
DOUBLE LAYER	->1596
ELLIPSOMETRY	"
FORMATION	"
GOLD	"
HYSTERESIS	"
OXIDE FILM	"
PLATINUM	"
REDUCTION	"
REFLECTANCE	"
SURFACE STATE	
HYDROGEN	-> 784
IMPLANTATION	"
INTERFACE	"
MOS STRUCTURE	"
OXYGEN	"
SILICON	"
SILICON DIOXIDE	"
SURFACE TENSION	
BINARY	-> 500
COULOMBIC	"
INTERACTION	"
LITHIUM CHLORIDE	"
MOLTEN SALT	"
POSTASSIUM CHLOR.	"
SWEEP	
CAPACITY	-> 512
DOUBLE LAYER	"
ELECTRODE	"
NICKEL	"
POROUS	"
POTASSIUM HYDROX.	"
TRIANGULAR	"
VOLTAGE	"
SWEEP RATE	
CAPACITY	->1444
DOUBLE LAYER	"
POTASSIUM HYDROX.	"
SILVER	"
SPECTROGRAPHY	"
TEMPERATURE	"
TRIANGLE	"
VOLTAMMETRY	"
SYNTHESIS	
ALUMINUM	-> 137
ANODE DISSOLUTION	> 249
BANDGAP	->1673
BARIUM	137
CALCIUM	"

PRIMARY TERM CO-TERM	PAGE NO.
SYNTHESIS (CONTD)	
CATHODOCHROMICS	-> 815
CHEMICAL	1673
COMPOUND	"
CRYSTAL	"
ELECTROCHEMICAL	249
EUROPIUM	137
FERRATE	249
GALLIUM	137
GERMANIUM	1673
IRON (VI)	249
METHOD	815
NITRIDE	1673
PHOTOCHROMICS	815
PHOTOLUMINESCENCE	137
POTENTIOSTATIC	249
PROPERTIES	1673
SEMICONDUCTOR	137
SODALITE	815
STRONTIUM	137
STRUCTURE	1673
STRUCTURE CONVER.	815
TERNARY	1673
VAPOR DEPOSITION	"
YTTERBIUM	137
ZINC	1673
SYSTEM	
ACTIVITY	-> 543
ALUMINUM CHLORIDE	> 212
ARSENIC	->1634
CHROMIUM	543
COMPOUND	1634
COPPER	212
DOPING	1634
FUSED SALT	212
GALLIUM	1634
GAS	-> 13
HYDROGEN	"
IRON	212
ISOTHERMS	1634
LEAD ACID	13
LEAD CALCIUM	"
LIQUIDUS	1634
MELT	212
METAL	543
METAL ION	212
NICKEL	543
OXYGEN	13
	543
PHOSPHORUS	1634
POLAROGRAPHY	212
RECOMBINATION	13
SEMICONDUCTOR	1634
SILICON	"
SILVER	212
SODIUM CHLORIDE	"
TERNARY	1634
VOLTAMMETRY	212
TAFEL	
CARBON OXIDE	->1289
CHLORINE ELECTRO.	"
GRAPHITE ANODE	"
TAFEL SLOPE	
AMMONIA	-> 230
COEFFICIENT	"
EVOLUTION	"
EXCHANGE CURRENT	"
HYDROGEN	"
LIQUID	"
NITROGEN	"
OVERVOLTAGE	"
TRANSFER	"
TANTALUM	
ANODE	-> 550
ANODE OXIDATION	-> 195
	-> 865
BACKSCATTERING	550
BEHAVIOR	865
BUFFERED	195
CONCENTRATION	"
ELLIPSOMETRY	-> 263
	-> 805
GOLD	->1076
HYDROGEN FLUORIDE	195
ION	550
ION IMPLANT	865
ION IMPLANTATION	195
MARKER	865
METALLIZATION	1076
MICROWAVE	"
NIOBIUM	805
NOBEL GASES	865
OXIDATION	263

PRIMARY TERM CO-TERM	PAGE NO.
TANTALUM (CONTD)	
OXIDATION	805
OXIDE	550
OXIDE DISSOLUTION	195
PLASMA	263
	805
PROFILE	195
REFRACTIVE INDEX	805
RELIABILITY	1076
RUTHERFORD	550
SCATTERING	"
SILICON	"
STABILITY	1076
THERMAL	"
THIN FILM	550
TRANSISTOR	1076
TANTALUM CARBIDE	
AC DISCHARGE	-> 714
DEPOSITION	"
FIBER GROWTH	"
VAPOR	"
TANTALUM OXIDE	
ANODE	-> 45
ANODE OXIDATION	-> 860
DISSOLUTION	"
IMPLANT	45
IMPURITY	860
ION	45
ION IMPLANT	860
RANGE PROFILE	45
TEFLON	
CHARGE	-> 591
DENSITY	"
DIELECTRIC	"
ELECTRET	"
FEP	"
HOMOCHARGE	"
INSERT	"
SPRAY	"
SURFACE	"
THERMOELECTRET	"
TELEVISION	
ARRANGEMENT	-> 894
CATHODOLUMINESCE.	"
CRT	"
DISTRIBUTION	"
PARTICLE	"
PHOSPHOR	"
SIZE	"
TELLURIDE	
ANALYSIS	->1366
ANTIMONY	->1523
CADMIUM	1366
CHALCOGENIDES	1523
CRYSTAL GROWTH	1366
DISTRIBUTION	"
DOPING	1523
INFRARED DEVICE	"
JUNCTION	"
LEAD	"
TEMPERATURE	1366
TERNARIES	1523
TIN	"
TRAVELING HEATER	1366
TEMPERATURE	
ANALYSIS	->1366
BERYLLIUM	->1429
CADMIUM	1366
CAPACITY	->1444
CERIUM DIOXIDE	-> 126
	->1198
	->1676
CHLORATE CELL	-> 70
	->1606
CHLORINE	70
CHROMIUM	->1192
CHRONOPOTENTIONE.	1429
COMMENTS	1676
COMPOSITION	126
COMPOSITIONAL	1676
CONCENTRATION	-> 132
CONDUCTIVITY	126
	1198
	1676
COPPER	-> 651
CORROSION	"
	1192
CRYSTAL GROWTH	1366
CURRENT	70
	1606
CURRENT DENSITY	70

PRIMARY TERM / CO-TERM — PAGE NO.

TEMPERATURE (CONTD)
CURRENT DENSITY - 1606
CYCLIC - - - - - 651
DEPENDENCE - - - 126
- - - 132
- - - 1198
- - - 1429
- - - 1676
DEPLETION - - - - 1429
DIFFUSION - - - - 132
DISTRIBUTION - - "
- - 1366
DOPED OXIDE - - - 132
DOUBLE LAYER - - 1444
EFFECT - - - - - 70
- - - - - 1606
EFFICIENCY - - - 70
- - - 1606
ELECTRICAL - - - 1676
ELECTROCRYSTALLI. 1606
ELECTROMIGRATION 1429
ELECTRON MOBILITY 126
ELEVATED - - - - 651
FLOURIDES - - - - 1429
GLASSES - - - - - "
HYDRODYNAMIC - - 70
IMPURITY - - - - 132
IONIC - - - - - - 1198
IRON - - - - - - 1192
LAYER - - - - - - 132
LITHIUM - - - - - 1429
LITHIUM HYDROXIDE 651
LUMINESCENCE - - 1676
MECHANISM - - - - 1606
MOLTEN HALIDES - 1429
MOLYBDENUM - - - 1192
MUTUAL - - - - - 70
NONSTOICHIOMETRIC 126
1198
NUMBER - - - - - "
OXYGEN - - - - - "
PH - - - - - - - 70
- - - - - - - 1606
PHOSPHORUS - - - 132
PITTING - - - - - 1192
POTASSIUM HYDROX. 1444
PRESSURE - - - - 1198
PROCESS - - - - - 1606
QUENCHING - - - - 1676
RESISTANCE - - - 1192
SILICON - - - - - 132
SILVER - - - - - 1444
SILVER ELECTRODE 1606
SPECTROGRAPHY - - 1444
STAINLESS STEEL - 1192
SWEEP RATE - - - 1444
TELLURIDE - - - - 1366
THEORY - - - - - 1676
THERMAL - - - - - "
TRANSFERENCE - - 1198
TRAVELING HEATER 1366
TRIANGLE - - - - 1444
VAPOR DEPOSITION 132
VOLTAMMETRY - - - 651
- - - 1444

TERBIUM
BARIUM CALCIUM ->1631
BARIUM MAGNESIUM "
BORATES - - - - - "
CALCIUM - - - - - "
CALCIUM MAGNESIUM "
CALCIUM STRONTIUM "
ENERGY TRANSFER -> 305
EUROPIUM - - - - "
HIGH PRESSURE - - "
LAMP - - - - - - "
LUMINESCENCE - - 1631
MAGNESIUM STRONT. "
MERCURY - - - - - 305
PHOSPHOR - - - - "
VANDATE - - - - - "
VAPOR - - - - - - "
YTTRIUM - - - - - "

TERNARIES
ANTIMONY - - - ->1523
CHALCOGENIDES - - "
DOPING - - - - - "
INFRARED DEVICE - "
JUNCTION - - - - "
LEAD - - - - - - "
TELLURIDE - - - - "
TIN - - - - - - - "

TERNARY
ARSENIC - - - - ->1634

PRIMARY TERM / CO-TERM — PAGE NO.

TERNARY (CONTD)
BANDGAP - - - - ->1673
CHEMICAL - - - - "
COMPOUND - - - - 1634
- - - - 1673
CRYSTAL - - - - - "
DOPING - - - - - 1634
GALLIUM - - - - - "
GERMANIUM - - - - 1673
ISOTHERMS - - - - 1634
LIQUIDUS - - - - "
NITRIDE - - - - - 1673
PHOSPHORUS - - - 1634
PROPERTIES - - - 1673
SEMICONDUCTOR - - 1634
SILICON - - - - - "
STRUCTURE - - - - 1673
SYNTHESIS - - - - "
SYSTEM - - - - - 1634
VAPOR DEPOSITION 1673
ZINC - - - - - - "

TETRABUTYL
AMMONIUM - - - -> 977
BROMIDE - - - - - "
CONDUCTANCE - - - "
DIMETHYLFORMAMIDE "
ELECTROLYTE - - - "
ISOTHIOCYANATE - "
NICKEL - - - - - "
NONAQUEOUS - - - "
POTASSIUM - - - - "
SOLUTION - - - - "
VISCOSITY - - - - "

TETRAGONAL
BORIDES - - - - -> 846
BORON - - - - - - "
CHEMICAL - - - - "
ELEMENTAL - - - - "
MODIFICATION - - "
NONMETAL - - - - "
STRUCTURE - - - - "
VAPOR DEPOSITION "

TETRAHYDROFURAN
BATTERY - - - - -> 656
- - - - ->1294
BEHAVIOR - - - - 656
CARBONATE - - - - "
CATHODE - - - - - "
COPPER - - - - - "
ELECTROINITIATE - 1294
HIGH ENERGY - - - "
LITHIUM - - - - - "
LITHIUM CELLS - - 656
MANGANESE - - - - "
MOLYBDENUM - - - "
PERCHLORATE - - - 1294
POLYMERIZATION - "
PROPYLENE - - - - 656

THALLIUM
ACTIVITY - - - -> 884
ALCOHOLS - - - ->1048
AMALGAMS - - - - 884
APROTIC - - - - -> 518
CELL - - - - - - 1048
COEFFICIENT - - - 884
DILUTE - - - - - "
DIMETHYLFORMAMIDE 518
ELECTROCHEMISTRY "
1048
ELECTRODE - - - - 518
- - - - 1048
HEXANOL - - - - - "
HYDROGEN - - - - 518
- - - - 1048
NORMAL - - - - - "
POTENTIAL - - - - 884
REVERSIBLE CELL - 518
SOLVENT - - - - - "
STANDARD - - - - 884

THEORY
CERIUM DIOXIDE ->1676
COMMENTS - - - - "
COMPOSITIONAL - - "
CONDUCTIVITY - - "
DEPENDENCE - - - "
ELECTRICAL - - - "
LUMINESCENCE - - "
QUENCHING - - - - "
TEMPERATURE - - - "
THERMAL - - - - - "

THERMAL
CALCULATION - - -> 588
CERIUM DIOXIDE ->1676
CHARACTERIZATION > 669
COMMENTS - - - - 1676
COMPOSITIONAL - - "
CONDUCTIVITY - - "
CONTACT ANGLE - - 669
DECOMPOSITION - ->1383
DEPENDENCE - - - 1676
ELECTRICAL - - - "
EPITAXY - - - - - 1383
ETCHING - - - - - "
GAN - - - - - - - "
GOLD - - - - - - ->1076
IMPURITY - - - - 588
- - - ->1107
LUMINESCENCE - - 1676
MEASUREMENT - - - 669
METALLIZATION - - 1076
MICROWAVE - - - - "
NUMERICAL - - - - 588
OXIDATION - - - - "
- - - - 1107
QUENCHING - - - - 1676
REDISTRIBUTION - 588
RELIABILITY - - - 1076
RF HEATING - - - 1107
SEMICONDUCTOR - - 588
SILICON - - - - - "
- - - - - 1107
SILICON DIOXIDE - 588
- 669
STABILITY - - - - 1076
SURFACE - - - - - 669
TANTALUM - - - - 1076
TEMPERATURE - - - 1676
THEORY - - - - - "
TRANSISTOR - - - 1076

THERMAL ANALYSIS
BATTERY FAILURE ->1546
CAPACITY - - - - "
CYCLE - - - - - - "
DECOMPOSITION - - "
ELECTRODE - - - - "
FORM - - - - - - "
LEAD DIOXIDE - - "
MECHANISM - - - - "

THERMAL NITRIDAT.
ATMOSPHERE - - -> 943
LOW PRESSURE - - "
LOW TEMPERATURE - "
MAGNESIUM - - - - "
NITROGEN - - - - "

THERMAL OXIDATION
EFFECT - - - - ->1613
ORIENTATION - - - "
OXYGEN - - - - - "
RATE CONSTANT - - "
SILICON - - - - - "
TRACE - - - - - - "
WATER - - - - - - "

THERMAL QUENCHING
LUMINESCENCE - -> 312

THERMODYNAMICS
ADSORPTION - - ->1167
ALLOY - - - - - ->1051
ALUMINIDE - - - - "
ALUMINUM - - - ->1228
COATING - - - - - 1051
DIFFUSION - - - - "
ELECTROCRYSTALLI. 1167
ELECTRODE - - - - "
FILM - - - - - - "
GROWTH - - - - - 1228
ION - - - - - - - 1167
KINETICS - - - - 1051
- - - - 1167
METAL - - - - - - "
MONOLAYER - - - - "
NICKEL - - - - - 1051
PACK - - - - - - "
PROTECTIVE - - - "
QUARTZ - - - - - 1228
SILICON - - - - - "
STRUCTURE - - - - 1167
TRANSPORT - - - - 1228
WHISKER - - - - - "
X RAY - - - - - - "

THERMOELECTRET
CHARGE - - - - -> 591

PRIMARY TERM / CO-TERM — PAGE NO.

THERMOELECTRET (CONTD)
DENSITY - - - - - 591
DIELECTRIC - - - "
ELECTRET - - - - "
FEP - - - - - - - "
HOMOCHARGE - - - "
INSERT - - - - - "
SPRAY - - - - - - "
SURFACE - - - - - "
TEFLON - - - - - "

THICKNESS
ACTIVE - - - - -> 531
AERATION - - - -> 183
AGITATION - - - -> 56
ANODE FILM - - ->1186
BATTERY - - - - - 531
BOROHYDRIDE - - - 56
CATALYSIS - - - - 1186
COATING - - - - -> 720
CONCENTRATION - -> 419
CORROSION - - - - 183
- - - - 531
CRT - - - - - - - 720
DEVICE - - - - - 419
- - - - - 720
DIFFERENTIAL - - 183
ELECTROLESS - - - 56
ELECTRON - - - - 720
ELLIPSOMETRY - - 1186
EPITAXIAL - - - -> 150
EVOLUTION - - - - 1186
FET - - - - - - - 419
FILM - - - - - - 183
GALVANOSTATIC - - 1186
GATE - - - - - - 419
GLASS - - - - - - "
GOLD - - - - - - 56
GRAPHITE SILICATE 720
GRID - - - - - - 531
IMPURITY - - - - 56
INTERFACE - - - - 419
INTERFEROGRAM - - 150
ION DRIFT - - - - 419
ION TRAPPING - - "
LAYER - - - - - - 150
LEAD ACID - - - - 531
LEAD ANTIMONY - - "
MATERIAL - - - - "
METAL - - - - - - 183
MOISTNESS - - - - "
OXIDE - - - - - - 419
OXYGEN - - - - - 1186
PASSIVATING - - - 183
PENETRATION - - - 720
PHASE SHIFT - - - 150
PHOSPHORUS - - - 419
PHOSPHOSILICATE - "
PLATING - - - - - 56
PLATINUM - - - - 1186
POLARIZATION - - 419
PROCEDURE - - - - 56
PROTECTION - - - 531
REACTION - - - - 1186
SILICON - - - - - 150
SILICON OXIDE - - 419
SULFURIC ACID - - 1186
THRESHOLD - - - - 419
VARIABLE - - - - 183
VOLTAGE - - - - - 419

THIN FILM
ABSORPTION - - ->1496
ADSORPTION - - ->1570
AMORPHOUSNESS - -> 394
ANODE - - - - - -> 550
ANODIZATION - - - 394
BACKSCATTERING - 550
CARBON FILM - - ->1551
CATALYZE - - - ->1115
CATHODE - - - - -> 42
CHEMICAL - - - ->1103
COMPOUND - - - - 1115
CONDUCTANCE - - - 1570
COPPER - - - - -> 202
CRISTOBALITE - - 1115
CRYSTAL QUALITY - 1496
CRYSTALLIZATION - 1115
DEPOSIT - - - - -> 685
DEVICE - - - - - "
DIFFUSION - - - -> 286
ELECTROCHEMICAL - "
ELECTRODE - - - - 1570
ELECTRODEPOSIT - 202
ELECTRON - - - -> 929
ETCHING - - - - - 286
EVAPORATION - - - 202

PRIMARY TERM / CO-TERM	PAGE NO.
THIN FILM (CONTD)	
FET	1103
FILM	286
FUSED SILICA	685
GASEOUS	1551
HETEROEPITAXY	->1345
INORGANIC	-> 925
	929
INSULATOR	1345
ION	550
IRON	1551
IRON OXIDE	42
	925
	929
KRAMERS KRONIG	1496
LASER	925
MASK	"
MEASUREMENT	1570
MOS	1103
NUCLEATION	202
OPTICAL INTERFER.	1496
OXIDATION	1551
OXIDE	550
PHOSPHOSILICATE	1115
PHOTOMASK	929
PHOTORESIST	925
PLATINUM	42
PRETREATMENT	1551
QUARTZ	1115
REDUCTION	42
REFRACTIVE INDEX	1496
RESIST	929
RUTHERFORD	550
SAPPHIRE	1345
SCATTERING	550
SEMICONDUCTOR	1345
SILICON	286
	550
	1345
SILICON DIOXIDE	1103
	1115
SILICON FILM	685
	1496
SINGLE CRYSTAL	202
SPINEL	1345
SPUTTERING	394
SURFACE	1570
TANTALUM	550
TIN	394
TRANSISTOR	685
VACUUM	"
VAPOR DEPOSITION	1103
THIN FILMS	
ELLIPSOMETRY	->1393
IRON	"
PHOSPHATES	"
REFRACTIVE INDEX	"
THORIUM	
LINEAR SWEEP	-> 86
LITHIUM FLUORIDE	"
MOLTEN FLUORIDE	"
POTASSIUM	"
SODIUM FLUORIDE	"
URANIUM	"
VOLTAMMETRY	"
THRESHOLD	
CONCENTRATION	-> 419
DEVICE	"
FET	"
GATE	"
GLASS	"
INTERFACE	"
ION DRIFT	"
ION TRAPPING	"
OXIDE	"
PHOSPHORUS	"
PHOSPHOSILICATE	"
POLARIZATION	"
SILICON OXIDE	"
THICKNESS	"
VOLTAGE	"
TIN	
ALLOY	->1526
AMORPHOUSNESS	-> 394
ANODIZATION	"
ANTIMONY	->1523
BATTERY	1526
BISMUTH	"
CALCIUM	"
CALCIUM LEAD	"
CHALCOGENIDES	1523
DOPING	"
GRID	1526
TIN (CONTD)	
INFRARED DEVICE	1523
JUNCTION	"
LEAD	"
SPUTTERING	394
TELLURIDE	1523
TERNARIES	"
THIN FILM	394
TITANIUM	
ADSORPTION	-> 848
CHLORINE	"
SURFACE	"
TITANIUM ALLOY	
CORROSION	-> 599
CRACKING	"
REPASSIVATION	"
TRIBOELLIPSOMETRY	"
TITANIUM CHLORIDE	
DIMETHYLFORMAMIDE>	79
ELECTRODE	"
LEAD CHLORIDE	"
MEASUREMENT	"
POTENTIAL	"
STANDARD	"
TITANIUM DIOXIDE	
DEPOSITION	->1160
METAL	"
NOBLE	"
OPEN CIRCUIT	"
PALLADIUM	"
PHOTOCATALYTIC	"
PHOTOGRAPHY	"
SEMICONDUCTOR	"
TITRATION	
ACTIVITY	-> 354
ARGON OXYGEN	"
CALCIA STABILIZED>	793
CONDUCTION	"
CONTROL	354
COULOMETRY	"
	793
ELECTRODE	354
HOLE	793
MIXTURE	354
OXYGEN	"
	793
PERMEATION	"
PLATINUM	354
POTENTIOSTAT	"
SOLID STATE	793
WUSTITE	"
ZIRCONIA	354
	793
TOPOGRAPHY	
COPPER	-> 289
DISPLACEMENT	"
IMPERFECTION	"
SILICON	"
SUBSTRATE	"
X RAY	"
TOWER	
ANALGAM	-> 337
	-> 340
	-> 343
COMPARISON	"
CRUSHED	"
DECOMPOSITION	337
	340
	343
GRAPHITE BED	"
RATE	340
SODIUM	337
SODIUM HYDROXIDE	340
	343
TRACE	
EFFECT	->1613
ORIENTATION	"
OXYGEN	"
RATE CONSTANT	"
SILICON	"
THERMAL OXIDATION	"
WATER	"
TRACE ANALYSIS	
BATTERY	->1045
CONTAMINATION	"
ELECTROLYTE	"
INFRARED	"
INORGANIC	"
TRACE ANALYSIS (CONTD)	
LIQUID	1045
LITHIUM	"
OXYHALIDE	"
WATER	"
TRACES	
BRONZE	->1029
ELECTROREDUCTION	"
HYDROGEN	"
HYDROGEN PEROXIDE	"
OXYGEN	"
PLATINUM	"
SODIUM	"
TUNGSTEN	"
TRANSFER	
ALKALI METAL	-> 994
ALUMINUM CHLORIDE	"
AMMONIA	-> 230
CALCIA STABILIZED>	506
CARBONATE	994
CATHODE	-> 867
CHLORIDE	994
COEFFICIENT	230
	867
	994
CONVECTION	867
CURRENT DENSITY	994
ELECTRODE	506
	994
ELECTROLYTE	506
ELECTROWINNING	867
EVOLUTION	230
EXCHANGE	994
EXCHANGE CURRENT	230
FORCED	867
GALLIUM	506
GALLIUM SESQUIOX.	"
HYDROGEN	230
KINETICS	506
	994
LIQUID	230
MASS	867
MODEL CELL	"
NATURAL	"
NITROGEN	230
OVERVOLTAGE	"
OXYGEN	506
PROPYLENE	994
SOLID	506
TAFEL SLOPE	230
ZIRCONIA	506
TRANSFERENCE	
ALKALI CHLORIDE	-> 991
CADMIUM CHLORIDE >	959
CARBONATE	-> 83
CERIUM CHLORIDE	991
CERIUM DIOXIDE	->1198
CONDUCTIVITY	"
DEPENDENCE	"
EMF	83
	959
	991
FREE ENERGY	959
GIBBS	"
ION MOBILITY	"
	"
IONIC	1198
LITHIUM CHLORIDE	959
LITHIUM ION	83
MEASUREMENT	"
	991
MIXTURE	"
MOLTEN MIX	959
MOLTEN SALT	991
NONSTOICHIOMETRIC	1198
NUMBER	83
	1198
NUMBERS	991
OXYGEN	1198
PRESSURE	"
PROPYLENE	83
SOLUTION	"
TEMPERATURE	1198
TRANSFORMATION	
ALUMINUM OXIDE	->1465
ANNEALING	"
ANODE FILM	"
ELECTROETCH	"
SURFACE GAIN	"
TRANSGRANULAR	
CORROSION	->1190
CRACK	"
TRANSGRANULAR (CONTD)	
FRACTOGRAPHY	1190
MORPHOLOGY	"
STAINLESS STEEL	"
STRESS	"
STRIATION	"
SULFURIC ACID	"
TRANSIENT	
ACETONE	->1563
CARBON	-> 527
CRYSTAL GROWTH	1563
DEPOSITION	527
DISSOLUTION	1563
DUTERIUM OXIDE	"
ELECTROLYTES	"
FORMAMIDE	"
IRON	527
IRON OXIDE	"
PASSIVATION	"
PLATINUM	"
POTENTIAL	1563
POTENTIOSTATIC	527
PRECIPITATION	1563
RING ELECTRODE	527
STEELS	"
TRANSISTOR	
AMMONIUM	->1215
ANODE	-> 280
BIPOLAR	"
	->1119
	1215
CHEMICAL	"
COMPLEMENTARY	1119
CONTAMINATION	-> 790
CRYSTAL DEFECT	280
DECORATION	"
DEPOSIT	-> 885
DEVICE	"
	1119
ETCHANT	1215
FLUORINE	790
FUSED SILICA	685
GALLIUM ARSENIDE	1215
GOLD	->1076
GOLD REFRACTORY	790
HYDROGEN PEROXIDE	1215
HYDROXIDE	"
INTEGRATION	1119
ION	790
ISOLATED	1119
JUNCTION	280
LEAKAGE	"
METALLIZATION	790
	1076
MICROWAVE	"
MONOLITHIC	1119
MOS	"
NPN	280
RELIABILITY	1076
REMOVAL	1215
RETENTION	790
SELECTIVE	1215
SEMICONDUCTOR	1119
SILICON	790
SILICON DIOXIDE	1215
SILICON FILM	685
STABILITY	1076
SURFACE	790
TANTALUM	1076
THERMAL	"
THIN FILM	685
VACUUM	"
TRANSITION ION	
ALUMINATE	-> 142
CANDOLUMINESCENCE	"
LANTHANUM	"
PHOSPHORS	"
WILLEMITE	"
ZINC PHOSPHATE	"
TRANSPORT	
ALUMINUM	->1228
CONCENTRATION	-> 370
CONVECTIONLESS	"
GRADIENTS	"
GROWTH	1228
INTERFEROMETRY	370
QUARTZ	1228
SILICON	"
THERMODYNAMICS	"
WHISKER	"
X RAY	"
ZINC ANODE	370
ZINC CATHODE	"

PRIMARY TERM / CO-TERM — PAGE NO.

TRAP
CORONA CHARGE -> 452
FIELD EFFECT "
INTERFACE "
MODULATE "
PHOTOLUMINESCENCE "
SEMICONDUCTOR "
ZINC OXIDE "

TRAPPING
ARGON -> 558
BACKSPUTTERING "
FILM "
IMPLANTATION "
ION "
METALLIZATION "
SILICON DIOXIDE "
SPUTTERING "

TRAVELING HEATER
ANALYSIS ->1366
CADMIUM "
CRYSTAL GROWTH "
DISTRIBUTION "
TELLURIDE "
TEMPERATURE "

TRIANGLE
CAPACITY ->1444
DOUBLE LAYER "
POTASSIUM HYDROX. "
SILVER "
SPECTROGRAPHY "
SWEEP RATE "
TEMPERATURE "
VOLTAMMETRY "

TRIANGULAR
CAPACITY -> 512
DOUBLE LAYER "
ELECTRODE "
NICKEL "
POROUS "
POTASSIUM HYDROX. "
SWEEP "
VOLTAGE "

TRIBOELLIPSOMETRY
CORROSION -> 599
CRACKING "
REPASSIVATION "
TITANIUM ALLOY "

TRICHLOROSILANE
BOAT ->1112
CVD "
PREPARATION "
PROPERTY "
QUARTZ "
REDUCTION "
SEMICONDUCTOR "
SILICON "
TUBE "

TRIETHYLINDIUM
ARSINE ->1642
->1646
CHARACTERIZATION 1642
CHEMICAL "
1646
ELECTRICAL "
GALLIUM ARSENIDE 1642
1646
GROWTH 1642
HETEROEPITAXY "
1646
INDIUM ARSENIDE 1642
1646
PROPERTIES "
VAPOR DEPOSITION 1642
1646

TRIFLUOROMETHANE.
ADSORPTION -> 987
ANION "
ELECTROLYTE "
HYDROCARBON "
MONOHYDRATE "
OXIDATION "
PROPANE "

TRIMETHYLSTIBINE
ANTIMONY -> 967
DOPING "
EPITAXY "
METALORGANICS "
SAPPHIRE "

TRIMETHYLSTIBINE (CONTD)
SILICON 967
SOURCE "

TUBE
BOAT ->1112
CVD "
PREPARATION "
PROPERTY "
QUARTZ "
REDUCTION "
SEMICONDUCTOR "
SILICON "
TRICHLOROSILANE "

TUNGSTEN
ARGON ->1372
BRONZE ->1029
->1530
CHEMICAL -> 298
CONDUCTIVITY 1530
CONTROL 1372
DEPOSITION 298
DIFFUSING 1372
ELECTROREDUCTION 1029
EQUILIBRIA 1372
ETCHING "
HELIUM "
HEXAFLUORIDE "
HYDROGEN 1029
HYDROGEN PEROXIDE "
LANGMUIR SHEATH 1372
METALLIZATION 298
NITROGEN 1372
OXYGEN 1029
PENTA FLUORIDE 1372
PLATINUM 1029
RATE 1372
REACTION "
SEMICONDUCTOR 298
SODIUM 1029
1530
SODIUM ION "
TRACES 1029
VAPOR 298

TUNGSTEN OXIDE
ANODE OXIDATION -> 782
HYDROGEN "
PLATINIZED "
TUNGSTEN TRIOXIDE "

TUNGSTEN TRIOXIDE
ANODE OXIDATION -> 782
HYDROGEN "
PLATINIZED "
TUNGSTEN OXIDE "

TUNNEL
ALUMINUM -> 583
CAPACITOR "
CORROSION "
ELECTROLYTE "
ETCHABILITY "
IRON "
MICROSEGREGATION "
PRECIPITATION "

TWO PHASE
ALLOY -> 718
ALUMINUM COPPER "
MICROSTRUCTURE "
OXIDATION "

ULTRA VIOLET
CATALYST ->1461
ELECTROLESS "
INHIBITION "
PLASTICS "
PLATING "

ULTRAVIOLET
CHLOROSTILBENES ->1667
ELECTROLESS -> 667
GLASS "
GROWTH INHIBITION "
IMAGING "
1667
INHIBITION 667
IRRADIATION 1667
LIQUID CRYSTAL "
NEMATIC "
PLATING 667
STILBENES 1667

UNDER POTENTIAL
DEPOSITION ->1610

UNDER POTENTIAL (CONTD)
ELECTRODE 1610
GOLD "
LEAD "
OPTIC "
SINGLE CRYSTAL "

UNDERCUTTING
CHROME COATING -> 29
DELAMINATION "
LACQUER FILM "
ORGANIC "
STEEL "

UNDERPOTENTIAL
ADSORPTION -> 474
DEPOSITION "
ELECTRODE "
GOLD EVAPORATED "
ISOTHERM "
LEAD "
REFLECTANCE "
SINGLE CRYSTAL "
SPECTROSCOPY "

UNDISCHARGED
AC -> 375
ALKALINE "
CATHODE "
CONDUCTIVITY "
DC "
DISCHARGED "
IMPEDANCE "
IONIC CONDUCTANC. "
LECLANCHE CELL "
MANGANESE DIOXIDE "
MEASUREMENT "
MERCURY OXIDE "
RESISTANCE "

UNSATURATED
CHRONOPOTENTIOME.> 769
COUPLING "
CURRENT REVERSAL "
ELECTROHYDRODIME. "
ELECTROLYTE "
KETONES "
REDUCTIVE "

URANIUM
LINEAR SWEEP -> 86
LITHIUM FLUORIDE "
MOLTEN FLUORIDE "
POTASSIUM "
SCOIUM FLUORIDE "
THORIUM "
VOLTAMMETRY "

VACANCY
CLUSTER ->1090
CONCENTRATION -> 153
CRISTOBALITE 1090
CRYSTAL GROWTH 153
GALLIUM "
GAP "
HETEROGENEOUS 1090
OXYGEN "
PHOSPHORUS 153
PRECIPITATION 1090
SILICON "
SILICON OXIDES "
SOLIDUS 153

VACUUM
DEPOSIT -> 685
DEVICE "
EVAPORATION ->1222
FLOAT ZONE "
FUSED SILICA 685
HIGH RESISTIVITY 1222
POLYCRYSTALLINE "
POLYDEPOSITION "
PROCESS "
PRODUCTION "
SILICON "
SILICON FILM 685
SINGLE CRYSTAL 1222
THIN FILM 685
TRANSISTOR "

VANADIUM
CHROMIUM -> 225
COBALT "
CORROSION "
EVOLUTION "
HYDROGEN "
MANGANESE "

VANDATE
ENERGY TRANSFER -> 305
EUROPIUM "
HIGH PRESSURE "
LAMP "
MERCURY "
PHOSPHOR "
TERBIUM "
VAPOR "
YTTRIUM "

VANDERPAUW
ANOMALOUS ->1212
CARRIER MOBILITY "
DISTRIBUTION "
GERMANIUM "
HALL "
IMPURITY "
INHOMOGENEITY "
METHOD "
MOBILITY "
RADIAL "
SEMICONDUCTOR "

VAPOR
AC DISCHARGE -> 714
ACTIVATION -> 681
ADSORPTION -> 676
BOROSILICATE "
CADMIUM -> 965
CHEMICAL -> 298
CONTAMINATION 681
DEFORMATION "
DEPOSIT 676
681
DEPOSITION 298
714
965
DICHLOROSILANE 681
DIFFUSION 676
ENERGY TRANSFER -> 305
EPITAXY 965
EUROPIUM 305
FIBER GROWTH 714
GLASS FILM 676
HETEROEPITAXY 965
HIGH PRESSURE 305
LAMP "
MERCURY "
METALLIZATION 298
NEUTRON 681
OXYGEN "
PHOSPHOR 305
PHOTOSENSITIVITY 965
POLYCRYSTALLINE 681
SAPPHIRE 965
SELENIDE "
SEMICONDUCTOR 298
SILANOL 676
SILICON FILM 681
SPECTROSCOPY 676
SULFIDE 965
TANTALUM CARBIDE 714
TERBIUM 305
TUNGSTEN 298
VANDATE 305
VAPOR PHASE 965
WATER 676
YTTRIUM 305

VAPOR DEPOSITION
ARSINE ->1642
->1646
BANDGAP ->1673
BORIDES -> 846
BORON "
CHARACTERIZATION 1642
CHEMICAL 846
->1103
1642
1646
1673
COMPOUND "
CONCENTRATION -> 132
CONTRAST ->1202
CRYSTAL 1673
DEPENDENCE 132
DIFFUSION "
DIODE 1202
DISTRIBUTION 132
DOPED OXIDE "
ELECTRICAL 1646
ELEMENTAL 846
FET 1103
GALLIUM ARSENIDE 1642
1646
GALLIUM NITRIDE 1202

PRIMARY TERM / CO-TERM — PAGE NO.

VAPOR DEPOSITION (CONTD)
GERMANIUM - - - - 1673
GROWTH - - - - - 1642
HETEROEPITAXY - - "
- - 1646
HETEROEXPITAXIAL 1202
IMPURITY - - - - 132
INDIUM ARSENIDE - 1642
- 1646
JUNCTION - - - - 1202
LAYER - - - - - - 132
LIGHT EMISSION - 1202
MICROSTRUCTURE - "
MODIFICATION - - 846
MOS - - - - - - - 1103
NITRIDE - - - - - 1673
NONMETAL - - - - 846
PHOSPHORUS - - - 132
PROFILE - - - - - 1202
PROPERTIES - - - 1646
- - - 1673
SILICON - - - - - 132
SILICON DIOXIDE - 1103
STRUCTURE - - - - 846
- - - - 1202
- - - - 1673
SYNTHESIS - - - - "
TEMPERATURE - - - 132
TERNARY - - - - - 1673
TETRAGONAL - - - 846
THIN FILM - - - - 1103
TRIETHYLINDIUM - 1642
- 1646
VOLTAGE - - - - - 1202
ZINC - - - - - - 1673

VAPOR PHASE
CADMIUM - - - - -> 965
CALCULATION - - ->1357
CRYSTAL GROWTH ->1516
DEPOSITION - - - 965
- - - 1357
DOPING - - - - - 1516
ELECTROLUMINESCE. "
EPITAXY - - - - - 965
- - - - ->1354
- - - - - 1357
- - - - - 1516
EQUILIBRIA - - - 1354
GAASP - - - - - - 1357
GAS PHASE - - - - 1354
- - - - 1516
HETEROEPITAXY - - 965
MORPHOLOGY - - - 1516
PHOSPHORUS - - - 1354
PHOTOSENSITIVITY 965
SAPPHIRE - - - - "
SELENIDE - - - - "
SILICON - - - - - 1354
STOICHIOMETRY - - 1516
SULFIDE - - - - - 965
VAPOR - - - - - - "

VAPOR PRESSURE
ALUMINUN - - - ->1239
BROMIDE - - - - - "
CRYSTAL GROWTH -> 835
INDIUM - - - - - "
IRON - - - - - -> 832
PENTACARBONYL - - "
PHASE EQUILIBRIUM 835
PHOSPHIDE - - - - "
PHOSPHORUS - - - "
SOLID - - - - - - 1239

VAPORIZATION
CALCIUM - - - - -> 534
CHROMIUM - - - -> 952
CHROMIUM OXIDE -> 945
- 952
DICALCIUM - - - - 534
ELECTROCHEMISTRY "
GALVANIC CELL - - "
MONOCALCIUM - - - "
OXIDATION - - - - 945
- - - - 952
OXYGEN - - - - - 945
OXYGEN ATOMS - - 952
STABILITY - - - - 534
STANNATE - - - - "

VARIABLE
AERATION - - - - -> 133
BASIC - - - - - - -> 253
COMPOSITION - - - "
CORROSION - - - - 183
DIFFERENTIAL - - "

VARIABLE (CONTD)
FILM - - - - - - - 183
LEAD CARBONATE - 253
LEAD OXIDE - - - "
LEAD SULFATE - - "
METAL - - - - - - 183
MOISTNESS - - - - "
PASSIVATING - - - "
THICKNESS - - - - "

VERTICAL ZONE
BEHAVIOR - - - - -> 448
CONVERGING - - - "
INDIUM ANTIMONIDE "
INTERFACE - - - - "
PRESSURE INDUCED "
SEGREGATION - - - "
SOLIDIFICATION - "
STATIONARY - - - "

VICKERS
BOROSILICATE - ->1098
GLASS FILM - - - "
GLASS METAL - - - "
HARDNESS - - - - "
SINTERING - - - - "
STRESS - - - - - - "

VIOLOGEN
COLORED FILMS - ->1555
COMPOUND - - - - "
INSOLUBLE - - - - "
RADICAL - - - - - "

VISCOSITY
AMMONIUM - - - -> 977
BROMIDE - - - - - "
CONDUCTANCE - - - "
DIMETHYLFORMAMIDE "
ELECTROLYTE - - - "
ISOTHIOCYANATE - "
NICKEL - - - - - "
NONAQUEOUS - - - "
POTASSIUM - - - - "
SOLUTION - - - - "
TETRABUTYL - - - "

VISIBLE
ANTHRACENE - - ->1341
COMPOSITE - - - - "
CONVERSION - - - "
LEAD CHLORIDE - - "
LIGHT - - - - - - "
LUMINESCENCE - - "
X RAY - - - - - - "

VOLTAGE
BRINE LEVEL - - ->1286
CAPACITY - - - -> 512
CHLORALKALI CELL 1286
CONCENTRATION - -> 419
CONTRAST - - - ->1202
DEVICE - - - - - - 419
DIODE - - - - - - 1202
DOUBLE LAYER - - 512
ELECTRODE - - - - "
FET - - - - - - - 419
GALLIUM NITRIDE - 1202
GAS LIFT - - - - 1286
GATE - - - - - - 419
GLASS - - - - - - "
HETEROEXPITAXIAL 1202
INTERFACE - - - - 419
ION DRIFT - - - - "
ION TRAPPING - - "
JUNCTION - - - - 1202
LIGHT EMISSION - "
MERCURY TYPE - - 1286
MICROSTRUCTURE - 1202
NICKEL - - - - - 512
OXIDE - - - - - - 419
PHOSPHORUS - - - "
PHOSPHOSILICATE - "
POLARIZATION - - "
POROUS - - - - - 512
POTASSIUM HYDROX. "
PROFILE - - - - - 1202
PUMP - - - - - - 1286
SCALE UP - - - - "
SILICON OXIDE - - 419
STRUCTURE - - - - 1202
SWEEP - - - - - - 512
THICKNESS - - - - 419
THRESHOLD - - - - "
TRIANGULAR - - - 512
VAPOR DEPOSITION 1202

VOLTAMMETRY
ACETONITRILE - -> 881
ADSORPTION - - ->1421
ALUMINUN CHLORIDE> 212
ANODE - - - - - -> 876
CAPACITY - - - ->1444
CHEMILUMINESCENCE>1178
CHRONOCOULOMETRY 1421
COPPER - - - - - 212
- - - - -> 651
CORROSION - - - - "
CYCLIC - - - - - "
DIETHYLFUMARATE - 881
DIMERIZATION - ->1412
DIMETHYLFORMAMIDE "
DMSO - - - - - - 881
DOUBLE LAYER - - 1444
ELECTROANALYSIS - 1178
ELECTRODE - - - - 1421
ELECTROGENERATE - 1178
ELECTROHYDRODIME. 881
ELECTRON - - - - 876
ELEVATED - - - - 651
ENERGY DEFICIENT 1178
FUSED SALT - - - 212
ION PAIRS - - - - 881
IRON - - - - - - 212
LEAD - - - - - - 876
LINEAR SWEEP - -> 86
LITHIUM FLUORIDE "
LITHIUM HYDROXIDE 651
LUMINESCENCE - - 1178
MELT - - - - - - 212
MERCURY - - - - 1421
METAL ION - - - - 212
MICROSCOPY - - - 876
MOLTEN FLUORIDE - 86
NONAQUEOUS - - - 1178
PHENYLNITROPROPE. 1412
POLARIZED - - - - 876
POLAROGRAPHY - - 212
POTASSIUM - - - - 86
POTASSIUM HYDROX. 1444
REDUCTION - - - - 881
RHODIUM - - - - - 1421
SILVER - - - - - 212
- - - - - 1444
SODIUM CHLORIDE - 212
SODIUM FLUORIDE - 86
SODIUM ION - - - 881
SOLVENT - - - - - 1178
SPECTROGRAPHY - - 1444
SWEEP RATE - - - "
SYSTEM - - - - - 212
TEMPERATURE - - - 651
- - - 1444
THORIUM - - - - - 86
TRIANGLE - - - - 1444
URANIUM - - - - - 86

WAFER
BREAKDOWN - - - ->1229
CARRIER - - - - - "
DIELECTRIC - - - "
ETCHING - - - - - "
GENERATION - - - "
IMPERFECTION - - "
MINORITY - - - - "
SILICON - - - - - "

WARBURG
ASYMPTOTIC - - -> 521
ELECTRODE - - - - "
IMPEDANCE - - - - "
ROTATING DISK - - "
SOLUTION - - - - "

WATER
ABSORPTION - - -> 434
ACETONE - - - - ->1584
ACTIVATION - - - 434
ADSORPTION - - -> 676
ANALYSIS - - - - 434
BATTERY - - - - ->1045
BOROSILICATE - - 676
CONCENTRATION - - 434
CONSTANT - - - - 1584
CONTAMINATION - - 1045
DEPOSIT - - - - - 676
DIFFUSION - - - - "
EFFECT - - - - ->1613
ELECTROLYTE - - - 1045
FORMATION - - - - 1584
GLASS FILM - - - 676
INFRARED - - - - 434
- - - - 1045
INORGANIC - - - - "

WATER (CONTD)
INTERACTION - - - 434
LIQUID - - - - - 1045
LITHIUM - - - - - "
MIXTURE - - - - - 1584
MOISTURE - - - - 434
ORIENTATION - - - 1613
OXYGEN - - - - - "
OXYHALIDE - - - - 1045
PHOSPHORUS - - - 434
PRODUCT - - - - - 1584
PSG FILM - - - - 434
RATE CONSTANT - - 1613
RESISTANCE - - - 434
SILANOL - - - - - 676
SILICON - - - - - 1613
SILVER HALIDES - 1584
SOLUBILITY - - - "
SPECTROSCOPY - - 676
THERMAL OXIDATION 1613
TRACE - - - - - - "
TRACE ANALYSIS - 1045
VAPOR - - - - - - 676

WATER CURVATURE
DEVICE - - - - -> 426
ELECTROPLATED - - "
FABRICATION - - - "
GAAS - - - - - - - "
HEAT SINKS - - - "
IMPATT - - - - - "

WATER VAPOR
AIR - - - - - - - -> 118
NICKEL ALLOY - - "
OXIDATION - - - - "

WAVEGUIDE
DETECTOR - - - ->1506
EPITAXY - - - - - "
GAAS - - - - - - - "
INGAAS - - - - - - "

WETTING
CAPACITANCE - - -> 639
ELECTRODE - - - - "
ELECTROLYTE CF.L "
GRAPHITE - - - - "
INTERFACE - - - - "
ROUGHENING - - - "
SILVER HALIDES - "
SOLID ELECTROLYTE "
SOLID STATE - - - "

WHISKER
ALUMINUM - - - - ->1228
GROWTH - - - - - "
QUARTZ - - - - - "
SILICON - - - - - "
THERMODYNAMICS - "
TRANSPORT - - - - "
X RAY - - - - - - "

WILLEMITE
ALUMINATE - - - -> 142
CANDOLUMINESCENCE "
LANTHANUM - - - - "
PHOSPHORS - - - - "
TRANSITION ION - "
ZINC PHOSPHATE - "

WIRE
COPPER - - - - - -> 661
- - - - - -> "
CURRENT - - - - - "
- - - - - "
- - - - - "
- - - - - "
DISTRIBUTION - - "
- - "
- - "
- - "
ELECTRODEPOSITION "
"
MEASUREMENT - - - "
- - - "
PRINTED CIRCUIT - "
- "
REDOX SYSTEM - - "
- - "
WIRE - - - - - - "
- - - - - - "
WIRE ELECTRODE - "
- "

WIRE ELECTRODE
BIPOLAR ELECTRODE> 622

PRIMARY TERM / CO-TERM	PAGE NO.
WIRE ELECTRODE (CONTD)	
COPPER	661
CURRENT	622
	661
	"
DISTRIBUTION	622
	661
	"
ELECTRODE	622
ELECTRODEPOSITION	661
MEASUREMENT	"
POTENTIAL	622
PRINTED CIRCUIT	661
REDOX SYSTEM	"
RESISTIVE	622
WIRE	661
	"
WORK	
ACIDIC	1141
ANODE	"
CHLORIDE	"
COLD	"
GRAIN	"
MICROSCOPY	"
NICKEL	"
POLARIZATION	"
POTENTIOSTATIC	"
SIZE	"
WUSTITE	
CALCIA STABILIZED	793
CONDUCTION	"
COULOMETRY	"
HOLE	"
OXYGEN	"
PERMEATION	"
SOLID STATE	"
TITRATION	"
ZIRCONIA	"
X RAY	
ALUMINUM	1228
ANTHRACENE	1341
COMPOSITE	"
CONVERSION	"
COPPER	289
CRYSTAL GROWTH	822
CZOCHRALSKI	"
DISPLACEMENT	289
ELECTRON RESISTS	1500
ENCAPSULATION	822
GALLIUM PHOSPHIDE	"
GROWTH	1228
IMAGING	822
IMPERFECTION	289
LEAD CHLORIDE	1341
LIGHT	"
LIQUID	822
LITHOGRAPHY	1500
LUMINESCENCE	1341
OXIDATION	673
POLYMER RESISTS	1500
QUARTZ	1228
SILICON	289
	1228
SPECTROSCOPY	673
SUBSTRATE	289
SURFACE	673
THERMODYNAMICS	1228
TOPOGRAPHY	289
TRANSPORT	1228
VISIBLE	1341
WHISKER	1228
XRAY	
CRYSTAL	1674
EXISTENCE	"
HEAT	"
INDIUM	"
MEASUREMENT	"
MONOSELENIDE	"
PHASE TRANSITION	"
SEMICONDUCTOR	"
SPECIFIC	"
STRUCTURE	"
YIELD	
CRITICAL	329
DENDRITE	"
GROWTH	"
INDUCTION TIME	"
OVERPOTENTIAL	"
ZINC	"
YTTERBIUM	
ALUMINUM	137
YTTERBIUM (CONTD)	
ANODE SPARK	1402
BARIUM	137
CALCIUM	"
DYSPROSIUM	1402
ERBIUM	"
EUROPIUM	137
GADOLINIUM	1402
GALLIUM	137
HOLMIUM	1402
PHOTOLUMINESCENCE	137
SAMARIUM	1402
SEMICONDUCTOR	137
SODIUM SILICATE	1402
STRONTIUM	137
SYNTHESIS	"
YTTRIUM	1402
YTTRIA DOPED	
ANION VACANCY	255
ANTI FRENKEL	"
CONDUCTIVITY	"
DEFECT STRUCTURE	"
ELECTRON	"
ION	"
ZIRCONIUM OXIDE	"
YTTRIUM	
ANODE SPARK	1402
DYSPROSIUM	"
ENERGY TRANSFER	305
ERBIUM	1402
EUROPIUM	305
GADOLINIUM	1402
HIGH PRESSURE	305
HOLMIUM	1402
LAMP	305
MERCURY	"
PHOSPHOR	"
SAMARIUM	1402
SODIUM SILICATE	"
TERBIUM	305
VANDATE	"
VAPOR	"
YTTERBIUM	1402
ZERO CHARGE	
IMMERSION	618
METAL ELECTRODE	"
METHOD	"
OPEN CIRCUIT	"
SCRAPE	"
ZINC	
ALKALI HYDROXIDE	1385
ALLOY	1129
ALUMINUM	"
AMALGAMATE	1385
ANODE OXIDATION	820
BANDGAP	1673
CHEMICAL	"
COMPOUND	820
	1673
CONCENTRATE	1385
CORROSION	1129
	1385
CRITICAL	329
CRYSTAL	1673
CRYSTAL GROWTH	1237
DENDRITE	329
DEVICE	820
DIFFUSION	"
	1237
DOPED	"
ELECTROOPTICAL	820
EPITAXY	1237
GAAS	"
GALLIUM ARSENIDE	820
GERMANIUM	1237
	1673
GROWTH	329
HISTOPATHOLOGY	1129
IMPLANTABLE	"
INDUCTION TIME	329
INVITRO	1129
INVIVO	"
MAGNESIUM	"
NITRIDE	1673
OHM	1237
OVERPOTENTIAL	329
POWER	1129
PROPERTIES	1673
SEMICONDUCTOR	820
	1237
SOURCE	1129
STRUCTURE	1673
SYNTHESIS	"
ZINC (CONTD)	
TERNARY	1673
VAPOR DEPOSITION	"
YIELD	329
ZINC OXIDE	1385
ZINC ANODE	
CONCENTRATION	370
CONVECTIONLESS	"
GRADIENTS	"
INTERFEROMETRY	"
TRANSPORT	"
ZINC CATHODE	"
ZINC CATHODE	
CONCENTRATION	370
CONVECTIONLESS	"
GRADIENTS	"
INTERFEROMETRY	"
TRANSPORT	"
ZINC ANODE	"
ZINC OXIDE	
ALKALI HYDROXIDE	1385
AMALGAMATE	"
BEHAVIOR	163
CARRIER	1332
CHEMISORPTION	163
CONCENTRATE	1385
CORONA CHARGE	452
CORROSION	1385
DIELECTRIC	163
DIFFUSION	"
DIODE	1332
DOPING	163
EFFICIENCY	1332
FIELD EFFECT	452
GALLIUM	1332
HEAT	"
HIGH TEMPERATURE	163
INTERFACE	452
LIFETIME	1332
LITHIUM	163
MODULATE	452
PHOSPHORUS	1332
PHOTOLUMINESCENCE	452
	1332
POLYCRYSTALLINE	163
SEMICONDUCTOR	452
SODIUM	163
TRAP	452
ZINC	1385
ZINC PHOSPHATE	
ALUMINATE	142
CANDOLUMINESCENCE	"
LANTHANUM	"
PHOSPHORS	"
TRANSITION ION	"
WILLEMITE	"
ZINC SELINIDE	
ALUMINUM	327
ALUMINUM SELINIDE	"
COPPER	"
SOLID SOLUTION	"
ZINC SULFIDE	"
ZINC SULFIDE	
ALUMINUM	327
ALUMINUM SELINIDE	"
COPPER	"
DIRECT CURRENT	109
ELECTROLUMINESCE.	"
GREEN	"
LEAD DOPED	"
PHOSPHORS	"
POWDER CELLS	"
SOLID SOLUTION	327
ZINC SELINIDE	"
ZIRCONIA	
ACTIVITY	354
ARGON OXYGEN	"
CALCIA STABILIZED	506
	793
CONDUCTION	"
CONTROL	354
COULOMETRY	"
	793
ELECTRODE	354
	506
ELECTROLYTE	"
GALLIUM	"
GALLIUM SESQUIOX.	"
HOLE	793
KINETICS	506
ZIRCONIA (CONTD)	
MIXTURE	354
OXYGEN	"
	506
	793
PERMEATION	"
PLATINUM	354
POTENTIOSTAT	"
SOLID	506
SOLID STATE	793
TITRATION	354
	793
TRANSFER	506
WUSTITE	793
ZIRCONIUM OXIDE	
ANION VACANCY	255
ANTI FRENKEL	"
CONDUCTIVITY	"
DEFECT STRUCTURE	"
ELECTRON	"
ION	"
YTTRIA DOPED	"
ZONE LEVELING	
ANALYSIS	1671
CRYSTAL	"
GROWING	"
ZONE MELTING	"
ZONE MELTING	
ANALYSIS	1671
CRYSTAL	"
GROWING	"
ZONE LEVELING	"